ELECTRONIC PROPERTIES OF WELL-ORIENTED GRAPHITE

AT LOW TEMPERATURES.

A thesis submitted to

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by

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ABSTRACT

Measurement and interpretation of galvanomagnetic effects in well-oriented pyrolytic graphite has been carried out over a temperature range from 300°K to 1°K in magnetic fields up to 17 k gauss.

A cryostat was designed and constructed to fit between the poles of a Newport electromagnet. The thin-walled stainless steel cryostat was thermally shielded by a silvered glass nitrogen dewar. Long tails were required on the dewar vessels because of the magnet shape. Pumping systems were built for lowering the temperature of the liquid helium bath and maintaining thermal isolation. A closed helium-3 system was incorporated in the cryostet design.

Graphite affords opportunity for studying the effects of extreme crystalline anisotropy and whilst much is known qualitatively about graphite, the present work makes a much-needed contribution to the quantitative knowledge of electronic conduction in graphite.

An analysis of the magnetoconductivity tensor components, following McClure's work on Soule's single crystal data, leads to values for carrier densities and mobilities over the above range of temperatures.

For the first time data are presented on the Shubnikov-de Haas oscillations in pyrolytic graphite. An analysis of these quantum oscillations at about 1° K was used to estimate carrier effective masses and Dingle temperatures. Oscillation periods were used to give estimates of the parameters Δ , γ_2 , E_f which appear in the Slonczewski-Weiss band model of graphite and are not well determined by previous work. It was necessary to present the band model with an algebraic clarity not evident in the literature before undertaking these calculations. Use was made of this to investigate the value of the Jones-Zener expansion of the low magnetic field magneto-conductivity tensor. Extensive use of the Imperial College IBM computer was made throughout the course of the work reported here.

Previous work on pyrolytic graphite has yielded general outlines only, though Spain's survey established that the electronic properties of the best pyrolytic graphite closely approaches that of single crystals. The present work affords a comparison between the two; we conclude that the electronic structure of both types are essentially comparable, differences lying partly in scattering introduced by the mosaic, microcrystalline nature of pyrolytic graphite. Recent experimental results obtained by other workers have thrown new light on the interpretation of the Hall effect in particular: there are strong indications that carrier-carrier scattering is of outstanding importance in determining electronic conduction processes in graphite.

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CHAPTER 1.

1.1 <u>INTRODUCTION</u>

The physical and electronic properties of graphite provide a unique opportunity for studying extreme crystalline anisotropy. Whilst a great deal is known qualitatively about graphite, there remains a great deal to be achieved in the quantitative description of electronic properties, particularly as they relate to the magneto conductivity tensor, Fermi surface metrication and carrierlattice interactions.

The anisotropy of graphite stems from its crystal structure which (see Section 2.1) consists essentially of strongly bonded twodimensional sheets weakly held together by van der Waals forces. Ratios of thermal and electrical conductivities in the basal planes to those perpendicular to the basal planes (along the c-axis direction) can exceed 200 and 5000 respectively, even at room temperature.

Unfortunately, very few single crystals of the required perfection exist. The best of these won from the calcite deposits of Essex County, New York included untwinned regions only 2 mm. in extent. The high melting point (about 3800°C at 100 atmospheres) and mechanical weakness in the direction of basal shear make the task of growing single crystals in the laboratory an unusually difficult one. Crystallisation from solution in iron or tantalum monocarbide yields

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graphite crystals with untwinned regions of adequate size, but no such single crystal has a thickness in the c-direction sufficient for accurate characterisation of the c-axis properties of graphite.

The present work grew out of attempts in this laboratory to produce graphite by pyrolytic deposition which closely approached natural single crystal graphite in electrical and some physical properties. It is the first detailed analysis of the magnetoconductivity tensor components σ_{xx} , σ_{xv} and the periods and Dingle temperatures of the Shubuikov-de Haas oscillations in pyrolytic graphite. Previous publications have given general outlines only. In particular, Spain's (1967) survey of the electronic properties of the welloriented material produced in this laboratory, though demonstrating convincingly the close approach of the best pyrolytic graphite to single crystal behaviour, did not extend to a detailed analysis of Hall-effect and conductivity data and he was unable to report any oscillatory behaviour observable under his experimental conditions. Some light is thrown on the striking low field behaviour of Soule's (1958) Halleffect data which showed large excursions in the positive $(77^{\circ}K)$ or negative (298°K) direction at fields less than 1000 gauss. Soule suggested that these originated in the narrow regions connecting the hole and electron Fermi surfaces (see Figure 2.6). Ono and Sugihara (1968) disagreed, suggesting that on the simple model used by Soule the high mobility electrons near the tips of the electron Fermi

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surfaces play the dominant part in displacing the calculated Hall coefficient in a negative direction. Only when this effect was reduced both by trigonal warping of the ellipsoidal energy surfaces and also by inclusion of carrier-carrier scattering between majority and minority carriers were they able to explain Soule's positive low temperature Hall coefficient. Later work by Yeoman has confirmed that carrier-carrier scattering is much more important in graphite than ever hitherto suggested.

1.2 Preparation of Pyrolytic Graphite.

Under suitable conditions very pure carbon can be deposited in highly-oriented layers by the pyrolysis of hydrocarbon vapours passed over a heated substrate. Subsequent manipulation of the deposit produces quite large slabs of substantially pure mosaic single crystals, with densities approaching 95% of the theoretical single crystal value.

Methane was used in this laboratory, but acetylene, cyclohexane, and other gases have been used elsewhere. Dilution with hydrogen, nitrogen or a rare gas serves to delay co-precipitation within the deposit of carbon particles nucleated in the gas phase as a fine black, and reduces the re-evaporation of the graphite crystallites which form with a finite distribution of c-axis directions centred about the normal to the substrate surface. Blackman et al. (1961) found that deposition temperatures around 2000[°]C led to deposits which were

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highly ordered in this respect. Crystal orientation improved progressively with increase in deposition temperature up to 2200° C and was brought still closer to ideal graphite by annealing at around 2700° C.

Such a deposition texture leads to an increasing temperature gradient through the thickening deposit normal to the substrate surface if the former is resistance heated because of the low c-axis thermal conductivity. Temperature gradients of up to 350°C/mm. perpendicular to the deposit surface can be sustained at these high temperatures so that a 2 mm. layer having an external temperature of say 2200°C may be close to 3000°C for the inner layers. Whilst clearly requiring less power for a given maximum temperature than a uniform heating configuration this method does lead to a marked radial inhomogeneity in the deposit. Further heat treatment at temperatures above 3000°C leads to increased crystallite size and improved properties but inhomogeneities remain. Samples from the best material of the inner layers are thin and curved. Deposits formed in this way are normally turbostratic and measure about 200 Å along the basal planes of the crystallites. The c-axis distribution at this stage is about 20° wide, but soot particles, 2 to 3µm across, falling on the surface act as nuclei for conical growths which can lead to misorientations of up to 80° for individual crystallites.

Fortunately it was discovered (Moore et al., 1964) that when the inner layers reached about 3700° C (corresponding to deposits about 4 to 5 mm. thick) they distorted parallel to the surface of the substrate and the resulting shear largely eliminated soot nuclei and ripples, leading to an orientation (plane-normal distribution) of less than 1[°] in width. Sample W3 used in the present work was cut from such highly-annealed inner-layer material.

Commercially produced pyrolytic graphite is usually made by cracking the hydrocarbon gas on to a former heated externally by radiation. Such homogeneous graphite is available in large sizes from High Temperature Materials Inc., and Le Carbone, but as it has not undergone basal shear nor has been treated at high temperatures, it is sooty, of small crystallite size, and not as well aligned as the inner-layer material described above. However, its homogeneity is an advantage as it offers the possibility of further heat treatments Moore et al. (1964) cut pellets of commercial material, selected to be practically soot inclusion free, and subjected them to temperatures up to 2900°C. in a r.f. inductively-heated graphite die whilst under a unidirectional c-axis presure of 400 atmospheres. The die flowed plastically and allowed basal plane shear to occur. This increased the diameter of the pellets by 15 to 20% and produced samples within the theoretical density of pure graphite (2.266 gm/cm³), compared with starting material densities as low as 2.04 gm/cm³. Crystallite c-axes were oriented

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within 0.4° on average, but crystallite size along the basal planes was only about 0.1 μ m. Subsequent annealing at 3600 °C in a few atmospheres pressure of argon, under slight c-axis constraint to prevent exfoliation, led to no change in density but did reduce the half-width of the angular distribution of c-axes to 0.2°. Layer buckling over distances of the order of millimeters was much greater than this, say 1° depending on the starting material; score marks and other irregularities in the original substrate are not removed by the small shear which takes place on hot-pressing. X-ray work has shown that a slight radial inhomogeneity is present, presumably introduced by interaction of the pellet edges with the surrounding dic. However, by this means, crystalline graphite of large c-axis dimensions and with crystallite basal planes some 2 to 3 µm wide has been produced with a spread of c-axis orientation angles small enough to make comparison of its properties with theoretical single crystal models rewarding, even though the basal plane vectors \underline{a}_1 , \underline{a}_2 are still oriented planar-isotropically. Samples W1 and W2 reported here are both cut from pyrolytic graphite hot-pressed and then annealed as described above.

1.3 <u>Texture of Pyrolytic Graphite</u>

Klein (1962) reported in general terms that heating to greater than about 3500° C was required to eliminate high angle grain boundaries in the as-deposited graphite, but in fact post-deposition heat

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treatment has three main effects:

(1) The layer order is increased with increasing temperature;

A useful measure is the probability of stacking disorder p related to c-axis spacing, d, as given by the Bacon-Franklin equation (Franklin, 1951; Bacon, 1958). This drops rapidly towards zero (ideal graphite) for material deposited at successively higher temperatures above 1900°C (Blackman et al 1961).

A value of less than 0.07 is to be expected for good (not hot-pressed) material, implying less than one layer in 14 is disordered with respect to its neighbours. Spain et al (1967) suggest. from electron microscopy that the crystallite dimensions in the c-axis direction were $L_c \sim 1000 \rightarrow 2000$ Å implying $p \sim 0.002$ for well-oriented hot pressed and annealed pyrolytic graphite.

(2) <u>The distribution of preferred orientation decreases markedly</u> <u>in width</u>. It has been pointed out that hot-pressing produces angular distribution half-widths of about 0.2^o although layerplane buckling sometimes leads to deviations of 1^o or so over distances of mms.

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(3) <u>Grystallite growth occurs in both directions at high temperatures</u>. This is reflected in the value of p, above, for the c-axis direction. In the basal planes Klein estimates from carrier mobility that crystallites have diameters ~ 1 µm after treatment above 3000°C. The approach of the low temperature thermal resistivity to the T² specific heat law was calculated by Hooker et al to yield values 2 → 5 µm for basal plane dimensions of the near-ideal material used by Spain et al in general agreement with Klein and the results of electron micrography.

Recrystallised soot nuclei, in orientations differing greatly from their surroundings (Moore et al, 1964) survived in some hotpressed material. In such materials the differential thermal expansion which occurs on thermal cycling can lead to basal dislocation formation and the production of voids. Accordingly care was taken to select soot-free materials. Even so, sample W1 (Spain's SA22) used in the present work has a very narrow angular c-axis distribution despite the inclusion of some soot particles.

The density of ideal graphite is 2.2654 g/cm^3 . With increasing deposition temperature above 1900° C (Blackman et al, 1961) the sample density quickly reaches values close to this. Hot-pressed graphites usually have densities greater than $2.263 \pm 0.001 \text{ g/cm}^3$, implying a void concentration of less than 0.1%.

Since the covalent bond strength within basal planes of ~ 5 eV per atom (Kanter, 1957) is many times that between the planes

(~ 0.2 eV per atom) it is not surprising that glide takes place between layer planes and that non-basal glide has not been observed. The most common type of dislocation has its line and Burgers vector both lying within the basal plane. Because of the low stacking fault energy which causes basal glide, dislocations split into two partial dislocations with the region between the partials becoming effectively a ribbon some 600 to 1000 Å wide of rhombohedral material.

Screw dislocations with line and Burgers vectors both in nonbasal directions have been observed, but are less common. Thus Hennig (1965) demonstrated 10^6 screws/cm² in pyrolytic graphite heated to 3600° C with the screw pitch equal to the layer spacing. Ticonderoga (New York) natural crystals show some screws and growth spirals with a pitch of 450 Å or more (for a review see Roscoe and Thomas, 1966).

Moiré patterns enabled Dawson and Follet (1959) to demonstrate the existence of crystallites of 3000 Å in diameterin material which X-ray line-broadening studies had led to mean estimates of ~ 800 Å. An interpretation of certain Moiré fringes in terms of a type of dislocation having its line in a non-basal direction and Burgers vector in the basal plane is not generally accepted, but the existence and importance of such dislocations in the graphitisation process seems indicated in experiments by Jenkins et al (1962)

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on the crystallisation of carbon films at 3000°C.

From electron microscope studies Spain et al (1967) estimate a dislocation content of 10^4 cm per cm² basal plane area for the best of their stress-annealed material.

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CHAPTER 2

2.1 BAND STRUCTURE

2.1.1 The Structure of Graphite and the Brillouin Zone

Graphite has a hexagonal close-packed structure with four atoms per unit cell (Bernal, 1924). Fig. 2.1 shows the stacking sequence abab.. and the interatomic separations. There are two inequivalent pairs of lattice sites, one (AA') having atoms immediately above and below in nearest planes and the other (BB') having atoms immediately above and below in next nearest planes.

A rhombohedral graphite modification with stacking sequence abc, obtainable by the passage of partial basal plane dislocations, can coexist with the stable hexagonal form, but does not concern us here.

The first Brillouin-zone is a flat hexagonal cylinder, shown in Figure 2.3.

If we take the origin of the unit cell at an A site then the atomic positions within the unit cell are $\underline{t}_A = 0$, $\underline{t}_B = \frac{1}{3}(\underline{t}_1 - \underline{t}_2)$, $\underline{t}_{A'} = \frac{\underline{t}_A}{2}$, $\underline{t}_{B'} = -(\underline{t}_1 - \underline{t}_2)/_3 + \underline{t}_{A'_2}$ where \underline{t}_1 , \underline{t}_2 , \underline{t}_4 are the primitive translations for a simple hexagonal Bravais lattice and $\underline{t}_1 = \underline{t}_2 = \underline{t}_3 = 2 \cdot 46 \begin{pmatrix} A \\ a \end{pmatrix}$, $\underline{t}_A = 6.74 \text{ Å } (C_0)$.

The reciprocal lattice vectors \underline{K}_{i} are obtained from these primitive translation vectors through the definition $\underline{K}_{i} \cdot \underline{t}_{j} = 2\Pi\delta_{ij}$ (i, j = 1,2,4). This is most conveniently expressed in the form $\underline{K} \cdot \underline{T} = 2\Pi \underline{I}$ where the matrices \underline{K} and \underline{T} are composed of the rectangular cartesian components

of $\underline{K}_1, \underline{K}_2, \underline{K}_4$ and $\underline{t}_1, \underline{t}_2, \underline{t}_4$ and \underline{I} is the unit matrix.

$$\underline{\mathbf{K}} = \begin{bmatrix} \mathbf{K}_{1x} \ \mathbf{K}_{1y} \ \mathbf{K}_{1z} \\ \mathbf{K}_{2x} \ \mathbf{K}_{2y} \ \mathbf{K}_{2z} \\ \mathbf{K}_{3x} \ \mathbf{K}_{3y} \ \mathbf{K}_{3z} \end{bmatrix} \underbrace{\mathbf{T}}_{\underline{\mathbf{T}}} = \begin{bmatrix} \mathbf{t}_{1x} \ \mathbf{t}_{2x} \ \mathbf{t}_{3x} \\ \mathbf{t}_{1y} \ \mathbf{t}_{2y} \ \mathbf{t}_{3y} \\ \mathbf{t}_{1z} \ \mathbf{t}_{2z} \ \mathbf{t}_{3z} \end{bmatrix} = \begin{bmatrix} \sqrt{3ao} & -\sqrt{3ao} & 0 \\ \frac{ao}{2} & \frac{ao}{2} & 0 \\ 0 & 0 & \mathbf{Co} \end{bmatrix}$$

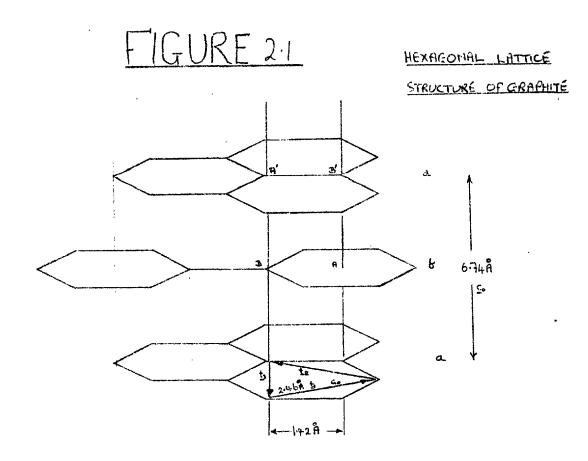
referred to axes in figure 2.2

For example, the equations for \underline{K}_1 are

$$K_{1x} \sqrt{\frac{3a0}{2}} + K_{1y} \frac{a0}{2} + K_{1z} \cdot 0 = 2\Pi \text{ and these give } K_{1x} = \frac{2\Pi}{\sqrt{3a0}}$$
$$-K_{1x} \sqrt{\frac{3a0}{2}} + K_{1y} \frac{a0}{2} + K_{1z} \cdot 0 = 0 \qquad K_{1y} = \frac{+2\Pi}{a0}$$
$$K_{1x} \cdot 0 + K_{1y} \cdot 0 + K_{1z} \cdot 0 = 0 \qquad K_{1z} = 0$$
$$K_{1z} = 0$$
$$i \cdot e \cdot K_{1} = \sqrt{\frac{2\Pi}{3a0}} \cdot \frac{+2\Pi}{a0} \cdot 0$$

The power of this way of finding the reciprocal lattice vectors, due to Jones, is that we may now write down all the required components simply by inverting <u>T</u>, for <u>K</u> = <u>K</u>.<u>T</u>.<u>T</u>.⁻¹ = 2<u>M</u><u>I</u><u>T</u>⁻¹ = 2<u>M</u><u>T</u>⁻¹ We find $T^{-1} = \begin{bmatrix} \sqrt{\frac{1}{3}ao} & \frac{1}{ao} & 0 \\ -\frac{1}{\sqrt{3}ao} & \frac{1}{ao} & 0 \\ 0 & 0 & \frac{1}{2}o \end{bmatrix}$

and so the required lattice vectors, referred to the cartesian axes shown in Figure 2.2. are $\underline{K}_1 = \sqrt{\frac{2\Pi}{3ao}}, \frac{2\Pi}{ao}, 0$) $\underline{K}_2 = \sqrt{\frac{2\Pi}{3ao}}, \frac{2\Pi}{ao}, 0$) $\underline{K}_3 = (0, 0, \frac{2\Pi}{Co})$



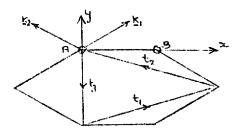
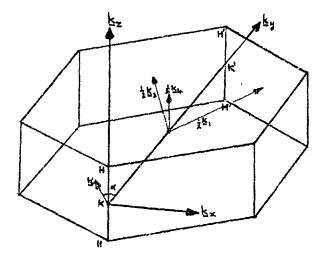


FIGURE 2.2

LATTICE VECTORS

FIGURE 2.3

THE FIRST BRILLOUIN ZONE OF GRAPHITE



Reciprocal Lattice vectors are shown, together with Mc Clure's notation for the coordinates of a point near a zone edge.

If we now construct planes to bisect the lines joining nearest neighbour reciprocal lattice points we see that all of reciprocal space can be filled by stacking together hexagonal prisms. We take the one arranged symmetrically about the origin to be the first Brillouin Zone, figure 2.3, where we have drawn the half vectors $\frac{K_1}{2} \cdot \frac{K_2}{2} \cdot \frac{K_4}{2}$ and also included the co-ordinates (K,α) of a point near the vertical zone edge HKH in McClure's notation (which will be employed later).

2.1.2 The Band Structure of Graphite

Early calculations of the graphite band structure were based upon a two-dimensional approximation because the large spacing between layers compared with the atomic spacing within the layers suggested that interplanar interactions might be neglected in a first approximation. In such an approach each layer is, in effect, a covalentlybonded two-dimensional crystal held to the next layer by much weaker Van der Waals forces.

Wallace (1947) constructed trigonally hybridised covalent bonds (sp^2) from three of the valence electrons, forming two *g*-bands; he considered the remaining one electron per atom to be in the $2p_z$ state with its symmetry axis perpendicular to the layer planes, forming two N-bands. Considering only nearest-neighbour interactions, he found that the highest occupied (valence) band and the lowest unoccupied (conduction) band were degenerate at the (two-dimensional)zone corners. Later tight-binding calculations by Coulson and Taylor (1952), Lomer (1955), McClure (1956), Corbato (1956) using different

approximations, agreed qualitatively with Wallace and with each other. The calculations asserted that graphite behaves like a two-dimensional semiconductor with a zero energy gap. It was necessary to invoke surface electrons or impurities to account for electrical and magnetic properties (Haering and Wallace 1957). Also, the model did not allow differing hole and electron masses (Galt, Yager, Dail, 1956).

The σ - Π energy gap was found to be large (Lomer ~ 1ev, Corbato ~ 6ev) at the zone corners so that transport properties are determined by the Π -bands only. Coupling between the σ and Π bands, though weak (~ 0.01 eV), is important in that it helps determine the sign of one of the parameters (γ_2) in the Slonczewski-Weiss band model in three dimensions (to be described below).

In Wallace's calculations for the three-dimensional case, he considered only the nearest-neighbour interactions between different planes and neglected the difference between A and B atom sites. This led to two bands being degenerate along the vertical zone edge (HKH). All bands were degenerate at the zone corners. Johnston (1955,1956) took more distant neighbours into account which gave a band overlap and anisotropy of the constant energy surfaces in the K_x - K_y plane.

Group theoretical studies were then undertaken to establish which types of structure are possible. The single layer Brillouin zone was

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investigated by Lomer (1955) and Slonczewski (1955) and the threedimensional zone by Carter (1953), Slonczewski (1955), and Slonczewski and Weiss (1955). The latter combined group theory with perturbation theory: previous calculations, reported above, had shown that the interesting part of the Brillouin zone was near the zone edge (not more than 1% of the distance from the edge to the zone centre). Thus, S-W made a Taylor expansion of the Hamiltonian in terms of K_x and K_y . In the K_z direction, however, they made a Fourier expansion which, because of the large layer spacing, was rapidly convergent becoming essentially equivalent to the tight binding approach. They used the "<u>K.P</u>" perturbation method of B.S.W. (1936) to calculate the change in the Hamiltonian for points just off the zone edge. This approach leads to a band model containing six constants which S.W. proposed should be obtained from experiment.

Three later papers contained band calculations based on the 1955 S.W. proposal and in 1958 SI-Weiss themselves published a full description of their group theoretical perturbation calculation.

McClure (1957) used the S.W. model to interpret the DHVA data of Shoenberg (1952), and Noziere (1958) interpreted the cyclotron resonance data of Galt, Yager and Dail (1956) using a modified form of the S.W. theory. He neglected the difference between A and B atom sites and replaced the hyperbolic bands by parabolic bands. Nozieres justified these approximations for interpretation of cyclotron resonance data, but pointed out that they lead to a completely false picture of the bands near the hexagonal zone faces. This would be very important for the interpretation of other properties, e.g. diamagnetic susceptibility.

We now describe the Slonczewski-Weiss band model in some detail.

2.1.3 Slonczewski-Weiss Band Model.

The increasing complexity of early band models of graphite compelled an examination of the possible structures from a general point of view. The group theoretical study by Slonczewski and Weiss (SW, 1955, 1958) filled this need and has stood the test of experiment admirably.

The two-dimensional calculations located the carriers in graphite on the BZ corners and three-dimensional calculations all agreed that the Fermi surface must be close to the vertical edges of the zone. In summary, SW found from their symmetry calculations that the wave functions for points on the vertical zone edge can be written in terms of Bloch sums of the single-layer eigenfunctions. Points just off the edge were treated by perturbation theory. They found four bands coming from 2p_z orbitals, two of which are degenerate along the zone edge HKH and H^{*}K^{*}H^{*}and on the hexagonal faces, the other two being degenerate only on the hexagonal faces in agreement with Hawring's finding that the small representations on the *Converts*

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hexagonal faces are 2-dimensional. Band 1 corresponds to the sum of Bloch waves made up from $2p_z$ orbitals on A and A' atoms and is generally the highest in energy. Band 2 corresponds to the difference between these same Bloch functions and is generally the lowest in energy. Bands 31 and 32 are degenerate along the zone edges and are made up from $2p_z$ orbitals based on B, B' atoms.

K.P. Perturbation Method

To explain the basis of this method we follow Callaway (p. 173, 1964), but mention that a concise derivation is given by Jones, (p.40, 1960). We start with wave functions $\#_n(\underline{K},\underline{r})$ for a state in the nth energy band with wave vector \underline{K} and $\#_j(\underline{K}_0,\mathbf{r})$ for a state in the jth band with wave vector \underline{K}_0 , and assume there is no degeneracy. Define the $i(\underline{K}-\underline{K}_0)\cdot\underline{r}$ $i\underline{S}\cdot\underline{r}$ functions $\Psi_j(\underline{K},\underline{r}) = e$ $\#_j(\underline{K}_0,\underline{r}) = e$ $\#_j(\underline{K}_0,\underline{r})$ (where $\underline{S} = \underline{K} - \underline{K}_0$).

These are satisfactory functions for describing one-electron states since they still have the Bloch forms-

$$\Psi_{j}(\underline{K},\underline{r}) = e^{i\underline{S}\cdot\underline{r}} \psi_{j}(\underline{K}_{0},\underline{r}) = e^{i\underline{S}\cdot\underline{r}} e^{i\underline{K}_{0}\cdot\underline{r}} e^{i\underline{K}_{0}\cdot\underline{r}} = e^{i\underline{K}\cdot\underline{r}} U_{j}(\underline{K}_{0},\underline{r}) = e^{i\underline{K}\cdot\underline{r}} U_{j}(\underline{K}_{0},\underline{r})$$

where $U_j(\underline{K}_0, \underline{r})$ has the required lattice periodicity, since ψ_j is assumed to be in a Bloch form. Also, if the ψ_j form a complete orthonormal set then so do the Ψ_j and any wave function can be expanded in a linear combination of the latter. In particular, we take;

$$\mathfrak{h}(\underline{K},\underline{r}) = \Sigma A_{j}(\underline{K}) \Psi_{j}(\underline{K},\underline{r}) = e^{i\underline{S}\cdot\underline{r}} A_{j}(\underline{K})\mathfrak{h}_{j}(\underline{K},\underline{r})$$

Substituting into the Schrödinger equation for the required energy eigenvalues, $E : H_{ij}(\underline{K},\underline{r}) = E(\underline{K})_{ij}(\underline{K},\underline{r})$

- where
$$H = \left[\frac{1}{2m_o} \left(\frac{\hbar}{i} \nabla\right)^2 + V(r)\right]$$

we obtain :- $H[e \sum_{j=1}^{i\underline{S}\cdot\underline{r}} A_{j}\psi_{j}] = E[e \sum_{j=1}^{i\underline{S}\cdot\underline{r}} A_{j}\psi_{j}]$ Now, the operator $(\frac{\hbar}{i}\nabla)^{2}$ acts on both parts of $e^{-\frac{i\underline{S}\cdot\underline{r}}{\psi_{j}}}$ so we have:

$$(\frac{\hbar}{i} \nabla)^2 e^{i\underline{S} \cdot \underline{r}} \psi_j = [\frac{\hbar}{i} \frac{\partial}{\partial x} (\frac{\hbar}{i} \frac{\partial}{\partial x} e^{i\underline{S} \cdot \underline{r}} \psi_j) + \dots + \dots]$$

$$= [\frac{\hbar}{i} \frac{\partial}{\partial x} (\frac{\hbar}{i} e^{i\underline{S} \cdot \underline{r}} \frac{\partial}{\partial x} \psi_j + \frac{\hbar}{i} i\underline{S} x e^{i\underline{S} \cdot \underline{r}} \psi_j) + \dots + \dots]$$

$$= (\frac{\hbar}{i})^2 [e^{i\underline{S} \cdot \underline{r}} \nabla^2 + 2i e^{i\underline{S} \cdot \underline{r}} \underline{S} \cdot \nabla - e^{i\underline{S} \cdot \underline{r}} S^2] \psi_j$$

Thus, operating with H in the Schrödinger equations-

$$\stackrel{\mathbf{i}\underline{S} \cdot \underline{r}}{e} \xrightarrow{\Sigma} \stackrel{\mathbf{i}\underline{F}}{j} \stackrel{\mathbf{j}\underline{\phi}}{j} \stackrel{\mathbf{i}\underline{h}}{m} \stackrel{\mathbf{2}}{e} \stackrel{\mathbf{i}\underline{S} \cdot \underline{r}}{\underline{S} \cdot \underline{r}} \xrightarrow{\Sigma} \stackrel{\mathbf{i}\underline{S} \cdot \underline{r}}{i} \stackrel{\mathbf{j}\underline{\phi}}{j} \stackrel{\mathbf{j}\underline{\phi}}{j} \stackrel{\mathbf{j}\underline{\phi}}{j} \stackrel{\mathbf{j}\underline{\phi}}{j} \stackrel{\mathbf{j}\underline{\phi}}{i} \stackrel{\mathbf{j}\underline{S} \cdot \underline{r}}{i} \stackrel{\mathbf{j}\underline{S} \cdot \underline{s}}{i} \stackrel{\mathbf{j}\underline{S} \cdot \underline{r}}{i} \stackrel{\mathbf{j}\underline{S} \cdot \underline{s}}{i} \stackrel{\mathbf{j}\underline{S} \cdot \underline{r}}{i} \stackrel{\mathbf{j}\underline{S} \cdot \underline{s}} \stackrel{\mathbf{j}\underline{S} \cdot \underline{s}}{i} \stackrel{\mathbf{j}\underline{S} \cdot \underline{s}} \stackrel{\mathbf{j}\underline{S} \cdot \underline{s}}{i} \stackrel{\mathbf{j}\underline{S} \cdot \underline{s}} \stackrel{\mathbf{j}\underline{S} \cdot \underline{s}}{i} \stackrel{\mathbf{j}\underline{S} \cdot \underline{s}} \stackrel{\mathbf{$$

 $-i\underline{S}\cdot\underline{r}$ * Multiplying by e ψ_i and integrating over the normalisation volume for the ψ_i :

$$E_{i}A_{i} - EA_{i} + \frac{\hbar^{2}S^{2}}{2m_{o}}A_{i} + \frac{\hbar}{m_{o}} \frac{S}{j} \sum_{ij} P_{ij}A_{j} = 0 \text{ where } \underline{P}_{ij} = \int \psi_{i}^{*} (\frac{\hbar}{i} \nabla) \psi_{j} dt$$

Similarly, we may multiply by all other e_{j_i} to generate further equations, obtaining a set of linear simultaneous equations for the coefficients A_i . For a non-trivial solution the determinant of the matrix of the coefficients of A_i must be zero, which leads to the usual polynomial in E:

The general element of this matrix is

$$M_{ij} = \frac{\hbar}{m_o} \underbrace{\mathbf{S}} \underbrace{\mathbf{P}}_{ij} + (\mathbf{E}_i - \mathbf{E} + \frac{\hbar^2 \mathbf{S}^2}{m_o}) \delta_{ij}$$

which we write as $H_{ij} - E(K)\delta_{ij}$ where $H_{ij} = (E_i(\underline{K}_0) + \frac{\hbar^2 S^2}{2m_0})\delta_{ij} + \frac{\hbar}{m_0} \underline{S} \cdot \underline{P}_{ij}$

Thus, we have the condition that $|H_{ij} - E\delta_{ij}| = 0$ and with this form of the equations we see that the required energy levels E at <u>K</u> (a distance <u>S</u> from <u>K</u>₀) are given as the eigenvalues of the Hamiltonian H_{ij} in terms of the eigenvalues $E_i(\underline{K}_0)$ at K_0 . Notice that if <u>S</u> = 0 then $H_{ij} = E_i \delta_{ij}$ and the values of E are simply the $E_i(\underline{K}_0)$ at \underline{K}_0 .

In the present case, we want to discover the effect on the energy levels of a very small change in $(\frac{|\underline{S}|}{|K_0|} \sim 1\%)$ so we appeal to perturbation theory for a further simplification. Second order perturbation theory gives an expression for the new energy levels in terms of the matrix elements of a perturbing Hamiltonian, H' (Schiff p.153).

$$\mathbf{E}_{n} = \mathbf{E}_{n}^{0} + \mathbf{H}_{nn} + \sum_{\substack{j=1\\j=n}}^{H_{i}} \frac{\mathbf{H}_{i}}{\mathbf{E}_{n} - \mathbf{E}_{j}}$$

- where E° is an unperturbed level, belonging to the wave vector K_{\circ} in our case. Thus, we have finally :-

$$E_{n}(\underline{K}) = E_{n}(\underline{K}_{o}) + \frac{\hbar^{2}S^{2}}{2m_{o}} + \frac{\hbar}{m_{o}} \underline{S} \cdot \underline{P}_{m_{1}} + \frac{\hbar^{2}}{m_{o}^{o}} \sum_{j \neq n} \frac{(\underline{S} \cdot \underline{P}_{nj})(\underline{S} \cdot \underline{P}_{jn})}{E_{n}(\underline{K}_{o}) - E_{j}(\underline{K}_{o})}$$

- which is the required expansion of the energy in terms of \underline{S} . The Hamiltonian Matrix

We shall now indicate how SW proceeded to derive their Hamiltonian for states near the vertical zone edges and relate this to McClure's Hamiltonian (1957) which is often used as a starting point for discussions relating to the SW band model. No attempt will be made to give a complete group-theoretical background to the derivation of the appropriate wave-functions.

First of all Slonczewski and Weiss considered the single-layer wave functions, U, satisfying the Bloch condition (imposed by translational symmetry) and having the local symmetry of the zone edge. By applying the <u>K.P</u> perturbation to the single-layer Hamiltonian they arrived at a secular equation giving energy values which varied linearly with <u>K</u>, the distance from the zone edge HKH (see Figure 2.3). The three-dimensional lattice has four atoms per unit cell, twice as many as in the single layer unit cell, so each layer state must give rise to two three-dimensional states. In particular, each of the layer Π states, U_1 , U_2 gives rise to two wave functions, ψ at \underline{K}_S where S labels a general point on the vertical zone edge HKH. These ψ 's can be constructed from single-layer functions but they must have the required symmetry at \underline{K}_S . The four wave functions are

$$\psi_{1} = \sqrt{2}$$

$$\psi_{1} = \sqrt{2}$$

$$\frac{1}{(a-a^{*})}$$

$$\psi_{2} = \sqrt{2}$$

$$\psi_{31} = b^{*}$$

$$\psi_{32} = b$$

$$\psi_{32} = b$$

$$\frac{1}{(a-a^{*})}$$

$$\frac{1}{(a-a^{*$$

This notation indicates the nature of the ¹⁰'s ; for example, if the function a were written as a linear combination of atomic orbitals, only those located on type A atoms would occur. Similarly for the a', b, b' functions and A', B, B'-type atoms respectively.

The symbols $\{\alpha \mid \underline{t}\}$ occurring in the above expressions are symmetry operators with the meaning $\{\alpha \mid \underline{t}\} f(\underline{r}) = \alpha f(\underline{r}) + \underline{t}$ where $f(\underline{r})$ is a function of position \underline{r} , α is a point group operator (e.g. a rotation) and \underline{t} is a translation vector. Thus, the $\{\epsilon \mid \underline{St}_4\}$ in ψ_{32} simply means that U_1 is to be displaced through the translation \underline{t}_4 (on to the next-but-one layer) each time a new term is added to the sum over S. (ε stands for the identity operation, ρ_3 is a reflection in the $\underline{t}_4-\underline{t}_3$ plane). We note that the above wave functions are approximate in that overlap energies between layers and $\sigma - \Pi$ band interaction energies have been neglected.

The way in which the energies $E_i(\underline{K}_z)$ of the above states vary with \underline{K}_z is not given by group theory and appeal must be made to tightbinding approximations and experiment for this information. However, the change in energy levels as the wave vector \underline{K} moves a short distance \underline{K} away from the vertical zone edge at \underline{K}_S can be obtained using the $\underline{K} \cdot \underline{P}$ perturbation method; the new set of energy levels is obtained by diagonalising the matrix of the perturbed Hamiltonian $H = H_0 + H^*$, where $H^* = \frac{\hbar}{m} \underline{K} \cdot \underline{P} + \frac{\hbar^2 \underline{K}^2}{2m}$ and H_0 has the eigenfunctions b_1 , b_2 , b_{31} , b_{32} with corresponding eigenvalues E_1^0 , E_2^0 , E_3^0 . Group theory gave the momentum matrix elements \underline{P}_{ij} apart from a constant factor.

SW obtained a Hamiltonian matrix given below with respect to the orthogonal set of wave functions b, a, a', b'. The element H_{aa} in the matrix below, for instance is given by $H_{aa} = [a(H_0+H^1)ad_T]$ which quickly reduces to

$$H_{aa} = \int aH_{0}ad\tau + \int a\frac{\hbar^{2}K^{2}}{2m} ad\tau + \int a\frac{\hbar}{m} \underline{K} \cdot \underline{P} ad\tau$$

$$= \frac{1}{2}(E_{1}^{0} + E_{2}^{0}) + \frac{\hbar^{2}K^{2}}{2m} + \int a\frac{\hbar\underline{K} \cdot P}{m} ad\tau$$

$$= \frac{1}{2}(E_{1}^{0} + E_{2}^{0}) + \frac{\hbar^{2}K^{2}}{2m} + \int a\frac{\hbar\underline{K} \cdot P}{m} ad\tau$$

$$= \frac{1}{2}(E_{1}^{0} + E_{2}^{0}) + \frac{\hbar}{m} ad\tau$$

$$= \frac{1}{2}(E_{1}^{0} + F_{2}^{0}) + F + \frac{1}{2}(E_{1}^{0} - E_{2}^{0}) + F^{*} D$$

$$= \frac{1}{2}(E_{1}^{0} - E_{2}^{0}) + \frac{1}{2}(E_{1}^{0} + E_{2}^{0}) + F + \frac{1}{2}(E_{1}^{0} - E_{2}^{0}) + F + D(1 + r^{*})$$

$$= \frac{1}{2}(E_{1}^{0} - E_{2}^{0}) + \frac{1}{2}(E_{1}^{0} + E_{2}^{0}) + F + D(1 + r^{*})$$

$$= \frac{1}{2}(E_{1}^{0} - E_{2}^{0}) + \frac{1}{2}(E_{1}^{0} + E_{2}^{0}) + F + D(1 + r^{*})$$

In the above, $F = \frac{\hbar^2 K^2}{2m}$ and $D = (\hbar^P o/_m) Ke^{i\alpha}$ - this comes from the momentum matrix P. The P, q, r are functions of $\underline{K}_{\underline{z}}$. One could diagonalise this matrix to obtain the required energy levels, but we prefer to switch to McClure's notation in order to pursue our investigation of the band structure. Unfortunately, McClure quotes but does not derive a Hamiltonian matrix (see below) which is different in form from the one given above. It is evident, in fact, that he has used a different set of basis functions to generate his matrix. To give the same eigenvalues, his matrix must be related through a unitary transformation to the SW matrix above and this implies that his basis functions are linear combinations of the a, a¹, b, b¹. In fact, it is fairly obvious that he has used the actual ψ 's above $(\psi_1, \psi_2, \psi_{31}, \psi_{32})$ as his basis. We proceed to demonstrate this :

We have
$$\psi_1 = \frac{1}{\sqrt{2}} (a+a^1)$$
, $\psi_2 = \frac{1}{\sqrt{2}} (a-a^1)$, $\psi_{31} = b^1$, $\psi_{32} = b$

Now, if our assumption is correct, McClure's Hamiltonian matrix elements are given by

 $H_{ij}^{MC} = \int \psi_i H_{\psi_j} d_{\mathbf{T}} \quad \text{where i, j stand for the labels on the}$ $\psi_i^{t} s ((1), (2), (31) \text{ etc.}).$

Substituting for the U's :-

$$H_{1,1}^{MC} = \int_{2}^{1} (a+a+)H_{2}(a+a+)d_{r} = \frac{1}{2} \int_{2}^{1} (a+a+)d_{r} + \frac{1}{2} \int_{2}^{1} (a+a+)H_{2}(a+a+)d_{r} = \frac{1}{2} \int_{2}^{1} (a+a+)d_{r} + \frac{1}{2} \int_{2}^{1} (a+a+)H_{2}(a+a+)d_{r} = \frac{1}{2} \int_{2}^{1} (a+a+)H_{2}(a+)d_{r} = \frac{1}{2} \int_{2}^{1} (a+)H_{2}(a+)H_{2}(a+)d_{r} = \frac{1}{2} \int_{2}^{1} (a+)H_{2}(a+$$

$$= \frac{1}{2} (H_{aa} + H_{aa'} + H_{a'a} + H_{a'a'})$$

where H_{ij} is the ijth element of the SW Hamiltonian matrix.

Thus we see that it is not necessary to recalculate the matrix elements; it is sufficient to take combinations of elements from the SW Hamiltonian to generate the matrix with respect to the new basis functions. We now list the required combinations

$$H_{1,1} = \frac{1}{2}(H_{aa} + H_{aa'} + H_{a'a} + H_{a'a'}) = E_1^0 + F$$

$$H_{1,2} = \frac{1}{2}(H_{aa} + H_{a'a} - H_{aa'} - H_{a'a'}) = 0$$

$$H_{1,31} = \sqrt{2}(H_{ab'} + H_{a'b'}) = P^*D - D(1 + r^*)$$

$$H_{1,32} = \sqrt{2}(H_{ab} + H_{a'b}) = P^*D^* - D^*(1 + r^*)$$

$$H_{2,1} = \frac{1}{2}(H_{aa} + H_{aa^{\dagger}} - H_{a^{\dagger}a} - H_{a^{\dagger}a^{\dagger}}) = 0$$

$$H_{2,2} = \frac{1}{2}(H_{aa} - H_{aa^{\dagger}} - H_{a^{\dagger}a} + H_{a^{\dagger}a^{\dagger}}) = E_{2}^{0} + F$$

$$H_{2,31} = \sqrt{2}(H_{ab^{\dagger}} - H_{a^{\dagger}b^{\dagger}}) = P^{*}D + D(1 + r^{*})$$

$$H_{2,32} = \sqrt{2}(H_{ab} - H_{a^{\dagger}b}) = -(P^{*}D^{*} + D^{*}(1 + r^{*}))$$

$${}^{H}_{31,1} = \frac{1}{\sqrt{2}} (H_{b^{\dagger}a} + H_{b^{\dagger}a^{\dagger}}) = PD^{*}_{-D} (1+r)$$

$$H_{31,2} = \frac{1}{\sqrt{2}} (H_{b^{\dagger}a} - H_{b^{\dagger}a^{\dagger}}) \Rightarrow PD^{*}_{+D} (1+r)$$

$$H_{31,31} = H_{b^{\dagger}b^{\dagger}} = E_{3}^{0} + F$$

This leads to the following matrix which can be directly compared, term by term, with McClure's (neglecting the second order in K term; F, and assuming r, F are real.

$$H = \begin{bmatrix} E_{1}^{o} & 0 & (PD-D(1+r) & (PD-D(1+r))^{*} \\ 0 & E_{2}^{o} & (PD+D(1+r)) & -(PD+D(1+r))^{*} \end{bmatrix}$$

$$(PD-D(1+r))^{*} & (PD+D(1+r))^{*} & E_{3}^{o} & qD$$

$$(PD-D(1+r)) & -(PD+D(1+r)) & qD^{*} & E_{3}^{o} \end{bmatrix}$$

From this point on we use McClure's notation (Figure 2.3) and the set of dimensionless cylindrical variables defined by:

$$\alpha = \operatorname{ten}^{-1}\left(\frac{K_{X}}{K_{Y}}\right), \quad \sigma = \frac{1}{2}/3 a_{o}|K|, \quad \zeta = K_{z}C_{o}$$

where, as shown in the figure (2.3) K is the perpendicular distance of a point <u>K</u> in the B.Z. from a vertical zone edge. The Hamiltonian matrix given by McClure is

$$H = \begin{bmatrix} E_{1}^{\circ} & 0 & H_{13} & H_{13}^{*} \\ 0 & E_{2}^{\circ} & H_{23} & -H_{23}^{*} \\ H_{13}^{*} & H_{23}^{*} & E_{3}^{\circ} & H_{33} \\ H_{13}^{*} & -H_{23} & H_{33}^{*} & E_{3}^{\circ} \end{bmatrix}$$

which, we have seen, follows directly from Slonczewski's work, where

$$E_{1}^{0} = \Delta + \gamma_{1} \Gamma + \frac{1}{2} \gamma_{5} \Gamma^{2}$$

$$E_{2}^{0} = \Delta - \gamma_{1} \Gamma + \frac{1}{2} \gamma_{5} \Gamma^{2}$$

$$E_{3}^{0} = \frac{1}{2} \gamma_{2} \Gamma^{2}$$

$$H_{13} = 2^{-\frac{1}{2}} (-\gamma_{0} + \gamma_{4} \Gamma) \sigma \exp(i\alpha) \text{ and } \Gamma = 2\cos(\frac{1}{2} K_{z} C_{0})$$

$$H_{23} = 2^{-\frac{1}{2}} (\gamma_{0} + \gamma_{4} \Gamma) \sigma \exp(i\alpha)$$

$$H_{33} = \gamma_{3} \Gamma \sigma \exp(i\alpha)$$

It is clear that to first order in σ (second order does not change the form of the Hamiltonian) and to second order in the Fourier expansion the band structure can be completely described by six parameters. S.W. did not attempt to derive these parameters from theory but proposed they be obtained from experiment; some of them may be negligible in a given application. We have neglected spin orbit effects at this stage as these have beer shown to be very small (G. Dresselhans and M.S. Dresselhans 1965), but of course each of the four bands obtained from this Hamiltonian is two-fold spin degenerate.

The secular equation for the above Hamiltonian matrix leads to an unwieldy quartic equation in energy which it is uninstructive to examine. Certain restrictions, however, lead to factorisation into two quadratics.

Multiplying out the secular determinant |H - EI| = 0 where I is the unit matrix, leads to the expression

$$\epsilon_{1}\epsilon_{2}\epsilon_{3}^{2} - \epsilon_{1}\epsilon_{2}\gamma_{3}^{2}\Gamma^{2}\sigma^{2} - \epsilon_{1}\epsilon_{3}(\gamma_{0}+\gamma_{4}\Gamma)^{2}\sigma^{2} - \epsilon_{2}\epsilon_{3}(-\gamma_{0}+\gamma_{4}\Gamma)^{2}\sigma^{2} + (\gamma_{0}+\gamma_{4}\Gamma)^{2}(-\gamma_{0}+\gamma_{4}\Gamma)^{2}\sigma^{4} - \epsilon_{1}\sigma^{3}\gamma_{3}\Gamma(\gamma_{0}+\gamma_{4}\Gamma)^{2}\cos 3\alpha + \epsilon_{2}\sigma^{3}\gamma_{3}\Gamma(-\gamma_{0}+\gamma_{4}\Gamma)^{2}\cos 3\alpha = 0$$

where $\varepsilon_1 = E_1^0 - E_{\chi}$, $\varepsilon_2 = E_2^0 - E_{\chi}$, $\varepsilon_3 = E_3^0 - E_{\bullet}$. This is the equation which must be solved for the energy, E. A numerical solution is possible, but more physical insight is gained by examining approximate solutions. For instance, neglecting γ_3 leads to :-

$$\varepsilon_{1}\varepsilon_{2}\varepsilon_{3}^{2} - \varepsilon_{1}\varepsilon_{3}(\gamma_{0}+\gamma_{4}\Gamma)^{2}\sigma^{2} - \varepsilon_{2}\varepsilon_{3}(\gamma_{0}+\gamma_{4}\Gamma)^{2}\sigma^{2} + (\gamma_{0}+\gamma_{4}\Gamma)^{2}(\gamma_{0}+\gamma_{4}\Gamma)^{2}\sigma^{4}$$
$$= 0$$

Which factorises into

$$(\varepsilon_{1}\varepsilon_{3} - (-\gamma_{0}+\gamma_{4}\Gamma)^{2}\sigma^{2})(\varepsilon_{2}\varepsilon_{3} - (\gamma_{0}+\gamma_{4}\Gamma)^{2}\sigma^{2}) = 0$$

Leading to solutions which are independent of angle α :

$$E_{1,31} = \frac{1}{2} (E_1^{\circ} + E_3^{\circ}) \pm [\frac{1}{4} (E_1^{\circ} - E_3^{\circ})^2 + (\gamma_{\circ} - \gamma_4 \Gamma)^2 \sigma^2]^{\frac{1}{2}}$$

$$E_{2,32} = \frac{1}{2} (E_2^{\circ} + E_3^{\circ}) \pm [\frac{1}{4} (E_2^{\circ} - E_3^{\circ})^2 + (\gamma_{\circ} + \gamma_4 \Gamma)^2 \sigma^2]^{\frac{1}{2}}$$
(2)

Now, the reciprocal effective mass tensor is defined by

$$R_{ij}^{*} = \frac{1}{n^{2}} \frac{\partial^{2}E}{\partial K_{i}\partial K_{j}}$$

Thus,

$$R_{xx}^{*} = \pm \frac{1}{\hbar^{2}} \frac{\partial}{\partial K_{x}^{*}} \left[\left(\frac{1}{2} \sqrt{3} a_{0}^{2} \right) (\gamma_{0} \gamma_{4} \Gamma)^{2} 2K_{x} \right] \left(\left(\frac{\Delta E^{0}}{2} \right)^{2} + (\gamma_{0} \gamma_{4} \Gamma)^{2} \sigma^{2} \right)^{\frac{1}{2}} \right]$$

$$= \pm \frac{1}{\hbar^{2}} (\gamma_{0} \gamma_{4} \Gamma)^{2} \frac{3}{4} a_{0}^{2} \left[\left(\frac{\Delta E^{0}}{2} \right)^{2} + (\gamma_{0} \gamma_{4} \Gamma)^{2} \frac{3}{4} a_{0}^{2} K_{y}^{2} \right] / \left[\left(\frac{\Delta E^{0}}{2} \right)^{2} + (\gamma_{0} \gamma_{4} \Gamma)^{2} \sigma^{2} \right]^{\frac{3}{2}}$$

where $\Delta E^{\circ} = E_1^{\circ} - E_3^{\circ}$ or $E_2^{\circ} - E_3^{\circ}$ depending on which surface the mass tensor is evaluated. The upper sign refers to the upper of two conjugate hyperboloids. For R_{yy}^{*} , K_y^2 should be replaced by K_x^2 . For R_{xy}^{*} the term ΔE° does not appear in the numerator, K_y^2 is replaced by $K_x K_y$ and the signs are written \mp : We see that the effective mass depends on K_z (through Γ and ΔE°), and also on the distance σ from the zone edge. However, for small enough σ one obtains paraboloidal bands and constant effective mass for a given value of K_z :-

$$R_{xx}^{*} = R_{yy}^{*} \simeq \pm \frac{3(\gamma_{0} - \gamma_{4} \Gamma)^{2} a_{0}^{2}}{2\hbar^{2} \Delta E^{0}}$$

 $R_{xy}^* = 0$

Inverting this tensor to give the effective mass tensor ;

$$\mathbb{M}_{ij}^{*} = (\mathbb{R}^{*-1})_{ij} = \frac{(\operatorname{adj} \mathbb{R})_{ij}}{|\mathbb{R}|}$$

leads to
$$m^* = \begin{bmatrix} 1 & 0 & 0 \\ R_{XX}^* & 1 & 0 \\ 0 & R_{XX}^* & 1 \\ 0 & 0 & R_{ZZ}^* \end{bmatrix}$$

where we have invoked crystal

symmetry (6/mm) to give $R_{iz} = R_{zi} = 0$ (where i = x, y). [See Birss, 1964]. Finally, then, we have an effective mass for directions parallel to the basal plane :

$$\frac{1}{m_{a}^{*}(K_{z})} = \pm \frac{3(\gamma_{0}-\gamma_{4}\Gamma)^{2}a_{o}^{2}}{2\hbar^{2}\Delta E^{o}}$$

The energy-wave number relationships for these four bands are quite complicated surfaces which can be envisaged by examination of figure 2.4.

Here an attempt has been made to indicate the variation of the bands with small excursions from the K_z axis (HKH) because this is all-important in determining where electrons and holes can exist. However, before examining this question further, we shall list the parameters defining the energy surfaces shown, indicating their main effects and where they arise in the theory. The latest values assigned by Dresselhams and Maveroides (1964) are quoted here, but are not pp completely independent of the method by which they were measured so various earlier experimental determinations will be discussed later.

- γ_0 . This is the same as Wallace's γ_0 and is most important in determining the dependence of energy on σ (i.e. |K|). It is the only parameter in the single-layer case and represents overlap between wave functions centred on nearest neighbour A and B atoms. (2.8eV).
- γ_1 . Represents the main splitting of the singly-degenerate bands caused by the interlayer interaction between wave functions on nearest A atoms. (0.39eV).

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- γ_2 . Determines the amplitude of the variation of the E₃ bands with K_z and so is responsible for the band overlap. It arises from both the next-nearest layer interaction between B atoms and from $\sigma - \pi$ coupling, but these two effects almost cancel. It is now thought that γ_2 is + ve. (+ 0.016eV).
- γ_3 . Arising from nearest layer interactions, this gives rise to anisotropy in the xy plane and to extra degeneracies found by Johnston (see below). Wallace neglected this term although it appeared in his Hamiltonian. (0.15eV).
- γ_4 . Although this does not have a qualitative effect on the band structure, it could give rise to appreciable (10% or so) quantitative effects. It would be the same as γ_3 if the orbitals on A and B atoms were identical and was assumed to be $\simeq \gamma_3$ in the absence of experimental evidence. However, Dress. and Mavr. estimate $\gamma_4 = -0.20$ eV.
- γ_5 . This is essentially the coefficient of the second term in the Fourier expansion along K_z and is often neglected. In the absence of an experimental value, it is assumed to be $\simeq \gamma_2$ (0.016eV).
- A Reflects the fact that A and B atomic sites are situated in different crystalline fields and also involves nextnearest layer overlap integrals. It causes a separation in the two sets of levels at $K_z = \pm \frac{\pi}{C_0}$. (-0.02eV).

In practice, one cannot assume that the sample is entirely free from impurities so the Fermi level (somewhere between 0 and $2\gamma_2$) must be regarded as another unknown parameter. However, on the assumption of pure graphite (equal numbers of electrons and holes) Dresselhans and Mavroides have calculated $E_f \simeq 0.019 \text{eV}$.

One must now decide where in the Brillouin Zone the holes and electrons must lie with these values of the band parameters. We still neglect γ_3 . By writing equations 2.1.3(2) for small values of σ it is easy to see that the variations of the energy levels with σ are as indicated in figure 2.3. For instance, the E₁ level increases in energy with a small excursion from the zone edge (a small increase in σ) at constant K_z near K_z \simeq zero but decreases in energy for a similar excursion made near K_z = $\pm \frac{\pi}{C_0}$. It is not so obvious at first sight where the change-over in behaviour takes place. We examine E₁ first and then ε_3 :

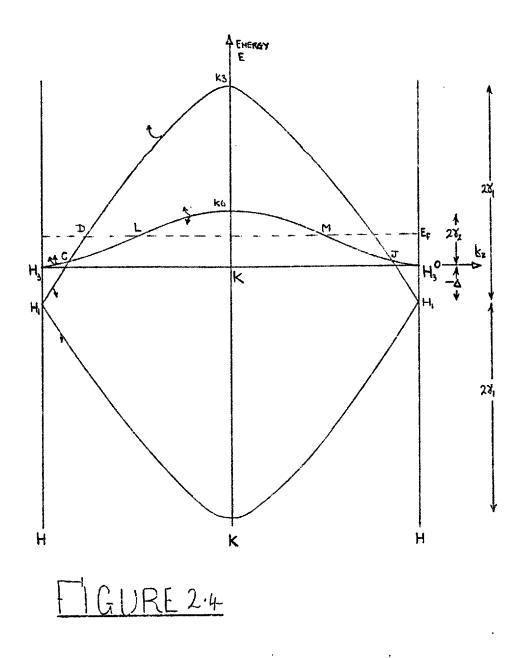
From 2.1.3(2) for small σ :

Now, the σ -variation changes its nature (towards or away from the K_z-axis) when the slope of this linear relation between E₁ and σ^2

changes sign. Notice the constant inside the bracket has been made independent of K_2 . Thus, the σ -variation changes its nature when $E_1^o(E_1^o-E_3^o) = 0$ i.e. $E_1^o = 0$ or $E_1^o = E_3^o$. So, as K_2 is increased from zero, where E_1 increases positively away from the K_2 -axis with a small σ -excursion, towards π/C_0 , the E_1 behaviour will change where E_1^o crosses E_3^o and so beyond here E_1 will decrease (towards the K_2 -axis) with increase in σ . At $E_1^o = 0$ the nature again changes so E_1^i will once more increase away from the axis with small increase in σ , but its sign also changes here so this represents a continuation of previous behaviour, viz. a downward change in E_1 with σ . Thus, E_1 changes its σ -variation from an increase in E with σ to a decrease in E with σ as K_2 is increased through the value where E_1^o and E_3^o intersect. Similarly for E_1 :

$$E_{31} \simeq E_{3}^{\circ} - \frac{1}{4} \frac{(\gamma_{\circ} - \gamma_{4}\Gamma)^{2} \alpha^{2}}{(E_{1}^{\circ} - E_{3})^{*}}$$
$$= E_{3}^{\circ} [1 - \frac{1}{4} (\frac{\gamma_{\circ} - \gamma_{4}\Gamma}{E_{3}^{\circ} (E_{1}^{\circ} - E_{3}^{\circ})^{*}}]$$

So we see E_{31} changes its nature from E - increasing at $K_z = 0$ (easily verified) to E - decreasing with small excusions of σ as K_z makes $E_1^{0}-E_3^{0}$ change sign, i.e. as K_z increases through the point of intersection of E_1^{0} and E_3^{0} .



ENERGY GANDS ALONG A ZONE EDGE HKH. Energy increases and decreases a short distance from the edge are indicated by arrows.

 E_{32} remains E-decreasing over the whole range $-\frac{\pi}{C_0} \leq K_z \leq \frac{\pi}{C_0}$. We can now see that the curve $H_3CK_6JH_3$ represents the bottom of the conduction band and $H_1CK_6JH_1$ the top of the valence band. With the Fermi level as shown we have holes in the central region below LK_6M and electrons above the two end curves H_3CL , MJH_3 :

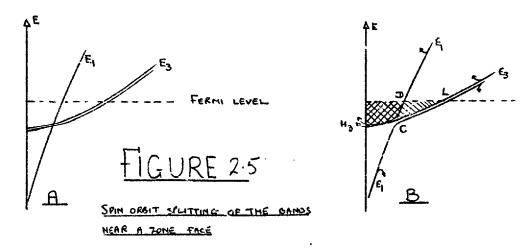
This is clear if we note the following properties of the bands. The effective mass tensor has only diagonal components m_{ij}^{π} for small enough σ and these have the same sign as the corresponding reciprocal mass tensor components R_{ii}^{*} . Now, by differentiating the expressions for the energy levels, E_i , twice with respect to the components of <u>K</u> (as we have demonstrated above in the case of $\frac{\partial^2}{\partial K_{-}\partial K_{-}}$) and also differentiating once with respect to σ_{i} we can see that the sign of $\frac{\partial E}{\partial \sigma}$ is the same as that of R_{xx}^{*} (= R_{yy}^{*}). Thus, we have finally that the sign of $\frac{\partial E}{\partial \sigma}$ is the same as the sign of m_{xx}^* (= m_{yy}^*) and so the σ -variation of a particular band indicates the electron or hole nature of the band; + ve means the band is electronic in nature at the given value of \underline{K}_z . This arises from the particular form of the bands near to the vertical zone edge. We see immediately that holes are located on the E_3 surface below the line LK₆M, which is the cross-section taken where the band reaches its highest point. A complication arises near the point C, however, where the bands E_1 and E_3 are degenerate. Group theory does not require more than the two-fold $E_{31}-E_{32}$ degeneracy at

this point on the zone edge so we have a case of so-called "accidental" degeneracy. To examine the probable consequences, it is convenient first to lift the degeneracy of the E_3 band by means of spin-orbit coupling. This effect is small, but enables one to draw E_{31} , E_{32} separately and thus see what is happening. We now have the situation shown in Figure 2.5A.

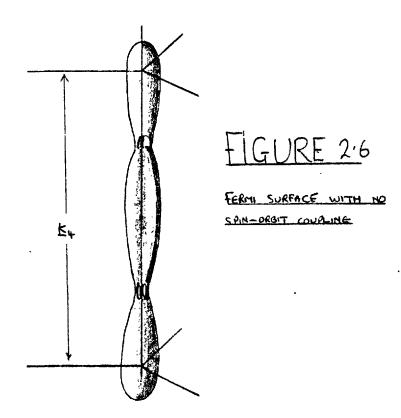
However, the interaction between these bands at this point will cause the wave-functions to mix and prevent their crossing (see Slater, Vol. II, p.270, 1967), leading to a situation shown in Figure 2.5B.

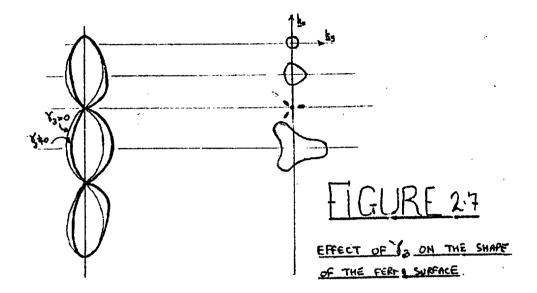
Putting in the σ -variation of energy in the usual way enables us to see immediately that there are two energy surfaces which can give rise to electron behaviour near the Fermi energy, LCH₃ and the new one DCH₃ which gives rise to a pocket of electrons. Indeed, in the presence of spin-orbit coupling, when the H₃ band splits all the way to the hexagonal zone face, the pocket is completely isolated. The Fermi surface is illustrated in Figure 2.6 for the case with no spinorbit coupling where the pockets may be translated by the reciprocal lattice vector \underline{K}_4 to join on to the ends of the electron surfaces. This join is perfectly smooth because of time reversal degeneracy on the horizontal zone faces (MoClure, IBM, <u>8</u>, 258, 1964).

The inclusion of the γ_3 in the Hamiltonian leads to the additional structure shown in Figures 2.6 and 2.7), destroying the rotational symmetry of the energy bands so far considered. Although it is



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no longer possible to factor the secular equation for general values of α , σ , this is possible for special values of α ($=\frac{1}{3}$ n Π).

Equation 2.1.3(1) reduces to that expression with $\cos 3\alpha = (-1)^n$ which immediately factorises into two quadratics;

$$(\varepsilon_{1}\varepsilon_{3}+\varepsilon_{1}\gamma_{3}\Gamma_{\sigma}(-1)^{n}-(-\gamma_{o}+\gamma_{4}\Gamma)^{2}\sigma^{2})(\varepsilon_{2}\varepsilon_{3}-\varepsilon_{2}\gamma_{3}\Gamma_{\sigma}(-1)^{n}-(\gamma_{o}+\gamma_{4}\Gamma)^{2}\sigma^{2})=0$$

Substituting for ε_1 , ε_2 , ε_3 gives two quadratics in E which can be solved, leading finally to the solutions:

$$E_{1,31} = \frac{1}{2} (E_1^0 + E_3^0 + \gamma_3 \Gamma_{\sigma} \cos 3\alpha) \pm [\frac{1}{4} (E_1^0 - E_3^0 - \gamma_3 \Gamma_{\sigma} \cos 3\alpha)^2 + (\gamma_0 - \gamma_4 \Gamma)^2 \sigma^2]^{\frac{1}{2}}$$

$$E_{2,32} = \frac{1}{2} (E_2^0 + E_3^0 - \gamma_3 \Gamma_{\sigma} \cos 3\alpha) \pm [\frac{1}{4} (E_2^0 - E_3^0 + \gamma_3 \Gamma_{\sigma} \cos 3\alpha)^2 + (\gamma_0 + \gamma_4 \Gamma)^2 \sigma^2]^{\frac{1}{2}}$$

$$(\alpha = \frac{1}{3} n \Pi)$$

These equations can be used to obtain the cross-section of the Fermi-Surface in the K_z-K_y plane ($\alpha = 0$) for, putting $\alpha = 0$, $E = E_f$ we have, for examples

$$(\gamma_{\sigma} \gamma_{4} \Gamma)^{2} = \mathbb{E}_{\mathbf{f}}^{2} + \mathbb{E}_{1}^{\circ} \mathbb{E}_{3}^{\circ} - \mathbb{E}_{\mathbf{f}} (\mathbb{E}_{1}^{\circ} + \mathbb{E}_{3}^{\circ} + \gamma_{3} \Gamma_{\sigma}) + \mathbb{E}_{1}^{\circ} \gamma_{3} \Gamma_{\sigma}$$

- which gives σ in terms of K_z (contained in Γ). Putting $\alpha = 3x\frac{11}{3}$ leads to the same equation with the sign attached to γ_3 changed, so we can find the cross section of the Fermi-Surface in both halves of the K_z-K_y plane. The Figure 2.7 (after NcClure) shows the cross sections for the cases $\gamma_3 = 0$ and $\gamma_3 \neq 0$ superimposed to emphasize the asymmetry introduced by this parameter.

Obtaining the $K_x - K_y$ cross sections is difficult because the secular equation has to be solved for general α and with γ_3 included. This can be done (in the case E_1 , E_2 are well separated from E_3) but note that this will still leave the exact structure in the region near C (Figure 2.4) income doubt.

Specifically, we assume $\varepsilon_1 \varepsilon_2 >> \varepsilon_3$, E, which reduces equation 2.1.3(1) to

$$E_{1}^{o}E_{2}^{o}\varepsilon_{3}^{2} - E_{1}^{b}E_{2}^{o}\gamma_{3}^{2}\Gamma^{2}\sigma^{2} - E_{1}^{o}\varepsilon_{3}(\gamma_{0}+\gamma_{4}\Gamma)^{2}\sigma^{2} - E_{2}^{o}\varepsilon_{3}(-\gamma_{0}+\gamma_{4}\Gamma)^{2}\sigma^{2}$$
$$- E_{1}^{o}(\gamma_{0}+\gamma_{4}\Gamma)^{2}\sigma^{3}\gamma_{3}\Gamma \cos 3\alpha + E_{2}^{o}(-\gamma_{0}+\gamma_{4}\Gamma)^{2}\sigma^{3}\gamma_{3}\Gamma \cos 3\alpha + (\gamma_{0}+\gamma_{4}\Gamma)^{2}\sigma^{3}\gamma_{3}\Gamma \cos 3\alpha + (\gamma_{0}+\gamma_{4}\Gamma)^{2}(-\gamma_{0}+\gamma_{4}\Gamma)^{2}\sigma^{4} = 0$$

Substituting for
$$\varepsilon_{3} = E_{3}^{0} - E$$
 leads to a quadratic in $E :=$
 $E^{2}E_{1}^{0}E_{2}^{0} + E[-2E_{1}^{0}E_{2}^{0}E_{3}^{0} + E_{1}^{0}(\gamma_{0}+\gamma_{4}\Gamma)^{2}\sigma^{2} + E_{2}^{0}(-\gamma_{0}+\gamma_{4}\Gamma)^{2}\sigma^{2}]$
 $E_{1}^{0}E_{2}^{0}E_{3}^{2} - E_{1}^{0}E_{2}^{0}\gamma_{3}^{2}\Gamma^{2}\sigma^{2} - E_{1}^{0}E_{3}^{0}(\gamma_{0}+\gamma_{4}\Gamma)^{2}\sigma^{2} - E_{2}^{0}E_{3}^{0}(-\gamma_{0}+\gamma_{4}\Gamma)^{2}\sigma^{2}$
 $-E_{1}^{0}(\gamma_{0}+\gamma_{4}\Gamma)^{2}\sigma^{3}\gamma_{3}\Gamma \cos 3\alpha + E_{2}^{0}(-\gamma_{0}+\gamma_{4}\Gamma)^{2}\sigma^{3}\Gamma \cos 3\alpha$
 $+(\gamma_{0}+\gamma_{4}\Gamma)^{2}(-\gamma_{0}+\gamma_{4}\Gamma)^{2}\sigma^{4} = 0$

+

This can be solved and simplified to give

$$E = E_{3}^{\circ} - \frac{1}{2E_{2}^{\circ}} (\gamma_{\circ} + \gamma_{4}\Gamma)^{2} \sigma^{2} - \frac{1}{2E_{1}^{\circ}} (-\gamma_{\circ} + \gamma_{4}\Gamma)^{2} \sigma^{2}$$

$$\pm \left\{ \frac{1}{4} \frac{(\gamma_{\circ} + \gamma_{4}\Gamma)^{4}}{E_{2}^{\circ 2}} \sigma^{4} + \frac{1}{4} \frac{(-\gamma_{\circ} + \gamma_{4}\Gamma)^{4}}{E_{1}^{\circ 2}} \sigma^{4} - \frac{1}{2} \frac{1}{E_{1}^{\circ}E_{2}^{\circ}} + \gamma_{3}^{2}\Gamma^{2} \sigma^{2} + \gamma_{3}^{2}\Gamma^{2} \sigma^{2} + \left(\frac{-1}{E_{1}^{\circ}} (-\gamma_{\circ} + \gamma_{4}\Gamma)^{2} + \frac{1}{E_{2}^{\circ}} (\gamma_{\circ} + \gamma_{4}\Gamma)^{2}\right) \gamma_{3} \sigma^{3} \Gamma \cos 3\alpha \right\}^{\frac{1}{2}}$$

Finally, this can be written :

$$E = E_{3}^{\circ} + A\sigma^{2} \pm \{B^{2}\sigma^{4} - 2\gamma_{3}\Gamma\sigma^{3}B\cos^{3}\alpha + \gamma_{3}^{2}\Gamma^{2}\sigma^{2}\}^{\frac{1}{2}}$$
(4)
where $A = \frac{1}{2}\{\frac{(-\gamma_{0}+\gamma_{4}\Gamma)^{2}}{-E_{1}^{\circ}} + \frac{(\gamma_{0}+\gamma_{4}\Gamma)^{2}}{-E_{2}^{\circ}}\}$
 $B = \frac{1}{2}\{-\frac{(-\gamma_{0}+\gamma_{4}\Gamma)^{2}}{-E_{1}^{\circ}} + \frac{(\gamma_{0}+\gamma_{4}\Gamma)^{2}}{-E_{2}^{\circ}}\}$

Apart from the terms $-E_1^{\circ}$, $-E_2^{\circ}$ in the denominators of A and B (McClure has $E_3^{\circ}-E_1^{\circ}$, $E_3^{\circ}-E_2^{\circ}$ respectively) this result is identical to that obtained by McClure (IBM, 1964) for levels near E_3 using a "perturbation treatment" under the restriction "E₁ and E₂ are well

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separated from E_3 ". We note here that the definition of A and B is wrong by factors of σ in the 1964 paper, but is given correctly in McClure's 1957 paper. The latter gives the wrong sign to the cos 3a term, however.

2.1.4 CROSS-SECTIONAL AREAS OF THE FERMI-SURFACE

It is now fairly straightforward to derive estimates of crosssectional areas of the Fermi surface in the x-y plane, for if we put $\gamma_3 = \gamma_4 = \gamma_5 = 0$ then equation 2.1.3(4) reduces to

$$\sigma^{4}(A^{2}-B^{2}) - 2\sigma^{2}(E_{f}-E_{3}^{0})A + (E_{f}-E_{3}^{0})^{2} = 0$$

- which can be solved for σ^2 to give the result below.

$$2\sigma^{2}\gamma_{0}^{2} = (E_{f} - E_{3}^{0}) [2E_{f} - (E_{1}^{0} + E_{2}^{0}) \pm (E_{1}^{0} - E_{2}^{0})]$$

Since the LHS is always +ve we must take the positive sign for electrons and the negative sign for holes, so:

$$\sigma_{e}^{2} = \frac{1}{\gamma_{o}^{2}} (E_{f} - E_{3}^{o}) (E_{f} - E_{2}^{o})$$
$$\sigma_{h}^{2} = \frac{1}{\gamma_{o}^{2}} (E_{f} - E_{3}^{o}) (E_{f} - E_{1}^{o})$$

These give :

$$\sigma_{e}^{2} = \frac{1}{\gamma_{o}^{2}} \left\{ E_{f}^{2} - E_{f} \left(\Delta - \left(\gamma_{1} - \frac{1}{2} \gamma_{2} \Gamma_{e} \right) \Gamma_{e} \right) + \left(\Delta - \gamma_{1} \Gamma_{e} \right) \left(\frac{1}{2} \gamma_{2} \Gamma_{e}^{2} \right)^{\frac{1}{2}} \text{ for electrons} \right\}$$

and

$$\sigma_{h}^{2} = \frac{1}{\gamma_{0}^{2}} \left\{ E_{f}^{2} - E_{f} (\Delta + 2(\gamma_{1} + \gamma_{2})) + (\Delta + 2\gamma_{1})(2\gamma_{2}) \right\} \qquad \text{for holes.}$$

 Γ_{r} is the value of Γ which maximises the electron cross-sectional area A_e and hence σ_e^2 :

$$\Gamma_{e} = \frac{1}{3\gamma_{1}} (\Delta - E_{f} + [(\Delta - E_{f})^{2} + 6\gamma_{1}^{2}/\gamma_{2} E_{f}]^{\frac{1}{2}})$$

Finally, we note that on the hexagonal zone faces $(\Gamma = 0)$ the cross-sectional area is given by

$$\sigma_{\rm m}^2 = \frac{1}{\gamma_{\rm o}^2} \qquad {\rm E}_{\rm f}({\rm E}_{\rm f} - \Delta)$$

Actual areas in K-space Λ are obtained from the above $\frac{2}{\sigma}$ by

$$A = \pi K^2 = \pi (\frac{2}{\sqrt{3a_0}})^2 \sigma^2$$
, where $a_0 = 2.46$ Å.

The above results are quoted in Anderson et al (1968) but they give no indication of the derivation. They also state formulae for F.S. volumes in the same approximation.

For the more interesting case $v_3 \neq 0$ a numerical solution of 2.1.3(4) is necessary but we can obtain a useful result by assuming that γ_2 merely introduces a trigonal perturbation in σ . Assume $\sigma = \sigma_0(1+\eta)$

using

where $\eta = \varepsilon \cos 3\alpha$, η , ε are to be found and σ_0 is the solution found above for the case $\gamma_3=0$. Substituting back into 2.1.3(4) and using the fact that σ_0 satisfies this for $\gamma_3=0$, we obtain a linear expression in η :

$$\eta = -\gamma_3^{\Gamma} \cos 3\alpha \left[\frac{(\gamma_0 + \gamma_4 \Gamma)^2}{E_3 - E_2} - \frac{(\gamma_0 - \gamma_4 \Gamma)^2}{E_3 - E_1} \right] \sigma_0 /_D$$

where

$$D = 4 \frac{(v_0 + v_4 \Gamma)^2 (v_0 - v_4 \Gamma)^2}{(E_3 - E_2) (E_3 - E_1)} \sigma_0^2 + 3v_3 \Gamma \cos 3\alpha \left[\frac{(v_0 + v_4 \Gamma)^2}{E_3 - E_2} - \frac{(v_0 - v_4 \Gamma)^2}{E_3 - E_1} \right] \sigma_0$$

+ 2(
$$E_{f}+E_{3}$$
) [$\frac{(\gamma_{0}-\gamma_{4}\Gamma)^{2}}{E_{3}-E_{1}}$ + $\frac{(\gamma_{0}+\gamma_{4}\Gamma)^{2}}{E_{3}-E_{2}}$] - $2\gamma_{3}\Gamma^{2}$

Recall here that the above equation $2 \cdot 1 \cdot 3(4)$ is not valid when $E_{1,2}$ are close to E_3 so there are no critical points to examine. Putting in typical values for the parameters, we find the first and third terms dominate D making D practically independent of α so we have finally :

$$\sigma = \sigma_{0}(1+\varepsilon \cos 3\alpha) \text{ where } \varepsilon = -\gamma_{3}^{\Gamma}\sigma_{0}\left[\frac{(\gamma_{0}+\gamma_{4}^{\Gamma})^{2}}{E_{3}-E_{2}}-\frac{(\gamma_{0}-\gamma_{4}^{\Gamma})^{2}}{E_{3}-E_{1}}\right]/_{D} \approx 0.01$$

A simple calculation now demonstrates the effect that γ_3 has on the oross-sectional area of the Fermi surface normal to the c-axis for this area (in σ -units) is

$$A = \frac{1}{2} \int_{0}^{2\pi} \sigma^{2} d\alpha = \frac{3}{2} \sigma_{0}^{2} \int_{0}^{2\pi/3} (1 + \varepsilon \cos 3\alpha)^{2} d\alpha$$

 $= A_0 (1 + \frac{1}{2} \varepsilon^2) \quad \text{where } A_0 \text{ is the cross sectional area}$ when $v_3 = 0$.

Therefore γ_3 produces a negligible change in the crosssectional area of the Fermi surface and will not measurably influence DHVA-type oscillation periods. Alternatively, measurement of periods will not give a reliable estimate of γ_3 .

2.1.5. Values of Band Parameters

Finally, values quoted in the literature for the band parameters appearing in the Sloncewski-Weiss model will be collected together.

The review by Harring and Mrowski (1960) on the Band Structure of Graphite Crystals contains details of earlier determinations. At that time there were two schools of thought concerning the magnitude of γ_1 . Herering and Wallace proposed a small ($\leq 0.005 \text{ eV}$)value of γ_1 on the basis of constant susceptibility results. The analysis yields $\gamma_0 \simeq 2.6 \text{ eV}$ and gives roughly the correct specific heat. However, the small γ_1 model can account for the presence of holes only at high temperatures, whereas Hall effect and cyclotron resonance experiments

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indicate the simultaneous presence of electrons and holes, the latter strongly suggesting equal concentrations of each (Nozieres, 1958). In the overlap model, γ_0 is determined by the susceptibility to be $\simeq 2.6 \text{ eV}$, which is in good agreement with theoretical predictions (Lomer, Johnston; 3eV) but γ_1 is calculated from the ratio $\frac{\gamma_0^2}{\gamma_1}$ whose value of 25 eV is given by DHVA, by cyclotron resonance and by electronic specific heat measurements. This gives $\gamma_1 \simeq 0.36 \text{ eV}$, much larger than the value indicated by the susceptibility experiments. Independent estimates of γ_1 give 0.32 eV (electron energy loss, Ichikawa, 1958), 0.14 eV (infra-red absorption, Boyle and Nozieres, 1958). Later confirmation that γ_1 must be large came from the work of Soule, MoClure and Smith (1964) in which they showed that both electron and hole Fermi surfaces are closed sheets. This is consistent with the overlap model whereas the small γ_1 model leads to an extended Fermi surface.

The DHVA effect yields a value of 0.016 eV for γ_2 the magnitude of which agrees with that given by Boyle and Nozieres (0.02 eV). Nozieres' analysis of cyclotron resonance data confirms the positive sign and a rough check is afforded by identifying the knee of the resistivity-temperature curve at 120° K with a carrier degeneracy temperature. Early determinations of Δ were uncertain in sign. Carter and Krumhanslestimate 0.01 eV while McClure's DHVA analysis indicated 0.02 eV and Dresselhaus and Mavroides obtain -0.02 eV. However, later experiments seem to agree on a larger negative value; Soule, McClure and Smith calculate -0.12 eV and McClure and Yafet obtain -0.1 eV. Johnston estimated γ_3 to be 0.13 eV and γ_4 was assumed equal to γ_3 until the g-shift in electron spin resonance (McClure and Yafet, 1962) gave $|\gamma_4| \sim 0.28$ eV and the 1964 magnetoreflection experiments of Dresselhans and Mavroides (on pyrolytic grawhite) led to $\gamma_3=0.145$ eV and $\gamma_4=-0.2$ eV. So far no experiment has yielded a value of γ_5 and it is assumed $\gamma_5=\gamma_2$ (McClure, 1960, Inoue, 1962).

2.2 GALVANOMAGNETIC PROPERTIES.

Introduction.

In this section we shall be concerned with understanding the galvanomagnetic effects in graphite, notably the magnetic-field and temperature-variation of the magnetoconductivity tensor $\sigma(\underline{H})$ and its inverse $\rho(\underline{H})$ with a view to correlating these experimental data with the SW band model. Broadly speaking, the phenomena can be divided between low field, high temperature effects; the classical effects, and quantum effects occurring at high magnetic fields and low temperatures. The weak field phenomena are strongly influenced by interactions between charge carriers and the lattice, e.g. the nature of the scattering process, whereas in strong magnetic fields certain transport processes become dependent upon charge carrier characteristics alone, such as density and Fermi energy. Section 2.3 will be devoted to the quantum effects.

2.2.1 Phenomenological Treatment.

One can write a relation between electric and thermal fields and fluxes in the following form:

$$J_{i} = \sigma_{ij}(\underline{H})\varepsilon_{j}^{*} + B_{ij}(\underline{H}) \frac{\partial}{\partial x_{j}} (\frac{1}{T})$$

$$Q_{i} = P_{ij}(\underline{H})\varepsilon_{j}^{*} + K_{ij}(\underline{H}) \frac{\partial}{\partial x_{j}} (\frac{1}{T})$$
(1)

where \underline{J} and \underline{Q} are the electric and thermal currents, T is the temperature and $\underline{\varepsilon}^*$ is the electrothermal field which is essentially the gradient of the electrochemical potential, μ ; $\underline{\varepsilon}^* = \frac{-1}{q} \nabla \mu$. The externally applied electrostatic field, $\underline{\varepsilon}$, is related to the electrothermal field by $\underline{\varepsilon}^* = \underline{\varepsilon} - \frac{\nabla \mu_c}{q}$ - where q is the charge of the carriers and μ_c is the chemical potential of the charge carriers.

Now experimentally it is more usual to define the current flows than the electric and thermal force-fields, so we invert these relations to give:

$$\varepsilon_{\rm m}^{*} = \rho_{\rm mn}(\underline{H})J_{\rm n}^{*} + \alpha_{\rm mn}(\underline{H})\frac{\partial}{\partial x_{\rm n}} T$$

$$Q_{\rm m} = \Pi_{\rm mn}(\underline{H})J_{\rm n}^{*} - K_{\rm mn}(\underline{H})\frac{\partial}{\partial x_{\rm n}} T$$
(2)

- where the arrays ρ , α , Π , K are known as the resistivity, the thermoelectric power, the Peltier coefficient, and the thermal con-

For an isothermal, uniform conductor these reduce to $\underline{\varepsilon}^* = \underline{\varepsilon}$, $Q_i = \pi_{ij}J_j$, $E_i = \rho_{ij}J_j$, where $\rho = \sigma^{-1}$ and $\pi = P\sigma^{-1}$.

The general thermodynamic relations of Onsager apply to these tensors :

$$\sigma_{ij}(\underline{H}) = \sigma_{ji}(-\underline{H}) \ \rho_{ij}(\underline{H}) = \rho_{ji}(-\underline{H}), \text{ etc.}$$

At first sight, one is still left with a large number of independent tensor elements to be obtained experimentally, but the requirements of crystal symmetry help to reduce this number. By Neumann's principle, the above tensors must be invariant under the symmetry operations of the point group of the crystal structure.

Graphite has the point group 6/mmm which consists of the symmetry elements 1, six of 21, 2_z , $\pm 3_z$, $\pm 6_z$, together with all of these multiplied by the inversion operation 1, making 24 in all. It is easily seen that second order tensor effects are isotropic in the basal plane for zero magnetic field and this leads immediately to drastic restrictions on the components.

Thus: $\sigma_{xx} = \sigma_{yy}$

Also, $\sigma_{xy} = \sigma_{yx} = \sigma_{xz} = \sigma_{zx} = \sigma_{yz} = \sigma_{zy} = 0$

Now, when a magnetic field is applied, the symmetry of the system (crystal plus magnetic field) is considerably reduced and in general $\sigma(\underline{H})$ will have nine non-zero components. For small magnetic fields the tensor components can be expanded in terms of magnetic field components, H_i , with field-independent coefficients a :

$$\sigma_{ij}(\underline{H}) = a_{ij} + a_{kij}H_k + a_{klij}H_kH_l + a_{klmij}H_kH_l_m + \cdots$$
(3)

(see Kao and Katz and Birss). The coefficients must allow σ to obey the Onsager relations and are further restricted by crystal symmetry From the former we have a ji a ji, a kij a kij a klij a klij

Following the method of Birss (1964) we find for the point group 6/mmm:

$$\sigma_{11} = a_{11} + (a_{1122} + a_{1221} + a_{1212})H_1^2 + a_{1122}H_2^2 + a_{3311}H_3^2$$

$$\sigma_{22} = a_{11} + a_{1122}H_1^2 + (a_{1122} + a_{1221} + a_{1212})H_2^2 + a_{3311}H_3^2$$

$$\sigma_{33} = a_{33} + a_{1133}H_1^2 + a_{1133}H_2^2 + a_{3333}H_3^2$$

$$\sigma_{12} = a_{312}H_3 + (a_{1212} + a_{1221})H_1H_2$$

$$\sigma_{23} = a_{123}H_1 + (a_{1313} + a_{3113})H_2H_3$$

$$\sigma_{31} = -a_{132}H_2 + (a_{1331} + a_{3131})H_1H_3$$

$$\sigma_{32} = a_{132}H_1 + (a_{1331} + a_{3131})H_2H_3$$

$$\sigma_{21} = -a_{312}H_3 + (a_{1221} + a_{1212})H_1H_2$$

Now, obviously $a_{klij} = a_{lkij}$, and Onsager's relations give $a_{1212} = a_{1221}, a_{1313} = a_{1331}, a_{3113} = a_{3131} a_{123} = -a_{132}$ so there are 10 independent coefficients to second order in magnetic field, 4 to first order, and only 2 in zero field as was mentioned above. It is interesting to consider the case when the magnetic field is confined to the c-axis direction; $\underline{H} = (Q,O,H)$. The conductivity tensor now reduces to

$$\sigma_{ij}(H) = \begin{pmatrix} \begin{pmatrix} a_{11}^{+a_{3311}H^2} & a_{312}^{H} & 0 \\ (-a_{312}H) & a_{11}^{+a_{3311}H^2} & 0 \\ 0 & 0 & a_{33}^{+a_{3333}H^2} \end{pmatrix}$$
(5)

To obtain the resistivity tensor we use the fact that ρ is the inverse of σ_i the above expressions for σ_{ij} apply to any second rank polar tensor property of graphite but to relate the coefficients a of the resistivity tensor ρ to those of its inverse, the conductivity tensor σ , we use the relation $\sigma_{ik}\rho_{kj} = \delta_{ij}$. These nine equations can be solved for a general (small) field but we restrict ourselves to the case $\underline{H} = (0, 0, H)$ which leads to

$$\rho_{11} = \rho_{22} = \frac{\sigma_{11}}{\sigma_{11}^2 + \sigma_{12}^2}, \quad \rho_{33} = \frac{1}{\sigma_{33}^3}, \quad \rho_{31} = \rho_{32} = \rho_{13} = \rho_{23} = 0$$

$$\rho_{21} = -\rho_{12} = \frac{\sigma_{12}}{\sigma_{11}^2 + \sigma_{12}^2}$$
(6)

- giving to second order in magnetic field:

$$\rho_{ij}(H) = \begin{pmatrix} \left[\frac{1}{a_{11}} - \left(\frac{a_{3311}}{a_{11}} + \frac{a_{312}^2}{a_{11}}\right)H^2\right] & \left(-\frac{a_{312}}{a_{11}^2} H\right) & 0 \\ \left(-\rho_{12}\right) & \left(\rho_{11}\right) & 0 \\ 0 & 0 & \left(\frac{1}{a_{33}} - \left(\frac{a_{3333}}{a_{33}^2}\right)H^2\right) (7) \\ \end{pmatrix}$$

- which is of the same form as $\sigma_{ij}(H)$. We can now see that the Hall coefficient is given by $-(\frac{a_{312}}{a_{11}^2})$ and the transverse magnetoresistance, $M_T^a = \frac{\rho_{xx}(H) - \rho_{xx}(0)}{\rho_{xx}(0)}$, by

$$\mathbb{M}_{\mathrm{T}}^{a} = -\left(\frac{a_{3311}}{a_{11}} + \frac{a_{312}^{2}}{a_{11}^{2}}\right) \mathbb{H}^{2}$$

The longitudinal c-axis magnetoresistance, $M_{L}^{\circ} = \frac{\rho_{zz}(H) - \rho_{zz}(O)}{\rho_{zz}(O)}$

is given by a similar expression:

$$M_{\rm L}^{\rm c} = -(\frac{a_{3333}}{a_{33}}) {\rm H}^2$$

2.2.2 Relation between single crystal and pyrolytic graphite.

The above tensors afford a description of the galvanomagnetic effects for single crystal graphite but it is not immediately obvious that they may be employed for the polycrystalline structure of pyrolytic graphite; although pyrolytic graphite is well aligned in the c-axis direction the a-axes of its individual crystallites are randomly orientated. To obtain rigorous expressions for the polycrystalline material would entail complex averaging calculations which are not at all well developed but it might be expected that the behaviour of such a material lies close to that of a hypothetical solid with perfect cylindrical symmetry about the c-axis. Calculation shows that none of the non-zero elements in the above tensors are reduced to zero by the increased symmetry of this solid so one expects the above tensors to hold for pyrolytic graphite for all effects which are not dependent too strongly upon crystallite shape and size.

Although the exact solution of this problem appears to be intractable at present (perhaps computer simulation studies would yield useful information as they do in the field of radiation damage) the above considerations provide reassurance. The following arguments, based on H.J. Juretschke's note in Appl. Phys. Letters, <u>12</u>,213,1968, concerning the 'third order elastic constants of polycrystalline media', elucidate a little more clearly the restrictions under which one might reasonably expect an equivalence between the tensors for single crystal and

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pyrolytic graphite. We start by writing the relation between current density \underline{J} , electric field \underline{E} , and conductivity tensor $\underline{\sigma} : J_i = \sigma_{ij} E_j$. For a polycrystalline specimen, we are interested in a spatial average, giving $\langle J_i \rangle = \langle \sigma_{ij} E_j \rangle$ which reduces to $\langle J_i \rangle = \langle \sigma_{ij} \rangle E_j$ when we make the (extreme) assumption of uniform electric field throughout the polycrystalline mass. The problem has now been reduced to an averaging of the single crystal tensor $\underline{\sigma}$ over all the orientations which occur. Pyrolytic graphite is composed of crystallites with randomlyorientated a-axes so one has to average over all possible rotations θ about the c-axis. For a rotation θ of the crystal about the z-axis (which is coincident with the crystal's c-axis) the tensor components are transformed in the following way: $\sigma_{ij}^{i} = \alpha_{ip} \alpha_{jq} \sigma_{pq}$ where repeated indices are summed in the usual manner. σ_{ij}^{i} denotes the new tensor components and $\underline{\alpha}$ is the rotation matrix describing θ ;

$$\begin{bmatrix} \alpha_{ij} \end{bmatrix} = \begin{bmatrix} -S & C & 0 \\ -S & C & 0 \\ 0 & 0 & 1 \end{bmatrix} \quad \text{where} \quad C \equiv \cos \theta$$
$$S \equiv \sin \theta$$

The average value of $\sigma_{i,j}$ is thus

$$\langle \sigma_{ij} \rangle_{\mathbf{g}} = \frac{1}{2\Pi} \int_{0}^{2\Pi} \sigma_{ij}(\theta) d\theta = \frac{1}{2\Pi} \int_{0}^{2\Pi} \alpha_{ip}(\theta) \alpha_{jq}(\theta) \sigma_{pq} d\theta$$

As an example, we take

$$\langle \sigma_{12} \rangle_{\rm E} = \frac{1}{2\pi} \int_{0}^{2\pi} (\alpha_{11} \alpha_{21} \sigma_{11}^{+\alpha} 11^{\alpha} 22^{\sigma} 12^{+\alpha} 12^{\alpha} 21^{\sigma} 21^{+\alpha} 12^{\alpha} 22^{\sigma} 22^{})^{\rm d\theta}$$
$$= \frac{1}{2\pi} \int_{0}^{2\pi} (-\sigma_{11} s \cdot c + \sigma_{12} c^{2} - \sigma_{21} s^{2} + \sigma_{22} s \cdot c)^{\rm d\theta} = (\sigma_{12} - \sigma_{21})^{\frac{1}{2}}$$

Similarly, we find

$$\langle \sigma_{11} \rangle_{E} = \langle \sigma_{22} \rangle_{E} = \frac{1}{2} (\sigma_{11} + \sigma_{22}) \langle \sigma_{12} \rangle_{E} = -\langle \sigma_{21} \rangle_{E} = \frac{1}{2} (\sigma_{12} - \sigma_{21}) \qquad \langle \sigma_{13} \rangle = \langle \sigma_{31} \rangle = \langle \sigma_{23} \rangle = \langle \sigma_{32} \rangle = 0 \langle \sigma_{33} \rangle_{E} = \sigma_{33}$$

The corresponding resistivity tensor is found by inverting $\langle \sigma \rangle$:

$$\langle \rho_{11} \rangle_{E} = \langle \rho_{22} \rangle_{E} = \frac{\langle \sigma_{11} \rangle_{E}}{\langle \sigma_{11} \rangle_{E}^{2} + \langle \sigma_{12} \rangle_{E}^{2}} = \frac{\frac{1}{2} (\sigma_{11} + \sigma_{22})}{\frac{1}{4} (\sigma_{11} + \sigma_{22})^{2} + \frac{1}{4} (\sigma_{12} - \sigma_{21})^{2}}$$

$$\langle \rho_{33} \rangle_{E} = \frac{1}{\langle \sigma_{33} \rangle_{E}} = \frac{1}{\sigma_{33}}$$

$$\langle \rho_{21} \rangle_{E} = -\langle \rho_{12} \rangle_{E} = \frac{\langle \sigma_{12} \rangle_{E}}{\langle \sigma_{11} \rangle_{E}^{2} + \langle \sigma_{12} \rangle_{E}^{2}} = \frac{\frac{1}{2} (\sigma_{12} - \sigma_{21})}{\frac{1}{4} (\sigma_{11} + \sigma_{22})^{2} + \frac{1}{4} (\sigma_{12} - \sigma_{21})^{2}}$$

$$All others zero$$

Referring to equation (5) for the single-crystal conductivity tensor under a magnetic field $\underline{H} = (0,0,H)$, we see that the average resistivity tensor reduces to :

$$\langle \rho_{11} \rangle_{E} = \langle \rho_{22} \rangle_{E} = \frac{\sigma_{11}}{\sigma_{11}^{2} + \sigma_{12}^{2}}$$

$$\langle \rho_{33} \rangle_{E} = \frac{1}{\sigma_{33}}$$

$$\langle \rho_{21} \rangle_{E} = -\langle \rho_{12} \rangle_{E} = \frac{\sigma_{21}}{\sigma_{11}^{2} + \sigma_{12}^{2}}$$

$$(8)$$

- under the assumptions of c-axis directed magnetic field and uniform electric field.

Now, we may carry through the same analysis under the assumption of uniform current density; $\langle E_i \rangle = \langle \rho_{ij} J_j \rangle = \langle \rho_{ij} \rangle J_j$. This leads to an average resistivity tensor expressed in terms of the single-crystal components:

$$\langle \rho_{11} \rangle_{J} = \langle \rho_{22} \rangle_{J} = \frac{\rho_{11} + \rho_{22}}{2}$$

$$\langle \rho_{33} \rangle_{J} = \rho_{33}$$

$$\langle \rho_{12} \rangle_{J} = -\langle \rho_{21} \rangle_{J} = \frac{1}{2} (\rho_{12} - \rho_{21})$$

Finally, these may be expressed in terms of the single-crystal conductivity tensor components under the assumption of $\underline{H} = (0,0,H)$:

$$\langle \rho_{11} \rangle_{J} = \langle \rho_{22} \rangle_{J} = \frac{\sigma_{11}}{\sigma_{11}^{2} + \sigma_{12}^{2}}$$

$$\langle \rho_{33} \rangle_{J} = \frac{1}{\sigma_{33}}$$

$$\langle \rho_{21} \rangle_{J} = -\langle \rho_{12} \rangle_{J} = \frac{\sigma_{12}}{\sigma_{11}^{2} + \sigma_{12}^{2}}$$

$$all others zero$$

$$(9)$$

Comparing (8) and (9) we see the average tensor components are the same under both extreme assumptions with the additional one that the magnetic field is along the c-axis in each case.

In short, provided one does not destroy the high symmetry of this material about the c-axis by H_1 , H_2 field components, the tensors describing the polycrystalline material have exactly the same components as the single crystal tensors under each of the assumptions; uniform current density and uniform electric field distribution. This does not prove the identity between the macroscopic descriptions of the two types of graphite, but it certainly makes a common assumption more plausible and indicates that one should be even more wary when the magnetic field has components in the basal plane.

2.2.3 The Boltzmann Transport Equation.

It was shown in Appendix 1 that for some purposes electrons in a crystal can be treated as fictitious particles with mass given by $\left(\frac{1}{m}\right)_{ij} = \frac{1}{\hbar^2} \frac{\partial^2 E}{\partial k_i \partial k_j}$ moving classically under the influence of the

external electric and magnetic fields. We now consider the average effect of the whole assembly of electrons on the transport processes; a statistical approach is necessary to condense the vast amount of information required for a complete description of the microscopic behaviour of the system. We define a distribution function $\underline{f}(\underline{K},\underline{r},t)dv_{\underline{K}}d^{3}r$ giving the probability of finding a particle with position \underline{r} and momentum \underline{K} lying within $d^{3}r$, $dv_{\underline{k}}$. The fundamental equation determining this distribution function is the Boltzmann equation, derived for instance in Wilson p.4.

$$\frac{\partial f}{\partial t} + \underline{V} \cdot \nabla_r f + \underline{k} \cdot \nabla_k f = \frac{\partial f}{\partial t}$$
 collisions

The term on the right-hand-side of the Boltzmann equation represents the effect of certain terms in the crystal Hamiltonian (which have so far been neglected) leading to transitions between electron states. Whenever the principle of detailed balance applies, such transitions do not influence the equilibrium distribution function (the Fermi function) but they do establish it in the first place, and in the presence of disturbing external fields they have the effect of limiting the response of the system so that in the steady state there is a balance between the external fields and the effects of scattering.

The change in f due to collisions can be written more explicitly in terms of the probability per unit time $W(\underline{K},\underline{K}^{t})$ that an electron will make the transition $\underline{K} \rightarrow \underline{K}^{t}$ induced by an aperiodic term in the crystal Hamiltonian resulting from an irregularity in the lattice. Such irregularities can be lattice vibrations (phonons), leading to temperature-dependent scattering, isolated impurities, electron-electron scattering due to the screened Coulomb repulsion between electrons remaining after the usual one-electron treatment has taken care of the average potential, and other lattice disturbances such as vacancies, grain boundaries and dislocations.

As an example, consider the scattering by a fixed impurity or grain boundary which are both massive compared to an electron. The energy change of such an irregularity is tiny because of the disparity in masses and we may regard the process as being one in which the electron energy is conserved; $W(\underline{K},\underline{K}^{I})$ is proportional to $\delta(E_{\underline{K}}-E_{\underline{K}})$. The probability of a transition occurring from state \underline{K} into any other state in time dt depends on the occupancy of the initial and final states and is given by

$$dt \int_{BZ} W(\underline{K}, \underline{K}') f_{K}(1-f_{K'}) dV_{K'}$$

Similarly, the probability of a transition into state K is

$$dt [W(\underline{K}^{\bullet}, \underline{K}) f_{K^{\bullet}} (1-f_{K}) dV_{K^{\bullet}}$$

Thus, the net increase in f_{K} due to collisions of this kind per unit time is

$$\frac{\partial f}{\partial t}\Big|_{coll} = \int_{BZ} \left[W(\underline{K}',\underline{K}) f_{K'}(1-f_{K}) - W(\underline{K},\underline{K}') f_{K}(1-f_{K'}) \right] dV_{K'}$$
(1)

A formally similar equation is obtained for processes which do change the electron energy with $\Omega(\underline{K},\underline{K}^{\bullet})$ in place of $W(\underline{K},\underline{K}^{\bullet})$, where Ω is no longer proportional to $\delta(\underline{E}_{K}-\underline{E}_{K^{\bullet}})$. Because of the additivity of independent-event probabilities, the total expression for $\frac{\partial f}{\partial t})_{coll}$ will be the sum of the appropriate integrals for the independent scattering processes.

In uniform equilibrium, the left hand side of the Boltzmann equation is zero which implies that $\frac{\partial f}{\partial t}_{coll}$ must be zero for all scattering processes. This forces the intergrand in (1) to be zero, leading to

$$W(K^{*},K) f_{o}(E_{K^{*}}) (1-f_{o}(E_{K})) = W(K,K^{*}) f_{o}(E_{K}) (1-f_{o}(E_{K^{*}}))$$

This is a consequence of the 'principle of detailed balancing'; every process and its inverse must occur with equal frequency in equilibrium.

The equilibrium solution is the Fermi distribution function

$$f_{o} = \frac{1}{e^{(E-\mu)KT} + 1}$$

where E is the total electron energy and μ is the electrochemical potential per electron or 'Fermi energy'.

Now, the electric current density \underline{J} is given by

$$\underline{J} = \frac{-\underline{e}}{\Delta \Pi^3} \int \underline{V} f \, dV_K$$

so our task is to solve the Boltzmann equation in the presence of electric and magnetic fields and then substitute in the above equation to obtain the conductivity. We note immediately that, since graphite obeys Ohms' law, we are only interested in functions f which lead to an integral proportional to electric field.

2.2.4 The Relaxation Time Approximation.

The solution of the Boltzmann equation is greatly simplified if it is assumed that disturbances die out with time with a time constant $\tau(\underline{K})$;

$$\frac{\partial f}{\partial t}$$
)_{coll} = $-\frac{f_{K}-f_{K}^{\circ}}{\tau_{K}}$

This is not always a valid assumption (e.g. for lattice scattering at low temperatures) but is ε commonly used starting point for transport calculations. S. Ono and K. Sugihara (1966) show that it is a reasonable assumption for graphite at least in the region 25° K to 400° K, where lattice scattering is dominant. When the approximation fails, it is necessary to solve the full integral equation for the distribution function as has been carried out by E.H. Sondheimer (1950) for some special cases.

Substituting in, and using the effective mass approximation, the Boltzmann equation in the steady state becomes

$$- \underbrace{\stackrel{\Theta}{}}{}_{n} \left(\underline{e} + \frac{1}{C} \underline{V} \wedge \underline{H} \right) \nabla_{\mathbf{K}} \mathbf{f} + \underline{V} \cdot \nabla_{\mathbf{r}} \mathbf{f} = - \underbrace{\stackrel{\mathbf{f} - \mathbf{f}}{}_{\mathbf{r}} \mathbf{o}}_{\mathbf{T}}$$

where (\underline{K}) and $\tau(\underline{K})$ must have the same symmetry as the crystal. For an isothermal, uniform conductor;

$$\frac{(\underline{e})}{2} = \frac{1}{2} \frac{\mathbf{E}}{2} + \underline{V} \wedge \underline{H}_{C} = \mathbf{O}_{K} \mathbf{f} + (\mathbf{f}_{O} - \mathbf{f}) / \tau = \mathbf{O}_{K} \mathbf{f} + \mathbf{O}_{O} \mathbf{f}$$

This is the starting point for our discussion of McClure's method of solution for a general band structure in section 2.4., but we note here that Chambers (1952) has given a formal solution which is of use in high magnetic fields and can be expanded in low fields. However, the same low-field expansion can be obtained more simply by an iterative procedure presented by Jones and Zener (1934).

2.2.5 The Jones-Zener Solution.

In the above-mentioned paper, Jones and Zener obtained a solution by simple iteration. Let us define a vector operator

$$\widehat{\Sigma} = C_{\hbar}^{\Phi} \nabla_{K} \nabla_{K}$$

and assume a solution of the form $f = f_{0} - \phi \frac{\partial f_{0}}{\partial E}$. Then the
Boltzmann equation can be written

$$\frac{\underline{\theta}}{\hbar} \cdot \nabla_{\mathbf{K}} \mathbf{f}_{0} - \frac{\partial \mathbf{f}_{0}}{\partial \mathbf{E}} = \frac{\underline{\theta}}{\hbar} \cdot \nabla_{\mathbf{K}} \phi + \frac{\Phi}{\tau} \frac{\partial \mathbf{f}_{0}}{\partial \mathbf{E}} + \frac{\underline{\theta}}{\hbar} \cdot \nabla_{\mathbf{K}} \mathbf{f}_{0} - \phi \frac{\underline{\theta}}{\hbar} \cdot \nabla_{\mathbf{K}} \frac{\partial \mathbf{f}_{0}}{\partial \mathbf{E}} = 0$$

$$- \frac{\partial \mathbf{f}_{0}}{\partial \mathbf{E}} = \underline{\theta} \cdot \nabla_{\mathbf{K}} \phi - \phi \frac{\underline{\theta}}{\hbar} \cdot \nabla_{\mathbf{K}} \frac{\partial \mathbf{f}_{0}}{\partial \mathbf{E}} = 0$$

This reduces to the following equation when we neglect all powers of $\underline{\varepsilon}$ higher than the first (to impose Ohm's law) and note that

$$\underline{\nabla}\underline{AH} \cdot \nabla_{K} \mathbf{f}_{0} = \frac{\partial \mathbf{f}_{0}}{\partial E} \quad \underline{\nabla}\underline{AH} \cdot \nabla_{K} E = 0 \quad \text{since } \nabla_{K} E = \hbar \underline{\nabla}$$
$$\frac{e}{\hbar} \underbrace{\varepsilon} \cdot \nabla_{K} E + \underline{H} \cdot \underline{\Omega} \phi + \frac{\phi}{\pi} = 0$$

Putting $\underline{H} = 0$ one obtains the zero-order solution

$$\phi_{o} = -\frac{Te}{\hbar} \underline{\epsilon} \cdot \nabla_{K} E$$

Higher-order solutions are obtained by substituting back successively into

$$\phi_{\mathbf{r}} = -\frac{\mathbf{r}_{\mathbf{e}}}{\hbar} \underline{\boldsymbol{\varepsilon}} \cdot \nabla_{\mathbf{K}} \mathbf{E} - \underline{\mathbf{H}} \cdot \underline{\boldsymbol{\Omega}} \phi_{\mathbf{r}-1}, \ \mathbf{r} = 1, 2, 3 \dots$$

Obviously, there is some critical value of magnetic field, \underline{H} , above which the series no longer converges for a given band structure. The critical value is best found by actual computation as no general expression is available. Jones and Zener themselves point out that the Boltzmann equation is only meaningful for values of H such that $\frac{eHT}{mc} \ll 1$ - this restricts the magnetic field to values below the quantumeffect region so that electrons never have time to complete more than a small fraction of an orbit in the field before being scattered. We shall mean by a 'small magnetic field' a value which satisfies the above condition and which is also small enough to ensure convergence of the Jones-Zener expansion. The development of this series solution is undertaken in Appendix 2 where the conductivity tensor $\sigma_{ij}(\underline{H})$ is calculated from $J_i = \sigma_{ij} \underline{E}_j$

and $\underline{J} = \int \frac{\underline{e}}{4\pi} \Im \nabla \phi \frac{\partial f_{od} \nabla_{K^{\circ}}}{\partial \underline{E}}$ The Jones-Zener terms are compared with the terms in the phenomenological expansion;

$$\sigma_{ij}(\underline{H}) = \sigma_{ij}(0) + \sigma_{kij}H_{K} + \sigma_{klij}H_{K} + \cdots$$

and integral expressions applicable to graphite are developed for the coefficients σ_{ij} , σ_{kij} , σ_{klij} . These final expressions involve integrations over the Fermi surface and have been derived under certain conditions: Degeneracy of the carriers, magnetic field parallel to the c-axis, and $\gamma_3 = 0$. The final expressions are:-

$$\sigma_{ij} = \begin{pmatrix} \Pi & 0 \\ 0 & \Pi \end{pmatrix} \frac{e^2}{4\Pi^3 \hbar} \int \tau & (\frac{\partial E}{\partial K}) K \ dK_z$$

$$\sigma_{3ij} = \begin{pmatrix} 0 & \Pi \\ \Pi & 0 \end{pmatrix} \frac{-e^3}{4\Pi^3 C_\hbar^4} \int \tau^2 & (\frac{\partial E}{\partial K})^2 \ dK_z$$

$$\sigma_{33ij} = \begin{pmatrix} \Pi & 0 \\ 0 & \Pi \end{pmatrix} \frac{-e^4}{4\Pi^3 c^2 \hbar^6} \int \tau^3 & (\frac{\partial E}{\partial K})^2 \ \frac{1}{K} \ dK_z$$

It is interesting to note, in passing, that the analysis in Appendix 2 yields as a condition for a non-zero c-axis longitudinal magneto-resistance or conductivity that the expression $(\tau(K_{\hat{z}}) \frac{\partial E}{\partial K_{\hat{z}}})$ must have some K or α -dependence; a K_{z} -dependence alone is insufficient. We are using here the cylindrical co-ordinate system instroduced in Section 2.1.3 ; K is the distance from the zone edge. The angle α has gone out of our expressions because the neglect of γ_3 leads to circular symmetry about a zone edge.

To proceed, one needs to know $\tau(K_z)$, $\frac{\partial E}{\partial K_z}$, $K(K_z)$. The latter two functions can be obtained in a straightforward manner from the Sloncewski-Weiss band model with $\gamma_3 = 0$, but τ is a very doubtful quantity. Perhaps the best one can do at present is to regard τ as a parameter (varying with K_z and temperature). K. Sugihara and H. Sato (1963) have calculated the relaxation time for two temperatures, 25° K and 50° K, where lattice scattering is dominant, but it could differ considerably at lower temperatures. In a later paper, S. Ono and K. Sugihara (1968) show that the inclusion of γ_3 causes τ to vary with position on the hodograph (with α), though the magnitudes at the two temperatures are maintained roughly at the same values of 1.3 x 10^{12} sec $(50^{\circ}$ K) and $3 \rightarrow 3.5 \times 10^{12}$ sec $(25^{\circ}$ K).

A computer programme has been written to evaluate the above integrals for a given set of band parameters $(\gamma_0, \gamma_1, \gamma_2, \gamma_4, \Delta, E_f)$. These parameters yield, through the equations of Sections 2.1.3, 2.1.4, expressions for the factors K (from the cross-sectional areas in Section 2.1.4) and $\frac{\partial E}{\partial K}$ in terms of the integration variable K_z . The range of K_z was split into three, corresponding to values of K_z between K and M, M and H, and J and H of Figure 2.4 which parts of the Fermi surface describe holes, electrons and minority electrons, respectively.

It was found that to prevent computational difficulties the region of the electron surface near M had to be excluded from the range of integration. We recall that the expressions developed in Sections 2.1 are not valid for this difficult region in any case. The lower limit on K_z for this integration was increased away from the K_z value of M by some 0.5 to 1%. No such automatic adjustment occurred for the other two types of carrier although this was allowed by the programme.

No absolute values are available for the magnetoconductivity tensor components at the present time, but using the Dresselhaus and Mavroides (1964) set of parameters (2.88, 0.39, 0.016, -0.2, 0.012), the following ratios $m_i \equiv (minority \ electron/majority \ electron)$,

 $h_i \equiv ($ hole /majority electron), for the contributions to the zero field conductivity (i = 1), Hall effect (i = 2) and magnetoconductivity (i = 3) were obtained;

$$m_1 = 0.06$$
, $m_2 = 0.3$, $m_3 = 0.96$
 $h_1 = 4.8$ $h_2 = 1.4$, $h_3 = 0.2$

showing the important influence of holes on the low field Hall effect and that of the minority electrons on the magnetoconductivity. Changing the Fermi level from 0.012 to 0.019 resulted ins

$$m_1 = 0.03, m_2 = 0.13, m_3 = 0.41$$

$$h_1 = 0.59, \quad h_2 = 0.22, \quad h_3 = 0.57$$

showing how sensitive electrical conduction is to changes in Fermi level, for the majority electrons now dominate completely.

The band parameter set (2.85, 0.3, 0.021, -0.2, -0.006, 0.029) yields:

$$m_1 = 0.14$$
, $m_2 = 0.05$, $m_3 = 0.11$
 $h_1 = 0.67$, $h_2 = 0.30$, $h_3 = 0.11$

The above calculations were performed with a constant relaxation time τ but the programme can accept any K_z -dependence one wishes to attribute to τ .

2.3 Quantum Oscillations.

In degenerate conductors it is possible under certain conditions to observe quantum effects in the electrical conductivity. The application of a magnetic field to an electronic system causes a quantisation of electron energy levels for motion perpendicular to the magnetic fields, such that the energy level spacing becomes $\hbar\omega$ where the cyclotron frequency $\omega = \frac{eH}{m^*c}$ At sufficiently low temperatures, where $\text{KT} \leq \hbar\omega$, the thermal broadening of the levels is less than the level spacing and the effects of this quantisation can be observed provided other level broadening mechanisms are not dominant. For graphite, the above condition requires liquid helium temperatures and magnetic fields above about 6kgauss.

This section illustrates the effect of magnetic condensation of energy levels in 2.3.1 by means of a semiclassical model, and goes on in 2.3.2 to present the 'generalised Landau' formula which is used for data analysis in Section 4.2.3. Literature cited below should be consulted for details.

2.3.1 Motion of Wave Packets in a Magnetic Field.

It was shown in Appendix 1 that, under conditions stated there, electrons in crystals may be regarded as classical particles with an effective mass m^* and with $\hbar \underline{K}$ replacing the classical momentum. In particular, under the influence of a magnetic field \underline{H} the representative point in \underline{K} - space, \underline{K} , is given by $\underline{K} = \frac{\underline{e}}{c\hbar} \underline{V} \wedge \underline{H}$ where \underline{V} is the velocity of the electron. Thus \underline{K} is normal to both <u>H</u> and <u>V</u>. The latter is normal to the Fermi surface, being given by $\underline{V} = \frac{1}{\hbar} \operatorname{grad} \underline{K} \underline{E}$. Thus <u>K</u> is confined to an orbit defined by the intersection of a plane normal to the magnetic field with the Fermi surface. The electron makes one revolution in a period

$$\frac{2\Pi}{\omega} = \frac{c\hbar}{eH} \oint \frac{dK}{V_1}$$
(1)

where $d\underline{K}$ is an element of the orbit and \underline{V}_{1} is the electron velocity perpendicular to \underline{H} in the plane of the orbit. For free electrons $E = \frac{\hbar^{2}\underline{K}^{2}}{2m}, \quad \underline{V} = \frac{\hbar\underline{K}}{m}$ so that $\omega = \frac{eH}{mc}$. It is convenient to define a 'cyclotron effective mass' for other band shapes $\underline{m}^{*} = \frac{eH}{\omega^{2}}$ (2) From (1) above this obviously varies from orbit to orbit in general.

We point out here that equation (1) leads usefully to the definition of a 'phase variable' $\phi = \omega_{eH}^{ch} + \frac{dK}{V_1}$ which is equal to 211 for a complete circuit. This is used in Section 2.4.1. to solve the Boltzmann transport equation.

The periodic motion of an electron in a magnetic field leads, as one might expect by analogy with a simple harmonic oscillator, to a quantisation of the electron energy levels in units of $\hbar\omega$ to motion perpendicular to the magnetic field. (See for instance Ziman, 1965).

It can be shown that (2) is equivalent to $m^* = \frac{\hbar^2}{2\Pi} \frac{\partial A}{\partial E}$ where A is the area of an orbit in K-space. Thus if $\delta E = \hbar \omega_1$ we have $\delta A = \frac{2\Pi m^{-}\omega}{\hbar}$ which indicates that the areas of orbits in <u>K</u>-space are themselves quantised. In a crystal the area of an orbit on the nth energy level is $A_n = \frac{2\Pi eH}{c\hbar}$ (n+ γ) where γ is $\simeq \frac{1}{2}$.

As the magnetic field is increased the ereas of occupied cylindrical energy surfaces increase, but these cylinders depopulate as they pass through the Fermi surface. Consequently, the density of states jumps (discontinuously at $O^{\circ}K$) every time a magnetic energy level passes through the Fermi surface of area $A_{\mathbf{F}}$. This happens as n changes by unity in intervals of reciprocal magnetic field of

$$\Delta(\frac{1}{H}) = \frac{2\Pi e}{c\hbar} \quad \frac{(n+1+\gamma)-(n+\gamma)}{A_{F}}$$
(3)

For a more complicated Fermi surface the energy cylinders may cut the Fermi surface in several places and cannot be said to be 'passing through' the Fermi surface at any given value of magnetic field; many values of A_F are involved. However, a more thorough analysis shows that the effects of all but the extremal cross sectional areas of the Fermi surface average out and the density of states changes periodically in $(\frac{1}{H})$ with (possibly superimposed) periods determined by the extremal cross sections. Electronic properties such as the electrical conductivity or Hall effect which depend directly on the density of states reflect the above changes in the form of oscillations superimposed on the classical background. The semiclassical model is presented in an interesting manner by Pippard (1965).

2.3.2 The Generalised Landau Formula.

Equation (3) of the last section gives the relation of Onsager (1952) and Lifshitz (1957) for the period P (gauss⁻¹) of oscillations in resistivity, known as the Shubnikov - de Haas effect (1930), and Hall effect. All theories of the SDH effect agree on this period behaviour and also on the thermal damping factor D (Landau, 1939) which describes the temperature dependence of the oscillation amplitude, $D = \frac{u}{\sinh u}$, where $u = \frac{2\Pi^2 KT}{\hbar \omega}$. T is the temperature, $\omega = \frac{eH}{m^*c}$ and m^* is an orbital effective mass. This factor is seen to reflect the condition mentioned in Section 2.3 above.

Extensive references to the literature on theories of susceptibility-type oscillations are given in the paper by Soule et al (1964). This presents data on a graphite single crystal which proves that the electron and hole Fermi surfaces of graphite are closed and effectively resolves the controversy mentioned in Section 2.1.5 in favour of the overlap model. Roth and Argyres (1966) give a review of magnetic quantum effects with an extensive bibliography of direct interest in the present case.

Imperfections affect the motion of the electrons in a variety of ways. Scattering is all-important for transport phenomena but another effect, the broadening of the unperturbed energy levels through collisions with imperfections, proves to be important in determining the amplitude of the oscillations. Dingle (1952) was the first to

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derive the effect of a finite level width (~ Γ) on the oscillations; the amplitude of the rth term is diminished by the factor $\exp(\frac{-2\Pi\Gamma_{T}}{\hbar\omega})$ This goes quickly to zero as the broadening becomes comparable with the level separation. It is sometimes useful to express Γ as an equivalent temperature ΔT , the 'Dingle temperature' $\Delta T = \frac{\hbar}{\Pi KT}$ where τ is the collision time. In the relatively low field region where an exponential approximation can be made to the hyperbolic sine term mentioned above the collision damping term amounts to a simple additive correction to the measured temperature.

Soule, McClure and Smith (1964) give a formula which can approximately reproduce most of the results of the various theories of the SDH effect. This gives for the oscillatory term due to one carrier:

$$G = H^{n} \sum_{K=1}^{\infty} W_{K} \frac{KU}{\sinh KU} \exp\left(\frac{KU\Delta T}{T}\right) \cos\left(\frac{2\pi K}{PH} - \psi_{K}\right)$$

where $U = \frac{2\Pi^2 \text{KTm}^* \text{c}}{\hbar \text{e}} \frac{1}{H}$ and ΔT is the effective temperature change due to collision broadening $\Delta T = \frac{\hbar}{\Pi \text{K} \tau}$ where τ is the collision time. Another similar term is added for the other carrier.

The results of various theories can be represented by choosing specific values of n, w, ψ . The generalisation comes in allowing these to have arbitrary values. In Section 4.2.3 this expression is used to fit experimental data in order to derive values for m^{*} and P the effective mass and period, respectively.

2.4 MAGNETO-CONDUCTIVITY TENSOR ANALYSIS

We follow McClure, 1956, in deriving the form of the magnetoresistance effect and Hall effect as functions of magnetic field strength. However, we shall not carry it through to the end with the generality of McClure's paper as this would be unjustified in view of our subsequent application of the theory.

2.4.1 General Theory

Wilson p.1%, gives the Boltzmann equation in the presence of uniform electric and magnetic fields, assuming a relaxation time τ (see section 2.2.4):

$$(e/\hbar)[\underline{e} + \underline{V} \wedge \underline{H}/c] \cdot \nabla_k \mathbf{f} + (\mathbf{f}_0 - \mathbf{f})/\mathbf{T} = 0$$
(1)

Writing the distribution function as

$$\mathbf{f} = \mathbf{f}_{o} - \mathbf{\Phi} \partial \mathbf{f}_{o} / \partial \mathbf{E}$$
(2)

Where Φ is proportional to electric field strength (leading to a solution satisfying Ohm's law) we find the Boltzmann equation reduces to:

$$e/\hbar \underline{e} \cdot \nabla_{\mathbf{k}} \mathbf{f}_{\mathbf{0}} - e/\hbar \mathbf{c} \frac{\partial \mathbf{f}_{\mathbf{0}}}{\partial E} \underline{v} \wedge \underline{H} \cdot \nabla_{\mathbf{k}} + \Theta \mathbf{\tau} \frac{\partial \mathbf{f}_{\mathbf{0}}}{\partial E} = 0$$

i.e.
$$-(e/\hbar c) \underline{v} \wedge \underline{H} \cdot \nabla_{k} \Phi + \Phi/\tau + \Theta \underline{e} \cdot \underline{v} = 0$$
 (3)

This is to first order in ε .

The first term represents the derivative of Φ along a curve called the hodograph, formed by the intersection of a plane perpendicular to H with a constant energy surface.

To describe the position of the representative wave vector of the electron on the hodograph we define a new variable S such that $\frac{\partial \mathbf{k}}{\partial S} = -(e/\hbar c) \underline{v} \wedge \underline{H}$. Thus S represents the time at which the representative point, moving in a magnetic field only, reaches the point \underline{k} . Equation (3) now becomes:

$$\frac{\partial \phi}{\partial S} + \phi/\tau + e \underline{\epsilon} \cdot \underline{v} = 0 \tag{4}$$

This is easily solved, to give:

$$\Phi = -\int_{\mathbf{r}}^{\mathbf{S}} d\mathbf{S}' \mathbf{e} \underline{\mathbf{c}} \cdot \underline{\mathbf{v}}(\mathbf{S}') \exp\left[-\int_{\mathbf{S}'}^{\mathbf{S}} d\mathbf{S}''(\mathbf{S}'')\right]$$
(5)

where r is to be determined by the boundary condition that ϕ must be a periodic function of S and turns out to be $-\infty$.

If we now assume that \mathbf{T} is constant on a given hodograph and use the periodicity of the velocity to write it as a Fourier expansion:

$$\underline{\mathbf{v}} = \sum_{-\infty}^{\infty} \underline{\mathbf{v}}(\mathbf{m}) \exp(\mathrm{i}\mathbf{m}\omega\mathbf{s})$$
(6)

where ω is the cyclotron frequency for the hodograph, given by $\frac{2\pi}{\omega} = \oint \frac{\hbar c}{eH} \frac{dk}{v\rho}$; v ρ is the velocity component perpendicular to H, our solution now becomes:

$$\phi = -\tau \sum_{-\infty}^{\infty} \frac{e \underline{\varepsilon} \cdot \underline{v}(m) \exp(im\omega_{B})}{(1 + im\omega_{T})}$$
(7)

To find the conductivity tensor we must first write down the current. For a single band this is:

$$\dot{\vartheta} = -e/(2\pi)^3 \int d^3k \underline{v} f = \frac{-e}{(2\pi)^3} \int_{BZ} d^3k \underline{v} \phi(\frac{-\partial f_o}{\partial E})$$
(8)

Now, since for a given band, the energy is a continuous function of \underline{k} within the Brillouin zone, we may replace the integrand at any point \underline{k} by the average over the hodograph through \underline{k} . This does not change the value of the integral over the BZ.

Thus,
$$\frac{1}{2} = e^2/(2\pi)^3 \int_{BZ} d^3 \underline{k} (-\partial f_0/\partial E) n \underline{M}$$
 (9)

Where the vector
$$\underline{M} = -\left(\frac{\omega}{2\pi e \tau}\right) \oint dS \phi \underline{v}$$
 (10)

Substituting for ϕ from 7 we find

$$\underline{\underline{M}} = \frac{\omega}{2\pi e_{T}} \sum_{m} \frac{1}{1 + im_{T}} \oint dS \left[\sum_{n} \underline{\underline{v}}(n) e^{in\omega B} \right] \underline{\underline{\varepsilon}} \cdot \underline{\underline{v}}(m) e^{im\omega B}$$
i.e.
$$\underline{\underline{M}} = \sum_{\infty} \frac{\sum_{n} [\underline{\underline{\varepsilon}} \cdot \underline{\underline{v}}(m)] \underline{\underline{v}}(-m) / (1 + im\omega T)$$
(11)

We now define a tensor \underline{S} by $\underline{M} = \underline{S} \cdot \underline{\varepsilon}$, and choose \underline{H} to be parallel to the z-axis. The components of \underline{S} give rise to the components of the magnetoconductivity tensor. Using the fact that $S_{xx} = \frac{M_x}{\varepsilon_x} = 0$ etc., it is easily shown that the components of \underline{S} are:

$$S_{xx} = v_{x}^{2}(0) + \sum_{m=1}^{\infty} \frac{|v_{x}(m)|^{2}}{1 + (m\omega\tau)^{2}}$$
(12)

$$S_{xy} = \sum_{m=1}^{\infty} \left[\frac{(v_x(m)v_y(-m) + v_x(-m)v_y(m))}{(v_x(-m)v_y(m) - v_x(m)v_y(-m))} \right] / (1 + (m\omega\tau)^2)$$
(13)

$$S_{zz} = v_2^2(0) + \sum_{m=1}^{\infty} \frac{|v_z(m)|^2}{1 + (m\omega\tau)^2}$$
(14)

Similar expressions hold for the other components. In general, $S_{ij}(\underline{H}) = S_{ji}(-\underline{H})$. McClure shows that $v_x(0) = v_y(0) = 0$, but this is imposed by our more severe symmetry restrictions in any case. Thus, S_{zz} is the only component which approaches a finite limit as $H \rightarrow \infty$.

The conductivity follows:

$$\underline{\boldsymbol{\sigma}} = e^2 / (2\pi)^3 \int_{BZ} d^3 k \ (-\partial f_0 / \partial E) \boldsymbol{\tau} \underline{\underline{S}}$$
(15)

If degenerate statistics apply, $\partial f_0/\partial E$ is only appreciable for energies near the Fermi energy so the integral can be transformed to one over the FS. If, in addition, τ is constant over the FS the form of $\underline{\sigma}$ would be the same as that of \underline{S} .

So far we have been dealing with one band only and we note here that summing the contributions from several bands would lead to additive contributions to $\underline{\sigma}$ from the different bands, each of the form derived above.

It is now necessary to find the Fourier components of velocity for use in 12, 13, 14. The energy can be expressed in cylindrical coordinates, $E = E(\rho, \theta, k_z)$. A given hodograph can be described by $k_z = \text{const.}, \rho = \rho$ (θ). Since the energy is a single-valued function of k_z for a given band, it must be periodic in θ :

We can write,
$$E = \sum_{n=1}^{\infty} E_{n}(\rho, k_{z}) \exp(in \theta)$$
 (16)

The velocity is obtained by taking the gradients of E. e.g. $v_x = \frac{1}{\hbar} \frac{\partial E}{\partial k_x}$.

It is easy to show that the gradient operators required are:

$$\frac{\partial}{\partial k_{x}} = \cos \theta \frac{\partial}{\partial \rho} - \frac{1}{\rho} \sin \theta \frac{\partial}{\partial \theta}$$
$$\frac{\partial}{\partial k_{x}} = \sin \theta \frac{\partial}{\partial \rho} + \frac{1}{\rho} \cos \theta \frac{\partial}{\partial \theta}$$

Thus

$$v_{x} = 1/\hbar \Sigma \left[\frac{\partial E_{n}}{\partial \rho} \cos \theta - i(n/\rho)E_{n} \sin \theta\right] \exp \left[in \theta\right]$$
$$v_{y} = 1/\hbar \Sigma \left[\frac{\partial E_{n}}{\partial \rho} \sin \theta + i(n/\rho)E_{n} \cos \theta\right] \exp \left[in \theta\right]$$

These can be written:

$$v_x = 1/\sqrt{2} (g + g^*)$$
 (17)

$$v_y = i/\sqrt{2} (g - g^*)$$
 (18)

where
$$g = \sum_{n=-\infty}^{\infty} 1/\sqrt{2\hbar} \left[\partial E_n/\partial \rho - (n/\rho)E_n\right] \exp(i(n+1)\theta)$$
 (19)

Now we shall restrict ourselves to a band structure with rotational symmetry about the k_z axis. This implies that E is independent of θ and so all Fourier coefficients, E_n , except $E_o(\rho, k_z)$ are zero. McClure considers less severe symmetry restrictions but as we intend to apply the Kramers-Kronig relations to our conductivity at a later stage, it is more convenient to impose one of the conditions for their validity, viz. cylindrical symmetry, at this point. (19) now becomes

$$g = \sqrt{\frac{1}{2\hbar}} \frac{\partial E_0}{\partial \rho} \exp(i\theta)$$
 (20)

But this must be expressed in terms of the time variable, S. In general, ρ is a function of θ and θ is a function of S ($\theta = \omega S + periodic$ function of S). For our symmetry, ρ is independent of θ and $\theta = \omega S$ so we have:

$$g = \left[\frac{1}{\sqrt{2\hbar}} \frac{\partial E_0}{\partial \rho}\right] \exp(i\omega S) = B \exp(i\omega S), \text{ say.}$$
(21)

Thus, the velocity components are

$$v_{x} = \frac{1}{\sqrt{2}} (B \exp (i\omega S) + B* \exp (-i\omega S))$$
$$v_{y} = \frac{i}{\sqrt{2}} (B \exp (i\omega S) - B* \exp (-i\omega S))$$

Comparing this with (6), we see that

$$v_x(1) = B//2$$
, $v_y(1) = iB//2$
all other $v(m)$'s are zero.
 $v_x(-1) = B*/\sqrt{2}$, $v_y(-1) = -i B*/\sqrt{2}$

Hence we have for the tensor \underline{S}

$$S_{xx} = S_{yy} = \frac{B^2}{1 + (\omega \tau)^2}$$

$$S_{xy} = -S_{yx} = \frac{B^2 \omega \tau}{1 + (\omega \tau)^2}$$
(22)

The conductivity follows from (15):

$$\sigma_{\mathbf{x}\mathbf{x}} = \sigma_{\mathbf{y}\mathbf{y}} = \sum_{\mathbf{b}} \frac{\mathbf{e}^2}{(2\pi)^3} \int_{\mathbf{BZ}}^{\mathbf{\tau}} \left(\frac{-\partial \mathbf{f}_0}{\partial \mathbf{E}}\right) \frac{\mathbf{B}^2}{1 + (\omega \mathbf{\tau})^2} d^3 \mathbf{K}$$

$$\sigma_{\mathbf{x}\mathbf{y}} = -\sigma_{\mathbf{y}\mathbf{x}} = \sum_{\mathbf{b}} \frac{\mathbf{e}^2}{(2\pi)^3} \int_{\mathbf{BZ}}^{\mathbf{\tau}} \left(\frac{-\partial \mathbf{f}_0}{\partial \mathbf{E}}\right) \frac{\mathbf{B}^2 \omega \mathbf{\tau}}{1 + (\omega \mathbf{\tau})^2} d^3 \mathbf{K}$$
(23)

where summation b is over the bands.

Now, for graphite, which is highly degenerate below 200° K, $\partial f_{\circ}/\partial E$ localises the integrand to the neighbourhood of the FS. We have thus reduced the number of independent variables to one, since the integration is over a surface with circular symmetry. Fixing any one of the functions τ , B, H (proportional to ω), k_x , k_y , or k_z immediately fixes the values of the others (with the reservation that some functions may be multivalued with respect to a given variable) and thus the value of the integrand.

McClure 1958, chooses a variable $S = \left(\frac{\omega\tau}{H}\right)$ which is proportional to relaxation time. The fact that τ has been taken to be constant on a given hodograph in the above analysis is of no consequence, nor is: the possibility that parts of the integrand may be multi-valued in the new variable, as this is easily absorbed into the function g(S) with which we now replace all explicit references to τ , <u>k</u>, B or E. Bearing this last remark in mind, we can see that the integration is merely being taken over all complete nodographs lying on the FS, each one being labelled by its relaxation time and that the appropriate limits of integration are from 0 to $^{\infty}$.

Thus, we have finally:

$$\sigma_{xx} = \sum_{b} \int_{0}^{\infty} \frac{g(s) ds}{1 + (SH)^{2}}$$

$$\sigma_{xy} = \sum_{b} \int_{0}^{\infty} \frac{SH g(s) ds}{1 + (SH)^{2}}$$
(24)

Where the summation b is over the bands.

2.4.2 Application to Graphite

We shall now employ the expressions obtained in the last section to show how the carriers in graphite can be separated and their properties found from measurements of the conductivity and Hall effect.

Dividing the carriers in graphite into positive and negative carriers, we can write:

$$\sigma_{xx} = \sigma_{xx}^{p} + \sigma_{xx}^{n} = \int_{0}^{\infty} \frac{dS gp(S)}{1 + (SH)^{2}} + \int_{0}^{\infty} \frac{dS gn(S)}{1 + (SH)^{2}}$$
(1)

$$\sigma_{xy} = \sigma_{xy}^{p} + \sigma_{xy}^{n} = \int_{0}^{\infty} \frac{dS(SH)g^{p}(S)}{1 + (SH)^{2}} + \int_{0}^{\infty} \frac{dS(SH)gn(S)}{1 + (SH)^{2}}$$

where σ^p , σ^n could each possibly contain additive contributions from several carriers of differing mass, etc. We recall, too, that these

expressions are based on circular orbits and a constant relaxation time on a given orbit.

Kramers-Kronig Relations

It can be snown, by contour integration, that

$$\frac{1}{i\pi} P \int_{-\infty}^{\infty} f(x)/(x-X) dx = f(X)$$

where P means that the Cauchy principal part of the integral is to be taken. Now suppose f(X) is complex: f(X) = f'(X) + if''(X). Then we find:

$$f'(X) = \frac{1}{\pi} P \int_{-\infty}^{\infty} \frac{f'(x) dx}{(X - x)}$$

$$f''(X) = \frac{1}{\pi} P \int_{-\infty}^{\infty} \frac{f'(x) dx}{(X - x)}$$
(2)

By applying these to two functions of magnetic field

and
$$f(H) = \sigma_{xx}^{P}(H) + i\sigma_{xy}^{P}(H)$$

 $f(H) = \sigma_{xy}^{n} + i\sigma_{xx}^{n}$,

we obtain relations between the diagonal and off-diagonal partial conductivities:

$$\sigma_{xx}^{P} = \frac{-1}{\pi} P \int \frac{\sigma_{xy}^{P} dx}{H - x} \quad \sigma_{xy}^{P} = \frac{1}{\pi} P \int \frac{\sigma_{xx}^{P} dx}{H - x}$$
$$\sigma_{xx}^{n} = \frac{1}{\pi} P \int \frac{\sigma_{xy}^{n} dx}{H - x} \quad \sigma_{xy}^{n} = \frac{1}{\pi} P \int \frac{\sigma_{xx}^{n} dx}{H - x}$$

These can be reassembled to relate the partial conductivities to the total conductivities:

$$\sigma_{\mathbf{X}\mathbf{y}}^{\mathbf{P}} - \sigma_{\mathbf{X}\mathbf{y}}^{\mathbf{n}} = \frac{\mathbf{P}}{\pi} \int_{-\infty}^{\infty} \frac{d\mathbf{H}'}{\mathbf{H} - \mathbf{H}'} \sigma_{\mathbf{X}\mathbf{X}}(\mathbf{H}')$$

$$- \sigma_{\mathbf{X}\mathbf{X}}^{\mathbf{P}} + \sigma_{\mathbf{X}\mathbf{X}}^{\mathbf{n}} = \frac{\mathbf{P}}{\pi} \int_{-\infty}^{\infty} \frac{d\mathbf{H}'}{\mathbf{H} - \mathbf{H}'} \sigma_{\mathbf{X}\mathbf{Y}}(\mathbf{H}')$$
(3)

It can now be seen that by simple addition and subtraction between 1 and 3 the four partial conductivities can be obtained. We assume, of course, that σ_{xx} and σ_{xy} can be written in the form of the integral expressions in (1); this point is taken up later.

Total Number of Electrons and of Holes

Swanson (1955), and Lifsnitz et al (1957), show that the number of carriers of a given kind is given by $pec = \int_{0}^{\infty} \frac{ds gp(S)}{S}$, where p is the number of noles per unit volume (n for electrons), e is the electronic charge and c is the velocity of light. Thus we can obtain p and n from nign-field Hall data for obviously $pec = (Ho_{XY}^{P})_{H \to \infty}$ and $nec = (Ho_{XY}^{n})_{H \to \infty}$. (4) Average mobilities of electrons and holes

For a given carrier, we have the relation between conductivity and mobility $\mu : \sigma = ne\mu$. Thus, using the zero-field partial conductivities:

$$\mu_{n} = \frac{\sigma^{n}(0)_{xx}}{ne}, \quad \mu_{p} = \frac{\sigma^{p}(0)_{xx}}{pe}$$
(7)

Where p and n are known from the above section. The mobilities so derived are obviously 'averaged' in the sense that they have been calculated from a combination of high and low-field data.

Finally, the difference in the zero-field conductivities can be shown to be given by:

$$\sigma_{xx}^{p}(0) - \sigma_{xx}^{n}(0) = \frac{2}{\pi} \int_{0}^{\infty} \frac{dH}{H} \sigma_{xy}$$
(8)

. :

For

$$[\sigma_{xx}^{p} - \sigma_{xx}^{n}]_{H = 0} = -\frac{1}{\pi} \int_{-\infty}^{\infty} \frac{dH^{\dagger}}{-H^{\dagger}} \sigma_{xy}(H^{\dagger})$$

Now,
$$\sigma_{xy}(H) = -\sigma_{yx}(-H)$$
 since $\sigma_{xy} = -\sigma_{yx}$ for graphite.

Hence,

$$LHS = + \frac{1}{\pi} \int_{-\infty}^{0} \frac{dH^{t}}{+H^{t}} \sigma_{xy}(H^{t}) + \frac{1}{\pi} \int_{0}^{\infty} \frac{dH^{t}}{+H^{t}} \sigma_{xy}(H^{t})$$

$$= -\frac{1}{\pi} \int_{0}^{\infty} \frac{+dH^{t}}{+H^{t}} \sigma_{xy}(+H^{t}) + \frac{1}{\pi} \int_{0}^{\infty} \frac{dH^{t}}{H^{t}} \sigma_{xy}(H^{t})$$

$$= \frac{2}{\pi} \int_{0}^{\infty} \frac{dH^{t}}{H^{t}} \sigma_{xy}(H^{t})$$

Total number of carriers

As a check on 4 and a useful result in itself, we shall show that the total number of carriers, (n + p), is given by

$$(n + p)ec = \frac{2}{\pi} \int_{0}^{\infty} dH \sigma_{xx}(H)$$
 (5)

The RHS is, from 1,

$$= \frac{2}{\pi} \int_{0}^{\infty} dH \left[\int_{0}^{\infty} \frac{(g_{\rm p} + g_{\rm n}) dS}{1 + (SH)^2} \right]$$

Hence, as there are no discontinuities in the plane of integration, we may reverse the order of integration, to obtain:

$$\frac{2}{\pi}\int_{0}^{\infty} dS \left[\frac{1}{S}\tan^{-1}\frac{H}{S}\right]_{0}^{\infty} = \frac{2}{\pi}\int_{0}^{\infty}\frac{dS}{S}(g_{p}+g_{n})\frac{\pi}{2}$$

which is the LHS by the relations $pec = \int_{0}^{\infty} \frac{dS gp(S)}{S} etc.$

In analogy to equations (4), a further expression for the total number of carriers is:

$$(n + p)ec = (H_{\mathcal{T}_{XY}})_{H \to \infty}$$
(6)

Representation of data as a function of magnetic field

Our problem at this stage is to obtain the integrals in (1) which describe the experimental variations of the conductivity with field. We follow McClure in using a sum of Lorentzians of the form

$$\sigma_{xx}, \sigma_{xy}/H = {}_{n}\Sigma \left\{ A_{n}/(1 + (H/H_{n})^{2}) \right\}$$
 (9)

where the A_n and H_n are constants to be used in fitting the experimental points. The justification for this is that very good fits can be obtained with two or three terms and that these expressions make it easy to apply the Kramers-Kronig relations. We regard this as a convenient way of representing the data and do not at first make any identification between the individual terms and the various carriers, though such might be justified if the carriers turned out to have very different characteristics. The procedure used in fitting data to these expressions is described elsewhere (4.1.3).

Let us now apply the K-K relations to these Lorentzians as required by (3). To evaluate the integrals (3) we use partial fractions

$$\int_{-\infty}^{\infty} \frac{dH^{*}}{H - H^{*}} \sigma_{xy}(H^{*}) = \sum_{i} \int_{-\infty}^{\infty} \left(\frac{H}{H_{i}^{2} + H^{2}} \frac{dx}{H - x} + \frac{H}{H_{i}^{2} + M^{2}} \frac{xdx}{H_{i}^{2} + x^{2}} \right)$$

$$= \frac{H_{i}^{2}}{H_{i}^{2} + H^{2}} \frac{dx}{H_{i}^{2} + x^{2}})$$

$$= \sum_{i} \frac{H_{i}^{2} + H^{2}}{H_{i}^{2} + H^{2}} \frac{1}{2} \left[\log \frac{H_{i}^{2} + x^{2}}{H^{2} - 2Hx + x^{2}} \right]_{-\infty}^{\infty}$$

$$= \sum_{i} \frac{H_{i}^{2}}{H_{i}^{2} + H^{2}} \frac{1}{H_{i}^{2}} \left[\tan^{-1} \frac{x}{H_{i}^{1}} \right]_{-\infty}^{\infty}$$

$$= -\sum_{i} \frac{H_{i}^{i} \pi}{H_{i}^{2} + H^{2}}$$

Similarly,

$$\int_{-\infty}^{\infty} \frac{dH'}{H-H'} \sigma_{xx}(H') = \sum_{i} \frac{\pi}{H_{i}} \frac{H}{H_{i}^{2}+H^{2}}$$

This equations (3) become:

$$-\sigma_{xx}^{p} + \sigma_{xx}^{n} = -\sum_{i}^{p} \frac{A_{i}^{i} H_{i}^{i}^{3}}{H_{i}^{2} + H^{2}}$$

$$\sigma_{xy}^{p} - \sigma_{xy}^{n} = H \sum_{i}^{p} \frac{A_{i}^{i} H_{i}^{i}}{H_{i}^{2} + H^{2}}$$
(10)

In accordance with the view that the A_i , H_i , A'_i , H'_i are merely fitting parameters, we do not expect the H_i and H'_i to be the same in general.

By combining (1) and (10) we obtain the four partial conductivities.

We now collect some of the above formulae for future convenience, using the fitting parameters to describe the magnetoconductivity tensor components.

Carrier densities

$$\binom{p}{n} ec = (H\sigma_{xy})_{H \to \infty} = \frac{1}{2} \begin{bmatrix} \Sigma A_{j}^{*} H_{j}^{*} \pm \Sigma A_{j} H_{j} \\ j & i \end{bmatrix}$$
(11)

$$(n + p) ec = \frac{2}{\pi} \int_{0}^{\infty} dH \sigma_{xx}(H) = \sum_{i=1}^{\infty} A_{i}H_{i}$$
(12)

Prtial conductivities

 $\sigma_{\mathbf{x}\mathbf{x}}^{\mathbf{P}}(0) - \sigma_{\mathbf{x}\mathbf{x}}^{\mathbf{n}}(0) = \frac{2}{\Pi} \int_{0}^{\infty} \frac{dH}{H} \sigma_{\mathbf{x}\mathbf{y}} = \Sigma \operatorname{A}_{\mathbf{j}}^{t} \operatorname{H}_{\mathbf{j}}^{t}$ (14)

Mobilities

$$\overline{\mu}_{n}^{p} = \frac{\prod_{n=1}^{n} (0)_{xx}}{\binom{p}{n} e} = \frac{\left(\sum A_{i} \pm \sum A_{i}^{e} H^{e}\right)}{\left(\sum A_{j}^{e} H^{e}_{j}^{2} \pm \sum A_{i}^{e} H_{i}\right)} c \qquad (15)$$

CHAPTER 3

EXPERIMENTAL

3.1 MATERIALS - PREPARATION OF SAMPLES

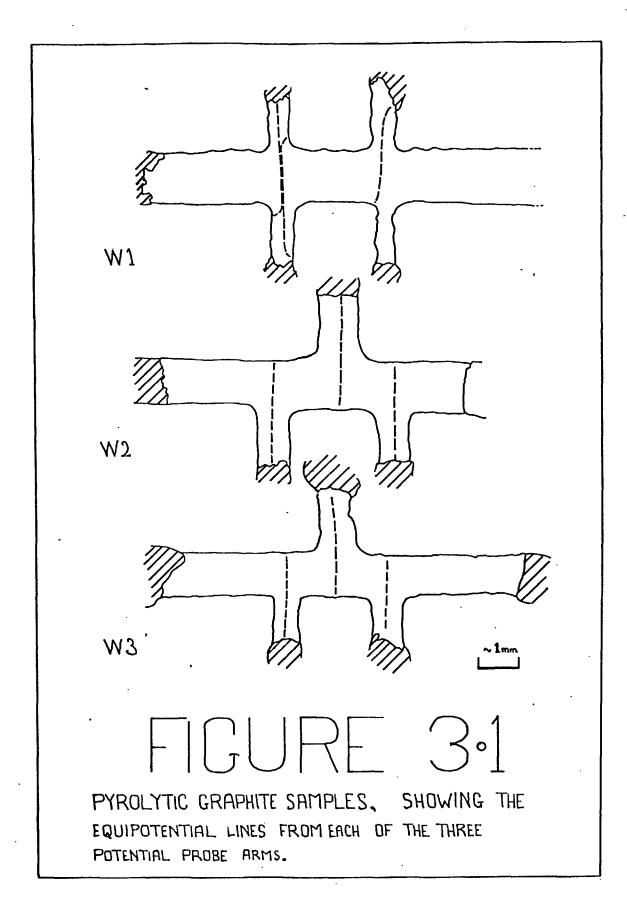
Sample Shape

With materials which are known to be highly anisotropic. it is essential to ensure that the current flow in principal directions is homogeneous. This makes the adoption of suitable sample shapes, electrode positions and application techniques more important than is perhaps the case with homogeneous isotropic media. Thus it is desirable to minimise the shorting effects of the current electrodes on the hall voltage and the perturbation of the potential probes on the uniform current distribution down the sample. Spain (967) used paper coated with a nearly uniform conductive layer to form a twodimensional analogue of the proposed sample configuration and verified that corrections were negligible provided that the ratio of sample length to width was greater than about four. The samples used in the present investigation were out with this finding in mind and a similar analogue technique was used to observe the actual current flow in the samples as fabricated. A photograph was taken of each sample and the outline traced onto the conductive paper from an enlarged print. Silver dag was then painted along the outlines of the plated contact areas and a current of about 10 mA was passed through the current electrodes from an accumulator. An ordinary pencil connected to a high impedance electronic voltmeter was used to plot the course of

the equipotential lines across the analogue. In particular, the positions of the three equipotential lines Leaving the silver paint on the three potential arms were noted, and it was found that a slight correction was necessary to give the actual distance between these equipotentials (electrical separation). The correction was usually less than 1%. The three analogues obtained for the samples reported here are shown in Figure 3.1.

Previous measurements of c-axis properties have depended upon having samples from 5 to 10 mm. thick in the c-axis direction. However, analogue experiments by M.L. Yeoman (unpublished) have shown that it is possible to perform useful measurements upon samples only 2 or 3 mms. thick. The technique is to cut a rectangular piece out of a sleaved disc of the required thickness and to copper-plate all of the top and bottom faces except for small islands near the centre of each face. These regions are plated separately, leaving a narrow annulus of untouched graphite between the two areas on each face. Current is fed into the large areas and potential leads attached with silver dag in the usual manner to the central areas. It is doubtful whether accurate absolute values of resistivity can be obtained by this means because of the difficulty in measuring the thickness of the slab and in making the side faces perfectly parallel to the c-axis. Additionally, corrections to the measured resistance of the order of a few % must be applied. Probably an analogue investigation of samples as-

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made rather than as-desired would enable the correction to be estimated with sufficient accuracy, as is the case with basal plane samples. Extra care must be exercised during plating to prevent the formation of copper globules on the edge of the sample since these would have a disatrous effect on the current distribution.

Cutting the samples

The samples reported here were cut from four different preparations of pyrolytic graphite. Their properties are listed in the table following. W1 had been prepared previously by Spain⁽¹⁹⁶⁷⁾ with four potential arms, only three of which were in good enough condition to be used. Unfortunately, these were wrongly disposed relative to each other for simple Hall measurements and it was necessary to reverse the magnetic field and subtract two sets of readings before a meaningful Hall voltage could be obtained. This considerably complicated the analysis of chart recordings for this sample. The other two basal plane samples were cut in the usual bridge pattern: starting with a cleaved disc in the case of W2 and a cleaved piece of inner-layer material in the case of W3 (the current path was parallel to the cylinder axis so this sample ended up with slightly curved potential probes), the pyrolytic graphite was fixed to a layer of tissue paper stretched over a hole in a brass plate. A suitable shaped mask, cut and filed from thin brass, was similarly fixed with a flexible red cement onto the upper face of the graphite and an air-carried jet of abrasive dust (alumina) was directed at the unprotected parts of the graphite. After a little practice it was possible to cut samples with

straight edges, at right angles to the front face, in about 20 minutes. A pencil brush was used to remove mask, tissue, and backing plate from the sample with the assembly immersed in acetone.

Before plating, the contact areas were slightly abraded with the dust jet. A simple mask was employed to shield the main body of the sample and one or two quick passes with the jet were all that was required. The coloured cement was used to shield all areas of the sample except the tips which were to be plated, particular care being taken with the edges of the graphite where plating occurs very readily. A plating lead was attached with silver dag cement and the sample left to plate in a slightly acid 10% solution of copper sulphate with a current density of about $1mA/cm^2$. Once a continuous copper sheath sufficient to short all the graphite layers together had formed, the plating wire was removed with acetone and wires were attached to all other contact areas of the sample with the conducting silver paint. This final contact was then completed in a similar manner. The initial copper plating was considered to be essential to the success of this technique because analogue experiments have shown the extreme importance of electrically tying all the high conductance basal planes together. Finally, all contact areas were given another plating to form copper caps over the dried

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silver cement. Great care was needed to prevent shorting the current and potential areas of c-axis samples, and for both types of sample there was a tendency for copper to be plated in globules along the "masked" edge of the graphite. Several carefully applied cement layers were needed to prevent this. The 40 swg copper wires used to make connection to the samples could be bent without fear of damaging the graphite but they were easily broken off at the sharp edges of the silver paint. Any short length of wire inadvertently sheathed in silver paint could not be safely bent at all. Contact resistances achieved by the above techniques were quite insignificant compared with the several ohms resistance of the wires leading out of the cryostat. Mounting of samples - alignment

Basal-plane samples were stuck to tufnol frames for ease of manipulation, the current leads being soldered to electrically insulated heat posts attached by "Araldite" to the copper sample block. By gently bending these wires until a travelling microscope indicated that the basal-planes were parallel to the axis of the copper block, the normal to the basal-planes was brought to within 0.2° of a position perpendicular to this axis. Once the copper block was screwed into position on the cryostat, the sample c-axis was within 0.2° of the horizontal plane. Because of the effective planar isotropy within the layer planes it was

SAMPLES USED IN THIS STUDY

W1 Starting material IFP53 (Spain et al. 1967). Hotpressed at 2970°C, annealed at 3500°C. Density 2.266 gms/cm³.

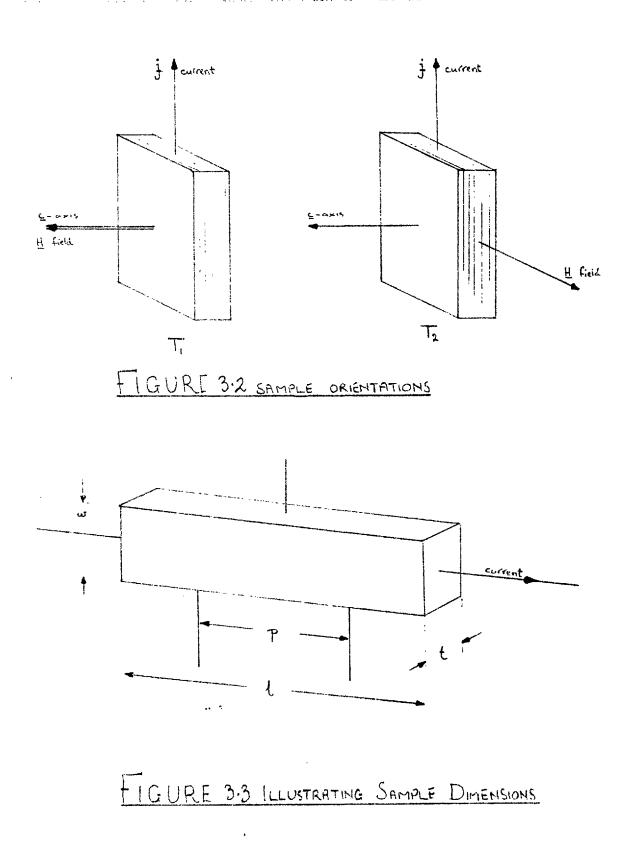
W2 Starting material IFP64T. Hot-pressed at 2850°C, annealed at 3500°C. Density 2.26gms/cm³.

W3 Selected inner layer material (Section 1.2); annealed at $\geq 3700^{\circ}$ C.

not necessary to align the current axis accurately to the vertical so this was done by eye. A simple rotation of the magnet about its vertical axis now brought the magnetic field vector (B) parallel to the c-axis (position T1), or normal to it (position T2) see Figure 3.2. Coloured cement was used to fix the sample into position and to hold the wires firmly in contact with the copper block. Forces of the order of fractions of a gram-wt were expected on the wires when the magnetic field was near its maximum value so they were coated with the cement to stiffen them sufficiently to prevent movement. Tissue paper was used where electrical insulation was required. C-axis samples were aligned in a similar way and fixed with the cement. The thermocouple bead was attached to the sample face with a thin layer of tissue paper to isolate it electrically but not thermally. Care was taken to prevent any wire from touching the outer copper cap which was slipped over the whole assembly to form the exchange gas space.

3.2 FORM OF THE RESULTS - TAKING THE MEASUREMENTS

Sample voltages were of the order from μV to hundreds of μV for the Hall effect and from μV up to mV for magnetoresistance. A Pye three-dial Vernier potentiometer, measuring to 1 μV on the last dial, was employed with a Tinsley galvanometer amplifier to enable voltages to be estimated to within 0.1 μV . By means



of a switchbox described below this potentiometer was used for measuring sample resistive and Hall voltages, sample current as measured by the voltage developed across a standard 0.1 Ω and the current supplying a Hall probe placed in the magnet pole gap. The Hall probe output could be switched to the potentiometer when required. Free inputs on the potentiometer itself were used for measuring the thermocouple output with respect to a liquid oxygen standard maintained in a dewar vessel. The Hall probe output and sample voltage were usually switched into the two axes of an X-Y chart recorder to produce a trace which was approximately a plot of sample voltage against magnetic field approximately because, although the electronic system was verified to be linear in response to about 1/10th percent, the Hall probe output was guadratic in field. A slow-sweep unit was used to change the magnetic field at a low rate, generating a trace on the chart recorder. It was usual to generate two sets of charts for each temperature - one set over the whole field range available (up to nearly 18 kgauss) and the other, using expanded recorder scales, up to about 6 kgauss. Calibration points were put onto charts by stopping the field sweep as was convenient and measuring relevant voltages with the potentiometer.

Consider now a sample with the dimensions shown in the diagram, Figure 3.3 of width ω , thickness t and with a uniform current flow down its length.

The Hall coefficient R_{H} and resistivity $\rho(H)$ in transverse magnetic field H are related to the Hall voltage V_{H} across the width of the sample and the voltage V_{S} down the length of the sample (between probes spaced a distance p apart) by

$$R_{\rm H} = \frac{V_{\rm H}/\omega}{{\rm HI}/\omega t} = \frac{V_{\rm H}t}{{\rm HI}}$$
$$\rho = \left(\frac{V_{\rm S}}{{\rm I}}\right) \left(\frac{\omega t}{{\rm p}}\right)$$

Now suppose we make a series of measurements of Hall voltage, reversing magnetic field and current to give four measured voltages:

$$V_{1} = V_{H} + RI + \Delta V + f(I)g(H)$$

$$V_{2} = -V_{H} - RI + \Delta V + f(-I)g(H)$$

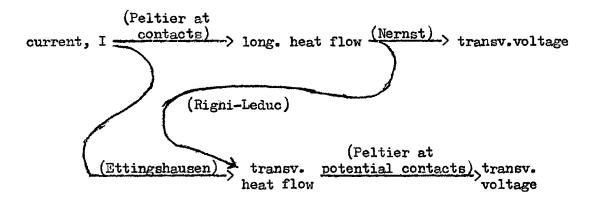
$$V_{3} = -V_{H} + RI + \Delta V + f(I)g(-H)$$

$$V_{\Delta} = +V_{H} - RI + \Delta V + f(-I)g(-H)$$

where RI represents a resistive drop due to misalignment of the two effective Hall potential probes, ΔV represents spurious current-independent thermal emf's in the copper leads, and

f(I)g(H) is a function of current I and field H representing magnetothermal effects. We see that the usual practice of taking the combination $(V_1 - V_2 - V_3 + V_4)/4$ gives $V_H + \frac{1}{4}(f(I)g(H) + f(-I)g(-H) - f(-I)g(H) - f(I)g(-H))$ which is just equal to the Hall voltage V_H if the second term is zero.

The second term is zero provided only that f(I)g(H) is not odd in both of the variables I or H. Now if we examine the consequences of the sample not being completely isothermal we see that there are three main sources of transverse voltage, stemming from combinations of magnetothermal and thermoelectric effects. Diagrammatically, we have



The final effects, the transverse voltages, depend on heat flows and so take time to decay and re-establish themselves if the current is reversed. Measurements taken so quickly that thermal gradients do not have time to change appreciably are termed 'fast'. 'Slow' measurements enable the thermal gradients to reverse completely. The effect of fast and slow reversals of I and H on

ABLE 3.1

			`Fast'	'SLOW'
(N	f(-1) g(H) =	रेत) ३७१)	- f(I) g(H)
REVERSAL of	RLP	f(-I) J(H) =	ર્ટા નિભો	- fa) 914)
CURRENT	EP	f(-I) g(H) =	f(1) g(H)	- f(z) g(н)
(Ν	f(I) g(H) =	- f(z) g(H)	-f(I) д(н)
REVERSAL of	RLP	f(I) g(-H) =	f(I) 9(H)	- f(I) g(H)
MAGNETIC FIELD	EP	f(I) g(-H) =	f(I) 9(H)	- f(1) g(H)

EFFECT OF CURRENT AND MAGNETIC FIELD REVERSAL

For example: The magnetuthermal voltages change sign on reversal of current ('slow') unless measurements are made before thermal gradients have time to change appreciably ('fact'). *3*~

the transverse voltages produced by the Nernst (N), Righi-Leduc-Peltier (RLP), and the Ettingshausen-Peltier (EP) combinations are shown in the following table 3.7.

We see that either of the two combinations formed by slow or by fast magnetic field reversal with fast current reversal leads to elimination of all these spurious effects but that the other two combinations, with slow current reversal, fail to eliminate either the Nernst (N) effect of any effect at all.

Hall measurements on sample W1 were performed by reversing both current and field at leisure, since there was no hope of being able to take 'fast' current-reversed measurements because of the high layer-plane thermal conductivity. This procedure eliminated the appreciable misalignment voltage inevitable with this particular sample and also thermal voltages in the leads but it left in the above effects. However, c.f. Putley (1960) P. 86, estimates give about 0.1 μ V at 5000 gauss for the dominant effect (Nernst) and orders of magnitude less for the others. Observation of these spurious voltages is possible with bismuth using an oscilloscope triggered by the current or field reversing switch but a high gain d.c. amplifier with sufficiently short response time was not available for checking in the present case. The other basal plane samples were measured by reversing the current. The field was not reversed partly because of the practically impossible task of

rotating the water-cooled magnet through 180° in the confined space around the cryostat without endangering the long-tailed glass dewar which rested, with little lateral movement, in the pole gap. The alternative procedure of slowly decreasing the field to zero, shutting down the generator, reversing the magnet leads and then re-setting the field to its original value took too long to be practicable for the time-limited low temperature runs and introduced the risk of inducing temperature changes through eddycurrent heating. 'Slow' current reversal alone eliminated the (not negligible) thermal voltages in the sample leads but accurate zero field balancing was necessary to ensure that no resistive term (RI) appeared in the measured voltage. Two resistance boxes gave a total of about 30 ohms connected across the sample potential arms and the Hall voltage was measured between the junction of the boxes and the third potential arm on the sample. In zero field, the measured voltage was set to zero by adjusting the box resistances to within 0.1 ohm. Thus, at worst, one third of one percent of the resistive voltage drop across the first two potential arms appeared added to or subtracted from the actual Hall voltage. This is most critical at magnetic fields near 3 kgauss where the Hall effect sometimes changes sign. Below this field the magnetoresistance voltage dropped rapidly to zero as H² whilst the Hall voltage increased in magnitude before dropping to zero. Above 3 kgauss

the Hall voltage increased more rapidly than the magnetoresistance voltage (though it was always of smaller magnitude) so the fractional error decreased once more. We see that, except for a slight shift in the position of zero Hall coefficient on the field axis, this effect is less than the error involved in measuring sample thickness which appears explicitly in the calculation of the Hall coefficient.

We define magnetoresistance by $\mathbb{M} = \frac{\rho(\mathbb{H}) - \rho(0)}{\rho(0)}$. In practice this reduced to $\mathbb{M} = \frac{\mathbf{v}_{g}(\mathbb{H}) - \mathbf{v}_{g}(0)}{\mathbf{v}_{g}(0)}$, since negligible current change occurred during a run. Once more, spurious thermomagnetic potentials could have arisen to perturb the potential difference due to the sample resistance. No current was drawn through the contacts in the potentiometer balance position so only Saebeck emfs due to longitudinal temperature gradients down the sample were likely to have an effect. 'Slow' current reversal does not eliminate these but the temperature gradient which can be established down the sample is held to low values by the high layer-plane thermal conductivity.

3.3 APPARATUS

The apparatus used in the present investigations may be divided into three parts for the purposes of description: the magnet, the cryostat and its associated vacuum equipment, and the electrical measuring equipment.

3.3.1 <u>MAGNET</u>

This dictated the main dimensions of the cryostat. The magnet employed was a Newport Type D electromagnet fitted with high-power, water-cooled coils. Special conical pole-pieces made by Newport to increase the maximum attainable field-strength at the expense of pole-gap. The working pole-gap with these polepieces was 4.5 cms, giving a maximum field of about 18 kgauss.

The magnet yoke was mounted on a turn-table inscribed in degrees and fitted with a vernier device reading to tenths of a degree. A trolley enabled the whole magnet assembly to be moved into position on a pair of rails.

A Newport Type 905 C power supply was used in conjunction with the magnet. This consisted of a 25 kW motor-generator whose output was controlled and stabilised from a bench consol. A slowsweep unit was used to vary the magnet current linearly with time, although this did not, of course, result in a linear variation of field-strength with time.

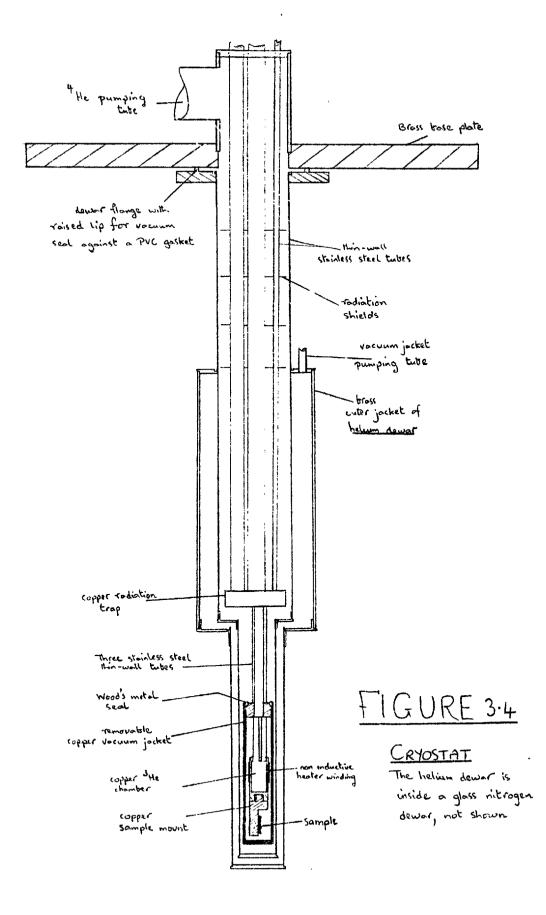
3.3.2 CRYOSTAT

It was required to maintain the samples at temperatures ranging from room temperature down to below 1° K. Because of the fairly narrow magnet pole-gap and the requirement that it should be possible to rotate the magnet about a vertical axis passing through the sample, the cryostat had to be quite long and thin. This severely restricted pumping speeds for tubes of reasonable diameter extending down to the sample, and it was apparent that the higher-vapour pressure liquid helium-3 would have to be used to attain temperatures below 1^oK.

A diagram of the cryostat appears in Figure 3.4.

The sample was mounted on a copper block screwed into the copper helium-3 chamber. This was kept evacuated at all but the lowest temperatures, when helium-3 was condensed into it. Stainless-steel tubes with thin walls were used to suspend the copper sample block in vacuum and to provide lines for the evacuation of the helium-3 chamber and connections to a vapour pressure manometer. The sample vacuum jacket, maintained within a removable copper cap, was produced by pumping through a further thin-walled stainless-steel tube. It was possible to fill the sample vacuum space with helium-4 gas during initial cooling operations to thermally short-circuit the stainless-steel tubes and ensure rapid cooling of the sample.

The above assembly was immersed in a bath of liquid helium-4 contained in a metal dewar extending upwards to the thick brass base-plate, keeping the steel pumping tubes at very low temperatures (and hence considerably reducing their thermal conductivity) for most of their lengths. In particular, the copper radiation trap was as low down in the dewar as possible to ensure that it



re-emitted energy at a low power to the sample block hanging immediately below it. Radiation shields consisting of foam plastic faced with aluminium foil were positioned at intervals along the pumping tubes. These helped to reduce room-temperature radiation reaching the liquid helium and so boiling off large volumes of cold helium gas; the shields acted as heat exchangers which caused the radiation to warm the helium gas already boiledoff by other thermal leakage currents. The helium dewar vacuum space was continuously pumped by means of an Edwards EO2 oil diffusion pump - it was not sealed for fear that a leak of superfluid helium into this space might cause an explosion on warming up.

To reduce radiation across the helium dewar vacuum space the standard procedure was adopted of surrounding the dewar by a jacket of liquid nitroger: a long-tailed glass dewar fitted over the metal helium dewar and was hung in a webbing harness from six stout springs attached to the base-plate.

Different parts and systems making up the cryostat will now be described in greater detail.

Sample Exchange-Gas Space

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This was filled with helium-4 gas to speed the initial cooling down process and, in fact, whenever a thermal tie was required between the copper sample block and the liquid in the metal dewar. For temperatures differing from that in the metal dewar, and especially for helium-3 work, the space was evacuated with an Edwards 102 oil diffusion pump backed by an ED 150 two-stage rotary pump. Exchange gas could be admitted from a small coiled copper tube reservoir (Figure 3.5), a Bourdon gauge enabling the pressure to be monitored up to 20 torr.

Helium-4 Dewar

Thin-walled stainless steel tubing was used for this dewar because of its low thermal conductivity and high mechanical strength. The limited width between the magnet pole-pieces precluded the use of a relatively thick-walled glass dewar. Flanges were machined from stainless steel plate and then the dewar was assembled and argon-arc welded commercially. Brass tubes were supplied to act as a thermal sink and spacing tube during the welding operations which were made more delicate by the thinness of the steel tubes. Six bolt-holes in the upper steel flange enable the dewar to be fixed to the brass base plate of the cryostat, using a plastic gasket to render the assembly vacuum-tight. The large outer tube of the vacuum jacket was constructed of 18 gauge brass for strength. It was hard-soldered into position.

A type EO2 oil diffusion pump was used to evacuate the helium dewar vacuum jacket through a liquid nitrogen vapour trap. The pressure, monitored on a Penning gauge, was usually 2.0 or 3.10^{-5} torr near the diffusion pump. However, because of space limitations, a small ($\frac{1}{4}$ " diameter) pipe had to be used near to the dewar and this constriction undoubtedly allowed the inner wall of the vacuum jacket to cryopump this space to a much lower pressure when the dewar was being used with liquid helium.

It was necessary to lower the temperature of the main bath to below 1.5° K to enable helium-3 to be condensed into its chamber at a reasonably low pressure. This meant lowering the pressure above the liquid helium-4 to below 3.6 torr. A large rotary pump, an Edwards ED450, was used through a $4^{"}$ diameter line to effect this. Metal bellows were placed strategically in the line to isolate pump vibrations. Temperatures close to 0.9° K were achieved using this system alone. This seems to indicate that esoteric devices for limiting the rate of flow of the superfluid film below the lambda-point (2.2° K), such as minute pinholes in an otherwise blocked pumping line, are unnecessary unless the lowest temperatures attainable with single-stage helium-4 cooling are desired.

In the event of a sudden energy input to the helium bath (through, for instance, failure of the vacuum jacket) considerable volumes of helium gas would have been boiled-off, because of the low latent heat of liquid helium. A flap valve was fitted on the pumping line at the top of the cryostat to prevent the internal pressure ever building up much above atmospheric pressure.

The dewar pumping system enabled temperatures down to about 50° K to be reached by pumping on liquid and solid nitrogen

contained in the metal dewar. A liquid nitrogen jacket in the glass outer dewar was not essential for this but did increase the length of runs at the lower temperatures.

By using a small (1SC35) rotary pump plugged into the helium transfer port it was possible to pump at the slow rates necessary at higher temperatures. A butterfly valve in the large 4" line and small valves in the transfer-port line made it possible to vary the pressure continuously over the whole range attainable.

Helium-3 System

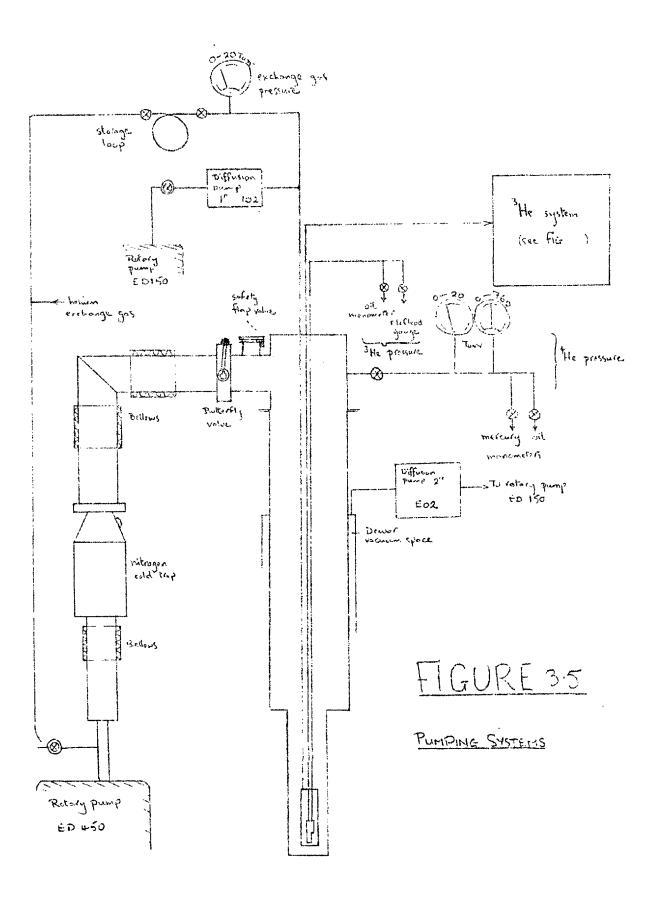
This was designed to enable helium-3 gas to be condensed into the small copper chamber on which the sample was mounted and then to pump on the liquid to lower its temperature. As the gas is expensive a closed system was necessary, (Figure 3.6).

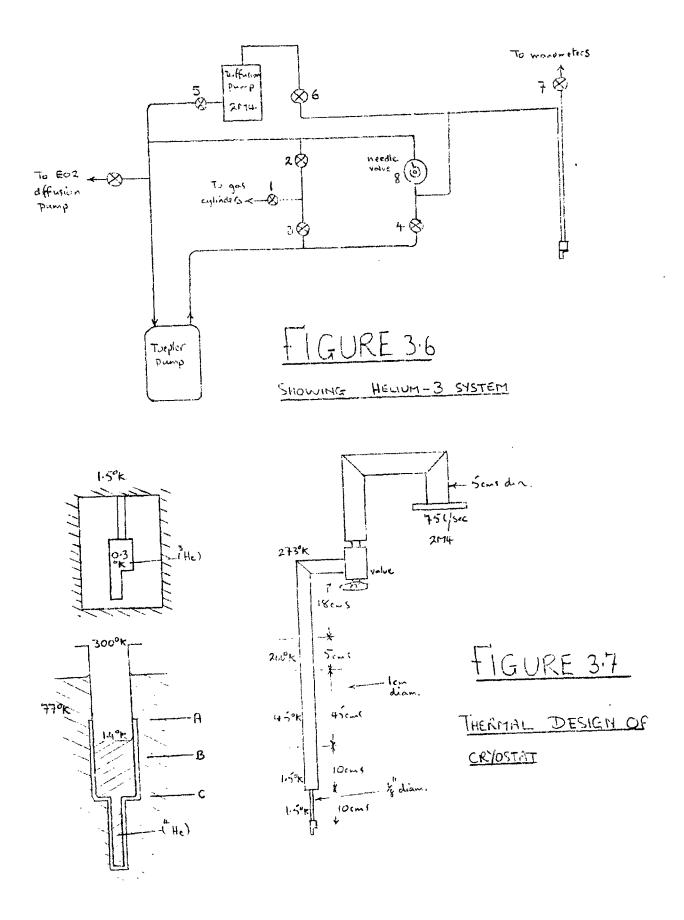
A mercury diffusion pump, type 2M4, was chosen to pump on the liquid helium-3 because it can work into backing pressures as high as 3.5 cms. Hg. This means that no rotary backing pump was required provided that the system was not filled to a pressure higher than 3.5 cms. Hg. In fact, a mercury Toepler pump was included for several reasons: it was not known (during the design stage) what temperature could be reached in the main helium dewar (mainly because of the uncertain effect of superfluid film-flow) and a value of 1.4° K was assumed. It then appeared that the condensing pressure required was greater than 3.5 cms. Hg. which meant that either the system had to be filled to the higher pressure, implying

some form of backing pump for the 2M4, or it could be filled to below 3.5 cms. Hg., implying some form of condensing jump. A Toepler pump could be switched to fulfill either of these functions as needed. In addition, it is normal practice to return as much as possible of the helium-3 to the storage vessels to avoid loss by diffusion out through glass parts of the system or contamination with atmospheric helium-A diffusing into the system.

From the diagram (Figure 3.6), it can be seen that suitable combinations of valve positions gave the following facilities:

- 1. The system could be evacuated through a connection to the EO2 diffusion pump prior to filling with helium-3 gas.
- 2. Filling was accomplished through value 1 and the storagecylinder values.
- 3. Once the sample chamber was below 1.4°K, condensation of helium-3 could be achieved by using the Toepler pump to force gas through the small-bore condensing line via valve 4. During this operation the large volume of the diffusion pump was isolated by means of valves 5, 6 and that of the vapour-pressure manometers by valve 7.
- 4. The liquid helium-3 could be pumped off rapidly through the diffusion pump and returned to storage via the path 6, 5, 3, 1. In this mode, the needle valve, 8, was effectively across the diffusion pump, controlling its pumping speed and hence the temperature of the sample.





Thermal Design of the Cryostat

The main dimensions of the cryostat were dictated by the magnet. Thus, the largest diameter of the outer, nitrogen, dewar was fixed by the distance between the magnet current coils and the diameter of the tail was fixed by the pole gap. This, in turn, decided the diameters of the stainless steel tubes used in the construction of the helium dewar - since there is a limited choice of diameters of thin-walled cryogenic-quality tubing.

It is proposed to examine the cryostat as constructed rather than report the design process which was affected by many outside influences.

Helium-3 System

The copper sample block was hung on two stainless steel tubes, $A \text{ cms. long, } \frac{1}{8}^{"}$ diameter, and of 0.006" wall thickness, within a vacuum space. These provide the thermal isolation necessary to maintain a temperature difference between the sample and the main helium bath. We shall consider the extreme case of the helium bath at 1.5[°]K and the sample at (about) 0.3[°]K (due to pumping on the helium-3), see (Figure 3.7). The actual sample temperature depends on the balance between pumping speed at the surface of the liquid helium-3 and the total heat flux into the helium-3 bath. Heat Leakage to the helium-3 Chamber

a) Down the two steel tubes. Taking a mean thermal conductivity of 0.7 mW deg⁻¹ cm⁻¹ this is easily calculated to be approximately ≤ 0.007 mW. b) Radiation from the copper cap at 1.5° K. Taking an area of 60 cms² and using the Stefan-Boltzmann constant $(5.67 \ 10^{-9} \text{ mW cm}^{-2} \text{ deg}^{-4})$ this is $1.7 \ 10^{-6} \text{ mW}$ -negligible. It is interesting to note here that if the radiation trap had been maintained at liquid nitrogen temperature then radiation down the two $\frac{1}{8}$ " diameter tubes would have been 70,000 times this value.

c) Joule heating of sample. A typical sample would have dimensions 1 x 0.1 x 0.05 cms. and resistivity 0.3 x 10^{-5} ohm-cm at these temperatures. Joule heating for the fairly high sample current of 200 mA is then 0.012 mW.

d) Heat down copper leads. There were seven copper wires of 40 s.w.g. Using a mean thermal conductivity of 2 Watts \deg^{-1} cm⁻¹ this gives 0.5 mW.

e) Joule heating of copper leads. Assuming all the heat generated flows into the helium-3 chamber, a resistivity of ~ 10^{-9} ohm-cm and a sample current of 200 mA, the heat input from the two current wires is ~ 0.001 mW. Calculation yields 46 gauge as the size of wire which minimises the sum of contributions (d) and (e), giving a value of 0.02 mW. However, such thin wire would overheat with reasonable currents for room temperature measurements.

f) Heat down thermocouple wires. The gold wire had a diameter of 0.012" which gives a heat leak of 0.2 mW. We expect the chromel contribution to be negligible.

g) Conduction through residual gas in the vacuum space. Assuming the abnormally high pressure of 10^{-4} torr this was estimated at less than $\frac{1}{10}$ th μ W which is negligible.

h) Eddy current heating due to changing the magnetic field. This was observed during the flyback of the magnetic field scanning system but was negligible during the slow measuring scan. Pumping Speed at the Surface of the helium-3

Figure 3.7 shows the layout of the helium-3 pumping line. Assuming the temperature distribution indicated, the conductance of the line was estimated to be 0.008 litres/sec. Now under equilibrium conditions, the gas flow rate through the line is equal to the rate of boil-off due to heat leaks into the helium-3 chamber. This, together with the above value for the line conductance, enables us to calculate the pressure drop across the line. Neglecting the pressure at the throat of the 2M4 diffusion pump then leads directly to an estimate of the vapour pressure in the helium-3 chamber. Calculation shows that the gas flow rate (throughput) is 7.84 x 10^{-4} W litre-torr/sec where W is the heat leak input in milliwatts, giving a pressure drop of 0.98 x 10^{-4} W torr. Thus we expect the lowest vapour pressure to be (W = 0.7 mW) 0.07 torr, corresponding to atemperature of 0.45°K. This is the worst value for the lowest attainable temperature because the greatest values for heat leaks have been used throughout the calculation and we might expect something a little better in practice. The run duration, assuming

 2 cm^3 of liquid helium-3 and a heat leak of 0.7 mW, comes out at about 20 minutes.

Helium-4 System

The purpose of this system during a very low temperature run was to maintain the liquid helium-4 in the metal dewar at 1.4° K or below for as long as possible. Figure 3.7 shows the essential features. The pumping system was shown in (Figure 3.5).

Helium-4 System - Heat leaks into the helium-4 bath

a) Down the wall of the dewar. Making the reasonable assumption that all heat from the top flange is dumped into the liquid nitrogen bath, we are left with a leak path from the nitrogen bath to the helium which grows longer as the helium level falls. With a full helium dewar (level at A Figure 3.7) this must completely dominate the situation and cause a rapid boil off of helium but as the level falls the low thermal conductivity of the wall quickly reduced the heat influx. With the level at B the heat leak is 0.076 watts. When the level has fallen to C the heat leak is reduced to 0.038 watts.

b) Down the pumping tubes leading to the radiation trap and the sample block. There were two tubes of $\frac{1}{2}$ " diameter, 0.010" wall thickness and one of $\frac{1}{8}$ " diameter, 0.006" wall thickness. They conduct heat directly from the room-temperature base-plate of the cryostat into the helium bath. Once again the length of the conduction path varies with the helium level. Calculations taking into account the variation with temperature of the thermal conductivity (p. 57, Rose-Innes) give heat leaks of 0.20 watts for a helium level at B and 0.15 watts for the case C.

c) Conduction down electrical leads. This is estimated at $\leq 5 \text{ mW}$.

d) Radiation. Shields were used in an attempt to stop direct room-temperature radiation. It was hoped that the cold helium gas would remove this heat from the shields and maintain the lower ones at least at nitrogen temperatures. We assume, then, that the lowest shield radiates at a temperature of 77° K, directly into the helium bath. This gives a heat influx of 6.3 mW. A surface maintained at room-temperature would radiate about 160 times as much power.

The above heat leaks into the helium bath, total about B: 0.29 and C: 0.20 watts, cause the helium to boil-off and limit the duration of a run. 0.3 watts correspond to 415 ccs of liquid helium per hour which is appreciable. However, the cold helium gas being driven off is capable of absorbing a lot of heat as it warms up to room-temperature. The enthalpy of the gas between a few degrees Kelvin and room-temperature is about 13 watts/mole. Thus, the gas boiled off by the above heat leaks is capable of absorbing all and more of the unwanted heat influx, implying that if efficient heat transfer is arranged between the issuing gas and the leakage paths a very low nett boil off rate will results.

The situation is complicated by the fact that liquid helium is in the superfluid state at temperatures below 2.2° K. The superfluid film is extremely mobile and climbs up all surfaces kept below the transition temperature (lambda point), greatly increasing the surface area from which the liquid can evaporate. The upper limit of the film corresponds to the position of the 2.2° K isothermal in the cryostat, for above this the helium could only exist as ordinary helium - without any climbing abilities. A typical maximum film flow rate is $6 \ge 10^{-2}$ ccs liquid/sec for a one cm film-width but a dirty wall surface or an air-film can increase this by an order of magnitude. Provided the pumping system can take care of this evaporation rate then temperatures below the lambda-point can be reached; at higher pumping rates the more distant parts of the film will become depleted and the evaporation area will be reduced once more.

Considering conditions at the lambda point; the maximum evaporation rate is around 20 x 6 x 10^{-2} ccs/sec, assuming the upper edge of the film to have a perimeter of about 20 cms. This is easily converted into the gas flow rate and corresponds to a throughput of 0.A liter-torr/sec. A vapour pressure of 3 torr is assumed under

impedance

these conditions. Now, the **conductance** of the pumping tube was made negligible and the main pressure drop will occur across the nitrogen trap in the line. This has a conductance of 601/sec. Hence the pressure drop is throughput/conductance or approximately 0.01 torr. This means the pressure at the inlet of the rotary pump will be 3 torr and the pump speed required will be throughput/ pressure or 0.4/3 liters/sec. A pump, then of some 10 liters per minute is required. Even if the film flow were much higher due to surface contamination 100 liters per minute would suffice. It appears that the pump actually used, an Edwards ED450, had an adequate reserve of pumping speed and its full 450 liters per minute could be used to take the system down to temperatures below the lambda point.

Estimates of durations of runs to be expected from one filling of the helium dewar are difficult to make because it is not known how much heat the cold gas takes up before reaching the top of the cryostat. However, assuming very poor heat exchange between the gas and the lower parts of the cryostat, the heat leaks calculated above lead to a boil off rate of 0.42 liters/hour for level B and 0.28 liters/hour for level C. These are maximum rates expected for these levels. Since the volume of the dewar between these levels is about 0.4 liters, a run duration of about 1.2 hours is to be expected and was in fact exceeded in practice. At lower temperatures, a large fraction of the liquid helium is used to cool the body of the rest of the liquid; approximately $\frac{1}{3}$ of the liquid is required to cool the helium bath from 4.2° K to the λ -point. However, the liquid-level will quickly approach B and less will have been boiled off uselessly by the heat leak from the nitrogen bath.

Procedure for Working at Chosen Temperatures up to Room Temperature

There are few easily-available refrigerant liquids: liquid nitrogen is by far the most convenient for higher temperatures and can be employed usefully in the solid form below 63°K down to about 50°K. Liquid oxygen has a boiling point of 90°K which is too close to that of nitrogen $(77^{\circ}K)$ to make it of considerable use but its high latent heat is an advantage in that long runs are possible. Helium-4 boils normally at 4.2°K and is convenient for temperatures down to about 1°K but below this very high pumping speeds are required and it is easier to use the higher vapour-pressure isotope, helium-3, for the very low temperatures down to 0.3° K, say. The large temperature gap between helium and nitrogen can be reached by heating the sample block with a small heater wound onto the helium-3 chamber. However, the extra power input resulted in considerably shorter runs. There are refrigerants with normal boiling points in the gap but they are expensive and sometimes

are only supplied on condition that the gas be returned to the suppliers - implying the possession of 2 complete gas recovery unit.

Below 1°K

The nitrogen dewar was filled and about 24 liters of liquid nitrogen poured into the metal dewar. Helium gas at about 20 torr was let into the exchange gas space to connect the sample thermally with the nitrogen in the metal dewar. The system was then allowed to cool to 77° K. When this temperature was reached, the metal dewar was evacuated and refilled with helium gas from a cylinder. Any remaining liquid nitrogen would cause a drop in sample temperature at this stage and pumping was continued until the temperature started to rise again. Solid nitrogen has a low thermal conductivity and would prevent successful cooling down to helium temperatures if allowed to remain. With the dewar and contents at 77° K in an atmosphere of helium gas the system was ready for helium transfer.

Liquid helium was transferred through a vacuum-jacketed tube by squeezing on a rubber bladder attached to the supply dewar. It came over as gas until the transfer line had cooled to 4.2° K when liquid started to issue from the tube, accompanied by a characteristic limpness in the rubber bladder. As liquid condensed in the metal-dewar tail the sample temperature decreased rapidly but it

took about half an hour for thermal gradients to die out. The transfer process was not hurried unduly to avoid wasting the liquid helium: gas issuing from the top of the cryostat should have absorbed heat from the cryostat interior in warming up to room temperature and not from the top of the cryostat. A gas rotameter plugged into the flap-valve port enabled the helium flow rate to be monitored. It was found that an average rate of about 1.3 liters/ minute with occasional puffs of over 3 liters/minute gave a reasonably short cooling time with little wastage of the liquid helium. When the dewar was full, as indicated by a rapid increase in the rotameter reading, the transfer tube was removed and the transfer port was plugged. After closing the flap valve against its rubber sealing ring, pumping on the helium bath was started. Again, the cryostat top was not allowed to cool appreciably as this would have meant inefficient cooling of the cryostat interior.

When the sample temperature had reached 1.4[°]K or below, helium-3 was condensed into its chamber by means of the Toepler pump, as described earlier. Pumping on the liquid helium-3 with the 2M4 diffusion pump then resulted in a further lowering of temperature, after evacuating the exchange gas space thoroughly by means of the 102 diffusion pump.

Temperatures between the lowest attainable and 1° K could be maintained either by adjusting the 2M4 pumping speed or by using

the sample block heater. The former method was preferable the point of view of run length.

1.0°K to 4.2°K

Temperatures below the normal boiling point of helium-4 were reached by pumping on the helium in the metal dewar, using helium gas in the exchange gas space. This gas condensed at about $\leq 1.9^{\circ}$ K and its vapour-pressure provided a convenient indication of temperature at lower temperatures. Temperature control was effected by varying the pumping speed of a small rotary pump plugged into the helium transfer-port, leaving the butterfly valve to the large rotary pump cracked open a convenient amount. The small pump could be used alone down to the lambda point but it could make no impression on the large volumes of vapour produced by the evaporating superfluid film at lower temperatures. 4.2° K to 50° K

This was the most difficult region to work in as refrigerants with boiling points in the region were not available. The procedure used was to fill the metal dewar with helium-4, as described above, and with a suitable helium exchange gas pressure, to pass a current through the constantan heater winding on the sample block. Temperature was controlled by varying this current.

At low temperatures a fairly high exchange gas pressure was required (10 to 20 torr) to reduce the sensitivity to small changes in current. At the higher temperatures a lower pressure (below 1 torr) enabled these temperatures to be reached with a reasonably small power dissipation.

50°K to 77°K

By filling the metal dewar with liquid nitrogen and pumping on this liquid, temperatures below the normal boiling point $(77^{\circ}K)$ down to about $50^{\circ}K$ could be reached. The nitrogen solidified at $63^{\circ}K$ and this proved to be a convenient, stable, point provided it was approached from below to ensure that an appreciable volume of the solid had formed. Pumping on the solid nitrogen lowered the temperature further but, because of the low thermal conductivity of the solid, cooling of the sample was very slow in this range.

77°K to Room Temperature

A similar technique was employed in this range to that employed for working above the normal helium boiling point; a suitable exchange gas pressure was used and the sample block heater current was adjusted to maintain the desired temperature. The exchange gas pressure was reduced from about 10 torr to about 10 microns as the working temperature was increased to avoid an unmanageable sensitivity to current variation at low temperatures and to enable reasonably small power levels to be used at higher temperatures.

3.3.3 ELECTRICAL MEASUREMENTS

Voltages from the sample arms were presented to one axis of an X-Y chart recorder or, for calibration purposes, to a Pye 1 uV Vernier potentiometer with a Tinsley photocell galvanometer amplifier enabling voltages to be estimated to 0.1 µV. A Keithley Model 149 milli-microvoltmeter was used to amplify sample voltages up to the millivolt level before they were presented to the Y-axis of the chart recorder. By this means, a sensitivity of better than $0.1 \ \mu V$ per 1% chart width could be obtained but the maximum useable sensitivity was usually determined by noise-broadening of the trace. This originated mainly in the Keithley because of mains-frequency pickup but was kept to acceptable levels by the insertion of a low-pass filter in the input lead to this instrument. The main source of interference appeared to be from the mains transformers of the various electronic instruments since capacitive coupling to their chasses caused currents to flow between the chasses giving rise to potential differences between the ends of the signal wires carrying these currents. Thorough grounding with thick wire seemed to have a useful effect. The X-axis of the chart recorder was driven by a signal from a commercial hall probe AEI Mk III placed in the magnet pole gap and supplied with a constant current of about 10 mA from a 250 V supply through large dropping resistors.

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The electrical measuring system was thus required to present either the sample hall voltage or the voltage across the sample potential probes to the chart recorder or to the potentiometer. In addition, the potentiometer was to be used to measure the sample and hall probe currents and it was necessary to ensure that the Keithley milli-microvoltmeter was never open-circuited for long because the ensuing drift of its output to the f.s.d. of 10 volts would have damaged the chart recorder. The fairly complicated switching arrangement dictated by these requirements is indicated in the block diagram, figure 3.8.

High quality (Cropico) stud switches were used to switch these low-level voltages, an aluminium box being used for screening. Screened cables were used for interconnecting the various instruments and the wires from the sample to this box were confined inside a rigidly-mounted copper pipe to prevent movement (noticeable voltages were induced by movement of wires in the laboratory stray magnetic field).

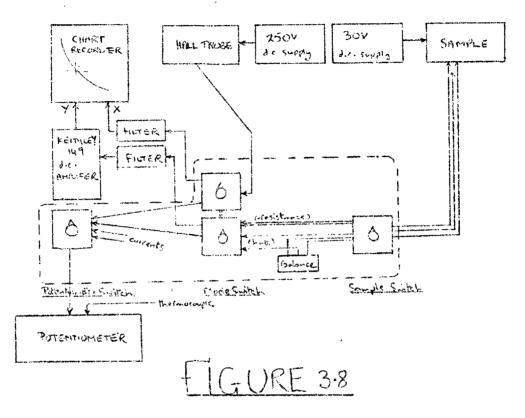
A 30 V Farnell constant voltage supply DSV 30/5 was available for the sample current. Two modes of operation were considered the usual case where a large dropping resistor is used to convert voltage stability into current stability and the method actually employed: a 100 ohm constantan resistor was wound non-inductively on a long thin-walled stainless steel tube and was connected in series with the negative lead from the supply as shown (Figure 3.9).

The voltage developed across this stable resistor was taken back to the 'feedback' terminals of the supply which consequently varied the output voltage to keep this feedback voltage, and hence the sample current, constant. It is estimated that the current stability using this method was better than that given by the usual method by a factor of at least four. Sample current was varied by means of the feedback controls on the supply unit which did not carry any large currents and could be changed without fear of drifting whenever required. Previous trials using a switched set of resistors to vary the sample current led to long periods of drifting current values between measurements. In the interests of current stability, again, it was found necessary to employ the on-off switches available in an unusual manner because of their relatively unreliable operation. Had such a switch been connected in series with the sample, its varying contact resistance would have ruined any current stability achieved in the power supply so it was connected across the sample current leads as shown. The 6 ohm lead resistance between the sample and switching box ensured that the sample current fell to the tens of μA level whenever the switch was closed ('off').

Magnetic Field Measurement

A commercial AEI hall probe was used either to drive the X-axis of the chart recorder or to provide a magnetic field-dependent

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BLOCK DIAGROM OF ELECTRICAL MEASURING SYSTEM

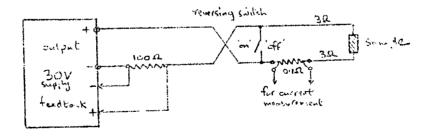


FIGURE 39

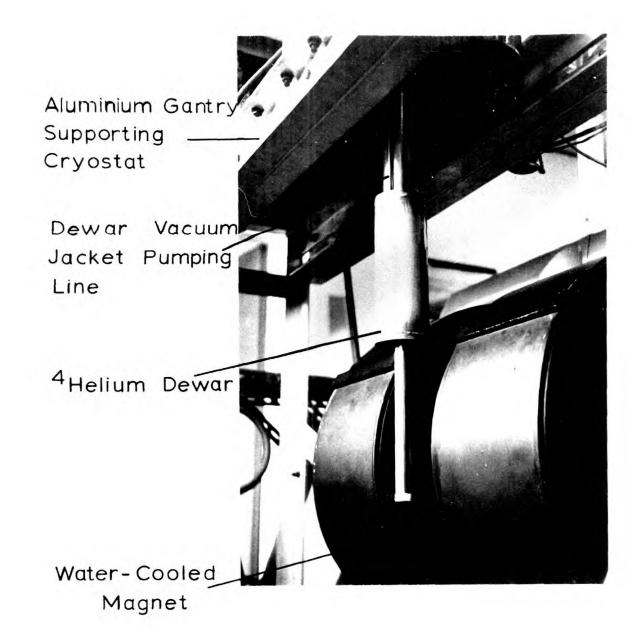
STARILISED SIAMPLE CURRENT SUPPLY

voltage for the potentiometer as determined by the position of the mode switch, see Figure 3.8. Constant current of about 10 mA was provided by a 250 V stabilised Roband power supply through a 25 kohm resistor. Calibration to 1% of the probe was effected using a Norma ballistic fluxmeter. It was found that the output voltage was related to the magnetic field through the relation $V/I = 10^{-3}B[(0.2346 \pm 0.001) - (0.496 \pm 0.025)10^{-6}B]$ where V is the probe output (volts), I the probe current (amps) and B is the magnetic field (gauss). The current was measured by connecting the potentiometer across a 0.1 ohm Rivlin standard resistor. With the probe head used, it was necessary to draw current out of one of the potential leads in order to obtain a zero output in zero field only two potential leads were provided on the hall plate. A simple variable resistor enabled the probe to be zeroed before each run, though this was only really necessary for low fields - it had very little effect on the high field readings. As with the Keithley voltmeter input, it was found necessary to use a low pass filter in the input circuit of the X-axis to prevent sluggish operation of the chart recorder induced by a.c.-mains pickup.

Temperature Measurement

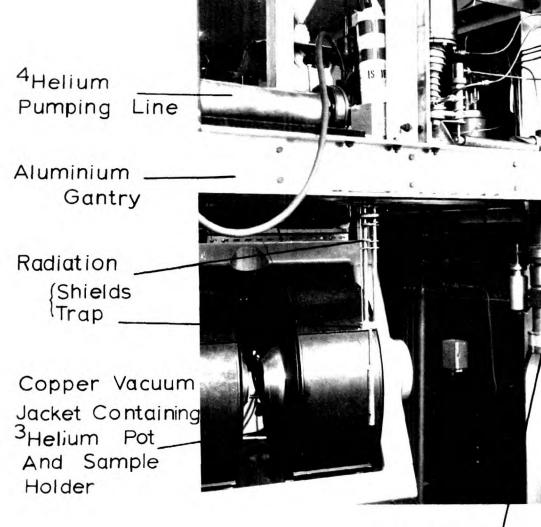
A gold (plus 0.03% iron) alloy - Chromel P thermocouple was used for measuring temperatures against a liquid oxygen standard. The gold wire (0.012" diameter) was from the same Johnson-Mathey batch that Berman et al (1963-64) used in their thermoelectric power measurements. Their emf - temperature data (private communication) was used for interpolation between calibration points, but it was first necessary to reduce this data graphically to values against an oxygen reference. We employed this particular combination because it maintains a high thermoelectric power down to below 4° K (~ 10μ /deg.) whilst having a reasonable value over the higher temperature range up to 300° K.

It is convenient to mention here that oil and mercury manometers were connected to monitor pressures in the main helium-4 dewar and these provided a useful indication of temperature when pumping on the refrigerant in this dewar (whether helium or not). An aneroidtype manometer (0-20 mm Hg) connected to the exchange-gas space proved very useful at temperatures below 4[°]K when it acted as a helium-4 vapour pressure thermometer, and an oil manometer and McLeod gauge were provided for the helium-3 system.



APPARATUS

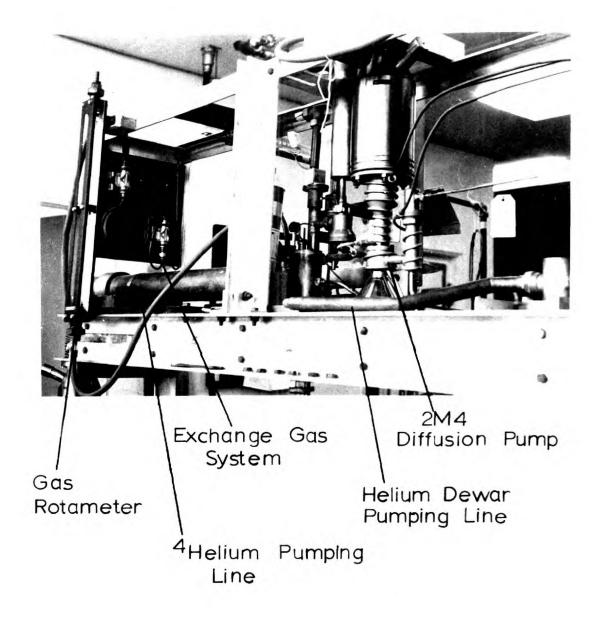
<u>Showing Helium Dewar in place</u>



EO2 Diffusion Pump

APPARATUS

Showing Cryostat Interior



APPARATUS

Showing Pumping Systems

CHAPTER 4

RESULTS - DATA

The present chapter deals firstly with the nature and the preliminary analysis of the non-oscillatory Hall effect R(H) and magnetoconductivity $\sigma(H)$, and secondly with the treatment of data obtained on Shubnikov - de Haas oscillations, observed at magnetic fields above 5kgauss for temperatures of 4.2° K or below. Procedures adopted for data fitting, described at the end of each of these sections, lead on to the derived results contained in the next chapter.

4.1 Non-Oscillatory Data.

4.1.1. Chart Reading.

It was described earlier ("experimental") how chart recordings were produced on which voltages proportional to the sample Hall or magnetoresistive voltage and the output of a Hall probe placed in the magnet pole gap were automatically plotted on an X-Y recorder by slowly scanning the magnetic field. Calibration points were inked on to the chart at intervals during each run, using the potentiometer to obtain voltage co-ordinates of each point.

The first stage in the chart reading process was to obtain the relationship between chart distances and voltage input for a particular channel (X or Y). This procedure was identized for both channels.

A pencil line ruled on the chart parallel to one axis served as a datum, and the distances of the calibration points from this line were measured using the printed lines on the chart as units. An engraved glass scale was used for interpolation between chart lines when necessary. Preliminary measurements of this sort produced straight line plots (within \pm 0.2%) of voltage against chart distance for between ten and twenty calibration points, so later runs usually employed only three to six calibration points. To avoid tedious graphical work, a simple least-squares fitting programme was written for use with an IME86S electronic desk calculator. One writes for the Hall probe (P) axis (X) and the sample (S) axis (Y):-

$$\frac{V_{P}}{I_{p}} = Q_{p} + K_{p}d, \quad \frac{V_{S}}{I_{S}} = Q_{S} + K_{S}d$$

where V and I are voltage and current respectively Q and K are the constants to be found and d is the chart distance. The programme reduced the problem of finding the best pair of coefficients in the linear law to a routine sequence of operations with the desk calculator on data for all samples and temperatures reduced to a common form in consistent units.

The actual reading of the chart then followed. Sixty or more lines were ruled at intervals along the Hall probe (magnetic field, X) axis and the corresponding distances of the trace along the other axis (Y) measured. Later analysis required that the data from both Hall and magnetoresistance charts, taken under a given set of conditions, be tabulated in pairs as functions of magnetic field, so it was necessary to derive the chart intervals corresponding to a given set of magnetic field values for each chart before laying off the construction lines along the Hall probe axis. A computer programme was written to generate chart distances for a batch of charts, corresponding to a standard set of magnetic field values contained within the programme. For this purpose it was only necessary to read-in the coefficients of the linear law between Hall probe voltage and chart distance along that (X) axis for each chart, the (non-linear) Hall probe calibration being written into the programme in a suitable form.

Conversion of the Y-axis chart distances into sample (voltage/ current) was performed either with the desk calculator or, later, as part of a larger computer programme. The latter went on to derive the actual values of Hall coefficient, R(H), and conductivity, $\sigma(H)$, and also the magnetoconductivity tensor components, σ_{xx} , σ_{xy} . It required the input data to be in the form of pairs of chart distances (from the Y-axes of Hall and magnetoresistance charts) together with the corresponding values of magnetic field. A printed output was produced tabulating R, σ , σ_{xx} , σ_{xy} and some intermediate products against magnetic field. Punched cards were also obtained as part of the output with the values of field, σ_{xx} , σ_{xy} coded on to them in a form suitable for later analysis.

The following Hall coefficient values, R(H), given in units of cm³/coulomb, are calculated from the expression $R(H)=(V_H/I_S)(t/H)$ where V_H is in volts, I_S in amperes, t in cms, and H is in gauss/10⁸. 4.1.2. <u>Results</u>, <u>Hall coefficient and conductivity</u>

We mention here that temperatures quoted on the following graphs should be regarded as labels; actual temperatures are given in the tables of Appendix 3 and in Table 5.1, which also contain data for temperatures other than the four selected for full presentation. The conductivity curves afford a close approximation to the desired σ_{xx} curves since the correction from the Hall effect usually amounts to less than 10% when deriving σ_{xx} .

Graphs 4.1, 4.2, 4.3 display conductivity against magnetic field for the three samples W1, W2, W3 at temperatures of 300° K and 77° K. Results for the three samples superimpose well at high magnetic fields but deviate markedly at low fields; successively higher zero-field values of σ are reached by W1, W2, W3 in that order. This high field behaviour provides a check on the reproducibility of our sample preparation technique, in particular the establishing of uniform current flow across the width of the samples. Similar superposition is evident at 63° K and 4° K (Graphs 4.4, 4.5, 4.6) with the same trend in the low-field deviations. Our extension of the range of measurement to magnetic fields above the 6kG used by Spain is fully justified by the significant tail on the conductivity curve at higher fields. The present analysis is based on estimating the area beneath such curves and the tail obviously contributes greatly to this, at least above helium temperatures. The maximum available field of 18kG is reasonable for all temperatures except room temperature where at least double this value would have been desirable.

At low fields, room temperature behaviour for samples W1 and W2 closely mirrors that shown by Soule's (1958) samples EP-14 and EP-7 respectively, in that one shows a downward trend towards zero magnetic field whilst the other has a pronounced positive-going excursion which leads to a positive Hall coefficient below a few hundred gauss. W3 shows an intermediate type of behaviour with a lesspronounced rise starting at a lower field than W2. At higher fields W1 and W2 slowly converge but W3 shows a steeper, roughly linear, increase in the negative direction. Such characteristic behaviour (Graph 4.7) for sample W1 follows closely that reported for Spain's materials SA19/20/22/12/18 and places this sample outside the group of best materials used in their study.

The insistent positive excursion at low fields of some of these Hall curves down to 63°K has not been detected before in pyrolytic graphite. At 77°K in particular the trend is most interesting; the peak at roughly 2kgauss appears to move to lower fields and less negative values with samples W1, W2, W3 whilst the low field side for the peak becomes more dominated by a positive-going tendency leading in the case of W3 to almost complete emoothing of the peak. It should be noted, however, that the exact details of the curves were markedly irreproducible at this temperature and appeared to change upon thermal cycling, an effect not present at other temperatures studied.

The general shape, viz. large negative values on either side of a peak rising towards zero at a few kilogauss, is a familiar picture for pyrolytic graphite (Spain at al., 1967). For material of high perfection the peak actually orosses the zero axis, having a range of positive Hall coefficient for a few kilogauss at around 77°K. We note that none of our samples crossed the axis in this region, although W2 practically touches the axis at 77°K (Graph 4.7) whilst all samples approach very closely at 63°K (Graph 4.10).

Graph 4.11 illustrates the result of fitting the magnetoconductivity tensor components, derived from the data presented above, to Lorentzian curves as described in Section 4.13. The fitting parameters for σ_{xx} , σ_{xy} have been used to regenerate Hall coefficient curves by means of the loop from <u>raw data</u> to <u>tensor</u> <u>components</u> to <u>fitting parameters</u> and thence back via <u>regenerated</u> <u>tensor components</u> to <u>Hall curves</u>. The fits obtained for the conductivity are usually so good that little is gained by showing them, but we will illustrate here extreme examples of good and of disappointing results one obtains for the more complicated Hall curves. Thus, sample W2 at 300[°]K yields a very good fit provided four Lorentzians are used, whereas sample W3 at 63[°]K has not been satisfactorily fitted even by four terms. This is discussed further in Section 5.1.1.

4.1.3. Data Fitting.

We now come to the fitting of the magnetoconductivity tensor components. It has been shown in Section 2.2.1 that only two independent components σ_{xx} , σ_{xy} need to be considered in the basal plane configuration and that these are given by

$$\sigma_{xx}(H) = \frac{\sigma(H)}{1 + (E_{T}H)^{2}}, \sigma_{xy}(H) = R_{T}H \times \sigma_{xx}(H)$$

- where R, σ are the (field-dependent) Hall coefficient and conductivity, respectively. Gaussian units are used throughout, various useful relationships being:

$$R(gaussian) = R(cm3/coulomb) \times \frac{1}{(9\times10^{19})}$$

$$\sigma(gaussian) = \sigma(ohm-cm)^{-1} \times (9\times10^{11})$$

where the value 9 comes from the velocity of light squared and is more accurately 8.988.

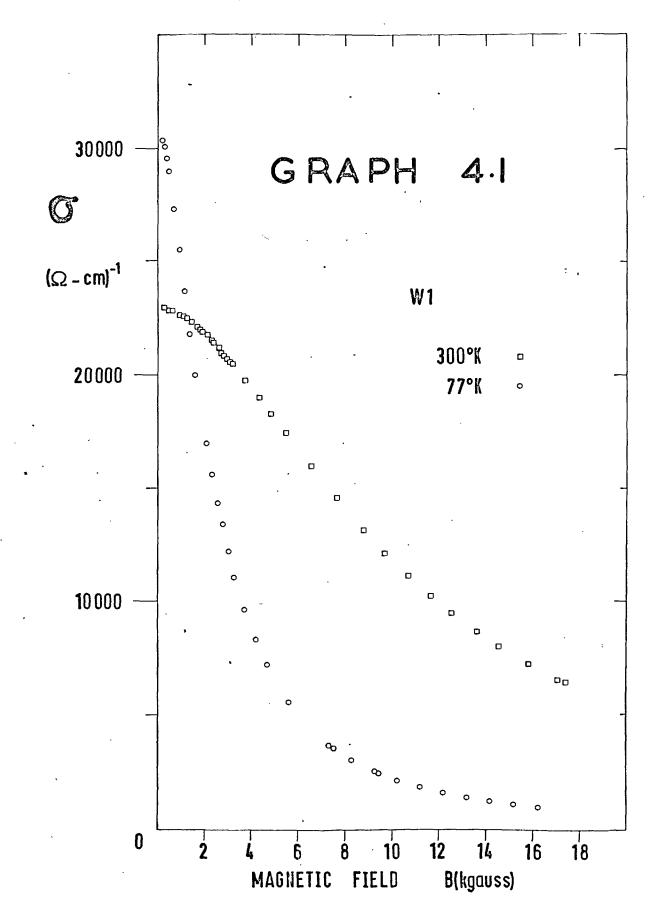
Calculated tensor components $\sigma_{xx}(H)$, $\sigma_{xy}(H)$ and the results of this fitting process are presented in chapter 5.

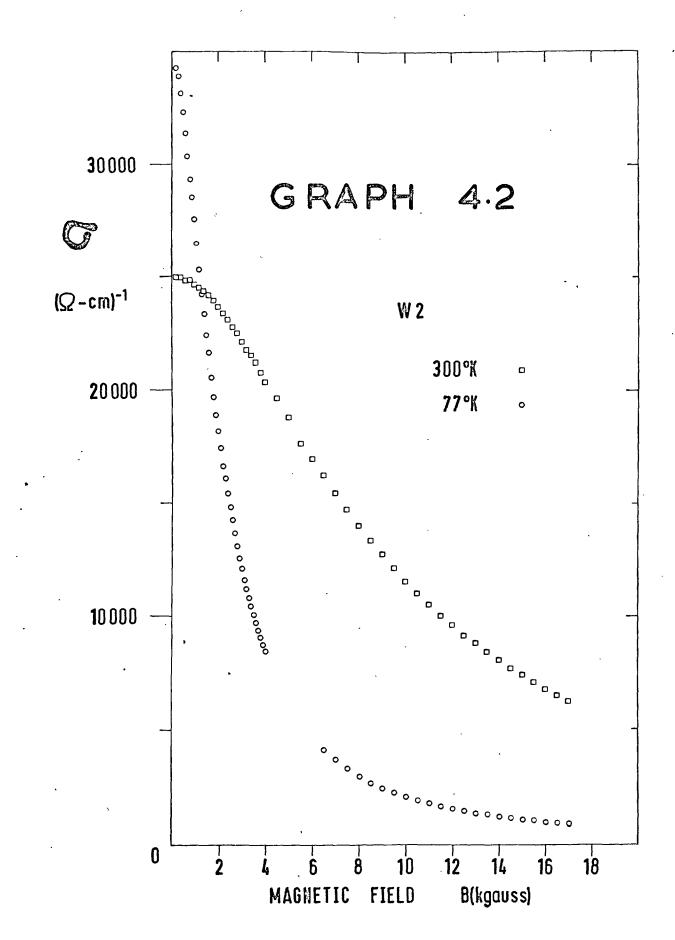
As indicated elsewhere, (Section 2.4.2) representation of the experimental data in the form

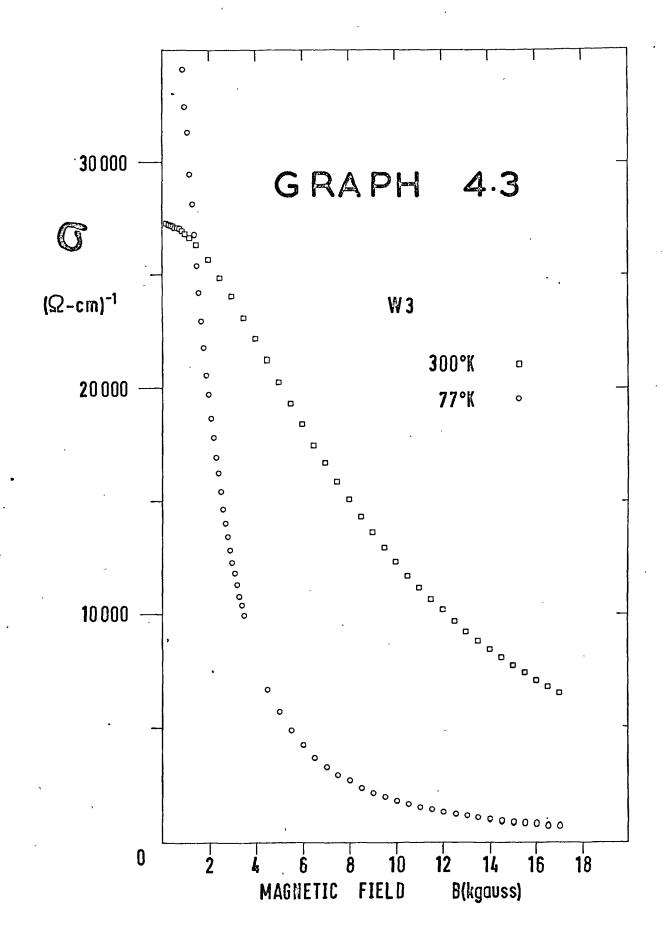
$$\sigma_{xx} = \sum_{i}^{A} \frac{A_{i}}{1 + (H/H_{i})^{2}}, \quad \sigma_{xy}/H = \sum_{i}^{A'} \frac{A'_{i}}{1 + (H/H'_{i})^{2}}$$

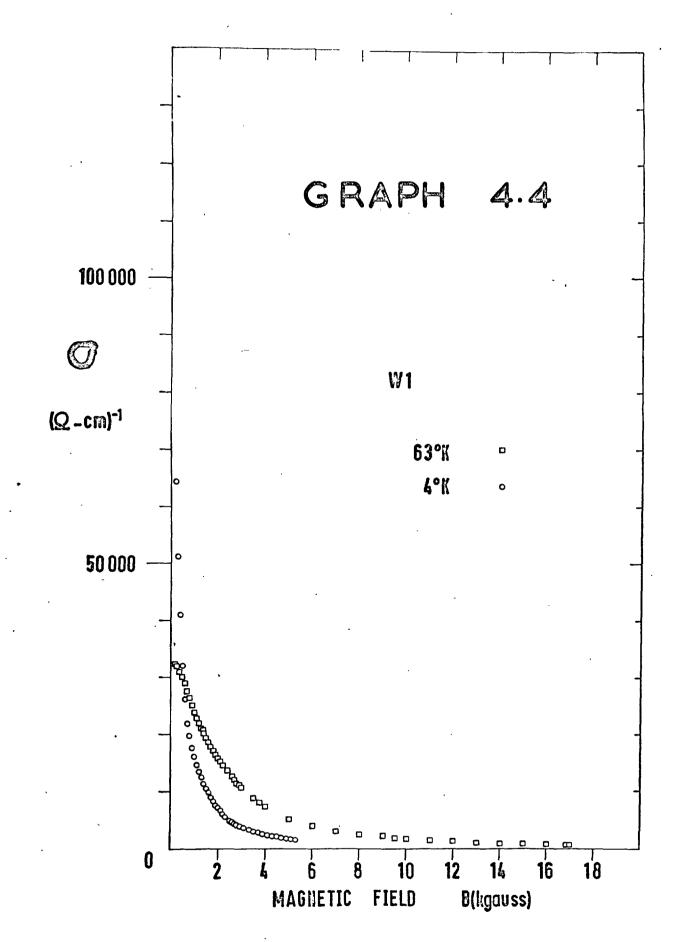
is necessary before the partial conductivities due to electrons and holes can be found. The present section deals with the methods employed to fit data to the expressions; we use $\sigma_{\rm XX}$ as an example, but all remarks apply equally to $\sigma_{\rm XY}/{\rm H}$.

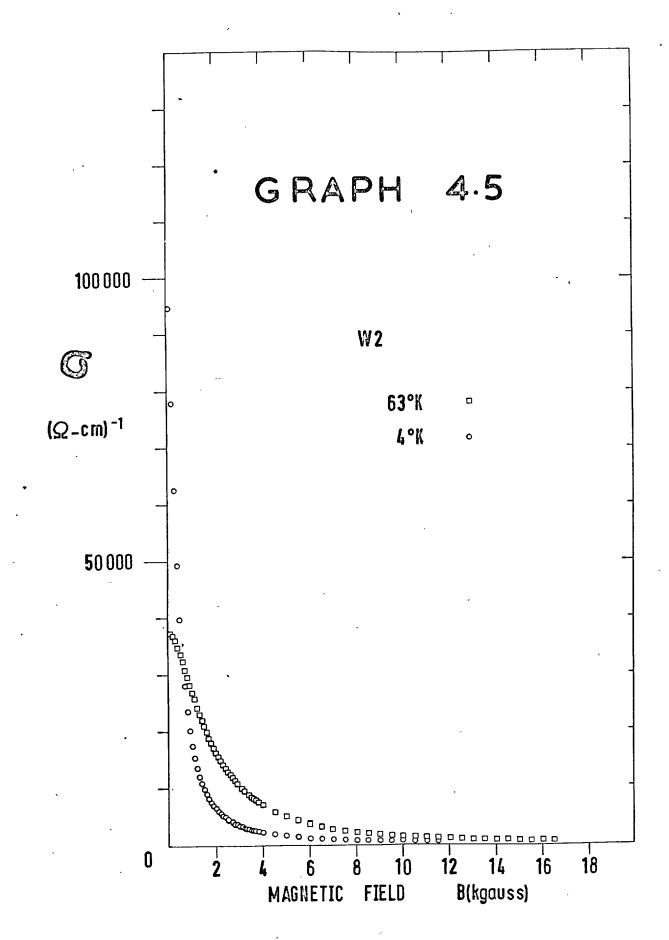
Were the data free from errors, it would be sufficient to take 2i (i=1, 2, 3 ...) data points and solve the resulting equations for the A_i , H_i . This is not the case in practice, where random errors are superimposed on data. The calculated values of $\sigma_{\chi\chi}(H)$ would not pass through all the experimental values unless the number of fitting parameters (2i) were equal to the number of data points, but our object is to represent the data to sufficient accuracy with as few terms as possible, preferably less than four, so some statistical criterion is necessary to decide upon the goodness of fit. We use the sum of the squares of residuals (the differences between experimental and calculated values) and employ the standard theory of linear least squares fitting where possible.

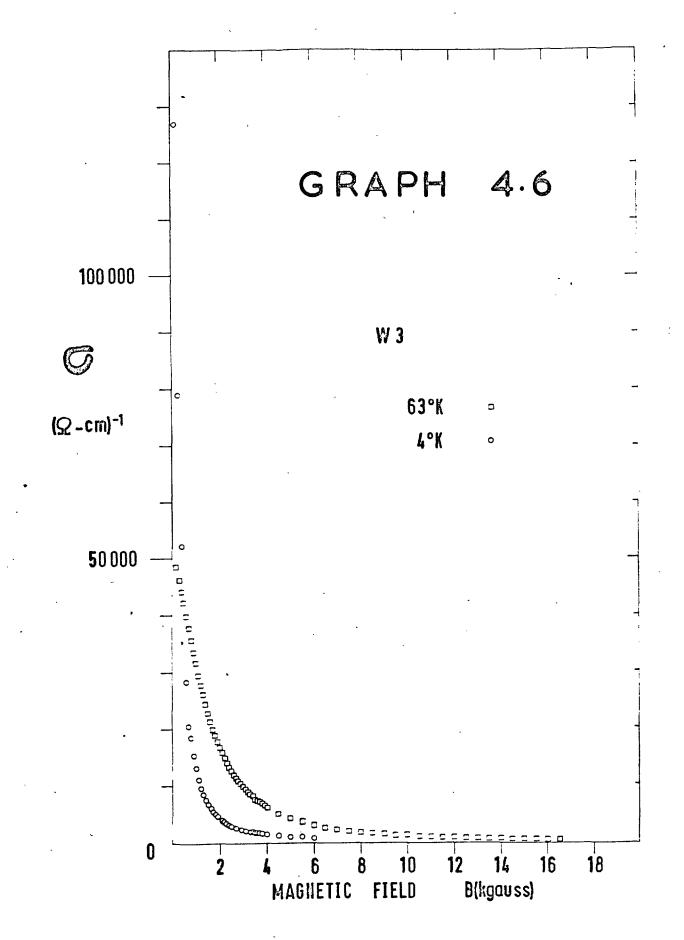


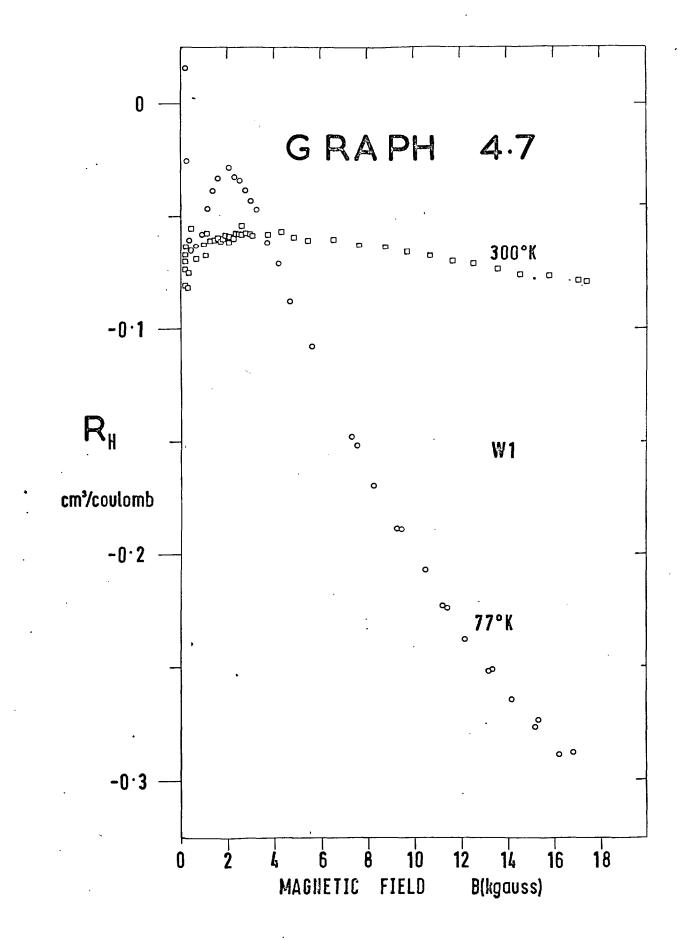


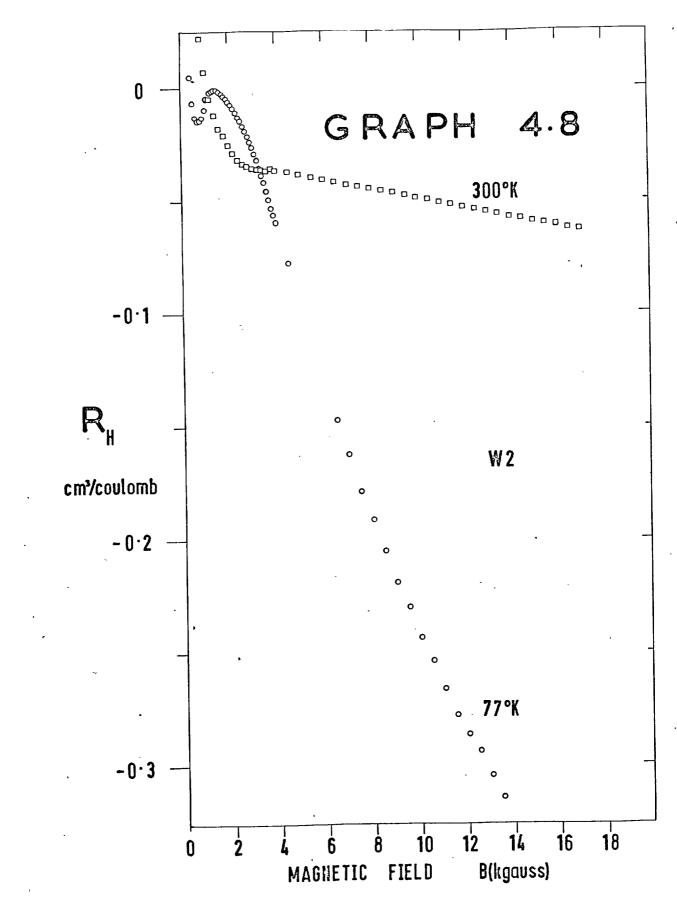




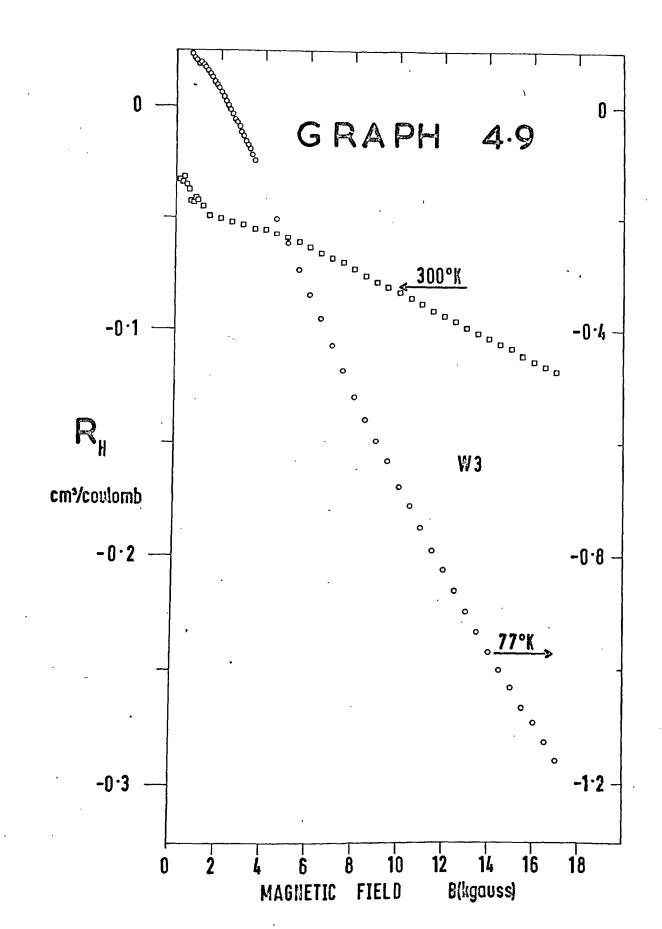


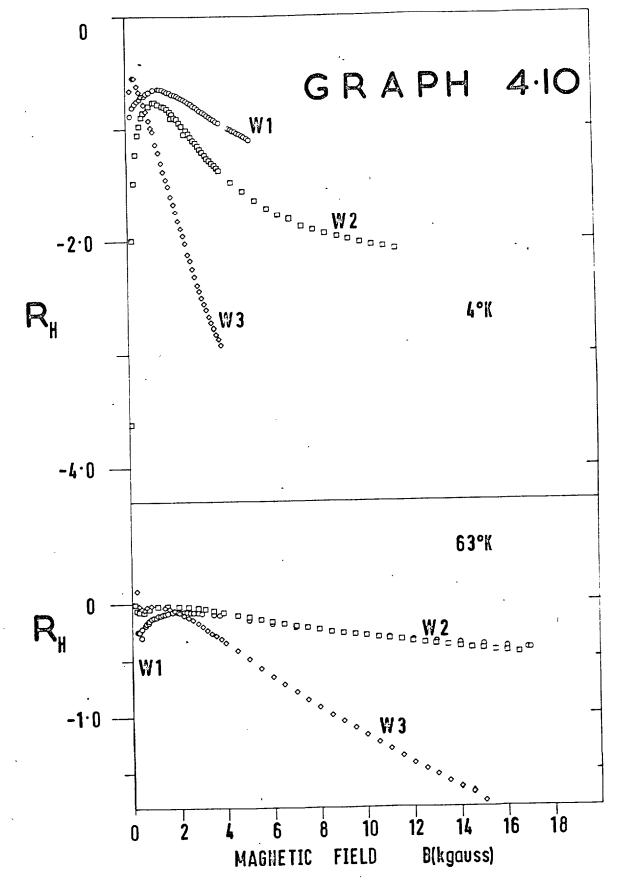




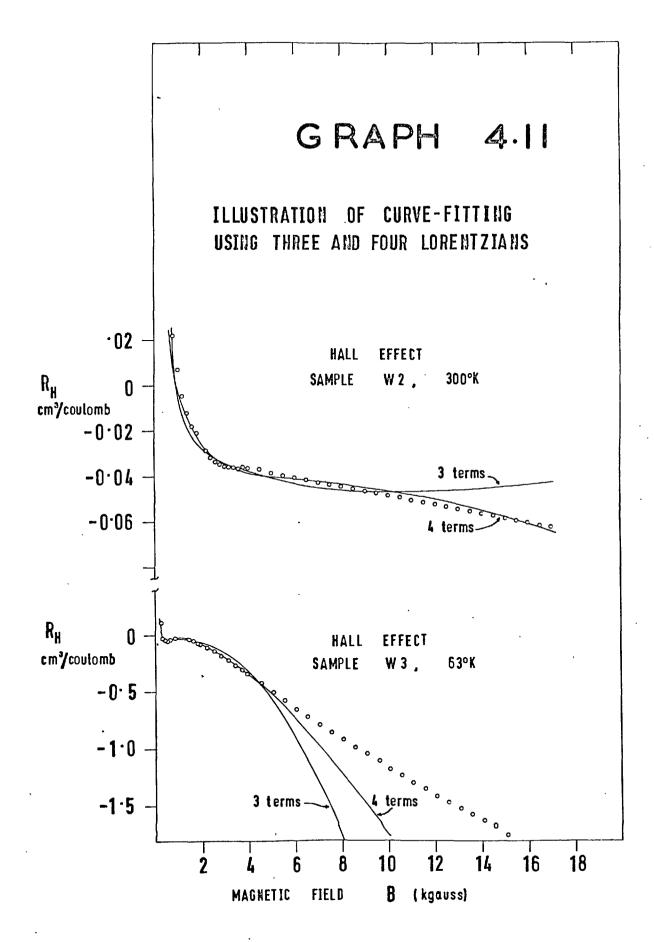


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The Method of Least Squares.

Suppose measured quantities y_1, y_2, \dots, y_n are related to the quantities x_{ij} by the equations $y_1 = x_{11} a_1 + x_{12} a_2 + \dots + x_m a_m$

$$y_n = x_{n1} a_1 + \cdots + x_{nm} a_m$$

or, using matrix notation, Y = XA where the a_j are the parameters which it is required to find. Since, in practice, n > m there are more equations (n) than unknowns (m), and we must determine a criterion for defining the 'best' set of parameters a_i . The best set of a_i is usually taken to be that which minimises the sum of the squares of the residuals. That is, we want the a_i which make

$$\sum_{i=1}^{n} (y_i - x_{ij}a_j)^2$$

a minimum.

Differentiating:

$$\frac{\partial}{\partial a_{K}} [(y_{1} - x_{1}a_{j})^{2} + (y_{z} - x_{2j}a_{j})^{2} + \cdots] = 0$$

ie $[y_1 - x_{ij}a_j] x_{1K} + [y_2 - x_{2j}a_j]x_{2K} + \cdots = 0$ for each $K(=1,2,\ldots,m)$

is
$$\sum_{i} [Y-XA]_{i} x_{iK} = 0$$
, $\sum_{i} \tilde{x}_{Ki} (Y-XA)_{i} = 0$ for each K

where \tilde{x} is transpose of X

if $[\tilde{x} (Y-XA)]_{K} = 0$

We want to find A :

$$(\tilde{X}Y)_{K} = (\tilde{X}XA)_{K}$$
 for each Kaite $\tilde{X}Y = \tilde{X}XA$

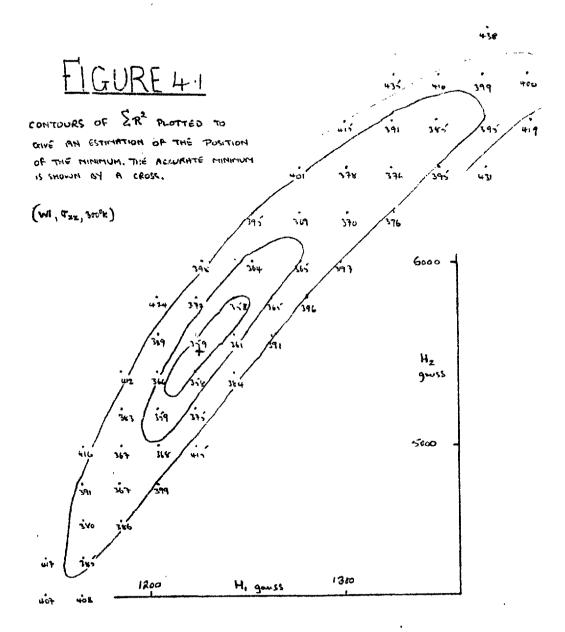
and so
$$A = \left(\frac{1}{\tilde{X}X}\right)\tilde{X}Y$$

Thus the procedure for finding the fitting parameters a_i is first to set up the matrices X, Y then calculate the products $B = \tilde{X}Y$, $C = \tilde{X}X$. The matrix C is then inverted and post-multiplied by B. Stated in this way, the problem is seen to be ideally suited for computer solution espcially if FORTRAN language is used since this is well adapted to the handling of matrices. The Imperial College IBM 7090 computer was used for all the data-fitting calculations - they would have been impossibly time-consuming without its use. It should be noted that the method depends upon the first set of equations (the 'observational equations') being linear in the parameters a_i . In the present case this is only true for the parameters A1 and not for the H_i so, unless the Lorentzian functions can be linearised by Taylor expansion for instance, one is only able to use the above matrix method to find the best set of A_i for a given set of H_i . The best set of H_i will have to be found by another method, but at least the number of parameters to be varied has been reduced by a factor of two.

Methods Employed in Fitting the Data.

Two-term fits.

First attempts employed the method indicated above, viz. a set of H_i was decided upon and the corresponding 'best' set of A_i calculated by the matrix formulation of the method of least squares. Two terms were tried at first as it was known that graphite has two majority carriers, and it was hoped that the minority carriers would merely represent a small correction term. Values of H1 and H2 were selected in turn so that all pairs of values within prescribed limits on H₁ and H₂ were tried. For each pair the corresponding values of A_1 , A_2 were calculated by least squares and the function (ΣR^2 termed the sum of the squares of residuals) evaluated. Finally the computer sorted the 30 sets of parameters giving the lowest values of ΣR^2 and printed them out for inspection. By plotting points representing these pairs of values of H_1 , H_2 and labelling each point with its ΣR^2 value, it was possible to draw 'contour' lines of constant ΣR^2 value. From such a diagram the next area in the $H_1 - H_2$ plane for exploration was selected. In favourable cases it was possible to select the area containing the lowest value of ΣR^2 at the first attempt, in which case the contours took the form of closed loops and the position of the minimum could be estimated. An example of such a diagram is shown in Figure 4.1.



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Unfortunately, the contours around the minimum were not simple circles or ellipses, but were shaped more like the longitudinal crosssection of a banana, so location of the minimum was not easy. A programme written to overcome this difficulty was based on a Taylor expansion of the Lorentzian expression about values of H_1 , H_2 which were considered to be close to the true values at the minimum. This essentially linearised the observational equations in all the parameters H1, H2, A1, A2 and enabled one calculation by the matrix method to find approximations to the best values of all parameters. Of course, the method depended upon discarding higher order terms in the expansion and so it was necessary to repeat the calculation several times, changing H1 H2 to the latest values before each colculation in order to arrive at the best set of values. Five or so repetitions were usually sufficient to produce unchanging values of the parameters, but the calculation was only stable provided the distance between the starting point and the actual minimum in the H_1-H_2 plane was less than about 20% of the values of H_1, H_2 . Stability also depended somewhat upon the direction in which the starting point lay from the minimum.

After two-term fits to the data of each sample at each measured temperature had been produced by the above methods it was decided to extend the fits to three terms.

Three-Term Fits.

With three terms to be fitted the problem became much more difficult. Although the linear parameters A_1 , A_2 , A_3 could still be found by the linear least squares method for a given set of H_1 , H_2 , H_3 , it was extremely difficult to find the best set of the latter parameters since this involved drawing contour diagrams in three dimensions - or at least superimposing two-dimensional plots. Even with closed-loop contours in the two-term problem it was not easy to decide where the minimum lay within the elongated contours, but with the contours of the three-term problem one could wander along the resulting narrow, curving tunnel without much indication as to the proximity of the minimum. It soon became evident that a new approach was needed and it was decided to try a gradient-following method:

A computer programme was written to find a minimum of the function ΣR^2 by, in effect, moving in H_i space in such a direction that ΣR^2 was always decreased. The principle is best illustrated by considering the two-term problem where one has to find two parameters H_1 , H_2 . (Perhaps it should be stressed that in all the methods described for fitting data to Lorentzians the only problem was in finding the best set of H_i . The A_i were always calculated by the matrix formulation of the method of least squares described above). By plotting ΣR^2 against the two parameters H_1 , H_2 in three dimensions one sees immediately that the problem is to find the lowest point of

the surface so defined. The computer programme was started at a point whose (H_1, H_2) co-ordinates were expected to be reasonably close to those of the minimum. It then proceeded to decide in which direction lay the steepest gradient down the surface by taking two side-steps parallel to the H1, H2 axes and noting the resulting changes in height: a simple calculation then gave the direction and values of the steepest down-gradient at this starting point. A step was then taken in this direction, this step being much longer than the two exploratory side "shuffles", and the whole process of shuffle-andstep was repeated until a particular step produced an increase in the 'height' of the surface (i.e. the value of ΣR^2) when it was deduced that a minimum had just been traversed. Going back to the s art of this last step, (Δ) the programme then proceeded to take a series of steps (each from the same position) and in the same direction as the step (Δ) , with the condition that each was half the length of the preceding step until one of them finally landed on the slope at a lower point than the commencement of step Δ . The usual process of shuffle-and-step was then resumed or the programme terminated itself according to criteria built into the programme concerning the accuracy with which the position of the minimum was desired. Of course, for a three-term fit the surface is plotted in four-dimensional space, but this makes little difference to the algebraic expressions for the gradient at any point - the programme could operate in either of these modes as required.

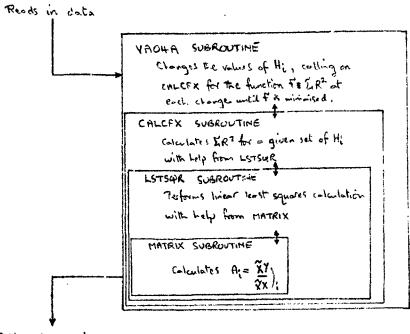
A further point embodied in the hill-descending programme was that an initial two-term fit was performed using only high-field data in the belief that the violent excursions of the data at low fields were caused by Lorentzians with low characteristic fields (H_{i}) and so would not unduly influence the main terms at high fields. The object in performing this two-term fit was to obtain a better estimate of the position of the minimum for three terms to save time on the three-term hill-descending. This was always desirable because the hill-descending programme was not very refined and tended to take a long time in reaching the minimum. especially if it were started on the side of a valley, when it would proceed to zig-zag across the valley. making only slow progress along the length. In summary, then, this method involved sorting the data into high and low-field then making a two-term hill-descent with the high-field data only and finally, after a rough scan with changing H_{χ} values, a three \cdot . term hill-descent down a new hill defined by all the data.

An extension to more terms soon became desirable, if only to check the effect of an extra term on the goodness of fit and, besides, the simple method of proceeding step by step downhill was timeconsuming. A more satisfactory way of reaching the minimum would be to try to predict its position from the local curvature and move each time to the predicted position. M.D. Powell has written several subroutines for minimising any function of several variables and one of these (VAOAA; see Computer Journal <u>7</u>, <u>303</u>, <u>1964</u>) was employed on a programme for fitting data to up to five Lorentzians. This proved to be extremely reliable and reasonably fast in operation though there is another subroutine (VAO2A) which might prove faster in this application since it is specially designed to minimise a function composed of the sum of the squares of quantities, however, VAOAA started working smoothly before VAO2A and it was felt that the fault-finding time necessary to make the latter work was not available. Programme to fit data to five or less Lorentzians.

We now describe in outline the fitting programme employing VACMA. A little knowledge of the FORTRAN computing language is assumed here but the essential points are that variables being manipulated must be given names of up to six letters (e.g. DATA, ESCALE, TEXT, etc.), that orders or 'statements' are obeyed sequentially in general; starting with the first and moving through to the last which is usually STOP, and that 'subroutines' are self-contained programmes which may be 'called' into operation by the main programme. Once a subroutine has been called, it performs its calculations until it reaches a statement within itself returning control to the main programme. The main programme, in effect, ties the separate subroutines together and may call a given subroutine as many times as necessary. Indeed one reason for writing a subroutine is to avoid having to write whole blocks of statements again and again.

The purpose of our main programme is to provide subroutine VA04A with a suitable set of input numbers and to accept the output from it. In addition, experimental data must be read in and the final set of fitting parameters printed out at the end. The essential input to VAO/A is the array X(I) of parameters which it has to vary in order to minimise the function ΣR^2 . Here $X(1) \equiv H_1, X(2) \equiv H_2, \cdots$ in previous notation. VAO4A returns execution to the main programme when it has found the minimum, in which case the array X will contain the set of best parameters H_1 , H_2 , and a variable, F, equal to the latest value of the function ΣR^2 . Now, VAO4A is a subroutine for minimising a general function so our function (which is Σ (Resid)²) must be explicitly stated. In fact, we must provide our own subroutine called CALCFX to calculate the function $F = \Sigma R^2$ each time it is required; the latest values of H1, H2, .. are fed in and the corresponding value of ΣR^2 must come out. So far no mention has been made of the linear parameters A_i. As in previous fitting programmes, these are found for each set of H_i 's by the matrix method described above. In fact CALCFX itself calls on a subroutine LSTSQR which takes the latest values of H1, H2, ... and sets up the matrices necessary to perform the least squares calculation. A final subroutine MATRIX is employed $\left(\frac{1}{\tilde{x}_{x}}\right)(\tilde{X}_{x})$ and so find the coefficients A_{i} . Once the to calculate best A_i are known for the given set of H_i, the function is calculated by LSTSQR and returned, via CALCFX, to VAO4A for examination. VAO4A

MAIN PRUGRAMME



Prints out coordinates of minimum.

FIGURE 4.2

BLOCK DIAGRAM OF CONPUTER PRODRAMME FOR AITTING DATA TO THE SUM OF UP TO FIVE LORENTZIANS.

calls for many (possibly over 300 on occasions) such calculations of ΣR^2 to be made with slightly different values of H_i before deciding on a change in one of the H_i . In operation, changes are made cyclically in the list H_1 , H_2 , ... and so on until a minimum is reached. It then only remains to print out the latest values of H_i , A_i and ΣR^2 , as shown in the block diagram below Figure 4.2. A photograph of the actual programme statements is included in Appendix 4.

Whilst very good fits were obtained for σ_{xx} by this method, it was found that better fits could be obtained for σ_{xy} /H by weighting the high-field data; the violent excursions in the data at low fields tended to make the sum of the squares of the residuals insensitive to the high field data points. More representative fits were obtained by making several copies of the high field data cards and including them with the data (the IBM 7090 accepts instructions and data coded on to punched cards).

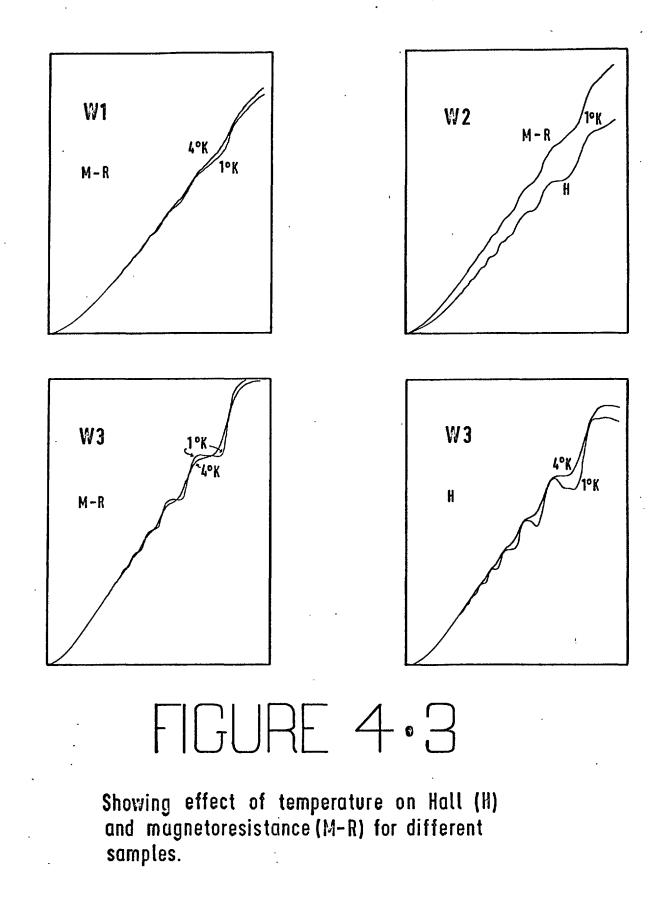
4.2 Oscillatory Data

At temperatures below about 5°K and for magnetic fields greater than a few kilogauss oscillations in the Hall effect and magnetoresistance (were observed) as the field was swept slowly upwards. These consequences of the quantisation of energy levels are reported here. We first describe how the oscillatory part of the data was separated from the monotonically varying background, since theories of these quantum effects do not include the background terms quantitatively at the present time.

4.2.1. Separation of Oscillatory Effects from the Background.

An example of the charts obtained at low temperatures is shown below. It can be seen that there is a strong background to the oscillations in the form of a fairly simple curve which might possibly be fitted to a polynomial expression. However, the difficulties attending such an attempt especially when beats were present made it attractive to use a simpler method of fitting the midline by eye: Tangents were drawn between the adjacent maximum excursions of the curve as shown, and points were constructed by taking mean Y-values from these straight-line segments. Finally a smooth curve was drawn to follow these points as closely cs possible.

Between 110 and 140 lines were then drawn on the chart parallel to the Y-axis at intervals of 1 mm. along the X (field)axis. The lengths of these lines between the chart trace and the midline were found by taking them off with dividers and pricking on to graph paper. In this way, a plot of the oscillatory function was built up as measurements were noted down. The fact that this plotted curve appeared to oscillate equally above and below the axis indicated that a satisfactory midline had been used. The figure (4.3) illustrates the necessity of associating a sign, + or -, with each measurement according as the trace lies above or below the



midline respective. By applying the chart calibration constants, found as described earlier (Section 4.1.1), it was possible to convert chart distances into magnetic-field values and sample (voltage/current). These pairs of values were then recorded on punched cards for later detailed analysis, described in Section 4.2.3. Most charts were not treated in such detail, but were merely examined for the field values at which the trace crossed the midline. Resulting "Nodal Plots" are presented below in Section 4.2.2.

Figure 4.3 shows tracings of the chart recordings obtained at helium temperatures. The horizontal axis for each trace represents a magnetic field change from zero to nearly 18kG and is the same to within 2% for all curves whilst the vertical axis is proportional to the sample voltage arising from the Hall effect (H) or magnetoresistance (M-R).

Superposition of the two M-R curves for sample W1 shows clearly how the oscillatory magnetoresistance changes with temperature. The oscillations deepen in the negative direction with a lowering of temperature, but the positive peaks and background are essentially unaltered. Sample W2 is used to illustrate the greater detail which is present in the Hall effect oscillations compared with magnetoresistance oscillations taken at the same temperature. It can be seen that the amplitude of the oscillatory part is a

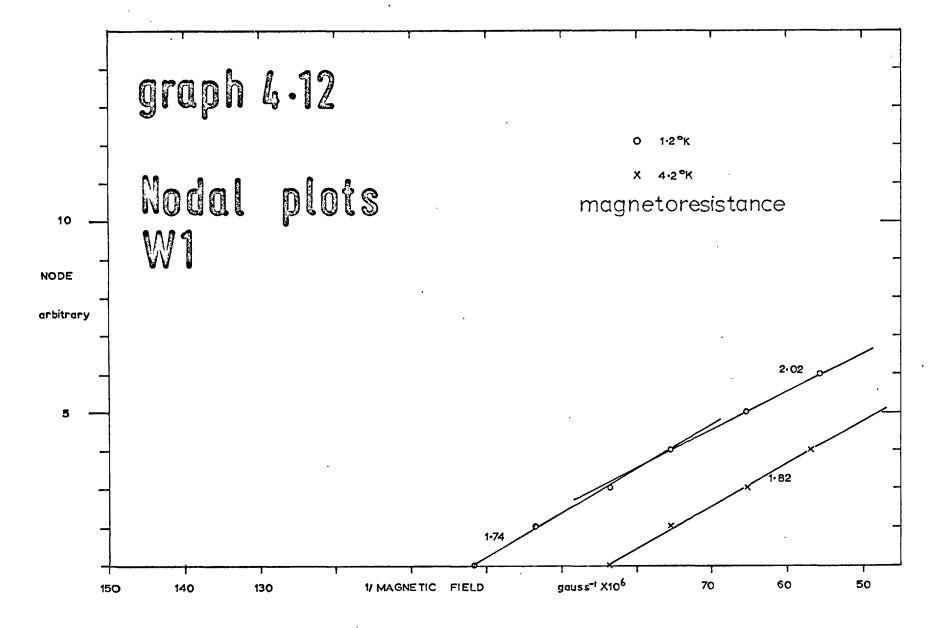
- 145 -

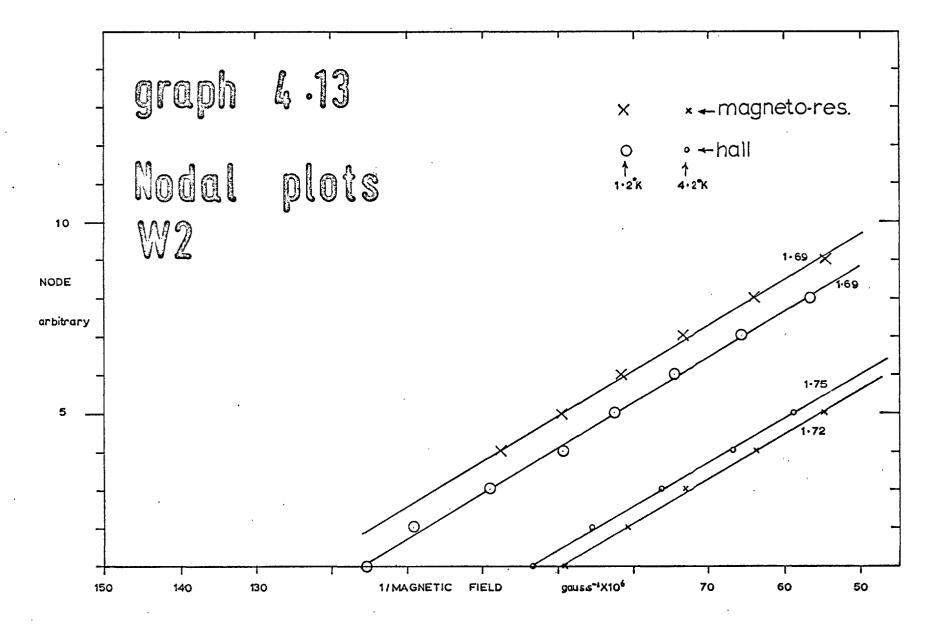
greater fraction of the background in the former case. This is not all, however, for the W3 curves bring out very clearly the increased structure visible in the Hall effect oscillations. The effect of a lowered temperature is much more dramatic in the case of this sample.

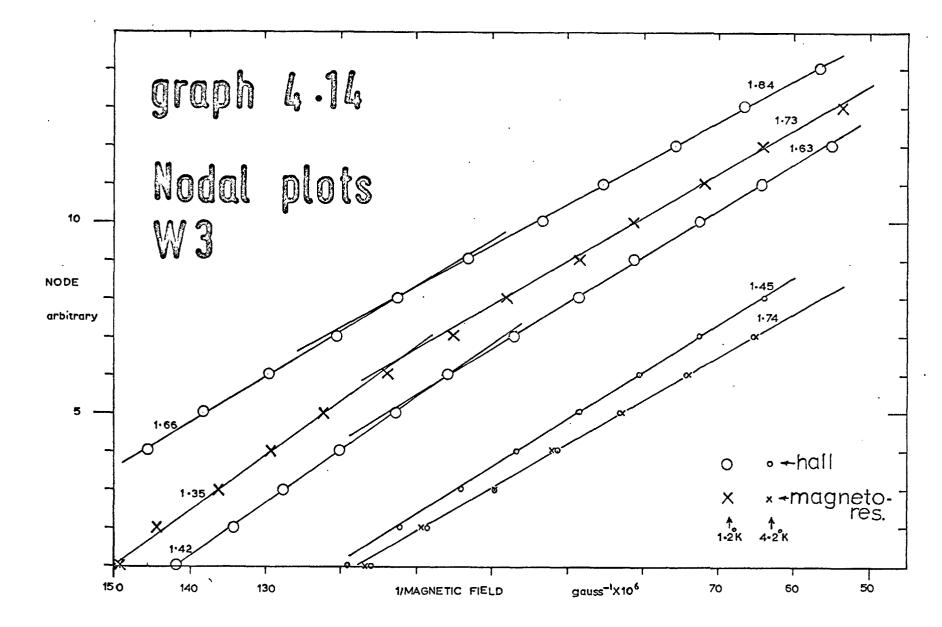
Data for three curves from which the background has been removed are included in appendix 3. One of these, the Hall effect at 1.2° K for sample W3, was intensively analysed in the manner reported in Section 4.2.3. The results of this analysis appear in Section 5.2.

4.2.2. Nodal Plots.

Suppose one attached integer labels to corresponding points of successive oscillations of a single-period function f(x). Then a plot of integer against x would yield a straight line whose slope gives the fraquency of f(x). Such a procedure is not valid in general for a function containing more than one periodic element. It is interesting, however, in the absence of sufficient data to make the periodogram technique of astronomy (Whittaker and Robinson, 1956, p.344) worthwhile. to plot the midline-crossing points ("nodes", labelled by integers) against reciprocal magnetic field. We do not at first sight expect much information from such Nodal Plots since the oscillatory effects in graphite have contributions from two majority carriers with distinct periods. However, the plots (shown for W1, W2, W3 in Graphs 4.12, 4.13, 4.14 respectively) turn out to be well represented by straight-line segments.







We attribute this to a rapid decline in the amplitude due to one carrier with decreasing magnetic field; at low fields only one carrier is contributing whereas at high fields both contribute. It should be pointed out that the slopes quoted on each curve (in units of 10^{-5} gauss⁻¹) could be in error by as much as $\pm 0.1 \times 10^{-5}$ gauss⁻¹ because it depends critically on the number of points chosen to be represented by the straight line.

At 1° K the mean behaviour of W3 is to move from a slope of 1.38 to 1.73 with increasing magnetic field. W2 has a constant slope of 1.69 whilst W1 moves from 1.74 to 2.02 x 10^{-5} gauss⁻¹. Since high fields must yield some sort of weighted mean of the separate periods one concludes that the more lightly damped carrier has an oscillation period around 1.4 x 10^{-5} gauss⁻¹ for W3 and this becomes mixed at higher fields with a period somewhat higher than 1.7 x 10^{-5} gauss⁻¹.

The single straight lines for W3 at 4.2° K most likely mean the observed behaviour is due to both carriers; the slope of two of these curves (1.74) bears this out but the third 4.2° K curve has a much lower slope. W2 yields single straight lines at both 4.2 and 1° K and moreover they have practically the same slope. This sample, like W1, showed no remarkable increase in structure when the temperature was lowered to 1° K.

4.2.3 Fitting Oscillatory Data to the Landau Expression

It was described earlier (Section 2.3) how we expect the oscillatory data to follow the generalized Landau expression:

$$\begin{array}{c} \begin{array}{c} -\mathrm{KU}\,\Delta\mathrm{T} \\ \mathrm{G} = \mathrm{H}^{\mathrm{n}}\,\Sigma \ \mathrm{W}(\mathrm{K}) & \underbrace{(\mathrm{KU})}_{\mathrm{K}} \mathrm{e} & \mathrm{T} \ \mathrm{cos} \ (\underbrace{2\mathrm{\Pi}\mathrm{K}}_{\mathrm{PH}} + \psi(\mathrm{k}))^{\mathrm{the other carriers}} \\ \mathrm{K} & \mathrm{sinh}(\mathrm{KU}) \end{array}$$
(harmonics)

where $U = \frac{2\Pi^2 KTm^*C}{he} = \frac{1}{H} = \frac{A}{H}$, say (A and U, P, η , n) can differ $\Delta T = W$

for the other carriers.

We attempted to fit our data to this expression by iteration. Powell's VAO4A subroutine was again employed to minimise a function defined as the sume of the squares of the differences between calculated and experimental values, but the main programme was complicated by provisions for choosing the number of carriers to be fitted and the number of harmonics of each to be included. In addition, it was decided to hold various parameters (PERIOD, POWER, A, DTET) constant when desired in order to have some control over the direction in which the minimum was approached and to prevent physically unrealistic swings during the initial stages. It should be borne in mind that for two carriers, with two terms each, a total of 16 parameters are being varied. This represents a major problem in data fitting and some control over the process was thought essential, even though it considerably complicated the computer programme. It is proposed to describe the fitting programme in outline, indicating the function of each subroutine in sufficient detail to enable an understanding to be gained of the FORTRAN listing (see photograph in appendix 4) if this is desired.

Once more, the main task was to supply subroutine VAO4A with a list X(I) of independent variables to be changed in order to obtain a minimum in the function defined in the subroutine CALCFX to be the sum of the squares of residuals. The MAIN programme first reads the number of carriers, and harmonics of each one it is desired to fit and a set of starting values for all the parameters: $P \equiv PERIOD$, $n \equiv POWER$, A, $\frac{AT}{T} \equiv DTET, W_{n,b} \equiv PSI$. In addition, a matrix NHOLD(I,J) must be filled with 1's or 0's depending on which of the parameters PERIOD, POWER, A, DTET it is desired to hold constant during this fitting attempt. For instance, if NHOLD(3,1)=1 and NHOLD(1,1),(2,1), (4.1) = 0 then A for carrier 1 will be held constant and PERIOD, POWER, DTET for carrier 1 will be allowed to vary. Similarly, NHOLD(1,2) where i = 1,2,3,4, defines which parameters for carrier 2 are to be allowed to vary.

This facility introduces complications in the programme in the form of two subroutines ADJINL and ADJUST, which are necessary to fill the matrix X(I) with only those parameters which are to be varied during the run. In effect, ADJINL is a shunting yard, filling the siding X with only those trucks marked "to be fitted", and with

NHOLD controlling the switching of points. Once ADJINL has filled X with the appropriate parameters (these always include W,PSI for all harmonics of each carrier) then VAO4A is called upon to take control.

VAO4A periodically calls upon CALCFX to supply it with the value of the function Σ (Residuals)², giving CALCFX the latest values of the fitting parameters in X(I). Before CALCFX can do this. however, it must change the values of PERIOD, POWER, A, etc. to the latest values in X, leaving unchanged the values of parameters not contained in X. To do this, CALCFX calls upon ADJUST which employs the array NHOLD as a translation key in unravelling X(I) and presents the latest values of all parameters to CALCFX. CALCFX next calls upon CALC to evaluate the value of the Landau expression G. given these parameters and the data points one at a time. As each value of G comes back from CALC. CALCFX subtracts from it the corresponding experimental value, squares this difference, and adds it to the current value of ΣR^2 . When all data points have been used CALCEX returns the final value of ΣR^2 to VA04A. This process is repeated each time VAO4A calls for a new value of ΣR^2 , which might happen several hundred times before it decides upon a new approximation to the best set of parameters (one 'iteration'). We see then, that ADJINL is called upon once only to perform the initial filling of X(I), while ADJUST is required each time VAO4A calls upon CALCFX.

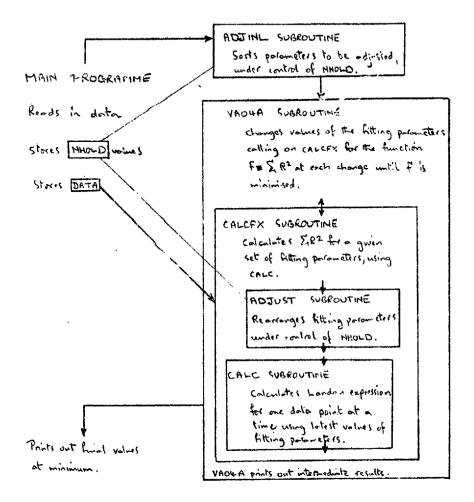
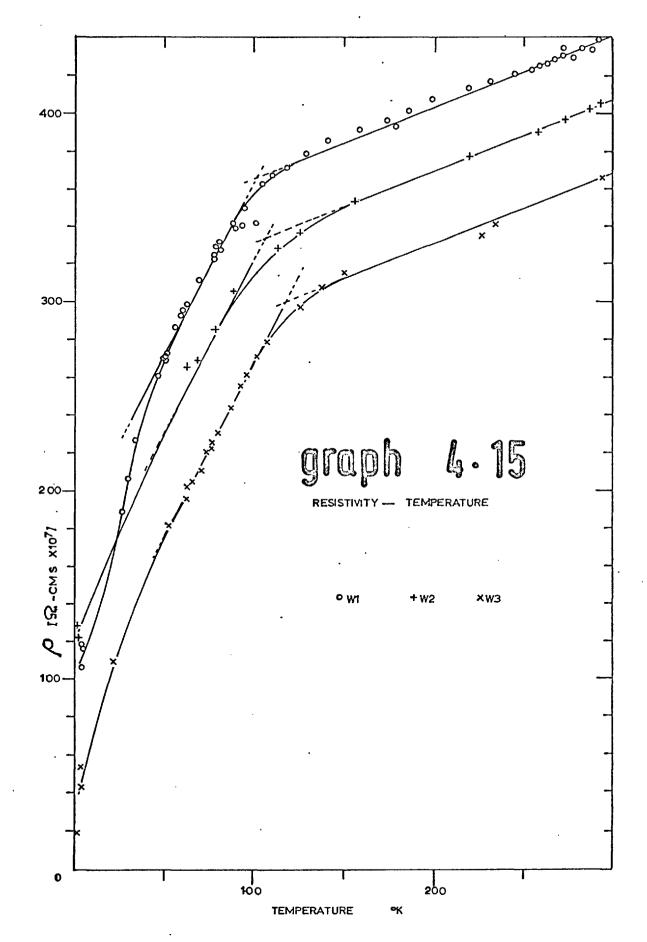


FIGURE 4.4

BLOCK DIAGRAM OF COMPUTER PROGRAMME FOR FITTING DATA TO THE GENERALISED LANDAU EXPRESSION. ("FRIER") Usually the programme was terminated automatically, having exceeded the five or ten minutes running time it was allowed. The print out from VAO4A was then examined to assess progress made in reducing ΣR^2 and the latest values were punched on to cards for the programme to be restarted, possibly with changes made in NHOLD (i,j). On occasions, however, probably under fairly restrictive conditions of NHOLD, VAO4A found a minimum in ΣR^2 and returned control to the main programme, which then printed out the complete list of parameters in easily readable form under appropriate headings. The fitting process was finally completed when this form of termination of the programme occurred under the conditions NHOLD(i,j)=0 for all i,j. A block diagram is shown below in Figure 4.4.

4.3 Resistance Variation with Temperature.

We briefly present here the variation of resistivity with temperature for the three samples W1,W2,W3. Graph 4.15 \cdot shows that the curves run parallel to each other at temperatures above 80° K and indeed would coincide if each were normalized by its room temperature value. The much greater resistance ratio $\rho_{295}/\rho_{4.2}$ for W3 should be noted; it is some four or five times the ratios for W2 and W1. This indicates a greater perfection in texture for sample W3 and probably explains the much greater amplitude of oscillatory effects observed with this material.



APPENDIX 3A

C- AKIS RESISTIVITY

For the sake of completeness we present here some results and comments on c-axis conduction, that is, with current normab to the basal planes.

The technique of sample preparation was described in chapter 3, p90. GraphA3 shows the temperature-resistivity plot for one sample of hot-pressed annealed pyrolytic graphite (HJCT $\frac{61}{2}/A(62)$) the dimensions of which were 0.065 x0.749 x 0.378 cms. Absolute values could be in error by as much as 10% because of (a) the error in the thickness measurement $\pm 4\%$, (b) possible correction of 5% or so from the effect of non-uniform current flow near the electrodes (mentioned on p90).

We have made use of c-axis results in the Discussion, pl65, and shall now briefly present a few comments on this subject.

Spain et al (1967) found that ρ_c was insensitive to sample perfection (as judged, for instance, by basal plane resistivity) and concluded that the behaviour shown for a range of their hot-pressed and annealed material mut be close to that of ideal graphite. Graph A3 agrees closely with their results for such material.

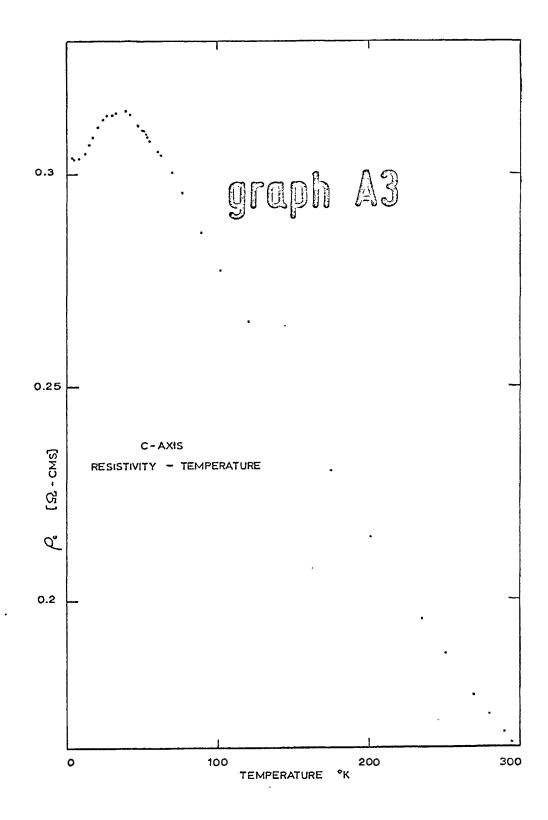
It has been conclusively at gued that shorting of the c-axis resistivity by misaligned basal planes does not contribute significantly to measured c-axis effects. The two main arguments are based on (a) based plane and c-axis redistivity have opposite temperature coefficients above 60° k; compare graphs A3 and 4.15, and (b) deutron irradiation increases based plane but decreases c-axis resistivity.

As the temperature is decreased from 300°E the c-axis resistivity rises because of the decrease in carrier concentration; it is thought that the mean free path in this region is limited to a few interlayer spacings. A constant mean free path at high temperatures is consistent with a conductivity pressure coefficient (Yeoman and Young, 1969) which closely follows the known (Anderson et al, 1967) carrier concentration pressure coefficient.

Below 50 - 60° K the scattering is dominated by the LA c-axis phonons which have the low Debye temperature of 185° K and couple strongly to charge carriers because of the sensitivity of band parameters such as χ_2 to interlayer spacing.

At the lowest temperatures we find β_c becomes constant with the mobility presumably dominated by some form of static obstacle scattering. We have seen some evidence for a minimum in the resistivity curve at around 4.5° K but the region appears to be structure-dependent and changes on thermal cycling.

The description of c-axis conduction in terms of a band model is not yet satisfactory, particularly at higher temp-



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CHAPTER 5

DERIVED RESULTS

We now present the tensor components σ_{xx} and σ_{xy} derived as described in Section 4.1.3. This is followed by a derivation of hole and electron mobilities and densities. Section 5.2 is devoted to the Landau expression for Hall effect oscillations in W3 and its interpretation.

5.1 Non-Oscillatory.

5.1.1 Derived Conductivity Tensor Components.

It has been described elsewhere (Section 4.1.3) how the Hall coefficient and conductivity curves were fitted to the sum of up to four Lorentzians in the form

$$\sigma_{xx} = \Sigma \frac{A_{i}}{\mathfrak{l} \diamond \left(\frac{H}{H_{i}}\right)^{2}}$$

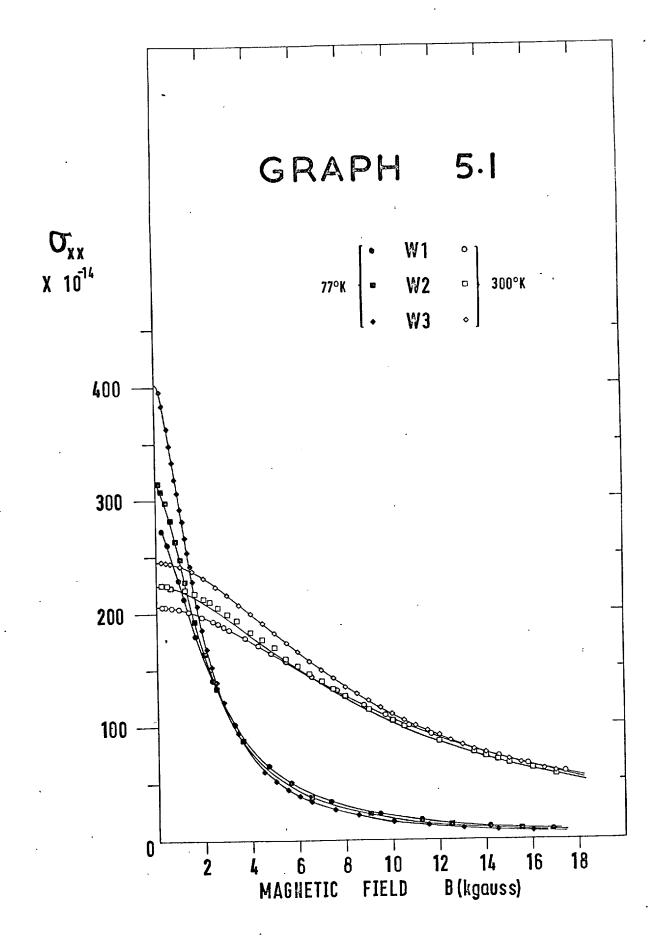
where A_i and H_i are the fitting parameters. Sections 2.4 show how this representation of the data can be used to separate out the effects of electrons and holes and derive partial conductivities for these two types of carrier. These, in turn, lead to values for electron and hole densities and mobilities. We present here the results of such an analysis, performed by a computer programme which accepted the fitting parameters for σ_{xx} and $\sigma_{xy/H}$ and then derived densitities and mobilities for each type of carrier. In addition, tables of conductivity σ and Hall coefficient R with corresponding magnetic field values were printed out for comparison with experimental curves, and total and partial conductivity tensor components

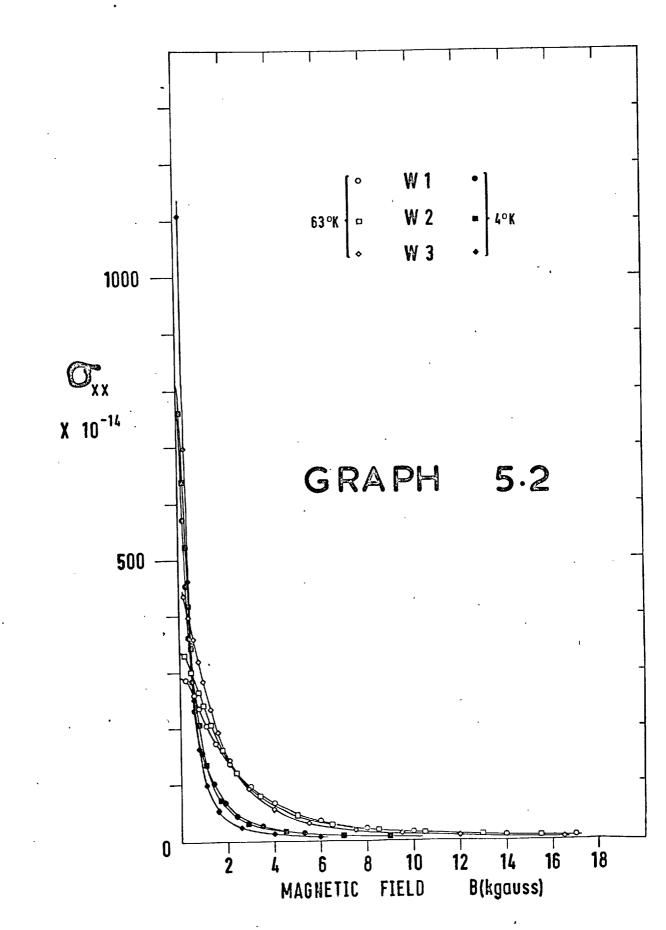
$$\sigma_{xx}$$
, σ_{xx}^{P} , σ_{xx}^{n} , σ_{xy} , σ_{xy}^{P} , σ_{xy}^{n}

were tabulated against magnetic field. Appendix 3 contains these results for the four standard temperatures for W1,W2,W3. Table 5.1 of Section 5.1.3. lists the carrier mobilities and densities.

Referring to Graphs 5.1 and 5.2, we see that the σ_{xx} curves have the appearance of being single Lorentzians. However, any attempt to fit them to a single term yields disappointing results. The appearance is due to the simple fact that a sum of Lorentzians has the same form as a single Lorentzian at both high and low values of the argument (magnetic field). The constants of these equivalent single terms are different at the two extremes, however. In practice, it was found that up to four terms were required to achieve a satisfactory fit. In all graphs presented in this section the data points are discrete symbols whilst the solid curve is the final result of the fitting process; it has been regenerated from the fitting parameters (up to eight in number) which best describe that data.

The σ_{xx} component presents little trouble, as the agreement between data and fitted curves in Graphs 5.1, 5.2 shows. The graphs are all arranged to facilitate comparison between samples.





Fitting σ_{xy} data proved more difficult as Graphs 5.3 to 5.6 demonstrate. Nevertheless, reasonable fits were achieved with the exception of curves having violent oscillations at low field. At 77°K there is a striking contrast between the excellent fit for W3 which shows no anomalous low field behaviour and those for W2 and W1. Both of the latter execute marked oscillations below 5kG. and we see that the fitted curves tend to smooth out such extremes. It is evident that more forceful application of the art of weighting the data points could have improved the fit in situations like this.

Except at 4° K all σ_{xy} curves move towards positive values at very low fields and in some cases actually cross the zero line. This behaviour is not visible at 4° K presumably because it has moved to much lo^{.,}er fields.

5.1.2 Average mobility and numbers, following Soule.

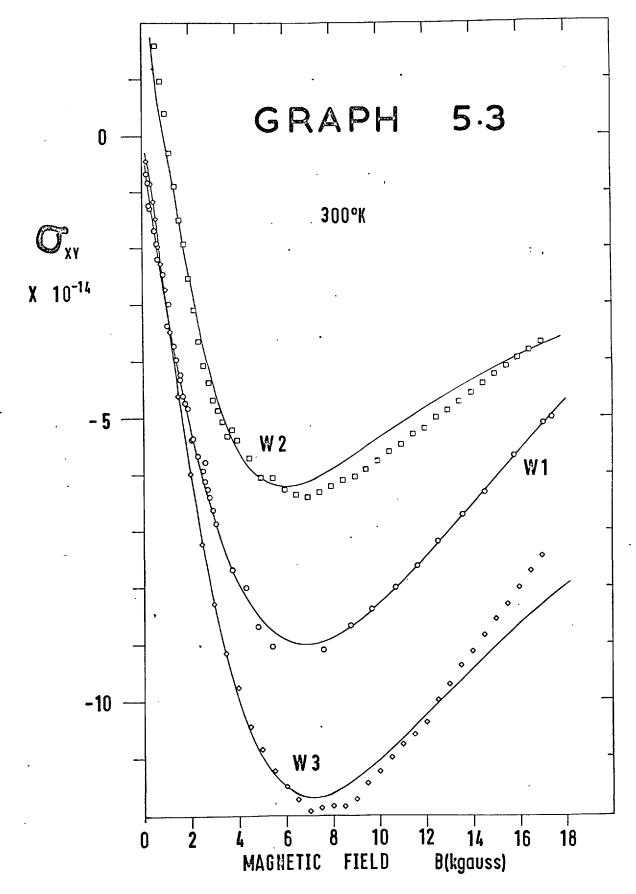
For later comparison, we present here the result of applying a two-band model to conductivity and Hall data, as employed by Soule (1958) in his analysis of single crystal data.

Using the expression $\rho = \sigma_{xx}^2 / (\sigma_{xx}^2 + \sigma_{xy}^2)$ and the representation of the tensor components below (c.f. Section 2.2.1).

$$\sigma_{xx} = \sum_{\text{carriers}} \sigma_{i} / (1 + H^2 / H_{si}^2) \qquad \sigma_{xy} = \sum_{\text{carriers}} (n_i e_i CH / H_{si}^2) / (1 + H^2 / H_{si}^2)$$

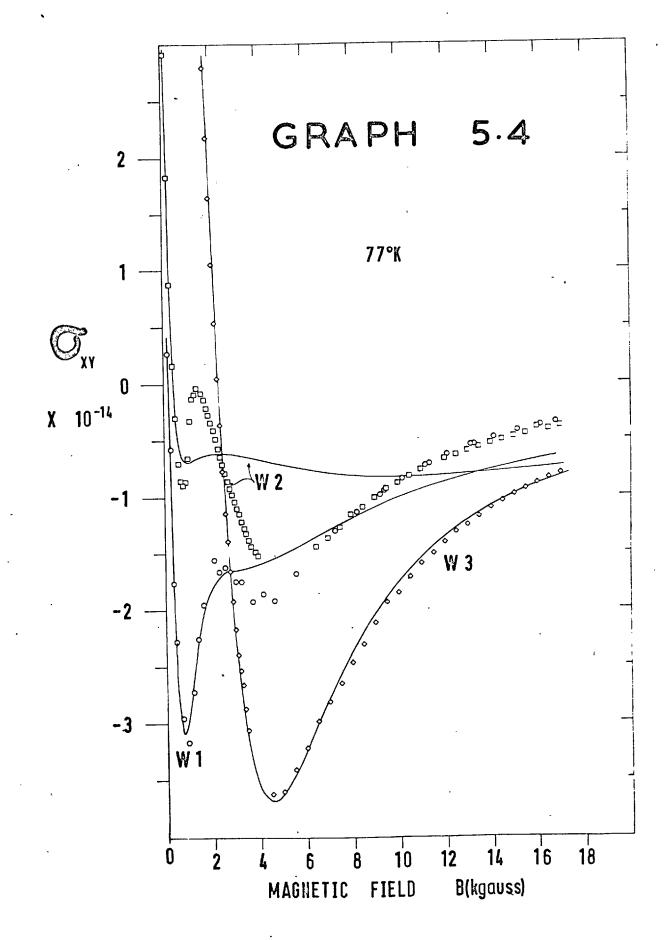
Soule derived an expression for the magnetoresistance

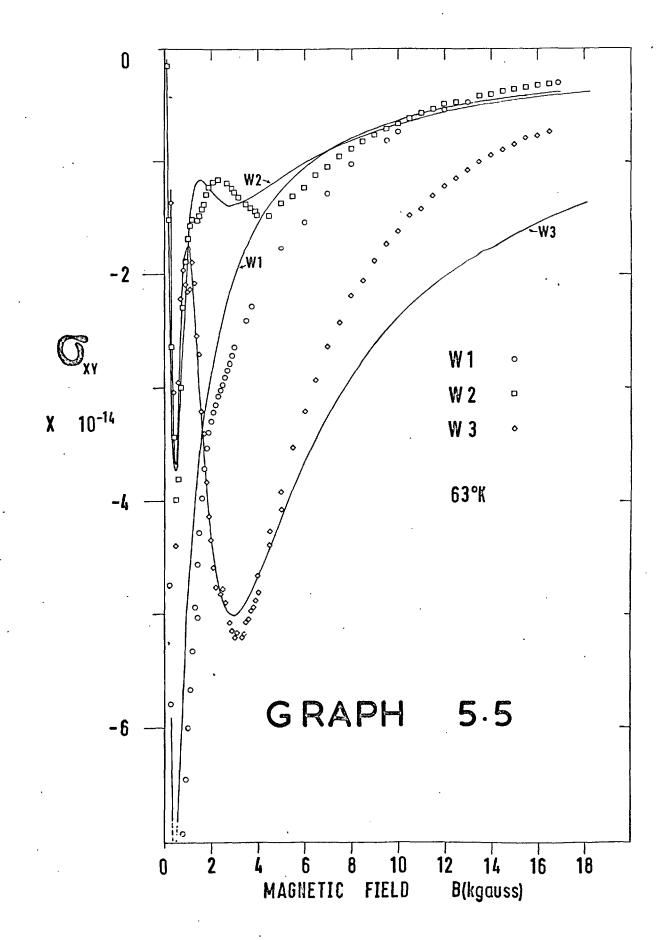
$$\Delta \rho / \rho_{O} \equiv (\rho(H) - \rho(O)) / \rho(O).$$

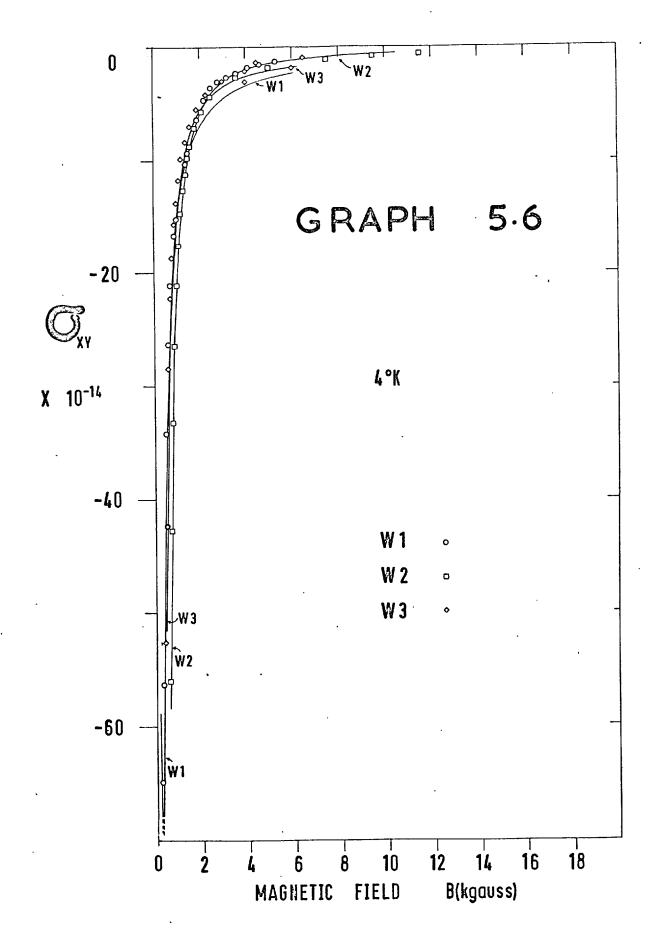


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Using $\sigma_{oi} = n_i e_i \mu_i$ and $H_{si} \equiv \frac{Cm_i^*}{e_{\tau_i}} \equiv \frac{C}{\mu_i^*}$ where μ_i^* is an average mobility (assumed equal to the conductivity mobility) an expression for the low field magnetoresistance is obtained:

$$\frac{\Delta \rho}{\rho_{\rm A} H^2} = \frac{ab}{c^2} \left[\frac{1+b}{a+b}\right]^2 \mu_h^2$$

where

$$a = \frac{n_{h}}{n_{e}}, \text{ the ratio of carrier densities}$$
$$b = \frac{\mu_{e}}{\mu_{h}} \text{ the ratio of carrier mobilities.}$$

This reduces further to $\frac{\Delta \rho}{\rho_c H^2} \simeq \frac{b}{c^2} \mu_h^2 = \frac{1}{c^2} \mu_e \mu_h = \frac{1}{c^2} (\overline{\mu})^2$ if a $\simeq 1$, which is a good approximation at the higher temperatures.

Graph 5.8 was calculated from conductivities at zero field and at 3kgauss, using

$$\frac{\Delta\rho}{\rho_{o}} = \left(\frac{-\Delta\sigma}{\sigma_{o}}\right) / \left(1 + \frac{\Delta\sigma}{\sigma_{o}}\right) \quad \text{and} \quad \bar{\mu} = \left(\frac{\Delta\rho}{\rho_{o}H^{2}}\right)^{\frac{1}{2}} \times 10^{8} \quad (\text{cm}^{2}\text{vollsec}^{-1})$$

Magnetic field values have been corrected by -4% because of a late discovery of a calibration error relating to our Norma fluxmeter. Tables of results in the appendices and graphs do not embody this correction, but it has been applied to all final derived values, in particular Table 5.1 and graphs arising from this.

Included in Graph 5.8 is the slope of Soule's EP-14 (-1.2) for comparison with samples W1,W2,W3 which give slopes of -0.94, -0.98, -1.09 respectively.

A rough determination of the total carrier density, $n_e + n_h$ can be made from the above mean mobility and zero field resistivity, for $n_e + n_h = 1/e\rho_o \mu$ (e = 1.602 x 10⁻¹⁹ coulombs, ρ_o is in ohm-cm). Graph 5.9 presents the result of this calculation and shows that W1,W2 yield practically coincident straight lines against temperature down to about 60° K whilst W3 has a slightly higher concentration. The analysis breaks down at lower temperatures as boundary and impurity scattering take over.

5.1.3. Carrier densities and mobilities.

This section contains the final stage of the magnetoconductivity tensor analysis. Expressions were derived in Section 2.4.2 for carrier mobilities and densities in terms of the parameters used to fit $\sigma_{,x}$, σ_{xy} data to Lorentzians as detailed in Section 4.1.3. A computer programme was written to perform the summations of equations 2.4.2 (11 to 15) and print out tables of mobilities and densities which are here presented as Table 5.1.

The -4.0% magnetic field correction mentioned earlier (5.1.2) has been applied and thus is embodied in graphs based on the table.

Table 5.1 is in three sections corresponding to the three samples W1, W2, W3. The six columns are as follows: Column 1; the sample temperature in degrees Kelvin. Column 2 is a code giving the conditions under which the data were fitted to Lorentzians; W means the points were weighted in an effort to improve the fit, U means the data were

	WEIGHTED					
N TERMS	UNWEIGHT	TED =NU				
			MOBILITY +10-4		NUMBER*10=18	
YEMP.			HOLES	ELECTRONS	HULES	ELECTRONS
295.0	3U _		0.90155	0.96987	7,25807	7.98818
295.0	3W -		0,04517	-0,03137	192,95218	-177.70593
295.0	411	,	0.03165	-0,00952	350,96486	
295.0	411		0,03424	HU.01293	•	-292,21623
88.0	30		1.70446	1.79080	m102.10783	107.31364
88.0	31		3.83725	3.83675	0.0000	0.00000
88.0	411	•	-4 ,55935	- 4,95373	.111.20354	-106.01037
88.0	414		2,35049	2,35179	0.00000	0.0000
77.0	30	•	3,93215	3.97473	2,40397	2.43490
77.0	3₩		3.95352	3.95363	2.37906	2.45981
77.0	40		3,96799	3.93794	2.38893	2.47668
77.0 -	4 W	•	3.95869	3.94687	2.39633	2.46928
63.0	3 U	•	3,06967	3,27026	3,21047	3.28602
63.0	3W -		0.00000	0.00000	3,21275	3.28375
63.0	4 U	•	2,60988	2.77278	3.70786	3.74830
63.0	4 W		2,73068	2.65263	3.73994	3.71622
15.0	311		0.00000	0,00000	6.25579	1.75090
15.0	3 W		0,00000	0,00000	3,24809	0.75859
15.0	40		0.00000	v.00000	#2.40828	5.77645
15.0	4 W		0.00000	ú,00000	0.00000	0.0000
4,5	30		17.91965	22:47239	1.26742	1.34091
4,5	314		17,82430	22,53929	1,26095	1.34738
4.5	4 U		13,80276	31.35004	1.82466	0.76742
4.5	4 W		17,59695	21.07825	î.54899	1.04308

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DENSTIES AND AVERAGE MODILITIES.

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SAMPLE W1

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	WEIGHTE	NW	SAMPLE WZ			
	UNWEIGH'					
			MOBILITY+10-4		NUMBER+10-18	
TEMP.		HOLES	ELECTRONS	HOLES	ELECTRONS	
291.0	30	1,04452	1,09858	7,31810	7.20997	
291.0	3W .	1.08430	1,05922	7.02708	7.50099	
291.0	411	1,08283	1,06750	7.01050	7.46108	
291.0	4 W	1,08345	1,06694	0.99806	7.47353	
77.0	30	13.93430	-4,96730	2.42180	2.40048	
77.0	34	10.73934	-1.70812	2.41489	2.40739	
77.0	4U	. 0,00000	0.00000	4.52909	4.73069	
77.0	4 W	0.0000	0.00000	4,57375	4.68603	
63.0	31	5,86269	5.01280	1.90685	2.36665	
63.0	31/	5.44456	5.37105	2,09830	2.21378	
63.0	4 U	5.32927	5.38337	2.15498	2.19944	
63.0	4 W	9.90581	10.76914	29.35896	-25.00299	
47.5	30	6.34459	7.55588	1.92618	1.90479	
47.5	3W -	=28,01369	42.31794	1.87227	1.89416	
47.5	40	-1.04187	6.91015	0.62482	6.73242	
47.5	411	-39,05044	51.84171	1 89584	1.96297	
4,5	30	0.00000	0.00000	1.44075	1.51068	
4,5	314	0.00000	0.00000	1.44077	1.51067	
4,5	40	0,00000	0.00000	45518	1.49188	
4.5	411	0.00000	0.00000	1.46379	1.48326	
1.0	30	0.00000	0.00000	0.00000	0.00000	
1.0	3 W	0.00000	0.00000	U.00000	0.00000	
1.0	40	0.00000	0.00000	9.00000	0.00000	
1.0	4W	0.00000	0.00000	0.00000	0.00000	
				· · · · · · · · · · · · · · · · · · ·		

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DENSTIES AND AVERAGE MOBILITIES. SAMPLE W2

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DENSTIES AND AVERAGE MOBILITIES. N TERMS WEIGHTED =NW N TERMS UNWEIGHTED =NU

MOBILITY*10-4 NUMBER+10-18 TEMP. HOLES ELECTRONS HULES ELECTRONS 293.0 311 7.13264 1,12930 8.20793 1.08731 . 293.0 3W 7.15618 1.08513 1.13132 8.18439 293.0 4U 1.08723 1.13087 7.12834 8,19381 293.0 4W 0.04793 -0.03267 217.32399 -202.00241 77.5 311 6.08992 5:05112 2.41405 2.62113 77.5 3 W 5.04892 2.41280 2.62238 6.09286 77.5 40 5.77998 2.55420 2.62477 5.03741 63.2 30 11,02604 4.58333 2,00546 2.33811 63.2 11.20319 3₩ 4.36984 2.02652 2.31705 63.2 4U 0.00000 0.00000 4.07277 4.23760 63.2 441 0.00000 0.00000 4.07509 4.23528 54.0 30 9.19685 9.29372 1.87581 2.02360 54.0 311 1.88386 2.01556 9.13873 9.34843 54.0 40 9.49395 9.57668 1.78968 1.98912 54.0 411 9.55334 9.51499 1.78788 1,99092 4.2 30 88.44487 1.71281 1.75974 1.06628 4.2 3W 88,48973 1.71376 1.75879 1.06830 4.2 2.30271 4U 26.35945 40.78255 2.50907 4.2 44 -26.52297 39.82773 2.37465 2.43712 1.5 30 23.69151 5.43289 2.71874 2.78293 1.5 3W 5.37372 2.70936 2.79230 23.81568 1.5 40 #65,15516 74.81471 0.00000 0.00000 1.5 4W 4.76858 4.89097 0.00000 0.00000

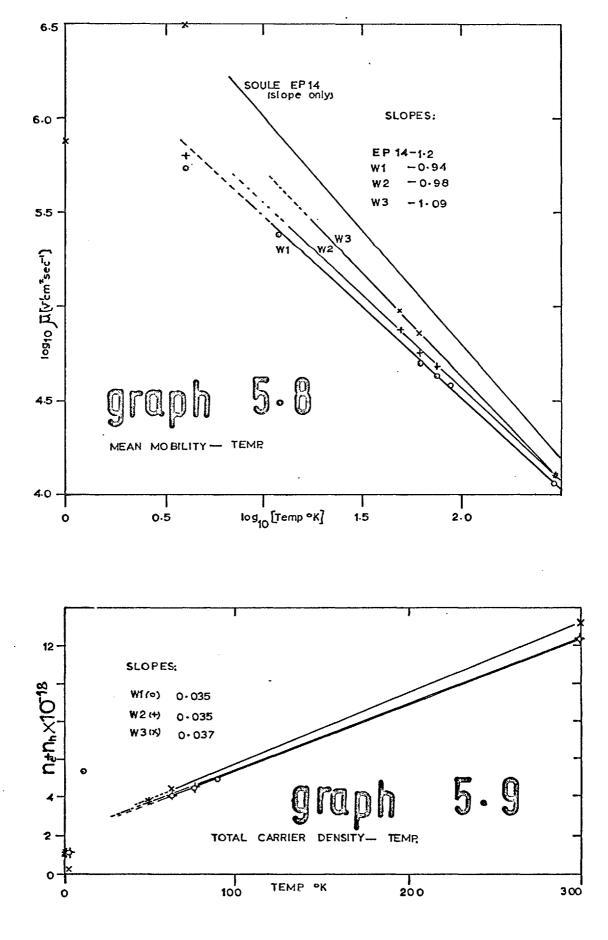
SAMPLE W3

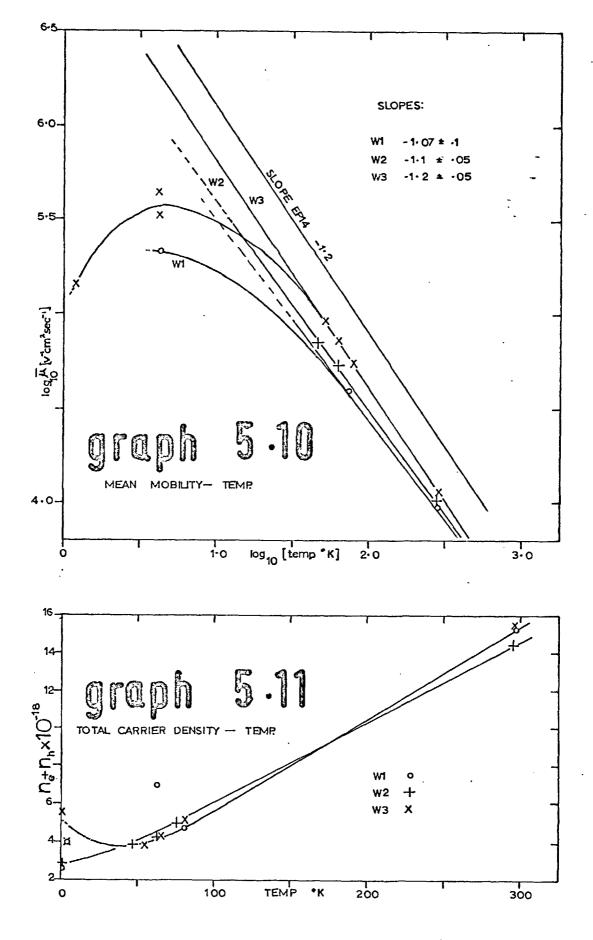
unweighted. The number preceeding U or W gives the number of Lorentzian terms employed to fit the data and hence used to generate the rest of that row of the table. Columns 3 and 4 give the carrier mobilities in units of $10^4 \text{cm}^2/\text{volt-sec}$ and the final two columns 5 and 6 give carrier densities in units of $10^{18}/\text{cm}^3$. All zero entries in the table are to be ignored as they represent large numbers which are physically unrealistic and have been set to zero to avoid an untidy appearnace. Negative entries once more result from unrealistic fits.

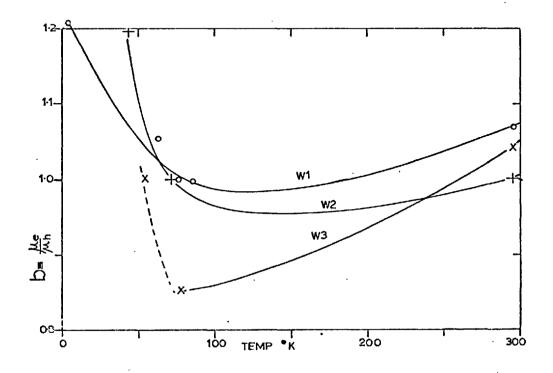
Graph 5.10 presents the mean carrier mobility as a function of temperature in the same way as Graph 5.8 which was based on simpler calculations. We see that the two approaches yield essentially the same results at high temperature, but Graph 5.10 indicates a decreasing slope at lower temperatures.

Carrier densities in Table 5.1 are a little higher (Graphs 5.11) than the values given by the simpler treatment (Graph 5.9) but the temperature dependence is essentially unaltered.

The mobility ratio ${}^{\mu}e/\mu_{h}$ is extremely dependent on the data-fitting process but the expected shape (Spain et al, 1967) is obtained in Graph 5.12.







graph 5.12

MOBILITY RATIO - TEMPERATURE

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5.2 Oscillatory derived results.

5.2.1 Result of the Landau fitting.

In Graph 5.7 is shown the analysis of the oscillatory part of the Hall effect in W3 at 1.2^oK. The circles are data points, obtained by eliminating the monotonic background from a chart recording as detailed in Section 4.2.1. The generalized Landau fitting programme (FRIER, Section 4.2.3) chose the 'best' set of sixteen fitting parameters to generate the continuous line superimposed on the data points. This curve, labelled "total", is composed of contributions from both holes and electrons each of which, in turn, are split into fundamental and 1st harmonic terms.

The function describing the electron term is (Section 2.5)

$$G_{e} = H^{n} \left\{ W_{1} \quad \frac{U}{\sinh U} e \quad \cos\left(\frac{2\Pi}{PH} - \psi_{1}\right) + W_{2} \frac{2U}{\sinh 2U} e \quad \frac{T}{\cos}\left(\frac{4\Pi}{PH} - \psi_{2}\right) \right\}$$

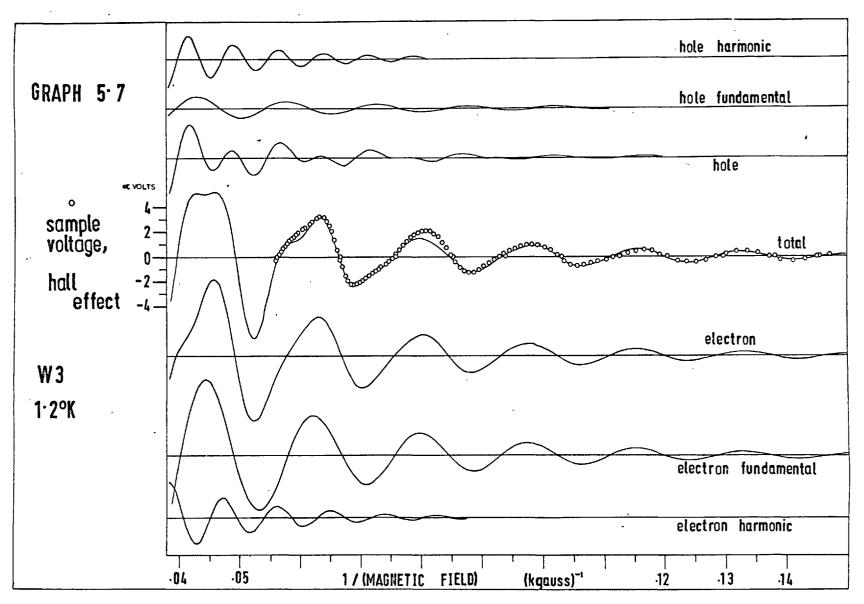
where $U = \frac{2\pi^2 KTm^*C}{\hbar e} \times \frac{1}{H} \equiv \frac{A}{H}$, say Thus, n, W_1 , W_2 , A, $\frac{\Delta T}{T}$, P, w_1 , w_2 are adjustable parameters. A similar expression holds for the hole term.

We report here the result of allowing FRIER to run until it was very close to the best fit as defined in Section 4.2.3. Under restrictions such as holding A, $\frac{\Delta T}{T}$, etc. constant the run did terminate itself (that is, it satisfied convergence criteria specifying approximately 1% accuracy of parameters) but under conditions where all sixteen parameters were allowed to change during the fitting process it had a little way still to go. We believe, however, that values of P, $\frac{\Delta T}{T}$ and n listed below are realistically close to their final values; errors were estimated by comparing an earlier run (where the sum of the squares of the residuals, ΣR^2 , was 20.41) with the final run ($\Sigma R^2 = 17.3$).

Electrons

n	Period	А	∆т/т	W	rb
0.5005	1.77x10 ⁻⁵	5303	5.034	0.1346	3.301
				-0.1406	17.90
<u>+</u> 0.5%	<u>+</u> 2%	± 20%	<u>+</u> 1%	± 50%	± 5%
Holes					
n	Period	A	∆т/т	W	th
0.4995	1.48x10 ⁻⁵	9654	2•509	0.0188	-0.496
				0.1032	-2.245
± 0.5%	<u>+</u> 10%	± 50%	<u>+</u> 20%	<u>+</u> 200%	<u>+</u> 100%

We see that the electron parameters are much more closely defined than those of the holes. A glance at Graph 5.7 will show that it is indeed the electron behaviour which dominates with the hole terms supplying detail and, of more importance, perturbing the zero-crossing points.



5.2.2. Effective masses, collision damping, periods.

Recalling the definition of the parameter A from Section 4.2.3 and 2.5.

$$A \equiv \frac{2\Pi^2 \text{KTm}^* C}{\hbar^e}$$

we can derive estimates for the effective masses. Calculation gives $m^*/m_0 = \frac{0.036, 0.065}{0.0107}$ for the electrons and holes respectively. These are to be compared with the values 0.030, 0.060 respectively found by Soule (1958) and 0.039, 0.057 respectively by Soule, McClure and Smith (1964) for single crystal graphite.

The factors $\Delta T/T$ yield values for the so-called Dingle temperatures; the effective increase in temperature due to collisions. We calculate $\Delta T = 6.0$, 3.0 for electrons and holes respectively.

Our corrected periods for pyrolytic graphite are 1.84×10^{-5} and 1.54×10^{-5} gauss⁻¹ for electrons and holes respectively. The electron period is much lower than values found in single crystal graphite (2.01, 1.57; Soule **2.**07, 1.51; Soule, McClure and Smith), though the hole period is in satisfactory agreement. Later, unpublished, work by J.D. Cooper has suggested that the present electron period is uncharacteristically low even for pyrolytic graphite, for which he reports periods in the region of $2.1 \times 10^{-5} \text{G}^{-1}$. The reason for the discrepancy is not known at present. Other features of the present analysis are fully confirmed, however.

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5.2.3. Estimation of γ_2 and E_F

The oscillation periods were used to calculate γ_2 and E_F given the well-established values of γ_0 , γ_1 and Δ ($\gamma_4 = \gamma_3 = \gamma_5 = 0.0$) and the oscillation periods P_0 , P_h .

It is difficult to obtain analytic expressions for γ_2 and E_F from the equations in Sections 2.1.3., 2.1.4, so a double iteration technique was used; assuming a value of K_z for the point M of figure 2.4 γ_2 and F_F were calculated and recalculated, in order, from starting values until a consistent pair of values was obtained. These were then used to obtain a better estimate of the position of N. The whole process was repeated until a consistent set of three values was obtained. In practice, convergence was extremely rapid and was chacked by calculating P_e and P_h from the final set of band parameters for comparison with the values supplied.

Using our corrected periods; $P_e = 1.84 \times 10^{-5}$, $P_h = 1.54 \times 10^{-5}$ gauss⁻¹ and $\gamma_o = 2.88$, $\gamma_1 = 0.395$, $\gamma_4 = \gamma_3 = \gamma_5 = 0.0$, we obtained for various values of Δ the values of γ_2 and E_F shown below:

Δ	γ_{2}	EF
-0.006	0.0162	0.0227
-0.01	0.0162	0.0225
-0.02	0.016	0.0221
-0.05	0.0156	0.0209

An extension to this computer programme accepted the complete set of band parameters and by perturbing these by $\pm 10\%$ produced estimates of the partial differential coefficients of the oscillation periods $\frac{\partial P}{\partial b}$ where b is a band parameter. It was found that for all the combinations above $\frac{\partial P}{\partial \gamma_2}$, $\frac{\partial P}{\partial E_F}$ were one or two orders of magnitude greater than the others. Their values were (for $\Delta = 0.006$):

$$\frac{\partial P_e}{\partial \gamma_2} = -0.53 \times 10^{-3} \qquad \frac{\partial P_e}{\partial E_F} = 0.12 \times 10^{-2}$$

$$\frac{\partial P_{h}}{\partial \gamma_{2}} = 0.35 \times 10^{-2} \qquad \frac{\partial P_{h}}{\partial E_{F}} = 0.17 \times 10^{-2}$$

The largest of the other differential coefficients was $\frac{\partial P_e}{\partial \Delta} = -0.46 \times 10^{-4}$

Finally, we mention that using Anderson et al's values $\gamma_{o} = 2.85$, $\gamma_{1} = 0.30$, $\Delta = 0.006$, $P_{e} = 2.088 \ 10^{-5}$, $P_{h} = 1.502 \ 10^{-5}$, we obtained $\gamma_{2} = 0.0194$ and $E_{F} = 0.0256$ which compare well with their quoted values of 0.02 and 0.26 respectively. Once more, their periods were more sensitive to γ_{2} and E_{F} than to other parameters by one or two orders of magnitude.

CHAPTER 6.

DISCUSSION AND CONCLUSIONS.

6.1 Classical Results

For the first time for pyrolytic graphite (PG) the present work provides a complete set of parameters whereby the zero field conductivity can be related to the electronic band structure in the sense that relaxation times and carrier densities are defined as a function of temperature. There is essentially nothing in the present analysis to identify physical restrictions on the mean free paths; one cannot discern the origins of scattering from these results alone. However, at the lowest temperatures it is reasonable to assume that carrier-phonon scattering is absent, the relaxation times being determined in the main by crystalline imperfections, whereas at high temperatures one supposes that scattering originating in thermal effects outweighs static obstacle scattering. At intermediate temperatures a mixed scattering régime evidently occurs.

In the past (cf Young 1968) the specific scattering mechanisms invoked have been high-angle scattering at basal plane crystallite boundaries and stacking faults for the lowest temperatures, with electron-acoustic phonon interactions at high temperatures in the spirit of the theoretical work of Sugihara and Sato (1963), Ono and Sugihara (1966) and McClure and Smith (1961). An apparently selfconsistent account of both basal plane and c-axis conduction could be obtained by considering out-of-plane vibrations associated with a deformation potential of ~ 18 eV and in-plane vibrations with a deformation potential of ~ 5 eV, with various assumptions involving the role of the trigonal warping parameter γ_3 . For present purposes a less sophisticated model is required. Thus we note that a mean mobility $\overline{\mu} = (\mu_e \mu_h)^{\frac{1}{2}}$ can be defined and that for the best single crystals (Soule's EP11) its temperature dependence can be represented between 4.2 and 295°K as $\alpha T^{-1.24}$. Following Klein (1962) and Hooker (1963), Spain et al (1967) assumed a dependence

$$(\bar{\mu})^{-1} = \frac{\bar{m}^* \bar{\nu}}{\exp 10^7} (\frac{1}{\lambda} + \frac{1}{\lambda} \text{ carrier-phonon})$$

to explain why $\bar{\mu}$ for PG always falls below Soule's limiting relationship particularly at low temperatures. λ' represents the effects of static obstacle scattering which, it was held, dominates the basal plane resistivity at the lowest temperatures. As the temperature is increased, interaction with the longitudinal acoustic c-axis mode $(\theta_D = 185^{\circ}K, Dolling and Brockhouse 1962)$, which couples strongly to the charge carriers via γ_2 , dominates c-axis resistivity up to $60^{\circ}K$ and basal plane resistivity up to $170^{\circ}K$, above which the c-axis mean free-path is limited to ~ 3\AA , leading to a decreasing resistivity with increase, whereby acoustic in-plane modes with high characteristic temberatures are invoked. However, Yeoman and Young have recently indicated (May 1969) that the source of charge carrier scattering has hitherto been completely misrepresented. They have measured the pressure coefficient of conductivity at temperatures in the range room to 4.2° K using pressures up to ~ 400 bar and find that conductivity always increases on application of pressure but the increase is always less than that expected from the known (Anderson et al 1967) pressure coefficient of carrier density, $\frac{d \ln n}{dP} \approx 37.5 \times 10^{-6} \text{bar}^{-1}$. Thus, they write for the pressure coefficient of conductivity

$$\frac{d \ln \sigma}{dP} = \text{constant} + \frac{d \ln n}{dP} + \frac{d \ln \Lambda}{dP}$$

The mean free path A is given by $\frac{1}{\Lambda} = \sum_{i=1}^{n-1} \frac{1}{\Lambda_{i}}$ where i stands for all possible scattering mechanisms. Now, carrier-obstacle and carriercharged acceptor scattering are expected to be pressure independent provided non-parabolicity is disregarded and carrier-phonon scattering would lead to the opposite pressure dependence, for increase in pressure would raise the characteristic temperature leading to a greater mean free path. One is left with carrier-carrier scattering of which Yeoman and Young only consider electron (e) - hole (h) inter-actions: e-e and h-h collisions would only affect conductivity via a randomisation of carrier energies which would be reflected by energy-dependent relaxation times were the electron and hole masses single-valued. The known range of electron masses in graphite will, it is true allow light electrons to be scattered by heavier carriers leading to the well-known anomalous low-field behaviour in the Hall effect (see Section 6.3), but not much change in the zero-field conductivity will thereby result since the partial conductivity of light electrons is only a few percent of the whole.

In the c-axis direction the fixed mean free path at high temperatures leads to a pressure dependence of conductivity which is nearly independent of temperature and close to that of the carrier density. The basal plane pressure coefficient, however, falls rapidly as the temperature is increased from 4° K, the carrier density change being almost completely compensated at room temperature. Yeoman and Young attribute this temperature dependence to e-h scattering which will increase in importance in the same way as does the carrier density. Neutron irradiation doses which are small enough not to affect the Fermi level as judged by electron and hole periods, nevertheless increased the pressure coefficient $\frac{d}{dP} \frac{\ln \sigma}{\ln \sigma}$ towards $\frac{d}{dP} \frac{\ln n}{\ln \sigma}$ because the e-h scattering can be no longer dominate in the presence of charged traps, even at room temperature.

For electron-hole scattering, $\frac{1}{\lambda_{e-h}}$ is approximately proportional to carrier density and thus to temperature, accounting for the observed mobility-temperature relationship. A corresponding relationship has been found to apply to $\frac{\partial \ln}{\partial P} \sigma$ by Young and Howell. It may be written $\left[\frac{\partial \ln n}{\partial P} \cdot \frac{\partial P}{\partial \ln \sigma} - 1\right] = \frac{\lambda!}{const} \times T$. We accordingly conclude with Yeoman and Young that carriercarrier scattering is of the foremost importance in graphite. In good PG samples at all temperatures $\overline{\mu} \sim T^{-1}$; in bad PG it is $\sim T^{-1}$ at high temperatures becoming independent of temperature at low temperatures. Typically $\lambda'(PG) = 17000$ Å. Good and bad single crystals show the same behaviour as PG except that here the exponent is closer to -1.2. In graphites which have not been irradiated there is an element of carrier-carrier scattering even at 0° K which reduces $\frac{\lambda \ln \sigma}{\partial P}$ by some 20% of $\frac{\lambda \ln n}{\partial P}$. At this temperature, carrier-carrier scattering is only made completely unimportant by the introduction of at least 10^{12} charged traps per cm³. It is reasonable to assume that any fixed mean free path, however introduced, will make carriercurrier scattering less important.

The experimental work which led to these conclusions became available after the bulk of this thesis was written. Accordingly, the analysis of low temperature data is put into a completely new perspective but the data itself exists, where it did not before, ready for analysis in the light of the latest interpretation.

6.2 Oscillatory Results.

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With the oscillatory phenomena the key point is the question:-"Can one replicate single crystal properties if one makes a mosaic well-oriented pyrolytic graphite or are the band parameters of single crystal and pyrolytic graphite intrinsically different?"

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It was argued that if one could observe oscillations at all the analysis of these would highlight any differences. At the start of this investigation no such oscillations had been observed, though they are now commonplace. One single crystal (\Im 14) had given a hole period of 1.5×10^{-5} gauss⁻¹ and an electron period of $2.07 \times 10^{-5} g^{-1}$. It was evident that the Dingle temperature for the electrons was higher than that for the holes, but no quantitative analysis for these had ever been attempted. Our aim was to determine both periods and Dingle temperatures for PG to answer the question whether PG is the same sort of material as single crystal graphite or whether the high basal dislocation content and mosaic structure measurably affects the band parameters.

The best sample, W3, at 1°K produced a sufficient number of oscillations for analysis though with only about 1/5th of the single crystal amplitudes. There is evidence of structure in the oscillatory pattern indicating that both electron and hole effects were being observed. The analysis described in the text (Section 5.2.2) leads to a hole period of $1.52 \times 10^{-5} g^{-1}$, in general agreement with that found in other work, but the electron period is somewhat less than is found elsewhere. The Dingle temperatures bear the correct relationship to the effective masses of the carriers involved. Later work by J.D. Cooper at Imperial College on other pyrolytic graphites suggests that the periods might be higher $(1.63, 2.15 \times 10^{-5} g^{-1}$ respectively), but the

Dingle temperatures are wholly confirmed. Accordingly the present results are used to compute values of γ_2 and the Fermi energy, E_f ; which are not well determined by the magnetoreflection experiments of Dresselhauss and Mavroides (1964).

We conclude that apart from uncertainty in the electron period the electronic structure of pyrolytic graphite is essentially comparable to that of single crystal graphite, the differences lying partly in scattering introduced by the microcrystalline nature of the former. At the lowest temperatures in single crystal graphite the mean free paths and thus the Dingle temperatures, are determined in the main by carrier-carrier scattering, whereas in PG highangle scattering events at grain boundaries are necessarily dominant. Ne therefore suppose that for our better graphites (W3) the Dingle temperatures will be smaller than for the less perfect materials (W1, W2) not merely because λ' is larger but also because low angle scattering on other carriers will play a part.

6.3 The low-field Hall coefficient

One outstanding problem is the sign of the Hall coefficient below 2kG. Spain et al (1967) using a range of PG always found a negative zero-field Hall coefficient at 77°K with a positive slope against magnetic field, indicating that the light electrons are exerting their proper Hall effect with a mean free path limited by static obstacle scattering. Soule, with good single crystal material

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observed a positive zero-field Hall coefficient at 77°K with a negative initial slope which he took to indicate the presence of minority holes. Now, it is true that in the electronic band structure of graphite as known there is a pocket for minority holes contained by the band E_{p} below Δ near to the hexagonal zone faces at H. This pocket might just be accessible by thermal spread of the electron energy distribution (~ kT) above 77°K, but Soule continues to observe this hole-like behaviour even at 4°K. Spain, with his more imperfect material consistently observed a negative Hall coefficient at 4°K in agreement with Sugihara's calculations (1966), but the present work shows clearly a tendency to more positive low field values for samples W1. W2. W3 in that order of increasing perfection. We conclude that Soule's attribution of the zero-field Hall coefficient to minority holes is incorrect. Following McLean and Paige (1960), Sugihara (1966) attributes a positive Hall coefficient (for the best material) to drag on light electrons by carrier-carrier interactions. Evidently, only when λ is controlled by carrier-carrier scattering can such a drag effect be of importance. Yeoman and Young confirmed that this is so in the best material. The effect can be suppressed by increasing the static obstacle scattering, permitting the light electrons to contribute their normal negative Hall coefficient. Pre-irradiation with light doses of fast neutrons has shown that this is so.

REFERENCES

Anderson, O'Sullivan and Schirber, Phys. Rev. 164, No. 3, 1038, 1967. Bacon, 1958, A.E.R.E. Report M/R 2707 Berman, Brock, Huntley, Cryogenics, 4, 233, 1964 Berman, Huntley, Cryogenics, 3, 1963 Bernal, 1924, Proc. Roy. Soc., A106, 749 Birss, 'Symmetry and Magnetism', North-Holland, 1964 Blackman, Saunders, Ubbelohde, Proc. Roy. Soc., A264, 19, 1961 Bloch, Z.Physik, <u>52</u>, 555, 1928 Blount, Solid State Physics, 13, p. 305, 1962. Boyle, Nozieres, Phys. Rev., <u>111</u>, 782, 1958 B.S.W. Bouckaert, Smoluchowski, Wigner, Phys. Rev., 50, 58, 1936 Callaway, "Energy Band Theory", Academic Press, 1964. Carter, Ph.D thesis Cornell University, 1953 Carter, Krumhansl, J.Chem.Phys. 21, 2238, 1953 Chambers, Proc. Phys. Soc. <u>A65</u>, 458 and 903, 1952 also <u>A238</u>, 344, 1958 Corbato, Proc. 3rd. Carbon Conf. Pergamon Press p173, 1956 Coulson, Taylor, Proc. Phys. Soc. A65, 815, 1952 Dawson, Follet, Proc. Roy. Soc. A253, 390, 1959 Dingle, Proc. Roy. Soc., <u>A211</u>, 517, 1952 Dresselhaus, Dresselhaus, Phys. Rev., 140A, 401, 1965 Dresselhaus, Mavroides, IBM Journal Res. and Devel. 8, 262, 1964 Franklin, Acta Cryst., 4, 253, 1951

Galt. Yager. Dail. Phys. Rev., 103, 1586, 1956 Haering, Mrowski, Prog. in Semicond., 273, 1960 Haering, Wallace, J. Phys. Chem. Solids 3, 253, 1957. Herring, J.Appl.Phys. 31, 1939, 1960 Hennig, Science, 147, 733, 1965 Hooker, Ubbelohde, Young, Proc. Roy. Soc., A276 83, 1963 ** A284, 17, 1965 also Hove. Phys. Rev., 100, 645, 1955 Ichikawa, Phys. Rev., 109, 653, 1958 Inoue, J.Phys.Soc. Japan, 17, 808, 1962 Jenkins, Turnbull, Williamson, J. Nucl. Mater., 7, 215, 1969 Johnston, Proc. Roy. Soc., A227, 349, 1955 also A237, 48, 1956 Jones. "Theory of Brillouin Zones" North-Holland 1960. Jones, Zener, Proc. Roy. Soc., A144, 101, 1934 Juretschke, Appl. Phys. Letters, 12, 213, 1968 Kao, Kata J. PHYS. CHEM-SOLIOS 6, 223, 1958 Kanter, Phys. Rev., 107, 655, 1957 Klein, Rev. Mod. Phys., 34, 56, 1962 Landau, Appendix D. Shoenberg, Proc. Roy. Soc. A170, 341, 1939. Lewis, Solid State Physics, 7, p.353, 1958. Lifshitz, note added in proof of Shoenberg, Prog. in Low Temp. Phys. 2, 226, 1957 Lifshitz, Azbel, Kaganov, Soviet Phys., JETP 4, 41, 1957 Lomer, Proc. Roy. Soc. A227, 330, 1955 McClure, Phys. Rev., 104, 666, 1956; 108, 612, 1957; 112, 715, 1958; 119, 606, 1960 also IBM J. Res. and Dev., <u>8</u>, 258, 1964

McClure, Smith, Proc. 5th Carbon Conf. 2, 3, 1961, Pergamon McClure, Yafet, Proc. 5th Carbon Conf. 1, 22, 1962, Pergamon Moore, Ubbelohde, Young, Proc. Roy. Soc., A280, 153, 1964 Nozieres, Phys. Rev., 109, 1510, 1958 Ono, Sugihara, J. Phys. Soc. Japan, 21, 861, 1966 also 24, 818, 1968 Onsager, Phil. Mag., <u>43</u>, 1006, 1952 Pippard, "Dynamics of Conduction Electrons", Blackie and Son, 1965 Powell, Computer Journal, 7, 303, 1964. Putley, "The Hall Effect and Related Phenomena", Butterworths, 1960 Roscoe, Thomas, Carbon, <u>4</u>, 383, 1966 Rose-Innes, "Low Temperature Techniques" English Univ. Press, 1964. Roth, Argyres, "Semicond. and Semimetals", Vol. 1, p159, 1966 Academic Press Schiff, "Quantum Mechanics", 1955, McGraw Hill Shoenberg, Trans. Roy. Soc. <u>A245</u>, 1, 1952 Shubnikov-de Haas, Commun. Phys. Lab. Univ. Leiden, No. 207a, 1930 Slater. "Quantum Theory of Molecules and Solids" McGraw-Hill 1963-65. Slonczewski, Ph.D. thesis, Rutgers University, unpubl., 1955 Slonczewski, Weiss, Phys. Rev., <u>99</u>, 636A, 1955 also <u>109</u>, 272, 1958 Sondheimer, Proc. Roy. Soc. A203, 75, 1950 Soule, Phys. Rev., 112, 698 and 708, 1958 Soule, McClure, Smith, Phys. Rev., 134, A453, 1964 Spain, Ubbelohde, Young, Phil. Trans. Roy. Soc., A262, 345, 1967 Sugihara, J. Phys. Soc. Japan, 21, supplement V111-2, 1966 Sugihara, Sato, J. Phys. Soc. Japan, <u>18</u>, 332, 1963

- Swanson, Phys. Rev., 98, 1534, 1955 also 99, 1799, 1955
- Wallace, Phys. Rev., 71, 622, 1947 also 72, 258, 1947
- Whittaker, Robinson, p344
- Yeoman, Young, J. Physics, part C (Solid State Physics) in press, 1969.
- Young, Carbon, 6, 135, 1968
- Young, Howell, Imperial College, 1969, unpubl.
- Wilson. "Theory of Metals" 2nd ed. Cambr. Univ. Press, 1953
- Ziman, "Principles of the Theory of Solids" 1965.
- Ehrenberg "Electric Conduction in Semiconductors and Metals" Oxf. Univ. press, 1958.

APPENDIX 1

Wave Mechanics of Conduction Electrons

In using the Pippard-type geometrical approach to visualise electron processes we are applying a model which, at first sight, is extremely unlikely. One would suspect the presence of many pitfalls in an unwary application of the model and we accordingly propose to outline the main quantum-mechanical arguments leading to a justification for our sometimes regarding electrons in a lattice as discrete particles obeying classical laws of motion.

The quantum-mechanical treatment is mainly due to Bloch, 1928 whose work was based on Schrodinger's early work. Born's theory of lattice vibrations is also of great importance in this field and an excellent accounts are given by Blount and Lewis 1962, 1958 respectively.

We start with Schrodinger's time-dependent wave equation

$$\left(H + \frac{\hbar}{1} \quad \frac{\partial}{\partial t}\right) \quad \mathfrak{D} = 0 \tag{1}$$

For an electron in a magnetic field \underline{H} described by a vector potential \underline{A} and an electric field \underline{E} described by a scalar potential V, we have the hamiltonian

$$H = -\frac{\hbar^2}{2m} \nabla^2 + \frac{ie\hbar}{mc} \underline{A} \cdot \nabla + \frac{ie\hbar}{2mc} \nabla \cdot \underline{A} + \frac{e^2}{2mc^2} \underline{A}^2 + \mathbf{\beta}$$
(2)

where curl $\underline{A} \equiv V \underline{A} \underline{A} = \underline{H}$, and, by Maxwell's laws, $\underline{c} = -\nabla V - \frac{1}{C} \frac{\partial A}{\partial \dot{c}}$ (3)

 ϕ is the potential energy of the electron, = eV. (See Schiff 1955, equation 23.24).

Now, by identifying $\mathfrak{P} \oplus \mathfrak{F}$ as the time-averaged density of matter and in particular for charged matter, $\mathfrak{P} \oplus \mathfrak{F} = \frac{\rho}{e}$ (where ρ is the charge density and e is the electronic charge), we can relate $\frac{\partial \rho}{\partial t}$ ($\mathfrak{P} \oplus \mathfrak{P}$) to current flow I through the conservation equation $-\frac{\partial \rho}{\partial t} = \nabla \cdot \mathbf{I}_{e}$.

Thus
$$\frac{\partial}{\partial t} (\Phi^* \Phi) = \frac{\partial}{\partial t} (\frac{P}{e}) = -\frac{1}{e} \nabla_e I$$

 $\frac{\partial}{\partial t}$ (Φ Φ) can be obtained from the Schrödinger equation (1) and the hamiltonian (2) to give a relation between current I and the quantities in the hamiltonian. Finally, identifying $\int Id_7$ with e_{ν} , where ν is the velocity of a wave packet described by Φ , we have

$$\underline{\nu} = \frac{\hbar}{\mathrm{im}} \int d\mathbf{r} \, \Phi \, \nabla \, \Phi - \frac{e}{\mathrm{mo}} \int d\mathbf{r} \, \underline{A} \, \Phi \, \Phi \qquad (4)$$

In the absence of a magnetic field, the Shrodinger equation simplifies to

$$i\hbar \quad \frac{\partial \Phi}{\partial t} = \left(- \frac{\hbar^2}{2m} \nabla^2 + \phi \right) \Phi \tag{5}$$

and if $\bar{\Phi}$ is zero at infinity or periodic boundary conditions are applied then $\bar{\Phi}$ can be split into time dependent and time independent parts

$$\Phi = \psi_{a} - iE t / \hbar$$
 (6)

is a solution of (5) where ψ does not depend on time and satisfies the time independent Schrodinger equation

$$\left(\frac{\hbar^2}{2m}\nabla^2 + E - \phi\right)\psi = 0 \tag{7}$$

The application of Born-Karman boundary conditions then leads to discrete eigenfunctions ψ_n and eigenvalues E_n , distinguished by the set of quantum numbers, n.

Linear combinations of solutions of type (6) can be constructed ... o describe any type of charge distribution. In general

$$\bar{\Phi} = \sum_{n} C_{n} \psi_{ne}^{-iEnt/\hbar}$$
(8)

where, by normalisation, $\Sigma |C_n|^2 = 1$.

Now let us assume we have the solutions to the above problem for a potential ϕ_0 and we apply small electric and magnetic fields. Thus, we require solutions of

$$i\hbar \frac{\partial \Phi}{\partial t} = \left(-\frac{\hbar^2}{2n} \nabla^2 + \phi_0 + H^* \right) \Phi$$
(9)

$$H^{*} = \frac{i e \hbar}{mc} \underline{A} \cdot \nabla + \frac{i e \hbar}{2mc} \nabla \cdot \underline{A} + \frac{e^{2}}{2mc^{2}} \underline{A}^{2} + eV \qquad (9A)$$

Then, for a small enough perturbation, the new solutions will still have the form (8), but the coefficients C_n will be time dependent. The $C_n(t)$ satisfy

$$\dot{C}_{n'} = (i\hbar)^{-1} \sum_{n} C_{n} H^{*}_{n'n} e^{i(E_{n'} - E_{n})t/\hbar}$$
(10)

where the matrix element $H_{nn'}^{i} = \int \psi_{n'}^{*} H^{i} \psi_{n} dr$

(H^{*} can be simplified for small H; H^{*} = $\frac{ie\hbar}{mc} \underline{A} \nabla + eV$) (10A)

Motion in a periodic potential

Bloch's theorem states that solutions of (7), when ϕ is periodic, are of the form

$$\psi_{\mathbf{k}} = \mathbf{C} \, \mathbf{e}^{\mathbf{i}\mathbf{k}\cdot\mathbf{r}} \, \mathbf{U}_{\mathbf{k}}(\mathbf{r})$$

where $U_k(\underline{r})$ has the same periodicity as the lattice. Substituting into the Schrodinger equation, (7), gives

$$\nabla^2 \mathbf{U} + 2\underline{i}\underline{\mathbf{k}} \cdot \nabla \mathbf{U} + \frac{2\mathbf{m}}{\hbar^2} (\mathbf{E} - \phi - \frac{\hbar^2 \hbar^2}{2\mathbf{m}})\mathbf{U} = 0$$
 (11)

Solving this equation for a given value of <u>k</u> leads to a discrete set of eigenfunctions, $U_{\underline{k},n}(\underline{r})$ and eigenvalues $\underline{E}_{\underline{k},n}$ characterised by parameters k and n.

However, as things stand, we have some ambiguity in the wave function ψ , for we can add to k some vector k^{i} leaving ψ unchanged

$$\psi = e^{i\underline{k}\cdot\underline{r}} \underline{U}_{\underline{k}}(\underline{r}) = e^{i(\underline{k} + \underline{k}')\cdot\underline{r}} (e^{-i\underline{k}'\cdot\underline{r}} \underline{U}_{\underline{k}}(\underline{r}))$$

This expression for ψ is still a solution of (7) provided $e^{-i\underline{k}'\cdot\underline{r}} Uk(r)$ has the required periodicity. If <u>R</u> is a lattice translation vector then we must have $e^{-i\underline{k}'\cdot\underline{r}} Uk(\underline{r}) = e^{-i\underline{k}'\cdot(r+\underline{R})}Uk(\underline{r}+\underline{R})$ i.e. $e^{-i\underline{k}'\cdot\underline{R}} = 1$, as $Uk(\underline{r})$ is periodic.

For a cubic lattice of primitive translation a the components of <u>k</u> have to satisfy $k_x a = 2\pi x$ integer, etc. Thus we can change the components of vector <u>k</u> by integral multiples of $\frac{2\pi}{a}$ without affecting ψ , provided the phase of the periodic function Uk(r) is changed at the same time.

In general, it is possible to make the <u>k</u> vector describing any state lie within the first Brillouin zone $\left(-\frac{11}{a} < k_{i} < \frac{11}{a}\right)$ for a cubic lattice). The resulting vector is called the "reduced wave vector".

By substituting $\psi_k = ce^{i\underline{k}\cdot\underline{r}} Uk(r)$ into the Schrodinger equation (7) and imposing Born-Karman periodic boundary conditions ψ_k ($\underline{r} + N\underline{R} = \psi_k$ (\underline{r}) where N is an integer, we find that \underline{k} can only take values such that $\underline{k}.N\underline{R} = 2\Pi n$ where n is an integer and \underline{R} is a translation vector of the lattice. For a cubic lattice, this means that components of adjacent k vectors are separated by $\frac{2\Pi}{aN}$. This is a very small quantity compared with the width of the Brillouin Zone and we can usually regard k as being continuous.

The sets of eigenfunctions $\psi_{\underline{i};,n}$ for different values of the quantum number n usually have widely separated sets of eigenvalues $E_{\underline{k},n}$. Almost all conduction processes involve much smaller energies than these gaps and n will not usually change for these processes. At most, we are concerned with a few such n values, corresponding to the "valence" and "conduction" bands and we shall omit the band index in what follows.

Velocity of electron packets

Let us construct a wave packet from Bloch states with wave vectors \underline{l} localised near $\underline{l} = \underline{k}$:

$$\Phi_{\underline{k}} = \Sigma C_{1} \psi_{1e}^{-iE_{1}t/\hbar}$$
(12)

By 4 and 12 the velocity of the packet is

$$\underline{\underline{v}}_{\underline{k}} = \frac{\hbar}{\mathrm{im}} \int (\underline{\Sigma} \ \underline{C}_{\underline{1}}^{*} \ \psi_{\underline{1}}^{*} \ \mathrm{e}^{\mathrm{iE}_{\underline{1}} t/\hbar} \ \nabla \ \underline{\Sigma} \ \underline{C}_{\underline{1}} \ \psi_{\underline{1}} \ \mathrm{e}^{-\mathrm{iE}_{\underline{1}} t/\hbar}) \ \mathrm{d}r \ - \frac{\mathrm{e}}{\mathrm{mc}} \int \underline{A} \ \underline{\Phi}_{\underline{k}}^{*} \ \underline{\Phi}_{\underline{k}} \ \mathrm{d}r$$

This can be reduced to

$$\underline{\mathbf{v}}_{\underline{\mathbf{k}}} = \frac{\hbar}{\mathrm{im}} \sum_{1} |\mathbf{c}_{1}|^{2} \int_{\mathbf{l}} \psi_{1}^{*} \nabla \psi_{1} \, \mathrm{d} \mathbf{r} - \frac{\mathrm{e}}{\mathrm{mc}} \int_{\mathbf{l}} \Delta \Psi_{\mathbf{k}}^{*} \Phi_{\mathbf{k}}^{*} \, \mathrm{d} \mathbf{r}$$

Now, if Φ_1 is localised near 1 = k and also $\Sigma |C_1|^2 = 1$ by normalisation of ψ then

$$\underline{\mathbf{V}}_{\underline{k}} = \frac{\hbar}{\mathrm{im}} \int_{\underline{\mathbf{l}}} \psi_{\underline{k}}^* \nabla \psi_{\underline{k}} \, \mathrm{d} \mathbf{r} - \frac{\mathbf{e}}{\mathrm{mo}} \int_{\underline{\mathbf{l}}} \underline{\mathbf{A}} \, \frac{\mathbf{e}}{\underline{\mathbf{k}}} \, \mathbf{e}_{\underline{\mathbf{k}}} \, \mathrm{d} \mathbf{r} \tag{13}$$

which relates the velocity of a wave packet to the wave vector of the eigenfunction which contributes most strongly to the wave packet. <u>k</u> is the "representative wave vector". The shape of the wave packet enters through the second term.

Now we must digress to point out that the magnetic field \underline{H} is still described by a vector potential \underline{A} when this latter is changed by addition of the gradiant of any scalar field, f.

For $\nabla \wedge (\underline{A} + \nabla f) = \nabla \wedge \underline{A} + \nabla \wedge \nabla f = \nabla \wedge \underline{A} = \underline{H}$

(since curl (grad f) $\equiv 0$).

But this "gauge transformation" changes the potential V.

Thus, for constant magnetic field <u>H</u> and electric field ϵ we have $\underline{A} = \frac{1}{2} \underline{H} \underline{A} \underline{r} + \nabla f$ and $\underline{V} = -\underline{\epsilon} \cdot \underline{r} - \frac{1}{C} \frac{\partial f}{\partial t}$ (from(3)).

Thus, (13) can be reduced to a single term if we add $\nabla f = -\frac{1}{2} H \Lambda r$ to $\frac{1}{2} H \Lambda r$, where $r = \int \Phi_k^* r \Phi_k dr$, for the second term is easily shown to be zero.

Then

$$\underline{\mathbf{v}}_{\underline{\mathbf{k}}} = \frac{\hbar}{\mathrm{im}} \int \boldsymbol{\psi}_{\mathbf{k}} \, \nabla \boldsymbol{\psi}_{\mathbf{k}} \, \mathrm{d} \boldsymbol{r} \tag{14}$$

This simpler expression is thus valid provided we use a vector potential whose mean value is zero. This is known as the "Jones-Zener condition".

Now the ψ_k have the Bloch form, and satisfy $\frac{\hbar^2}{2m} \nabla^2 \psi_k + (E_k - \phi)\psi_k = 0$ where ϕ is the periodic potential. By operating with $\frac{\partial}{\partial k}$, multiplying by $\psi_{\underline{k}}^*$ and integrating, we find $\hbar \dot{x}_{\underline{k}} = \frac{\partial}{\partial k_x} E_{\underline{k}}$. Thus, combining similar equations for the other components, we have for the velocity of the wave packet:

$$\hbar \underline{\underline{V}}_{\underline{k}} = \nabla_{\underline{k}} \underline{\underline{E}}_{\underline{k}}$$
(15)

Acceleration of the electron

Taking $\underline{\underline{V}}_{\underline{k}}$ formally as a function of $\underline{\underline{k}}$ and $\underline{\underline{r}}$ we have $\frac{d}{dt} \underline{\underline{V}}_{\underline{k}} \equiv \underline{\underline{V}}_{\underline{k}} = (\frac{\partial \underline{x}}{\partial k_{x}} \dot{\underline{k}}_{x} + \frac{\partial \underline{x}}{\partial k_{y}} \dot{\underline{k}}_{y} + \frac{\partial \underline{x}}{\partial k_{z}} \dot{\underline{k}}_{z}) + (\frac{\partial \underline{x}}{\partial x} \dot{\underline{x}} + \frac{\partial \underline{x}}{\partial y} \dot{\underline{y}} + \frac{\partial \underline{x}}{\partial z} \dot{\underline{z}})$ or $\underline{\underline{V}}_{\underline{k}} = \hbar \underline{\underline{T}} \underline{\underline{k}} + \hbar \underline{\underline{T}} \underline{\underline{V}}_{\underline{k}} \qquad (16)$

where the tensors have elements:

$$T_{ij} = \frac{1}{\hbar} \frac{\partial \underline{V}_{ki}}{\partial k_{j}} = \frac{1}{\hbar^{2}} \frac{\partial^{2} \underline{E}_{k}}{\partial k_{i} \partial k_{j}}$$

$$T_{ij} = \frac{1}{\hbar^{2}} \frac{\partial^{2} \underline{E}_{k}}{\partial k_{i} \partial x_{j}}$$
(17)

Rigorous justification for letting the eigenvalues $\underline{E}_{\underline{k}}$ vary with position in this way is not easy. It is as if the conductor were made of adjoining pieces, each having slightly different sets of eigenvalues.

We must find an expression for \underline{k} . From (10) we have

$$\dot{c}(1) = \frac{1}{(i\hbar)} \sum c(1) H'_{1'1} \exp(i(E_{1'} - E_{1}) \frac{t}{\hbar})$$
(18)

Now, using the vector potential satisfying the Jones-Zener con-

$$\frac{\partial \mathbf{f}}{\partial t} = -\frac{1}{2} \left(\underline{\mathbf{H}} \wedge \frac{\partial \mathbf{r}}{\partial t} \right) \cdot \mathbf{r} = -\frac{1}{2} \left(\underline{\mathbf{H}} \wedge \underline{\mathbf{V}}_{\underline{\mathbf{k}}} \right) \cdot \mathbf{r}$$

Hence the new potential $V = -\underline{E} \cdot \underline{r} - \frac{e}{2c} (\underline{V}_k \wedge \underline{H}) \cdot \underline{r}$ (19)

So, using (18), (10A), (19) and $\underline{A} = \frac{1}{2} \underline{H} \wedge (\underline{r} - \underline{r})$ we have for small values of \underline{H} , t and $(\underline{E}_1, - \underline{E}_1)$:

$$\dot{c}(1') = \Sigma c(1) \int \psi_{\underline{1}}^{*} \left(\frac{\underline{i} e\hbar}{2mc} \underline{H} \wedge (\underline{r} - \underline{r}) \nabla - \frac{e}{2c} (\underline{V}_{\underline{k}} \wedge \underline{H}) \cdot \underline{r} - e \underline{c} \cdot \underline{r} \right) \psi_{\underline{1}} dr$$

This must be evaluated for the Bloch waves $\psi_{\underline{1}} = c e^{i\underline{1} \cdot r} U_{\underline{1}}(\underline{r})$. After some involved calculation we find (Ehrenberg, P.99)

$$\dot{\mathbf{c}}_{\underline{1}} = -\left(\frac{\mathbf{e}}{\hbar} \underbrace{\mathbf{e}}_{\underline{1}} + \frac{\mathbf{e}}{2c\hbar} \left(\underbrace{\mathbf{V}}_{\underline{1}} + \underbrace{\mathbf{V}}_{\underline{k}} \right) \mathbf{A} \underbrace{\mathbf{H}} \right) \nabla_{\mathbf{k}} \mathbf{c}_{\underline{1}}, - \frac{\mathbf{i} \mathbf{e}}{2c\hbar} \mathbf{c}_{\underline{1}}, \underbrace{\mathbf{H}}_{\underline{1}} \mathbf{A} \underbrace{\mathbf{E}}_{\underline{1}} \nabla_{\mathbf{k}} \mathbf{c}_{\underline{1}}, - \frac{\mathbf{i} \mathbf{e}}{2c\hbar} \mathbf{c}_{\underline{1}}, \underbrace{\mathbf{H}}_{\underline{1}} \mathbf{A} \underbrace{\mathbf{E}}_{\underline{1}} \nabla_{\mathbf{k}} \mathbf{c}_{\underline{1}}, - \frac{\mathbf{i} \mathbf{e}}{2c\hbar} \mathbf{c}_{\underline{1}}, \underbrace{\mathbf{H}}_{\underline{1}} \mathbf{A} \underbrace{\mathbf{E}}_{\underline{1}} \nabla_{\mathbf{k}} \mathbf{c}_{\underline{1}}, - \frac{\mathbf{i} \mathbf{e}}{2c\hbar} \mathbf{c}_{\underline{1}}, \underbrace{\mathbf{H}}_{\underline{1}} \mathbf{A} \underbrace{\mathbf{E}}_{\underline{1}} \nabla_{\mathbf{k}} \mathbf{c}_{\underline{1}}, - \frac{\mathbf{i} \mathbf{e}}{2c\hbar} \mathbf{c}_{\underline{1}}, \underbrace{\mathbf{H}}_{\underline{1}} \mathbf{A} \underbrace{\mathbf{E}}_{\underline{1}} \nabla_{\mathbf{H}} \mathbf{c}_{\underline{1}} \mathbf{c}_{$$

For the representative vector, $\underline{1}' = \underline{k}$, this can be written

$$\frac{\partial}{\partial t} \left| \mathbf{o}_{\underline{k}} \right|^{2} = -\frac{\mathbf{e}}{\hbar} \left(\underline{\mathbf{e}} + \frac{1}{\mathbf{c}} \underline{\mathbf{v}}_{\underline{k}} \Lambda \underline{\mathbf{H}} \right) \cdot \mathbf{v}_{\underline{k}} \left| \mathbf{o}_{\underline{k}} \right|^{2}$$

which is satisfied by

$$|c_k|^2$$
 = function of $(\hbar \underline{k} - \underline{e}\underline{c} + -\underline{e}\underline{c} + \underline{h})$.

For \underline{k} to continue to denote the representative wave vector as the wave packet moves, \underline{k} must change with time to keep the argument constant. Thus the rate of change of the representative wave vector of the wave packet, \underline{k} , is given by

$$\hbar \underline{k} = e \underline{c} + \frac{e}{c} \underline{V}_{\underline{k}} \underline{\Lambda} \underline{H}$$
(20)

But the RHS is the Lorentz force F acting on a particle with charge e. Thus, $\hbar \underline{k}$ changes under the force F just as does \underline{mV} for a charged particle outside the lattice.

Equation (16) now reduces to

$$\underline{\underline{V}}_{\underline{k}} = \hbar \underline{\underline{T}} \underline{\underline{k}} + \hbar \underline{\underline{T}} \underline{\underline{V}}_{\underline{k}} = \underline{\underline{T}} \underline{\underline{F}} + \hbar \underline{\underline{T}} \underline{\underline{U}}_{\underline{k}}$$

For a homogeneous material, $\underline{\underline{T}}^{t} = \underline{\underline{0}}$ and

$$\frac{V}{V_{k}} = \frac{T}{F}$$
(21)

Comparing this with Newton's relation $\underline{V} = \frac{1}{m} \underline{F}$ we see that \underline{T}^{-1} is analogous to a mass tensor. This discovery is subject to the approxi-

mations we have made, viz. that the material is homogeneous and that the field H is small enough to neglect A^2 in(9A), leading to (10A). Jones and Zener have given the condition for the validity of neglecting A^2 as (eH/2mc)t \ll 1, where t is the time over which $\hbar \underline{k} - \underline{egt} - \frac{\underline{e}}{c} \underline{r} \wedge \underline{H}$ = constant is valid essentially the relaxation time. For graphite, taking m = 0.02 m_o, t = 5 x 10⁻¹³ secs, this gives H \ll 250 kgauss.

A further condition is that the carriers can be described by Bloch waves taken from single bands i.e. no band degeneracy is allowed or the effective mass approximation will break down. Of course, our picture suffers from the fundamental drawbacks of the independentparticle model; correlation effects are entirely neglected. "Electrons" and "holes" strictly exist, respectively, well above and below, the Fermi energy. Close to the Fermi energy neither particle is wellcefined and there exists the possibility of strongly correlated states. However, for a semimetal like graphite we put our faith in the low density of carriers compared with the density of available states and hope that correlation effects are reasonably small.

APPENDIX 2.

Application of the Jones-Zener Expansion to Graphite

The object of this appendix is to reduce the Jones-Zener solution of the Boltzmann equation to a form where comparison can be made between Jones-Zener terms and terms in the phenomenological expansion of the magneto-conductivity tensor, $\sigma_{ij}(\underline{H})$. These tensor components are then reduced to fairly simple integrals over the Fermi surface which enable one to relate the low field magnetoconductivity tensor directly to the Slonczewski-Weiss band parameters.

We recall the solution of the Boltzmann equation $f = f_0 - \frac{\partial f_0}{\partial E}$ where ϕ is given by $\frac{1}{r}\phi + \frac{e}{\hbar} \underline{\epsilon} \cdot \nabla_K \underline{\epsilon} + \underline{H} \cdot \underline{\rho} \phi = 0$ and $\underline{\rho} = \frac{e}{C\hbar^2} \nabla_K \underline{\epsilon} A \nabla_K$ This can be solved for ϕ to any order by iteration; for instance, the zeroth order solution is $\phi_0 = -\frac{re}{\hbar} \underline{\epsilon} \cdot \nabla_K \underline{\epsilon}$. Substituting back, one obtains higher order solutions. Jones and Zener first obtained the series solution in 1934:-

 $\phi = -\frac{e}{\hbar} [\tau_{\underline{e}} \cdot \nabla_{\underline{K}} E - \tau \underline{H} \cdot \underline{\Gamma} (\tau_{\underline{e}} \cdot \nabla_{\underline{K}} E) + \tau_{\underline{H}} \cdot \underline{\Gamma} (\tau_{\underline{e}} \cdot \nabla_{\underline{K}} E)) \cdots]$

- where e is positive for electrons.

Now, bearing in mind the definition of \underline{J} , e, and ϕ , particularly in respect of their signs, one can write the current density \underline{J} in terms of the above expansion :

$$\underline{J} = \frac{\underline{e}}{4\pi^3} \int \underline{V} \phi \frac{\partial \underline{F}}{\partial \underline{E}} dV_{K}$$

Hence
$$J_{i} = -\frac{e^{2}}{4\pi^{3}}\int_{\partial \tau}^{\partial f_{o}} \nu_{i}[\tau \underline{\epsilon} \cdot \underline{v} - \tau \underline{H} \cdot \underline{\Omega}(\tau \underline{\epsilon} \cdot \underline{v}) + \tau \underline{H} \cdot \underline{\Omega}(\tau \underline{H} \cdot \underline{\Omega}(\tau \underline{\epsilon} \cdot \underline{v}))]dv_{K}$$

- where we have used $\underline{V} = \frac{1}{\hbar} \nabla_{K} E = (\nu_{1}, \nu_{2}, \nu_{3})$

It is easily shown that any function of energy alone commutes with the operator \underline{C} ; $\underline{\Omega} f(\underline{E}(\underline{K})) = f(\underline{E}(\underline{K})) \underline{C}$ so one may bring out the electric field components from within $\underline{\Omega}$:

$$J_{i} = -\frac{e^{2}}{4\pi^{3}} \int_{\partial E}^{\partial f_{o}} \nu_{i} [\tau^{\varepsilon}_{j} \nu_{j} - \tau^{\varepsilon}_{j} \frac{H}{H} \cdot C(\tau \nu_{j}) + \varepsilon_{j} \tau H \cdot \Omega(\tau H \Omega(\tau \nu_{j}))] dv_{K}$$

The conductivity tensor follows immediately

$$\sigma_{ij}(H) = \frac{e^2}{4\pi^3} \int_{\partial E}^{\partial f_0} \nu_i [\tau \nu_j - \tau H \Omega(\tau \nu_j) + \tau H \cdot \Omega(\tau H \cdot \Omega(\tau \nu_j))] dV_K$$

Comparing this with phenomenological expansion

$$\sigma_{ij}(\underline{H}) = \sigma_{ij} + \sigma_{Kij}H_{K} + \sigma_{Klij}H_{K}H_{1} + \cdots$$
where $\sigma_{ij} = \sigma_{ij}(0)$, $\sigma_{Kij} = \frac{\partial \sigma_{ij}(\underline{H})}{\partial H_{K}} \Big|_{\underline{H}=0}$, $\sigma_{Klij} = \frac{1}{2} \frac{\partial^{2} \sigma_{ij}(\underline{H})}{\partial H_{K}\partial H_{1}} \Big|_{\underline{H}=0}$

one can identify the coefficients in the two expansions :-

$$\sigma_{ij} = -\frac{e^2}{4\pi^3} \frac{\partial f_0}{\partial E} \nu_i \tau \nu_j \, dV_K$$

$$\sigma_{Kij} = +\frac{e^2}{4\pi^3} \frac{\partial}{\partial H_K} \int_{\overline{\partial E}}^{\overline{\partial f_0}} \nu_i \tau \underline{H} \cdot \underline{\Omega} (\tau \nu_j) dV_K = \frac{e^2}{4\pi^3} \int_{\overline{\partial E}}^{\overline{\partial f_0}} \nu_i \tau \Omega_K (\tau \nu_j) dV_K$$

$$\sigma_{\text{Klij}} = -\frac{e^2}{4\pi^3} \stackrel{1}{=} \frac{\partial^2}{\partial H_{\text{K}} \partial H_{1}} \quad \left[\frac{\partial f_o}{\partial E} \quad \nu_1 [\tau_1 H \cdot \mathcal{Q}(\tau_1 V_j)) \right] dV_{\text{K}}$$

One can remove the product of the Ω - operator from the last expression by using $\Omega(AB) = A \Omega B + B \Omega A$ with $A \equiv (\tau \nu_i)$, $B \equiv (\tau H \cdot \Omega (\tau \nu_i))$. Then

$$\sigma_{\mathrm{Klij}} = -\frac{e^2}{4\pi^3} \frac{1}{2} \frac{\partial^2}{\partial H_{\mathrm{K}} \partial H_{\mathrm{I}}} \int_{\overline{\partial E}}^{\partial f_{\mathrm{O}}} (\underline{H} \cdot \underline{\Omega}(\tau \nu_{\mathrm{i}}(\tau \underline{H} \cdot \underline{\Omega}(\tau \nu_{\mathrm{j}})) - \tau \underline{H} \cdot \underline{\Omega}(\tau \nu_{\mathrm{j}})) \underline{H} \cdot \underline{\Omega}(\tau \nu_{\mathrm{i}})) \mathrm{d} v_{\mathrm{K}}$$

We now show that the first integral is zero: Operate on any scalar field A with $(\underline{H} \cdot \nabla_{\underline{K}} \wedge \underline{V})$. By writing the scalar triple product in determinantal form it can be seen that this operation results in

$$(\underline{\mathrm{H}} \cdot \underline{\nabla}_{K} / \underline{\mathrm{V}}) \mathbb{A} = - (\underline{\mathrm{H}} \cdot \underline{\mathrm{V}} / \underline{\nabla}_{K}) \mathbb{A} + \mathbb{A} (\underline{\mathrm{H}} \cdot \underline{\nabla}_{K} / \underline{\mathrm{V}})$$

However, the last expression is zero, for its terms cancel in pairs. Taking the pair associated with the H_x component as an example, we see

$$\operatorname{AH}^{x}\left(\frac{9k^{2}}{9n^{3}}-\frac{9k^{3}}{9n^{5}}\right)=0$$

since $v_i = \frac{1}{\hbar} \frac{\partial E}{\partial K_i}$, i = 1, 2, 3. Thus, we are left with

$$(\underline{H} \cdot \underline{\Omega}) A = -(\underline{H} \cdot \underline{\nabla}_{K} \wedge \underline{V}) A = -(\underline{\nabla}_{K} \cdot \underline{V} \wedge \underline{H}) A = \operatorname{div}_{K} (-A(\underline{V} \wedge \underline{H}))$$

- which means that any scalar field can be transformed into the divergence of a vector field by application of the operator (H, Ω) .

The above integral has thus been transformed into the integral over volume of the divergence of a vector field

$$\begin{bmatrix} \frac{\partial f_{o}}{\partial E} \tau \nu_{i} \tau H \cdot \Omega(\tau \nu_{j})(\underline{V} M) \end{bmatrix}.$$

By Gauss' theorem, this can be written as a surface integral of the vector field which immediately reduces to zero because $E(\underline{K})$ has the same values on opposite faces of the Brillouin zone.

One is left with:

$$\sigma_{\text{Klij}} = \frac{1}{2} \frac{e^2}{4\pi^3} \frac{\partial^2}{\partial H_K \partial H_1} \int_{\overline{\partial E}}^{\partial f} \tau \underline{H} \cdot \mathcal{O}(\tau \nu_i) \underline{H} \cdot \mathcal{O}(\tau \nu_j) dV_K$$

i.e.

$$\sigma_{\text{Klij}} = \frac{e^2}{8\pi^3} \int_{\partial E}^{\partial f_0} \boldsymbol{\tau} [\Omega_{\text{K}}(\boldsymbol{\tau}\boldsymbol{\nu}_j) \Omega_1(\boldsymbol{\tau}\boldsymbol{\nu}_i) + \Omega_1(\boldsymbol{\tau}\boldsymbol{\nu}_j) \Omega_{\text{K}}(\boldsymbol{\tau}\boldsymbol{\nu}_i)] d\boldsymbol{v}_{\text{K}}$$

To go further, we look for simplifications resulting from the symmetry of the graphite crystal and impose the condition that the magnetic field vector lie parallel to the c-axis, $\underline{H} \equiv (0,0,H)$. It was shown in section 2.2.1. that the only tensor elements contributing to $\sigma_{i,j}(\underline{H})$ with the magnetic field along the z-axis are $\sigma_{11}, \sigma_{22}=\sigma_{11}$. $\sigma_{33}, \sigma_{312}, \sigma_{321}=-\sigma_{312}, \sigma_{3311}, \sigma_{3322}=\sigma_{3311}, \sigma_{3333}$, so one can work with K = 3, 1 = 3 from now on.

Taking σ_{3ij} first, one requires an expression for Ω_3 . By expanding $\frac{e}{C_h} \underline{VAV}_K$ one obtains

$$\sigma_{3ij} = \frac{e^2}{4\pi^3} \frac{e}{C_h} \left(\frac{\partial f_0}{\partial E} \nu_{iT} \left(\nu_1 \frac{\partial}{\partial K_2} - \nu_2 \frac{\partial}{\partial K_1} \right) (\tau \nu_j) dV_K \right)$$

The reduction of σ_{Klij} to σ_{33ij} follows simply:

$$\sigma_{33ij} = \frac{e^2}{4\pi^3} \int_{\overline{\partial E}}^{\overline{\partial f_0}} \tau \Omega_3(\tau \nu_i) \Omega_3(\tau \nu_j) dV_K$$
$$= \frac{e^2}{4\pi^3} (\frac{e}{C_h})^2 \int_{\overline{\partial E}}^{\overline{\partial f_0}} \tau (\nu_1 \frac{\partial}{\partial K_2} - \nu_2 \frac{\partial}{\partial K_1}) (\tau \nu_i) (\nu_1 \frac{\partial}{\partial K_2} - \nu_2 \frac{\partial}{\partial K_1}) (\tau \nu_j) dV_K$$

Now, since the energy-band structure of graphite is not known over the whole Brillouin zone, we must introduce an approximation here to change the volume integral to an integral over the Fermi surface.

Using the well-known expansion for an integral $I(EF) = \int_{0}^{\infty} \frac{\partial f}{\partial E} f_{O}(E) dE$ where G(E) is a known function of energy; I(EF) = G(EF) - G(O) $(\Pi kT)^{2} = \partial^{2}G$

$$+\frac{6}{(11KL)_{-}}\frac{9E_{5}}{9-6}$$

one can verify, by integrating by parts, the following relation for any function g(E) of energy:

$$-\int_{0}^{\infty} g(E) \frac{\partial f_{0}}{\partial E} dE = g(EF) + \frac{(\Pi kT)^{2}}{6} \frac{\partial^{2}g}{\partial E^{2}} \Big|_{EF} \cdots$$

We use the lowest order approximation, obtaining:

$$\sigma_{ij} = \frac{e^2}{4\pi^3} \int \nu_i \tau \nu_j \qquad \frac{dS}{E=Ef} \quad |\nabla_K^E|$$

- since $dV_{K} = \left| \frac{dEdS}{V_{K}E} \right|$ where dS is an element of Fermi surface area.

$$\sigma_{3ij} = \frac{-e^3}{4\pi^3 c\hbar} \left[\nu_i \tau \left(\nu_1 \frac{\partial}{\partial K_2} - \nu_2 \frac{\partial}{\partial K_1} \right) \tau \nu_j \frac{ds}{|\nabla_K^E|} \right]$$

$$\sigma_{33ij} = \frac{-e^4}{4\pi^3 c^2 \hbar^2} \int \tau \left(\nu_1 \frac{\partial}{\partial K_2} - \nu_2 \frac{\partial}{\partial K_1} \right) (\tau \nu_i) \left(\nu_1 \frac{\partial}{\partial K_2} - \nu_2 \frac{\partial}{\partial K_1} \right)$$

$$(\tau \nu_j) \frac{ds}{|\nabla_K^E|}$$

Our task is now to perform these integrations over the Fermi surface of graphite, and so relate the band parameters to the low-field conductivity tensor. To do this, we recognise that one can - not obtain an analytic expession for the Fermi surface from the secular equation of Sloncewski-Weiss's band model for $\gamma_3 \neq 0$. We accordingly assume $\gamma_3 = 0$ throughout and make great use of the resulting circular symmetry about the K_z -axis.

In view of the circular symmetry, let us transform to the cylindrical co-ordinates K, α , K_z as defined in section 2.1.3 . In what follows we make use of the relations

$$\frac{\partial}{\partial K_1} = \cos \alpha \frac{\partial}{\partial K} - \frac{\sin \alpha}{K} \frac{\partial}{\partial \alpha}, \quad \frac{\partial}{\partial K_2} = \sin \alpha \frac{\partial}{\partial K} + \frac{\cos \alpha}{K} \frac{\partial}{\partial \alpha}$$

and the resulting expressions for the Fermi velocities:

$$\nu_{i} = \frac{1}{\hbar} \frac{\partial E}{\partial K_{i}}; \quad \begin{pmatrix} \nu_{1} \\ \nu_{2} \end{pmatrix} = \frac{1}{\hbar} \begin{pmatrix} \partial E \\ \partial K \end{pmatrix} \begin{pmatrix} \cos \alpha \\ \sin \alpha \end{pmatrix}$$

The expression $(\nu_1 \frac{\partial}{\partial K_2} - \nu_2 \frac{\partial}{\partial K_1})(v_j)$ reduces as follows:

$$\frac{1}{\hbar} \left[\cos\alpha \left(\frac{\partial E}{\partial K} \right) \left(\sin\alpha \frac{\partial}{\partial K} + \frac{\cos\alpha}{K} \frac{\partial}{\partial \alpha} \right) - \sin\alpha \left(\frac{\partial E}{\partial K} \right) \left(\cos\alpha \frac{\partial}{\partial K} - \frac{\sin\alpha}{K} \frac{\partial}{\partial \alpha} \right) \right] \\ \left(r_{\hbar}^{1} \frac{\partial E}{\partial K} \right) \left(\frac{\cos\alpha}{\sin\alpha} \right) = \frac{r_{\mu}}{\hbar} \left(\frac{\partial E}{\partial K} \right)^{2} \left(\frac{-\sin\alpha}{\cos\alpha} \right)$$

where one takes the $(-\sin\alpha)$ if j = 1 and $(\cos\alpha)$ if j = 2. In deriving this, we have used the key fact that $\frac{\partial E}{\partial \alpha} = 0$ for our band model with $\gamma_3 = 0$. An additional assumption is that τ is constant on an orbit round the Fermi surface in a plane perpendicular to the c-axis; $\tau = \tau(E_{\mu}K_{\mu})$.

The element of surface area is given by

$$dS = K d\alpha dK_{z} (1 \cdot (\frac{dK}{dK_{z}})^{2})^{\frac{1}{2}}$$

Because of the circular symmetry, one may integrate with respect to α immediately.

$$\int_{0}^{2\Pi} \nu_{i} \tau \nu_{j} d\alpha = \int_{0}^{2\Pi} \left(\frac{1}{\hbar} \frac{\partial E}{\partial K}\right)^{2} \tau \left(\frac{\cos \alpha}{\sin \alpha}\right) \left(\frac{\cos \alpha}{\sin \alpha}\right) d\alpha = \tau \left(\frac{1}{\hbar} \frac{\partial E}{\partial K}\right)^{2} \left(\frac{\pi}{0} \frac{0}{\pi}\right)$$

which shows that $\sigma_{21} = \sigma_{12} = 0$, $\sigma_{11} = \sigma_{22}$ as we have already seen from other symmetry considerations, in Section 2.2.1.

$$\int_{0}^{2\Pi} r \nu_{i} \left(\nu_{1} \frac{\partial}{\partial K_{2}} - \nu_{2} \frac{\partial}{\partial K_{1}} \right) \left(\frac{\partial}{\partial r} \nu_{j} \right) d\alpha = \int_{0}^{2\Pi} \frac{\varphi^{2}}{K_{h}^{2}} \left(\frac{\partial E}{\partial K} \right)^{2} \left(\frac{1}{h} \frac{\partial E}{\partial K} \right) \left(\frac{\cos \alpha}{\sin \alpha} \right) \left(\frac{-\sin \alpha}{\cos \alpha} \right) d\alpha$$
$$= \frac{\varphi^{2}}{K_{h}^{2}} \left(\frac{\partial E}{\partial K} \right)^{3} \left(\frac{\partial E}{\Pi} \right)^{3} \left(\frac{\partial E}{\Pi} \right)$$

showing $\sigma_{311} = \sigma_{322} = 0$, $\sigma_{312} = -\sigma_{321}$

$$\int_{0}^{2\Pi} \tau (\nu_{1} \frac{\partial}{\partial K_{2}} - \nu_{2} \frac{\partial}{\partial K_{1}}) (\tau \nu_{1}) (\nu_{1} \frac{\partial}{\partial K_{2}} - \nu_{2} \frac{\partial}{\partial K_{1}}) (\tau \nu_{1}) d\alpha$$

$$= \int_{0}^{2\Pi} \frac{\tau^{2}}{\frac{\tau^{2}}{\hbar^{2}K}} \left(\frac{\partial E}{\partial K}\right)^{2} \left(-\frac{\sin\alpha}{\cos\alpha}\right) \frac{\tau}{\frac{2}{\hbar^{2}K}} \left(\frac{\partial E}{\partial K}\right)^{2} \left(-\frac{\sin\alpha}{\cos\alpha}\right) d\alpha$$

$$= \frac{\tau^{3}}{\left(\frac{\pi^{2}}{\hbar^{2}K}\right)^{2}} \left(\frac{\partial E}{\partial K}\right)^{4} \left(\int_{0}^{\Pi} \int_{\Pi}^{0}\right)$$

showing $\sigma_{3311} = \sigma_{3322}$, $\sigma_{3312} = \sigma_{3321} = 0$.

For i, j = 3 we see that for σ_{33}

$$\int_{0}^{2\Pi} v_{3} \tau v_{3} d\alpha = \frac{r}{\hbar^{2}} \left(\frac{\partial E}{\partial K_{z}}\right)^{2} 2\Pi$$

Since $\tau \nu_3 = \frac{\tau}{\hbar} \frac{\partial E}{\partial K_z}$ has no K or α dependence we see that our assumption of $\gamma_3 = 0$ has imposed $\sigma_{3333} = 0$, whereas it is not necessarily zero from the symmetry of the crystal structure. One

deduces that a K or α - dependence of $\tau_{\partial K_z}^{\partial E}$ is essential to explain c-axis magneto-resistance or conductivity, both of which are proportional to σ_{3333} .

Before collecting our results, we present another simplification which leads to considerable reduction in the computational difficulties ahead.

We note simply that, since the integrations are being taken over the Fermi surface whose energy is, by definition, constant, the following relation must hold :

$$dE = \frac{\partial E}{\partial K} dK + \frac{\partial E}{\partial K} dK_z = 0$$
$$(\frac{\partial E}{\partial \alpha} = 0 \text{ since } \gamma_3 = 0)$$

This leads to

$$\frac{1K^{2}}{3K} = -\frac{9K^{2}}{9E} \sqrt{\frac{9K}{9E}}$$

Now, the integrals all contain a factor $\left[\frac{1 \div \left(\frac{dK}{dK_z}\right)^2\right]^{\frac{1}{2}}}{|\nabla_K E|}$ and it

is this which we simplify by realizing that

$$|\nabla_{\mathbf{K}} \mathbf{E}| = \sqrt{\left(\frac{\partial \mathbf{E}}{\partial \mathbf{K}}\right)^2} + \left(\frac{\partial \mathbf{E}}{\partial \mathbf{K}}\right)^2$$

and using the above result;

$$\frac{\left[1+\left(\frac{\mathrm{d}K}{\mathrm{d}K}\right)^{2}\right]^{\frac{1}{2}}}{\left|\nabla_{K}E\right|} = \frac{1}{\left(\frac{\mathrm{d}E}{\mathrm{d}K}\right)}$$

The integrals may now be collected, in preparation for the final integration over ${\rm K}_{\rm z}$.

$$\sigma_{i,j} = \begin{pmatrix} \Pi & 0 \\ 0 & \Pi \end{pmatrix} \stackrel{e^2}{\underset{A\Pi^3 h^2}{\underbrace{4\Pi^3 h^2}} \stackrel{[r (\frac{\partial E}{\partial K}) \ K \ dK_z}{\underset{A\Pi^3 C h^4}{\underbrace{4\Pi^3 C h^4}} \int \tau^2 (\frac{\partial E}{\partial K})^2 \ dK_z$$

$$\sigma_{33ij} = \begin{pmatrix} \Pi & 0 \\ 0 & \Pi \end{pmatrix} - e^4 \int \pi^3 \left(\frac{\partial E}{\partial K}\right)^3 \frac{1}{K} dK_z$$

To proceed further we must find the functions $K(K_z)$, $\frac{\partial E}{\partial K}(K_z)$ and assume some K_z -dependence for $\pi(K_z)$, but these expressions represent a remarkable simplification of the original Jones-Zener expressions.

APPENDIX 3

DATA.

The following tables of data are in three sections. First there is raw data on the variation of conductivity and Hall coefficient with magnetic field at stated temperatures for each of the three samples. This makes up the bulk of Appendix 3.

After this comes a short section detailing the results of fitting the raw data to Lorentzians. The solid curves of the graphs in Chapter 5 were plotted from the total conductivities σ_{xx} , σ_{xy} listed here. However, the tables also contain partial conductivities e.g. σ_{xy}^{n} , σ_{xy}^{p} from which the contribution of negative (n) and positive (P) carriers can be ascertained. Gaussian units are used. Magnetic field values are in gauss.

The last section presents raw data on the oscillations observed on W3 in three experiments at 1.2° K, two on the Hall effect and one on the magnetoresistance oscillations. The columns are magnetic field B (gauss), reciprocal field ¹/B (gauss⁻¹x10⁶), and sample voltage V, arbitrary units. One of these experiments was subjected to the detailed analysis of Section 5.2.

Errors.

Errors were introduced mainly in the chart reading process. Chart calibration, involving measurement of chart distances ($\langle 1\% \rangle$), sample current ($\langle 0.1\% \rangle$) and sample voltages (1% for low field Hall voltage at 1°K, though greater for values of magnetic field giving near-zero Hall coefficient) introduced a slightly smaller error. Total errors from these sources to be expected at 1°K vary from 10% at 200 gauss for magnetoresistance and 30% for Hall effect. This quickly drops to 3% for both effects at 2000 gauss and 2% or less above 4000 gauss. At 300°K errors are similar in magnitude for both effects, being about 10% at 200 gauss and less than 2% above 5000 gauss.

The magnetic field values must be corrected by the factor 0.960 because of a late-discovered calibration error in our fluxmeter. Finalderived values in Chapter 5, in particular Table 5.1 embody this -4% correction. Calibration of the Hall probe was accomplished to within 2%. It should be remembered what the magnetic field appears explicitly in the definition of Hall coefficient.

		W1 295	5⁰K	~		W1 295	5 ⁰ K
	B gauss	- ^R H (cm ³ /C)	σ (Ω-cm) ⁻¹ x10 ⁻³		B gauss	-R _H (cm ³ /0)	σ (Ω-cm) ⁻¹ x∶0 ⁻³
	647	.06365	22.8		17080	.07919	6.51
	1093	.067529	22.56		17420	.07876	6.40
	1602	.05993	22.17		205	.07031	22,819
	2128	.05969	21.71		205	.07408	22,936
	2644	.05447	21.15		214	.06736	22,918
	3758	.05841	19.75		218	.08176	22,914
	4335	.05696	18,99		229	. 06294	22.827
	4860	.05983	18.25		273	.06529	22.897
	5470	.05069	17.42		319	.0823	22.883
	6560	.06064	15,95		365	.07546	22 . 859
4	764.0	.06284	14.55		456	.05416	22.764
	87 90	•06398	13.13		548	.06611	22.831
	9705	.06587	12,11		683	.06916	22.772
	10710	.06789	11.10		914	.05886	22.575
	11660	.07014	10,22		1003	.06281	22,595
:	12550	.07168	9.47		1139	.0576	22.526
	13620	.07 39 4	8.65		1253	.06111	22.449
:	14550	.07616	8.00		1364	.06133	22.283
	15830	.07695	7.23		14.59	.06087	22.288

	W1 2	95 [°] K
B gauss	-R _H (cm ³ /C)	σ (Ω -cm) ⁻¹ x10 ⁻³
1 <i>5</i> 95	.06132	22.168
1713	.06161	22.052
1822	.06039	2 1. 905
1916	05877،	21,851
2056	.06197	21,715
2278	.06017	21,453
2374	.05828	21.380
2516	.05831	21,219
2630	.05823	21.0 90
2736	.05805	20.936
2836	.05784	20.852
2976	.05804	20.676
3090	.05885	20,525

Pro 44900 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4	w1 88	°ĸ			W1 8	38 ⁰ K
B gauss	- ^R H (cm ³ /C)	σ (Ω -om) ⁻¹ x10 ⁻³	-	B gauss	$-\frac{R_{H}}{m}$ (cm ³ /C)	σ (Ω-cm) ⁻¹ x10 ⁻³
3480	•0465	11.759		786	.1055	26.044
4436	. 0637	8,831		974	.0837	25.036
5395	.0825	6.847		1163	.0707	23.867
6360	.1012	5.3916		1352	.061	22,432
7330	.1197	4.3203		1537	. 0536	21.350
8300	.137	3.5679		1541	•0535	21,252
9280	.1525	2.9792		1731	.0482	20.274
10260	.1666	2,521		1920	<u>₀</u> 0442	19.004
11245	.1792	2.1453		2110	.0416	17.948
12240	.191	1.8612		2298	.0403	16.887
13225	.2015	1.6350		244.5	.04.02	15.838
14220	.2117	1 . 4 38 5		2680	.0412	14.913
15225	. <u>2</u> 213	1.2719		2682	.0412	14.870
16225	.2297	1.1325		2908	.0425	14.0495
16230	.2298	1.1314		3059	.0437	13.261
221	.282	28,661		3251	.0452	12.445
410	.1775	28.163		3421	.0468	11.766
598	.133	27.062		3632	.0492	11.094

	₩1 88 [°] K							
B gauss	$- R_{\rm H}$ (cm ³ /C)	σ (Ω-om) ⁻¹ x 10 ⁻³						
3832	.0517	10.494						
4208	.0562	9.377						
4780	.0632	7.967						

	W1 77 ⁰ K	5	•		W1 7	7 ⁰ K
B gauss	$\frac{-R_{\rm H}}{(\rm cm^3/C)}$	σ (G- cm) ⁻¹ x10 ⁻³		B gauss	$-R_{\rm HE}$ (cm ³ /C)	$(\Omega-cm)^{\sigma} - 1_{x10}^{-3}$
	-	31.020		9435	0,1891	2.4349
206	-0.0156	30,328		11370	0.2238	1.7732
278	0.02546	30.043		13320	0,25112	1.3486
370	0.06087	29.516		15290	0.27381	1.0613
463	0.06532	28,947		16790	0,28802	0,9030
695	0.06342	27.311		610	-	28.0097
926	0 .0586 5	25.471		1551	-	20.986
1158	0.0469	23,627		24,98	0.03	14.714
1391	0.03807	21.748		3446	0.0502	10.477
1624	0,03344	19.9896		4400	0.0737	7.758
1857	0.03289	18.422		5355	0.0975	5.8986
2092	0.02888	16.948		6315	0.1233	4 . 601
2324	0.03295	15.570		8250	0.1697	3.0116
2558	0.03446	14.331		9225	0.189	2.5141
2790	0.03852	13.367		10200	0.207	2.114
3022	0.04344	12,178		11185	0.223	1.8041
3260	0.04737	11.244		13160	0,252	1.3588
3730	0.06193	9.6309		14150	0.2648	1.1975
4200	0.07155	8.3080		15150	0.277	1.0622
4670	0.08833	7.2106		7300	0.1485	3.6675
5615	0.10796	5.5612		12140	0.2377	1.5634
7515	0.1517	3.5422		16180	0.289	0.94761

	W1 63	^{5°} K		• W1 63	5°K
B gauss	$-R_{\rm H}$ (cm ³ /c)	o (Q-cm) ⁻¹ x10 ⁻³	B gauss	^{-R} H (cm ³ /C)	σ (Ωm) ⁻¹ x10 ⁻³
-	-	33.100	1300	0.0972	20.86
204	0.2495	32.222	1400	0.0905	20.02
372	0.2975	30.947	1500	0.0855	19,28
699	0.1703	27.761	1600	0.0808	18,51
1400	0.09358	20.685	1700	0.0768	17.8
2808	0.0834	11.335	1800	0.0748	17.1
3750	0.1082	7.9227	1900	0.074	16.4
9520	0.2772	1.8549	2000	0.074	15.74
16885	0.4128	0.6951	2100	0.0744	15.13
250	0.254	31.88	2200	0.0753	14.55
400	0.219	30.85	2300	0.0759	14.0
500	0.1945	30.0	2400	0.0772	13.48
600	0.1718	28,88	2500	0.0788	12.96
700	0.154	27.5	2600	0.0803	12.44
800	0.140	26.24	2700	0.082	11.97
900	0.1278	25.0	2800	0.0838	11.5
1000	0.1189	23.75	2900	0.0856	11.04
1100	0.111	22.73	3000	0.0875	10.6
1200	0.104	21.8	4000	0.1262	7.25

	W1 63	°K	₩1 63 ⁰ K					
B gauss	$-R_{\rm H}$ (cm ³ /C)	σ (Ω-on) ⁻¹ x10 ⁻³	B gauss	-R _H (cm ³ /C)	σ (Ω-om) ⁻¹ x10 ⁻³			
5000	0.1517	5.095	12000	0.3304	1.23			
6000	0.1839	3.94	13000	0.35	1.075			
7000	0.2128	3.10	14000	0.368	0.94			
8000	0.239	2.44	15000	0.3852	0.84			
9000	0.2643	2.28	16000	0.4008	0.755			
10000	0.2879	1.685	17000	0,415	0.698			
11000	0.3098	1,422	3 500	0.1002	8.75			

	W1 15	°K		W1 15 [°] K			
B gauss	-R _H (cm ³ /C)	σ (Ω-cm) ⁻¹ x10 ⁻³		B gauss	$-R_{\rm H}$ (cm ³ /C)	σ (Ω-om) ⁻¹ x10 ³	
220	2.75	144.46		2000	0.632	8.45	
3 50	1.8	104.0		2100	0.636	7.8	
400	1.61	83.0		2200	0.640	7.28	
500	1,36	67.0		2300	0.645	6.76	
600	1.19	48.0		2400	0.650	6.26	
700	1.05	38.0		2500	0.656	5.82	
800	0.94	32.0		2600	0.662	5.44	
900	0.86	27.0		2700	0.670	5.12	
1000	0.79	23.2		2800	0.677	4.84	
1100	0,74	20.0		2900	0.685	4.58	
1200	0.70	17.4		3000	0.694	4.32	
1300	0,665	15.4		3500	0.740	3.42	
1400	0.64	14.0		4000	0.789	2.78	
1500	0.6181	12.8		4500	0.8335	2.27	
1600	0.62	11.7		5000	0.879	1.92	
1700	0.623	10.7		5500	0.925	1.64	
1800	0.626	9.9	l	6000	0.970	1.44	
1900	0.629	9.1		6500	1.0115	1,27	

<u></u>	₩1. 15 ⁰	ĸ			W1 15	5 ⁰ K
B gauss	-R _H (cm ³ /C)	σ (Ω-cm) ⁻¹ x10 ⁻³		B gauss	-R _H (cm ³ /C)	σ (Ω-on) ⁻¹ x10 ⁻³
7000	1.053	1.14		12000	1.264	0.538
7500	1.08	1,052		12500	1.275	0.510
8000	1.113	0,944		13000	1.285	0.485
8500	1.142	0.860		13500	1,295	0.467
9000	1.168	0.794		14000	1.3055	0.438
9500	1.1895	0.733		14500	1.315	0.417
10000	1.208	0.682		15000	1.323	0.399
10500	1.224	0.638		15500	1.331	0.382
11000	1.239	0.601	ŀ	16000	1.34	0.366
11500	1.2515	0,568		16500	1.349	0.352
				17000	1.357	0.340

	W1 4.	.5 [°] K		W1 4.	5°K
B gauss	$\frac{-R_{H}}{(cm^{3}/C)}$	σ (Ω-on) ⁻¹ ::10 ⁻³	B gauss	^{-R} H (cm ³ /C)	σ (Ω-cm) ⁻¹ x:0 ⁻³
200	0,882	64.4	2100	0.697	6,58
300	0.81	51.2	2200	0.702	5.88
400	0.778	40.9	2300	0,717	5.4
500	0.754	32.0	2400	0.728	5.0
600	0.733	26.0	2500	0.739	4.70
700	0.715	21.8	2600	0.751	4.45
800	0.699	19.56	2700	0.765	4,22
900	0.683	17.5	2800	0.778	4.01
1000	0.67	16.0	2900	0.792	3.83
1100	0.66	14.6	3000	0.806	3.661
1200	0.651	13.43	3100	0.820	3,518
1300	0.644	12.4	3200	0.834	3.372
1400	0.6415	11.38	3300	0.849	3.24
1500	0.643	10.44	3400	0.864	3.115
1600	0.65	9.8	3500	0.878	2.99
1700	0.658	8.83	3600	0.892	2,875
1800	0.667	8,15	3700	0.905	2.76
1900	0.6765	7.5	3800	0,918	2.648
2000	0.6865	7.0	3900	0.935	2.542

	W1 4.5	°K	₩1 4.5 [°] K			
B gauss	$\frac{-R_{H}}{(cm^{3}/C)}$	σ (Ω-cm) ⁻¹ x10 ⁻³	B gauss	$\frac{-R_{\rm H}}{(\rm cm^3/C)}$	σ (Ω- cm) ⁻¹ x10 ⁻³	
4000	0.948	2.442	4700	1,023	1.90	
4100	0.912	2,35	4800	1.032	1.84	
4200	0,925	2,26	4900	1.043	1.78	
4300	0.936	2,18	5000	1.053	1.725	
44.00	0.996	2.103	5100	1.069	1.68	
4500	1.005	2.035	5200	1.081	1.63	
4600	1.014	1.962	5300	1.095	1.583	

	W2 291°K				W2 291	۱° _K
B gauss	-R _H (om ⁵ /C)	σ (Ω- cm) ⁻¹ x10 ⁻³		B gauss	-R _H (cm ³ /C)	σ (Ω-om) ⁻¹ x10 ⁻³
0	-	25.006		2000	0.02526	23.628
100	F R			2100	-	-
200	- 0.2472	24.967		2200	0.02879	23.249
300	-			2300	-	~
400	- 0.0978	24.928		2400	0.03176	23.060
500	-	-	-	2500	-	-
600	- 0.0482	24.791		2600	0.03373	22.746
700	-	-		2700	-	-
800	- 0.0218	24.791		2800	0.03453	22 . 440
900	-	-		2900	-	-
1000	- 0.00715	24.637		3000	0.03564	22.081
1100	-	-		3100	-	-
1200	+ 0.00472	24.485		3200	0.03582	21.733
1300	-	-		3300	-	-
1400	+ 0.01229	24.316		340 0	0.03597	21.483
1500	-	-		3500	-	
1600	0.01796	24.168		3600	0.03682	21,153
1700	-	~		3700		-
1800	0.02095	23.931		3800	0,03556	20,724
1900	-	-		390 0	-	-

	W2 291 ⁰ K				₩2 291 [°]	ĸ
B gauss	$- R_{\rm H}$ (cm ³ /c)	σ (Ω) ⁻¹ x10 ⁻³		B gauss	- R _H (cm ³ /C)	σ (Ω-cm) ⁻¹ x10 ⁻³
4000	0.03634	20.339		10000	0.04863	11.501
4500	0.03686	19.597		10500	0.04936	10,983
5000	0.0383	18.773		11000	0.05061	10,482
5 500	0. 03948	17.635		11500	0.05165	9.987
6000	0.04046	16.965		12000	0.05270	9.582
6500	0.04.149	16.202		12500	0.05377	9.119
7000	0.04274	15.445	ļ	13000	0.05475	8.752
7500	0.04348	14.693		13500	0.05587	8.373
8000	0.04445	13.962		14000	0.05691	8.011
8500	0.04530	13.312		14.500	0.05783	7.67
9000	0.04.649	12.699		15000	0.05909	7.314
9500	0.04741	12.107		15500	0.05989	7.029
				16000	0.06084	6.741
				16500	0.06210	6.464
				17000	0.06290	6.205

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	w2 77	^{, о} к		W2 7	7 ^о к
B gauss	^{-R} H (cm ³ /C)	σ (Ω-cm) ⁻¹ x10 ⁻³	B gauss	- ^R H (cm ³ /C)	σ (Ω-cm) ⁻¹ x10 ⁻
0		35.547	1900	0.004559	18.885
100	0.264	34•998	2000	0.005805	18.160
200	-0.087	34.205	2150	0.007167	17.422
300	-0.0283	33.840	2200	0.008853	16.645
400	-0.00422	33.098	2300	0.01071	16.079
500	+0.00648	32.257	2400	0.01262	15•422
600	0.01321	31.363	2500	0.01447	14.789
700	0.01483	30.314	2600	0.01675	14.232
800	0.01451	29•305	2700	0.01904	13.650
900	0.01318	28.489	2800	0.02152	13.076
1000	0.00965	27•524	2900	0.02391	12.528
1100	0.00475	26.468	3000	0.02640	12.093
1200	0.00190	25.286	3100	0.02909	11.670
1300	0.001375	24.205	3200	0.03202	11.177
1400	0.000573	23.332	3300	0.03553	10.778
1500	0.000687	22.393	3400	0.03881	10.403
1600	0.001269	21.410	3500	0.04192	10.021
1700	0.002206	20.510	3600	0.04580	9.688
1800	0,003448	19.658	3700	0.04961	9•345

Citation Colory of Spinlars	W2 77 [°] K		ļ,	<u> </u>	W2 7'	(K
B gauss	$\begin{pmatrix} n \\ H \\ (cm^3/C) \end{pmatrix}$	σ (_Ω -cm) ⁻¹ x10 ³		B gauss	H	თ (ი-cm) ⁻¹ x10 ⁻
3800	0.05322	9.036		14000	0.3264	1.139
3900	0.05615	8.723		14500	0.3362	1.074
4000	0.05940	8.444		15000	0.3449	1.009
4500	0.07780	-		15500	0.3545	0.9557
7000	0.1623	3.672		16000	0.3388	0.9032
7500	0.1788	3.258		16500	0.3736	0.8647
8000	0.1913	2.907		17000	0.3820	0.8118
8500	0.2052	2.642				
9000	0.2192	2.391				
9500	0.2301	2.184				
10000	0.2435	2.010				
10500	0.2538	1.853				
11000	0.2651	1.711	Î	ł		
11500	0.2783	1.578		a series and the series of the		
12000	0.2869	1.475			1	
12500	0.2941	1•391				
13000	0.3051	1.299	Ì	Į	1	
13500	0.3147	1.220				

	W2 63°K		•	W2 63°	K
B gauss	$ \begin{array}{c} -R \\ H \\ (cm^3/C) \end{array} $	σ (Ω-cm) ⁻¹ x10 ³	B gauss	$\frac{-R}{H}$ (cm ³ /C)	σ (Ω-cm) ⁻¹ x10 ³
4000	0.0823	7.028	13500	0.3826	0•954
4500	0.1102	5.776	14000	0.3952	0.8982
5000	0.1255	4•931	14500	0.4076	0.8462
5500	0.1447	4.280	15000	0.4191	0.7987
6000	0.1673	3.698	15500	0.4321	0.7546
6500	0.1855	3.205	16000	0.4427	0.7150
7000	0.2029	2.8618	16500	0.4546	0.6793
7500	0.2191	2.551	0		37.348
8000	0.2339	2•293	100	0.01214	37.086
8500	0.2506	2.077	200	0.06274	36.657
9000	0.2658	1.891	300	0.07578	35.991
9500	0.2772	1.728	400	0.07943	34.692
10000	0.2931	1.587	500	0.07933	33•447
10500	0.3050	1.462	600	0.06802	32•224
11000	0•3174	1.349	700	0.0502	30.785
11500	0.3288	1.258	800	0.03685	29•441
12000	0.3450	1.164	900	0.02961	28.085
12500	0.3565	1.088	1000	0.02611	26.735
13000	0.3704	1.017	1100	0.02422	25.633

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<u></u>	W2 63 ⁶	^D K	-		• W2	63 ⁰ к
B gauss	-R H (cm ³ /C)	σ (Ω-cm) ⁻¹ x10 ⁻³		B gauss	-R H (cm ³ /C)	σ (Ω-cm) ¹ x10 ³
1200	0.02412	24•113		3000	0.04567	10.182
1300	0.02486	22•944		3100	0.04968	9.7'44
1400	0.02510	21•959		3200	0.05256	9•342
1500	0.02532	20.833		3300	0.05438	8.980
1600	0.02551	19•695		3400	0.05978	8.633
1700	0.02567	18.762		3500	0.06405	8.272
1800	0.02519	17.814		3600	0.06793	7.971
1900	0.02507	16.974		3700	0.07222	7.672
2000	0.02607	16.169		3800	0.07627	7•395
2100	0.02673	15•355		3900	0.08069	7.141
2200	0.02809	14.626	1	4000	0.08660	6.887
2300	0.02883	13•993		4500	0.1084	5.762
2400	0.03069	13•351				
2500	0.03241	12.729				
2600	0.03464	12.158				
2700	0.03650	11.619				
2800	0.03925	11.102				
2900	0.04238	10.623				
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	₩2 47.5	2°K			W2 47.5 [°] K		
B gauss	$\frac{-R_{H}}{(cm^{3}/C)}$	σ (Ω-om) ⁻¹ x10 ⁻³	-	B gauss	- ^R H (cm ³ /C)	σ (Ωo m) ⁻¹ x10 ⁻³	
0		45.168		1906	0.09054	14.322	
100	0.1727	43.856		2000	0,09613	13.499	ļ
200	0.05768	42.053		2100	0.1028	12,709	
300	0.1172	40.341		2200	0,1095	12.006	
400	0.1262	37.838		2300	0.1144	11,292	
500	0.1198	35.631		2400	0.1209	10.734	
600	0.1078	33.307		2500	0.1255	10,212	
700	0.09733	31.55		2600	0.1279	9.617	
800	0.09276	29.414		2700	0.1312	9.154	
900	0.08920	27.814		2800	0.1344	8.659	
1000	0.08567	25,695		2900	0.1400	8,281	ł
1100	0.08218	24.26		3000	0.1466	7.884	
1200	0.07870	22.633		3100	0.1530	7.514	
1300	0.07524	21.069		3200	0.1612	7.169	
14.00	0.07228	19.707		3300	0.1674	6.816	
1500	0.07286	18.510		3400	0.1736	6.523	
1600	0.07505	17.299		3500	0.1736	6.2615	
1700	0.08056	16.277		3600	0.1868	6.0019	
1800	0.08507	15.259		3700	0.1914	5.7474	

	W2 47.	5 [°] K		W2 47.5	ĸ
B gauss	$\frac{-R_{\rm H}}{(\rm cm^3/C)}$	σ (Ω-cm) ⁻¹ x10 ⁻³	B gauss	-R _H (cm ³ /C)	σ (Ω-cm) ⁻¹ x10 ⁻³
3800	0.1981	5.5366	11000	0.5856	0.98534
3900	0.2058	5.2971	11500	0.6095	0.91642
4000	0.2140	5.1011	12000	0.6275	0.8563
4500	0.2414	4.2408	12500	0.6492	0.8029
5000	0.2941	3.596	13000	0.6704	0.7535
5500	0.3161	3.130	13500	0.6936	0.7060
6000	0.3424	2.679	14000	0.7093	0.6689
6500	0.3646	2.330	14500	0.7295	0.6323
7000	0.6714	2.071	15000	0.7493	0.6008
7500	0.4107	1.856	15500	0.7721	0.5696
8000	0.4441	1.670	16000	0.7872	0.5449
8500	0.4644	1.496	16500	0.8034	0.5185
9000	0.4913	1.375	17000	0.8218	0.4942
9500	0.5119	1.257	17500	0.8342	
10000	0.5368	1.1497			
10500	0.5623	1.0637			

	W2 4.5	ĸ			W2 4.5	5°K
B gauss	- ^R H (cm ³ /C)	σ (Ω-cm) ⁻¹ x10 ⁻³		B gauss	- ^R H (cm ³ /C)	σ (Ω-cm) ⁻¹ x10 ⁻³
1500	0.9566	9.223		11000	2.0477	0.5978
2000	0.9060	6.397		11500	2.0707	0.5675
2500	1.0448	4.564		0	-	100,342
3000	1.1374	3.315		100	3.609	94.651
3500	1.2708	2.744		200	1.99	77.907
4000	1.3708	2.2536		300	1.475	62.541
4500	1.4696	1.8885		400	1,2278	49.236
5000	1.5583	1.6244.		500	1.0497	39.685
5500	1.6387	1.4289		600	0.9737	33.272
6000	1.7067	1.2755		700	0.8982	27.937
6500	1.7706	1.159		800	0.8517	23.592
7000	1.805	1.0427		900	0.8230	20.171
7500	1.8700	0.9508		1000	0.7967	17.355
8000	1.8973	0.8689		1100	0.7819	15.237
8500	1.9301	0.8151		1200	0.7662	13.47
9000	1.9586	0.7580		1300	0.7701	11.983
9500	1.9840	0.7117	1	1400	0.7768	10.796
10000	2.0096	0.6706		1500	0.7821	9.715
10500	2.0354	0.6315		1600	0.7960	8,827

	₩2 4.5 [°] K				°ĸ	
B gauss	-R _H (cm ³ /C)	σ (Ω-cm) ⁻¹ x10 ⁻³		B gauss	- ^R H (cm ³ /C)	σ (Ω- cm) ⁻¹ x10 ⁻³
1700	0.8083	8.015	ſ	3100	1.152	3.2243
1800	0.8211	7.403		3200	1.1837	3.0875
1900	0.8447	6.783		3300	1.2088	2.9414
2000	0.8658	6.3051		3400	1.2323	2.8085
2100	0,8921	5.899		3500	1.2609	2.6871
2200	0.9156	5.473		3600	1,2797	2.5758
2300	0.9406	5.104		3700	1,3036	2.4695
2400	0.9728	4.8086		3800	1.3242	2.3787
2500	0.9906	4.486		3900	1.3475	2.2927
2600	1.0155	4.2148		4000	1.3659	2,2020
2700	1.0441	3.9839		4500	1.4691	1.8630
2800	1.0733	3.7766				
2900	1.1005	3.5715				
3000	1.1234	3.3876				

	W2 1 ⁰ K				W2 1 ⁰ F	5
B gauss	-R _H (cm ³ /C)	σ (Ω-cm) ⁻¹ x10 ⁻³		B gauss	R _H (cm ³ /C)	σ (Ω-cm) ⁻¹ x10 ⁻³
3500	1.2172	2.602		1200	0.8191	13.011
4000	1.3295	2.1688		1300	0.8132	11.752
4500	1.4489	1.8392		1400	0.8307	10,591
5000	1.554	1.5966		1500	0.8459	9.4398
5500	1.6485	1,4018		1600	0.8559	8.5930
6000	1.728	1.2314		1700	0.8833	7.9211
6500	1.780	1.1212		1800	0.9047	7.2575
0	-	113.469		1900	0.9238	6,6488
100	-	82.789		2000	0.9411	6.1966
200	1.845	67.464		2100	0.9746	5.783
300	1.266	52.015		2200	0.99999	5.398
4.00	1.056	44.409	2	2300	1.0254	5.0259
500	0.9714	37.164		2400	1.0532	4.6712
600	0.9860	30.875		2500	1.0831	4.4322
700	0.9502	26.579		2600	1.1107	4.1738
800	0.9242	22,205		2700	1.1206	3.9262
900	0.8920	19.276		2800	1.1447	3.7436
1000	0.8669	17.020		2900	1,1636	3.54444
1100	0.8261	14.572		3000	1,1848	3.3426

	₩2 1 [°] K	
B gauss	$-R_{\rm H}$ (cm ³ /C)	σ (Ω-cm) ⁻¹ x10 ⁻³
3100	1.2149	3.1765
3200	1.2398	3.040
3300	1.2535	2.8957
3400	1.2788	2.7596
3500	1.3027	2.6490
3600	1.3254	2.5407
3700	1.3410	2.4391
3800	1.3655	2.3540
3900	1.3943	2.2714
4000	1.3966	2.1974
4500	1.4954	1.8586

	W3 293°K	5			₩3 293 ⁰	ĸ
B gauss	-R _H (cm ³ /C)	σ (Ωcm) ⁻¹ x10 ⁻³		B gauss	^{-R} H (cm ³ /C)	σ (Ω-cm) ⁻¹ x10 ⁻³
200	0.0333	27.2668		6000	0.0635	18.3775
300	0.0345	27.2223		6500	0.0662	17.4547
400	0.0320	27.1780		7000	0.0685	16.6867
500	0.0354	27.1338		7500	0.0705	15.8618
600	0.0377	27.0897		8000	0.0731	15.0601
700	0.0428	27.0897		8500	0.0763	14.3109
800	0.0436	27.0020		9000	0.0789	13.6105
900	0.0415	26.9149		9500	0.0810	12,9353
1000	0.0423	26.8284		10000	0.0835	12.3056
1200	0.0454	26.6569		10500	0.0863	11.6852
1500	0.0495	26.3205		11000	0.0887	11.1540
2000	0.0506	25,6726		11500	0.0916	10.6418
2500	0.0523	24.8320	1	12000	0.0940	10.1870
3000	0.0534	24.0102		12500	0.0963	9.6788
3500	0.0549	23.0484		13000	0.0990	9.2291
4000	0.0554	22.1607		13500	0.1015	8.7915
4500	0.0574	21,2302		14000	0.1040	8.4189
500 0	0.0590	20,2511		14500	0.1062	8.0610
5500	0.0613	19.2911		15000	0.1081	7.7323

	W3 293 [°] K							
B gauss	-R _H (cm ³ /C)	σ (Ω-cm) ⁻¹ x10 ⁻³						
15500	0.1114	7.3767						
16000	0.1139	7.0525						
16500	0.1160	6.7555						
17000	0,1183	6.4775						

	₩3 77.5 [°] K			₩3 77•5 [°] K				
B gauss	$\frac{-R_{\rm H}}{({\rm cm}^3/{\rm C})}$	σ (Ω-cm) ^{−1} x1ວ ⁻³		B gauss	$\frac{-\mathbf{R}_{\mathrm{H}}}{(\mathrm{cm}^{3}/\mathrm{C})}$	σ (Ω-cm) ⁻¹ x10 ⁻³		
4500	0.2437	6.6547		14000	1.0979	0.9698		
5000	0.2953	5.6913		14500	1.1351	0.9116		
5500	0.3513	4.8812		15000	1.1731	0.8557		
6000	0.4000	4.2593		15500	1,2088	0.8071		
65 0 0	0.4452	3.7048		16000	1.2453	0.7612		
7000	0.4929	3.2383		16500	1.2804	0.7202		
7500	0.5309	2.8886		17000	1.3135	0.6834		
8000	0.5879	2.6020		200	-0.0667	43.8892		
8500	0.6322	2,3422		300	-0.0355	42.8163		
9000	0.6786	2,1330		400	-0.0233	41.7945		
95 0 0	0.7228	1.9299		500	-0.0267	40.3502		
10000	0.7702	1.7621		600	-0.0222	38.8941		
10500	0.8058	1.6172		700	-0.0210	37.3394		
11000	0.8566	1,4910	ļ	800	-0.0200	35.8124		
11500	0.8964	1,3802		900	-0.0148	34 . 237 3		
12000	0.9350	1,2774		1000	-0.0066	32.4907		
12500	0.9725	1.1930		1100	-0.0060	30.9136		
13000	1.0168	1.1080		1200	-0.0078	29.6072		
13500	1.0560	1.0343		1300	-0.0051	28.0653		

	W3 77.4 [°] K			W3 77.4 [°] к				
B gauss	$\begin{pmatrix} -R_{\rm H} \\ ({\rm cm}^3/{\rm C}) \end{pmatrix}$	α (Ω-cm) ⁻¹ x10 ⁻³		B gauss	-R _H (cm ³ /C)	σ (Ω-cm) ⁻¹ x10 ⁻³		
4500	0.2030	6.6521		14500	1.0022	0.9006		
5000	0.2478	5.6993		15000	1.0332	0.8470		
5500	0.2940	4.8634		15500	1.0676	0.8004		
6000	0.3395	4.2114		16000	1.0940	0.7568		
6500	0.3812	3.6792		16500	1.1276	0.7142		
7000	0.4290	3.2487		17000	1.1599	0.6792		
7500	0.4732	2.9013		200	-0.3171	44.0033		
8000	0.5198	2•5869		300	-0.1989	42.6506		
8500	0.5608	2•3340		400	-0.1515	41.7179		
9000	0.5973	2.1111		500	-0.1240	40.3929		
9500	0.6322	1.9086		600	-0.1073	38.7519		
10000	0.6783	1.7569		700	-0.0940	37.0581		
10500	0.7120	1.6100		800	-0.0852	35•4238		
11000	0.7512	1.4766		900	-0.0809	34.0791		
11500	0.7907	1.3667		1000	-0.0747	32•4143		
12000	0.8242	1.2680		1100	-0.0769	31.2848		
12500	0,8618	1.1756		1200	-0.0728	29•5866		
13000	0.8981	1.1018		1300	-0.0676	28.1668		
13500	0.9333	1.0278		1400	0.0621	26.8299		
14000	0.9690	0.9600		1500	-0.0564	25.3587		

	W3 77.4°K								
	B gauss	-R _H (cm ³ /C)	σ (Ω-om) ⁻¹ x10 ⁻³						
	1600	-0.0496	24.1547						
	1700	-0.0423	22.9212						
	1800	-0.0365	21.7455						
	1900	-0.0302	20•5730						
	2000	-0.0235	19•7222						
	2100	- 0 0159	18.6611						
]	2200	-0.0085	17.7910						
	2300	-0.0008	16.9230						
;	2400	0.0065	16.2042						
	2500	0.0145	15•4184						
	2600	0.0228	14.6489						
	2700	0.0293	14.0037						
	2800	0.0368	13•4129						
	2900	0.0451	12.8052						
	3000	0.0538	12.2403						
	3100	0.0623	11.7593						
	32000	0.0695	11.2729						
	3300	0.0775	10.7641						
	3400	0.0875	10.3692						
	3500	0.0990	9•9241						

₩3 63.2 [°] К				W3 63.2 [°] K				
B gauss	-R _H (cm ³ /C)	σ (Ω-cm) ⁻¹ x10 ⁻³		B gauss :	-R _H (cm ³ /C)	σ (Ω-cm) ⁻¹ x10 ⁻³		
3500	0.2996	7•5794		13500	1.5838	0.7318		
4000	0.3592	6.0285		14000	1.6381	0.6842		
4500	0.4291	4.9803		14500	1.7009	0.6424		
5000	0.5062	4.1739		15000	1.7501	0.6062		
5500	0.5757	3•5429		15500	1.7962	0.5694		
6000	0.6513	3.0413		16000	1.8525	0.5447		
6500	0.7153	2.6641		16500	1.9055	0.5153		
7000	0.7852	2•3274		200	-0.1162	48•4404		
7500	0.8505	2.0745		300	0.0239	46.0864		
8000	0.9165	1.8379		400	0.0433	44.1781		
8500	0.9872	1.6657		500	0.0549	42.2118		
9000	1.0461	1.5052		600	0.0345	39.8470		
9500	1.1025	1.3657		700	0.0247	37.7332		
10000	1.1744	1 . 2483		800	0.0216	35•5340		
10500	1.2328	1.1393		900	0.0230	33•5770		
11000	1.2955	1.0619		1000	0,0241	31.5887		
11500	1.3589	0.9737		1100	0.0249	29•4117		
12000	1.4214	0.9021		1200	0.0229	27.6940		
12500	1.4761	0.8417		1300	0.0263	26.0064		
13000	1.5279	0.7841		1400	0.0341	24•3727		

	W3 б3.2°К				W3 63.2°	² K
B gauss	-F _H (cm ³ /C)	σ (Ω-cm) ⁻¹ x10 ⁻³		B gauss	-R _H (cm ³ /C)	σ (Ω-cm) ⁻¹ x10 ⁻³
1500	0.0386	22.8095		2900	0.1900	10.2073
1600	0.0488	21•3811		3000	0.2051	9.7192
1700	0•0559	19•9797		3100	0.2181	9•2354
1800	0.0659	18.9590		3200	0.2345	8.7976
1900	0.0767	17.7746		3300	0.2489	8.4159
2000	0.0864	16.7294		3400	0.2645	8.0205
2100	0.0967	15.8591		3500	0.2752	7.6743
2200	0.1077	14.9691		3600	0.2892	7.3568
2300	0.1162	14.0801		3700	0.3033	7.0412
2400	0.1269	13.2908		3800	0•3184	6.7623
2500	0.1353	12•5483		3900	0•3336	6.4800
2600	0.1496	11.8514		4000	0.3473	6.2293
2700	0 . 1591	11.2574		4500	0.4190	5.1104
2800	0.1751	10.7471		5000	0.4988	4.2887

<u>be reconstance con tran</u>	W3 54 [°] K			W3 54°K				
B gauss	$-R_{\rm H}$ (cm ³ /C)	σ (Ω-cm) ⁻¹ x10 ⁻³			R _H (cm ³ /C)	σ (()-cm) ⁻¹ x10 ⁻³		
3500	0.6920	5•4802		13000	2.7663	0•5374		
4000	0.8193	4•2490		200	0.0827	55.1862		
4500	0.9514	3•4515		300	0.1379	52.4828		
50 00	1.0645	2.8558		400	0.1656	49•2650		
5500	1.1942	2.4002		500	0.1738	45•1158		
6000	1.3209	2.0571		600	0.1794	41.6112		
6500	1.4195	1.7901		700	0.2011	38•1535		
7000	1.5571	1.5620		800	0.1863	34•8444		
750 0	1.6764	1.3913	,	900	0.1886	31.4363		
8 00 0	1.7901	1.2448		1000	0.1904	28.8929		
8500	1.8948	1.1111		1100	0. 1994	26.0796		
9000	1.9961	1.0063		1200	0.2001	23•9425		
9500	2.1181	0.9222		1300	0 .20 38	22.1292		
10000	2.2055	0.8489		1400	0.1981	20.3112		
10500	2.3130	0.7699		1500	0.2235	18.7146		
11000	2.4107	0.7142		1600	0.2303	17.1654		
11500	2.5225	0.6581	}	1700	0.2508	15.9316		
12000	2•5971	0.6119		1800	0,2668	14.8290		
12500	2.6866	0.5747		1900	0.2920	13•7212		

		₩3 54 [°]	ЪК
	B gauss	$-R_{\rm H}$ (cm ³ /C)	σ (Ω-cm) ⁻¹ x10 ⁻³
	2000	0.3125	12.7927
	2100	0.3391	11.8933
	2200	0•3594	11.0738
	2300	0.3762	10•3934
	2400	0.3933	9•7325
	2500	0.4189	9.0988
	2600	0•4331	8.6228
	2700	0.4600	8.1319
	2800	0.4849	7.6487
	2900	0.5125	7.2349
	3000 -	0.5382	6.8204
	3100	0.5609	6.4508
	3200	0.5873	6.1899
	3300	0.6072	5.8732
	3400	0.6295	5.5776
	3500	0.6588	5.3104
	3600	0.6831	5.0756
	3700	0.7093	4.8314
	3800	0.7299	4.6363
	3900	0.7515	4.4317
1	4000	0.7700	4.2670
	4500	0.8822	3•4737

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W3 4.2°K					W3 4.2	° _K
B gauss	$\frac{-R_{\rm H}}{({\rm cm}^3/{\rm C})}$	σ (<u>Ω</u> -cm) ⁻¹ x10 ⁻³		B gauss	$-R_{\rm H}$ (cm ³ /c)	(Ω-cm) ⁻¹ x10 ⁻³
3500	3.9411	1.7602		1500	1.2910	6.6680
4000	4.3071	1.4627		1600	1.3741	6.0206
4500	4.5667	1.2271		1700	1.4473	5•4358
5000	4.7407	1.0569		1800	1.5044	4.9760
5500	4.9854	0.9471	1	1900	1.5975	4•5515
6000	5.1142	0.8424		2000	1.6632	4•1861
200	0.6590	126.8895		2100	1.7399	3.8948
300	0.5364	78.8938	1	2200	1.8196	3.6070
400	0.5478	52.0479		2300	1.8861	3•3441
500	0.6129	39•5022		2400	1.9469	3.1255
600	0.6684	28.2968		2500	2.0146	2.9262
700	0.7081	22.4756	ę	2600	2.1107	2.7640
800	0.7833	18.3428		2700	2.1672	2.6011
900	0.8418	15.2873		2800	2.2406	2.4563
1000	0.9177	13.0300		2900	2.3089	2.3315
1100	0.9798	11.0794		3000	2.3823	2.2017
1200	1.0195	9•5965		3100	2.4322	2.0971
1300	1•1314	8.4950		3200	2.4926	2.0019
1400	1.2065	7•4959		3300	2•5494	1.9055

	W3 4.2	² K
B gauss	$-R_{\rm H}$ (cm ³ /C)	σ (Ω-ο≖) ^{−1} x10 ^{−3}
3400	2.6028	1.8295
3500	2.6657	1.7540
3600	2.7170	1.6820
3700	2.7694	1.6134
3800	2.8191	1.5501
3900	2.8625	1.4956
4000	2.9146	1.4429

	W3 1.	.5 ⁰ К	Ĩ		₩3 1.5 [°] ¥	c .
B gauss	$\frac{-R_{\rm H}}{({\rm cm}^3/{\rm C})}$	σ (Ω-cm) ⁻¹ x10 ⁻³⁻¹		B gauss	^R H (cm ³ /0)	σ (Ωon) ⁻¹ x10 ³
1500	· 1 . 9933	6.3412		1300	1,0288	8.3338
2000	2.44.26	3.9935	-	1400	1.1404	7.3097
2500	2,8754	2.8528		1500	1,2610	6.5817
3000	3.2987	2.1655		1600	1.3943	5.9408
3500	3.6207	1.7229		1700	1.5015	5.3891
4000	3.9132	1.4305		1800	1.6266	4.9007
4500	4.1066	1.2119		1900	1.7385	4.5277
200	~ 1.9790	101.2501		2000	1.8347	4.1487
300	-1.1109	67.0239		2100	1.9601	3.8407
400	-0.5875	47.1155		2200	2.0537	3.5752
500	-0.3270	33.2772		2300	2.1742	3.3069
600	-0. 1236	26,5845		2400	2.2548	3.0920
700	0.1238	21,5322		2500	2.3433	2 .9 069
800	0.2870	17.5595		2600	2 .4 594	2.7301
900	0.4338	14.7326		2700	2,5635	2,5820
1000	0.6049	12,5557		2800	2.6347	2,4391
1100	0.7773	10.7418		2900	2.7164	2,3338
1200	0.8641	9.4982		3000	2.8284	2,1818

	₩3 1.	5°K
B gauss	$-^{R}_{H}$ (cm ³ /C	σ • (Ω -cm) ⁻¹ x10 ⁻³
3100	2.8985	2.0862
3200 3300	2.9755 3.0478	1 . 9902 1 . 9012
3400	3.1368	1.8225

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field	Gxx	σ₹x	σxx	field	σxy	σxy	σxγ		field	ซ ์ xx	σxx	ØXX	field	л бху	Ōxy	бху
υ.		153.5929	205,9659	э.	- <u>,</u>	0.	-0.		υ.			216.9616		-9.	Γ. 7.4202	1.04+
100.0		151.5645	205.8992	122.2	-1.3358	0.9566	-0.3491		100.0 200.0	140.3871		275.8151 272.9119	100.0	-6.3721 -13.2192	13.5633	0.344
200+0		153.5168 154.4518	205.7423	201.0	-2.5727	. 1.8921	-0.6806		300.0		131,1503		300.0	-19 .8 242	18.9328	-0.891
400.0			205.3157	437.0	-3.4742 -5.0147	2.8147	- C. 9895 - 1.2807		409.0	134.9645	128.8302	263.1947		-25.8425	23.9371	-1,905 -2,56f
500 . 0	51.7698	154.2790	205,0488	512.1	-6.7126	4.6536	-1.5550		500.0	131.8014			500.0 600.0	-31.2308 -36.0167	28.6642 31.0867	-2.921
600.0 707.0		1 53. 1642		600.0	-7.4013	5.5710	-1.8304		600.0 700.0	128.3247	123.4728		100.0	-43.2470	37.1681	-3.07"
800.0		153.02HH 152.8727	204.3879	700.0 457.0	-H.5914 -9.7571	6.4550 7.3940	-2.0964	•	800.0	120.06/4		218.0287	800.0	-43.9519	40.8731	- 3. 72
400.0	50 .H4H1	152.6963	201.5446	903.3	-10.912/	8.2969	-2.6157	Derived	900.0	111.0380	113.1661	230.8047	900.0	-47.1930	44.1941 47.1377	-2.995 -2.872
L000 .n	50+5545	195.2000	205.0544		-12.0619	9.1927	-2.P691	Derived	1000.C	113.2122	110.2002	223.5604	1102.0	-52.4550	49.7223	-2.121
1100.0	50.2154	157./843 157.0499	202.5197 201.9414		-13,1986	10.0806 10.9596	-3.1180	- ·	1200.0	105.7045	103.2652	208,9722	1403.0	-54.5514	51.9776	-2.572
1300.0		151.1912			-15,4303	11.8292	-3.3621		1300.0	102.0721	59.7912	201,8633	1300.0	-56.3529	53.9165 55.5826	-2.436 -2.30*
1490.0	49.1326	151.5276	200.6591	1401.7	-16.5234	12.6888	-3.8346	A 1 1 1 1	1400.0 1500.0	98.5341 95.10C5	46.3755	194,9056	1403.0	-57.8884 -59.1881	56.9985	-2.185
1500.0			154.4542		-11.6104	13.53/8	-4.0626	Conductivity ×10 ¹⁴	1600.0	91.1/54	84.1869	101.5560	1500.6	-60.2186	58.1899	-7.080
1/09.0		150.9463	144.2210 144.4467	1/02.0	-18.6695	14.3757	-4.2848 -4.5011	oundoctivity	1/00.0	88.5607	86.6208	175.1815	1700.0	-61.1831	59.1805	-2.002
1800.0	41.3551	150.2829	147.6380	1436*0	-20.7278	16.0166	-4.7113	×10 ⁻¹⁴	1800.0	85.4565	81,5601	169,0166 163,0631	1933.0	-61.9218	59.9916 60.6425	-1,53° -1,87°
1900-0		144.4343	146. 1466		-71.7342	16.8187	- 4.9154	NIU .	1400.0 2000.0	82,4619 74,5753	0.6C11	163,0641	2000.0	-62.9/13	61.1501	-1.821
2000+0 2100+0	46.3520 45.8253	144.5714 144.1565	195.9240 195.0218		-22.7717 -23.6403	17.6084	-5.1134		2100.0	16.1945	74.9911	151.7856	2100.r	-63.3114	61.5799	-1.781
2200.0	45.2831	LAH. NCEA	144.0417		-24.6 398	14.1488	-5.4909		2200.0	74.1170	12.3384	146.4550	2203.0	-63.5452 -63.6835	61.7955 61.9590	-1.744 -1.724
2 30 1	44.12+1	148.4084	194.1352		-25.5698	19.4994	- 5.+764		2300.0 2400.0	/1.5401 69.0611	64.1205	141.3266 136.3931	2433.0	-63.1362	62.0316	-1.704
2400+0	44.1559	147.9979	142+1544 141+1491		-26.4875	20.6363	-5.8442		2500.0	66.6771	64.4730	131.6501	2500 . ^	-63.7121	62.0729	-1.685
2600.0	42.4176	14/.1445	190.1725		-28.2434	71.3544 27.0649	-6.1735	x10 ⁻¹⁴	2600.0	64.1851	62.168	12 / 0521	2603.1	-63.6189 -63.4643	61.9419 61.7966	-1.67/ -1.667
2100 .n	42.1715	146. 1044	1 59.0152	2/00.9	-24.0457	22.7662	- 6.3294	•	2/00.0	62.182E	60.5307 58.4418	122.7135	2803.0	-63.2540	61.5940	-1.660
2800.0 2900.0	41.154/	148.2941	188,0088 186,9244		-/9.9286	23.4489	- 6.4797		2900.0	58.C 140	56.4572	114.4712	2962.3	-62.9947	61.3408	-1.653
3000.0	41.1215	145.1299	185.4234		-37.7423 -31.5368	24.1180 74.7734	-6.6243 -6.7635		3000 .0	56.0815	54.5141	110.5960	3000.0 3100.0	-62.6916 -62.3497	61.0428 60.7053	-1.648 -1.644
3100*0	14 .H50 2	144.8566	184.1068	3127.1	- 12. 3174	25.4152	-6.8972	W1	1100 . U	54.2077	52.6653		3200.0	-61.9135	67.3332	-1.64
3200.0	49.1443	144.1765	1 44.5758	1273.3	-33,7691	26.0434	-7.0257	67 I	3200.0 3300.0	52.4084 50.6813	50.4000 49.2034	101.3084	4300.0	-61.5672	59.9308	-1.636
5400.0	*8.541F 37.8775	145, 8900	187.4416	3401.0	-33,8773 -34,5769	24.6582 27.2596	-7.1491 -7.2674		3407.0	44 .0 2 16	41.5764	96.6000	3401.0 3500.0	-61.1345 -63.6788	59.5021 59.3507	-1.632 -1.62F
1500.0	31.2014	142.8548	180.1014	3500.0	-35.2244	27.9477	-7.3807		3500.0	47.4521	46.0104	53.4492	3603.3	-67.2334	58.5798	-1.623
\$609.0	30.5726	147.3568	1 / 8. 47 44	3500.0	-15.9119	24.4226	-7.4892	A A A A Y	1600.0 1/00.0	45.466C 44.4402	44.52C8 43.0863	40.4266 81.5272	3700.0	-59.7111	58.0924	-1.618
\$700.0 \$800.0	35.852M 35.1687	141.4842	111.14/0		-36.5715 -37.2257	28.4445 24.5335	-7.5930	300°K	1800.0	43.0341	41./110	54.7457	3902.1	-59.2144	57.5910 57.0780	-1.613 -1.607
\$90.0 n	14 4404	140.8514	1 15. 1424	3402.0	-31.8565	ም • ግፅዓፅ	-7.7869	500 N	3400.0	41.6853	46.352C	82.0174	3900.0 4000.0	-50.6857	56+5557	-1.601
4000.0	11 . 784M	140.3470	1/4.1418	4000.0	-38 .470 2	30.5931	-7.P772		4000.0	40.3901 34.6510	35.1276 33.5326	79.5172 68.1831	4500 0	-55.4277	51.8637	-1.564
4500.ii) 5098.ii	***2935 26.1197	132.7018	164.0003	4573.0	-41.7415 -43.1229	33.0754 15.1634	- 8.2661 - 8.5596		4500.0 5000.0	29.9578	28.9687	58.9265	5000.0	-52.6716	51.1543	-1.517
5500.0	23-2103	152.3139	155.5841	550.0	-45.7957	17.0263	-8.1689	77 °K	5500.0	26.0991	25.2244	11.3235	5500.0 5000.0	-49.4926 -47.4459	48.5279 46.0367	-1.464 -1.405
6000.0	14 18000	129.1204	149.4204	5023.1	-47.5391	74.6339	- 8.9042	// N	0.0004	22.4060	22.1306	45.0365 39.7998	6500.0	-45 .568	43.1037	-1.353
6500.0 7000.0	16.4924	124.9555	143. 3479	6500.0 /000 0	-48,4405 -50,1503	40.0054	- 4.9751		6500.0 7000.0	20.2447	14.5551 11.3441	15.4051	7003.0	-42.8333	41.5355	-1.257
7500.0	4640+15 14 8+12	124.4357	131.6118	7520.3	-51+0740	41.16^r 47.1164	- 8.99°2 - 8.9578		/ 500 .0	10.1207	15.5688	11.6896	7500.0 8000.0	-40.7730 -38.8683	34.5288 37.6754	-1.244 -1.192
H000*U	6./155	119.2830	125.9985	4000.0	-51.7171	47.8976	-8,2844		8060.6	14.5110	14.0143	28.5254	8500.0	-3/+1089	35.4646	-1.144
9,000 - 0	3.1095	116.8640	120.5785	450c.r	-52.28 13	43.5667	-8.7771		8500.0 9000.0	13.1304 11.4383	12.6815	25.0119 23.4694	4000.0	- 35 . 48 34	34. 3851	-1-798
9500.0	0.8744	114.5390	115.3633		-52.6152 -52.7431	43.9738 44.3111	-8.6414 -8.4872		9500.0	10.9026	10.5318	22.4344	9552.0	-33,9504 -32,5891	32.9255 31.5748	-1.054 -1.014
10000 .0	-4.5712	110.1456	105.5174	10000.0	-57.8 3/0	44.5330	-8.3040		10000.0	4.9974	9.6587	1410301	13570.7	-31.2991	30.3231	-0.576
10 500 . 1	-1.0852	108.0854	101.0007		-52.7635	44.6530	-8.1105		10500.0	4.2020 8.4992	8.8414 8.2136		11001.2	-30.1011	29.1610	- [. 94['
11500.0	-9.4/48	106.118C 104.240F	96.6432 1 97.4960 1		-52,5886 -52,3267	44.6837 44.6367	-7.9049 -7.6900		11500.0	7.6754	1.6119	15.4872	11500.0	-28.9865 -27.9478	28.0801 27.0730	- C. 5CE - C. 874 ·
	-11.848 #	102.4525	8H. 553H	12000.r	-51.9974	44.5723	-7.4681		12000.0	7.5190	1.0752	14.334%	12500.0	-26.9779	26.1328	-0.8454
	-15.9405	100.7508	H4. H055	12500.0	-51.5911	44, 3499	-1.2411		12500.0	6.8206 6.3124	6.5445 6.1622	12.5346	13000.0	-26+0706	25.2535	-0.817
	-17-8758	99.1329 57.5957	H1.25/71	13000.0	-51.1987	44.1280 43.8640	-7.0107		13500.0	5.9678	5.1118	11. / 196	13500.0	-25.2204	24.4297 23.6565	- C. 190 - C. 765'
	-21.441C	96+1359	74.6979		-50.1093	43.5646	-6.5447		14000.0	5.012	5.4182	11.01.74	14000.0	-24.4223 -23.6719	22.9295	-0.742
	-24.0852	94.7500	11.66481		-44.5468	43.2356	- 6.3112		14500.0	5.2680 4.9642	5.0566 4.3034	9. 16 16	15000.0	-22.9652	22.2449	- ^ . 720
	-24.639 2	93.4346 92.1860	68.19491 66.01441		-48.4606 -48.3559	42,4822 42,5089	-6.0785 -5.8470		15500.0	4.6863	4.5353	4.2215	15530.0	-22.2985	21.5991 20.9891	-9.6954 -1.6791
	-21.504 3	92.1860	63.49673		-47.7372	42.0089	-5.6173		16000.0	4.4314	4.2893	8. /207	16000.0	-21.6687 -21.0729	20.4121	-0.000
16500.0	-28.8236	89.8760	61.05243	16500+0	-4/.1082	41.7183	-5,3899		16500.0	4.1971	4.0631 3.0546		17002.0	-20.5083	14.8654	-0.643
1/000.0	-30.0735	88,8079	58. /345 1	17000.0	-46 .4727	41.3073	-5.1649		1/000.0	3.9812	2*0240	11 0 7 9 1				
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	XX 07CHAPPE	139,1164	CXX 288.9(30	field	бху -₀.	0 .	-0.		0.	439.6111	321.2521	160.8691	0.	-6.	0.	-0.
•	150. 1985 -	138.6628	248.9613	100.0	-7.6519	6.8879	-0.7641		100.0 200.0	398.1652 113.2258	303.7952 261.0789	701.8694 574.3047		-122.9160		- 57,9932
;	149.4861	137.9950	247.4443	200.0 300.0	-16.9703	13.4447 20.5566	-3.4754 -5.9770		300+0	236.4139	213.0564	449.5301	306.0	-202.7061	142.5266	-62.1793
		144.8510		400.0	-35.0633	28.0959	-6.9664		400.0 500.0	181.5309 144.3045	172.3641	353.4150 285.5252		-195.3550	147.3641 143.5577	
<u>ر</u>		131.1759	268.4000	500.0 500.0	-42.0855 -47.6645	35.1539 41.1458	-6.9338 -6.5188		600.0	118.8027	118.7481	231. 5528	0.000	-166.9554	136.5649	-30.3904
í	125.2361	121.4161	257.749) 245.6574	700+0	-52.0149	45.9747	-6.040?		100.0	87.4205	101.1029 88.9007	202.5371		-153.9310 -142.6925		-25.0258
1	117,4444	114.2652	2 35 . 71 115	800.0	-55.3839 -57.4980	49.7874 52.7915	-5,5965 -5,2065	D	400.0	11.2245	18.4001	150.0254		-133.1071	114.9249	-18.1842
;	113,9623	111.2631 105.4975	225+2254	900.0 1000.0	-60.0397	55.1736	-4. Roft	Derived	1006.0	67.1484	10.6121	139.8110 126.4927		-124.9231 -111.8767	108.7841 103.7634	-15.9391 -14.1733
1	104.0035	101.4769	205.9804	3100+0	-61+6464 -62.4370	57.0799 58.6169	-4.5665 -4.300"		1200.0	6215293 5819357	58.3053	120-4927		-111.7505	98.9933	-12.15/2
	99.4844 45.2449	47.7048 91.6695	197.1947 188.9144	1200+0 1300+0	+63.9208	59.8599	-4.0609		1300.0	52.2464	53.4428	105.0410		-106.3038	94.7016 90.9462	-11.5962 -10.6303
•	91.2402	89.8478	1 41.0780	1400.0	-54.1074	40.8622	-3.P457	0 1	1400.0	48.1106 44.4683	44.2014 45.4585	41. 3125 39. 9208	1500.0	-131.5766 -97.2714	81.4631	-9.8143
,	47.4495 87.8511	86.1942	1/3,641/ 166.5747	1500.0	-65.7120 -65.7598	61.6622 67.2896	-7.6498 -3.4712	Conductivi	V 1500.0	41.2221	42.1220	83. 3441	1600.0	-93.3812	84.2046	-9.1100
	H0.4217	19.4074	154.4351	1700.0	-66.0705	67.7623	-3.3082		L800-0	38.9080 35.6736	19.1261 36.4197	17+434l 72=0933	1100.0		81.JC/7 78.5575	-0.5120 -7.9859
1	17.1657 14.4527	16.2395 13.2043	153.4044		-66,2594 -66,3393	63.1008 63.3185	-3.15H6 -3.0208	×10 ⁻¹⁴	1300.0	33.2811	5.1.9634	51.2450	1906-0	-83.5081	15.1013	-7.5214
	11.0801	70.4091	141.1903	2000.0	-66.3211	A3.4274	-2.8937		210710	31.1019 29.1087	31.1213 24.0333	ウビ・ガビタ1 ンヴ・プリイン	2000.0		73.5748	-7.1686 -6.7395
	64.2417	67.5343	135.7760	2100.0 2200.0	-66.2145 -66.0285	63.4384 63.3614	-2.7763 -2.6671		2200.0	27.2420	21.5122	>>+0%2	2200.0	-15.5522	69.1541	-6.4081
;	67.31741 67.3174	54.8782 52.3355	125.2739	2300.0	-55.7711	63.2052	-2.5659		2300.0	25:0041 24:0609	26.3941	51.0442	2366 .C 2490 .P		67.1200 65.1878	-6.1084 -5.8359
	60.4612	59,9051	120. 1663	2400.0	-65.4500	42,4785 62,6894	-2.4715		2400.0	22.0338	24.5148 21.3605	45.6447	2500.0		03.3247	-5.5872
•	58.{1454 55.R364	57.5798 55.3547	115.6157	2500.0 2500.0	-65.0720 -64.6437	67. 1474	-2.3013		2604.0	21.3204	21.7190	43.0454	2600.0		61.0677 57.9426	-5.3591 -5.1434
	51.6794	53.2321	106.9121	2700.0	-04.1713	61.9471	-2.242		2700.0 2800.0	20.1138 18.9920	20.4096 19.3344	40. 5434 38. 3264	2100.0		50.3541	-4.4555
	51•4208 44•4554	51.2423 44.2634	102.8211 48.9198	2400.0 2400.0	-03.0603	A1.5084 61.0319	-2.1519 -2.084)		2900.0	17.9530	14.2733	30.22138	2910.1	-61.0132	50.0361	-4.1105 -4.6091
۲	41.1101	41.4120	45.1417	3000.0	-62.5430	60.5230	-2.0201		3000.0	16.9896 16.0952	16.3182	34.2831 12.4731	0.03CE 5106.0		55.3866 53.9997	-4.4541
1	45,9400	45.5441	91.6347	3100.0	-61.9459 -61.3284	50,9810	-1.9599 -1.9030		\$209.0	15.2639	15.5305	30. 1944	9 200 •U	-50.9018	52.6724	-4. 3094
, 1	44.1974 47.4719	44,9569 42,3462	84,2447 84,3945	3700+0	-60.6942	59.4754 58.8451	-1.9481	****	3300+9 3409+0	14.4905 13.7701	14./420 14.JU//	29.2324	3\$)L.O 3470.G		51.401C 50.1824	-4.1139 -4.0461
	41.0440	40,4049	81.9079	3400.D	-60.0468	54.7485	-1.7483	W 1	350.0	13.0985	13.3234	20.4219	3470.0		44.6141	- 3.9267
1	49.6161	39.3416	19.4578 16.1474	3500.0 3500.0	-59,3887 -58,7229	57.63P8 57.018P	-1.7499	44 1	3600.0	12.4/1/	12.684B	25+1565	3600.3		47.8935	-3.8138
•	** . 8 5 3 3	36.5844	13.4555	4700.0	-58.0516	56.3911	-1.+605		9.00°6 9.00°6	11.8867	12.0881 11.5301	23+4141 22+8682	3700±0 3800±0		40.1174 45.1841	-3.1016 -3.6010
:	15,5626 74,14,24	45.52HZ	70.840P	1,009F	-57.3770	55.7579 55.1213	-1.5796	0.001/	3900+0	10.8251	11.0014	21.8339	3,400.0	-45.3330	44.1909	-3.5120
	35.1546	37.9467	58.4475 65.1049	4000.0	-56.0249	54.4829	-).5420	63°K	4000+0	16 . 3443 8. 3435	10.5183 8.4870	20.8627	4000.0 4500.0		43.8363 34.5717	-3.4219 -J.6331
,	29.0313	21.9623	55.8915	4500+0 5000+0	-52.6923 -49.5173	51.3149 48.2733	-3,3773 -1,2439	00 1	5000.0	6.8544	6,9615	13.8223	5000.0	- 18 - 1400	36.0159	-2.7241
	24.0327 20.6291	23,795) 20,5349	47.7219 41.1449	5500.0	-40.5575	45.4237	-1.1339		- 5500.0 6000.0	5.1222 4.8434	5.8158 4.9222	11.5340 9.7456	5500.3		33.0150 39.4574	-2.4727 -2.2641
	17,9418	17.8456	15.7874	6000.0	-43.8314	42.7900	-1.0415		6 500 - 0	4.1494		5. 306/	6500.0	-37.3418	20.2537	-2.0880
	15.7355	15.5517 11.4565	41.4987 21.7440	5500.0 7000.0	-41.3366 -39.0602	40,3738 39,1650	-0.9529 -0.9352	Loi	1000.0	3.5927 3.1398		7. 2435 6. 3301	1000.0 1560.0		25.3382 24.6598	-1.9374 -1.8072
	12.4797	12.3111	24.6414	7500.0	-36,9841	36.1483	-0.9364	-9·8	8000.0	2.1666	2.8112	2.0110	9000-0		23.1779	-1.6934
	11,0471 9,4446	11,0375 9,9501	22.120H 19.94H9	8000.0 8500.0	-35.0915 -13.3623	34.3068 32.6232	-0.784P -0.7391		8509.0	2.4551	2.4973	4. 4505	8500.0		21.8006	-1.5731
	9.06*1	4.0200	18,0831	9000.0	-31.7800	31.0816	-0.1984		4000+0	2.1940		4.4234 3.9177	9000.0		20.6826 19.6233	-1.5042
	4.2574 7.5540	8.2346 7.5240	16.4760	9500.0 10000.0	-30,329) -28,9955	29.6670 24.3663	-0.6620		10000.0	1.7816	1.8103	3.5414	10 100 .0	-26.0188	18.6658	-1.3536
	A.4500	6.43840	14.8643	10500.0	-27.7669	27.1675	-0.5994		10500.0	1.61/5 1.4/51	L.6436 L.4988	3.2011			17.0034	-1.2083 -1.2295
	0.4117 5.9459	A. 4873	12.8035	11000.0	-26.6324 -25.5827	26.0600 25.0346	-0.5723 -0.5476		11500.0	1.3505	1.3122	2.1221	11203*0	-11.4234	10.2774	-1.1/59
	5.9459	5.9194	11.0167	12000.0	-24.6080	24.0831	-0.5249		12000.0	1.2411	1.1627	2+5021 2+39/1	12000.0		15.6104	-1.1268 -1.CJ16
	5.1542	5.L36A	10.2960	12500.0	-23.7022	23.1981	-0.5041		12500.L 13000.0	L.1444 1.0585		2.501			14.4267	-1.0378
	4.42#6 4.5127	4•91018 4•5129	9.6364	13000.0	-22.8582 -22.0701	22.3734 21.0032	-0.4847 -0.4669		13500.0	0.4820		1+3141	13500.0		13.8994	-1.0013
	4.2655	4.7476	P. 51 51	₹4000.0	-21,3329	20.4826	-0.4503		14000.0	6.9134 0.8518		1.8415	14000.U		13.4090	-C.9654 -C.9320
	4.024H 3.4067	4.00H) 3.7411	8.C328 7.6470		-20,6419 -19,9971	20.2073	-0.4348		15000.0	C + 196 1	0.4084	1.6051	15000.0	-13.4254	12.5245	-0.9009
	1.60%6	3.5940	7.2026	15500.0	-19.3829	18,9760	-0.4069		15500+0	0./458		1.5936			12.1244 11.7490	-0.8/18. -0.8445
	3.4/41 3.2643	3.4144	6.8476	16500.0	-18,8079 -18,2654	18.4137 17.883)	-0.3942		16500.0	0.6584	0.4640	1. 32 14	16500.0	-12.2148	11.3929	-2.8188.
	3,1123	3.1 003	5+2124	11000.0	-17.7527	17.3817	-0.3711	•	11000.0	0.6204	0.6303	1.2507	1/000.0	-11.8582	11.0634	-0.7447
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0.		109.1914	223.9844	0.	-0.	0.	•			14 14 .250 06			0.	-c.	0.	C. 2.9041
100 .0	115.2734	104+5441	223.9375	/ 100.0	-0.3303	2.4937	0. 2.1634		196.0 206.0	158.0578 155.4368	156.4306			3285.6964		1.833
100.0	116.4175	107.6884 FR6.9453	223.5625	200.0	-1.4315	4.2104	2.7789		300.0		149.9407		300.0-	1115.8608	1116.6625	0.801
400.0	116./56H	104+4776	223.2344	300.0 400.0	-3.0413 -4.7356	5.4045 6.4979	7.7632 1.7623		400.0	156.1077	147.0145				849.8377 691.9722	0.0954 -0.304
500 <u>.</u> 0	116.6900	106.1392	222.8281	500.0	-6.3570	7.6354	1.7784		5013.P	142.4(52	143.6285			-642.2768 -588.7958	588.2816	-0.514
500.0 700.0	116.5099)05.4104 FR5.4699	222.7203	600.0	-7.8997	8.8247	0.9250		100.0		135.6189		102 .0	-515.8891	515.2694	-0.619
809.0	115,4952	105-0751	721.0103	700.0	-9.3540 -10.8299	10.0770 11.2496	0.6529	Derived	800.0	134.4350	111.1938	264.6281		-461.8/13		-0.668 -0.688
980+8	115.6814	104.5545	720.3359	900.0	-12.248)	12.4471	0.1901	ngliagn	900.0 1000.0	L28.7355 L23.9484	126.6218	255.3574			414,5840 386,5389	-0.691
	114.93304	104,2009	214,69317	1000.0	-13.6430	13.6207	-0.0273		1100.0	119.2828	117.3596	2 36. 6 9 3 4	1100.0	-360.3110	359.6231	-0.6879
' ∠ 00 . 0	114.5152	103.2714	211.1266	1100+0	-15.0152 -16.3700	14.7650 15.8840	-0.25C7 -0.4860		1200+0	114.0342	112.1515	221.4015	1200.0	-337.9054 -318.9148	331.2250	-0.686:
	114,0535	102.5829	216.7344	.1300.0	-17.6964	16.9677	-0.7787	Conductivity	1300.0	110.0052	108.2730	2114.5522	1403.0	-302.5652	101.9028	-0.662
	113,0104		215.6875 274.5478	1400+0 1500+0	-19.0040 -20.2831	18.0775	-0.4765	CONDECTIVITA	1500.0	101.3805	44.6491	201.0302	1200.0	-266.2974	287.6433	-C.654
1600.0	172+4586	101-0053	213.4609		-21.5339	19.0559 20.0554	-1.2277	Conductivity	1600+0	91.2446	95,5510	1 42. 8006	1600.0	-215.6984 -264.4575	263.0518	-0.640
	111.8657		212.7813	1700.0	-22,7559	21.0274	-1,7285	710	1700.0 1900.0	93.2760 89.4625	81.4167	1 11.2192	1800.0	-254.3370	233.7022	-0.634
	10.60#4		211.0703 204.8281	1900.0	-23.9576	21.9771 72.9998	-1.9755		1400.0	85.8044	84.1853	164,9947	1400 *0	-245,1520	244,5215 236,1299	066.0 156.0
	109.4421	08.6047	209.5469	2000.0	-26.2500	23.7951	-2.7180 -7.4549		2760.0	82.4149 78.9760	HP./104 //.3894	161,0251	2000.0	-236.7571 -229.0364		-0.624
	108.2403	47.4172	201.7766	5100*0	-27.3559	24.6706	-7.6453		2100.0	15.1840	14.2181	150.00//	220C .0	-221.8966	221,2733	-0.623
	107.8271		2114.5469		-28.4335 -29.4779	25.5251 26.3547	-2.9084 -3.1237		2300.0	12.1492	/1.1941		2300.0	-215.2615 -209.0689	204.4403	-0.622 -0.622
	101-0841	96.0731	201.1563	2400.0	-30.4908	27.1599	-3.3309		2400.0	67.9912	68.110/ 67.5035			-20 3.2668	202.6436	-0.623
	105.5712		201.7655 200.3516		-31.4790	27.9493	-3.5707		2600.0	64.4621	62.9410	121.4042	2600.0	-197.8122	191.1918	-1.624
	1 114 . 79 44		148.4210	2500.0	-32,4378 -33,3694	28.7179 29.4695	-3.7199		2700.0	61.9591	60.4560	122.4151		-192.6686	192.C425 187.L768	-0.626
	104.0128	43.4677	19/.4805	2800+0	-14.2702	30,1959	-4.0743	W 2	2890+0 2900+0	54.5764 51.3686	55.02844	111.0614		-183.1952	187.5645	-0.630
	103,2204		146.0273		-35.1440 -35.9916	30,9954	-4.7386	V Z.	3100.0	55.1545	51.6809			-1/8.8163	1/8.18/7	-0.633
4100.0	1 111 . 61 1 5		193.0820		-36.8134	31.5972	-4.3944 -4.5479		32r0.0	55.0463 51.1411	51.83/5 44.6928	104, 1338 107, 8142		-174.6487	174.0119 176.0350	-0.640
\$200.0	100.7995	90.7441	191.5977	3200.0	-37.6097	32.9287	-4.6810		3300.0	44.2814	47.8421	91.1226	3300.0	-166.8808	100.2309	-0.643
4300.0 3490.0	99.99ns	90.1250 84.4474	190.1055		-38.3778	33,5655	-4.9]22	300°K	3409.0	47.5089 45.8220	44.U806 44.4036	53, 5895 40, 2256		-103.2521	162.6044 159.1257	-0.647
4500.0	98.3419	**.7595	187.1016		-39,1242 -39,8431	34.2885 34.7915	-4.9357 -5.0518	JUU N	3500+0 3600+t	44.2155	42.8069	57.0724	3600+0	- 156.4463	155.1903	-0.656
1600.0 1700.0	97.5019 96.6735	88.0974 87.4095	185.5439 184.0P20	3500.0	-40+5413	35.3811	-5.1601	•	3100.0	47.6450	41.2861	81. 9/12		-153.2492	152.5889	-0.660
1800.0	95.8430		182.5103		-41.2142 -41.8677	35.9526 36.5114	-5.20]a		3800°6 3800°0	41.2261 39.446h	14.3314 38.4366	H1. U641 78.2934		-156.1776	146.5548	-0.669
1900.0	95.0067		181.0459		-42.4948	37.0505	-5.356? -5.4441	770	4000.0	48.5111	51.1404	15.6520	4000.0	-144.3812		-0.673
4000.0 4500.0	94.1744		179 5313	4000.0	-43.1034	37.5774	-5.5261	77°	4500.0	12.7386	31.4156 26.5693			-131.6256		-0.696
5000.0	85.9158	75.5256	144.4414		-45.8289 -48.0787	47.0792	-5.8486 -6.0494		5500.0	28.1364 24.4213	23.1981	41.6233	5500.0	-111.6967	110.9560	-0.740
5509.0	HT.9061		157.0684	5500.0	-49.9069	43.751 A	-6.1552	*	6000.0	21.4645	20.2221			-103,//41	103.0142 96.0961	-0.159
6500.0	74.2734		142.9736		-51.3625	45.1742	-6.1983		6500.0 7000.0	18.9142	15.1542	32.5508	1000.0		90.0212	-0.791
/000.0	10.6850	65.35/2	1 16.2427		-52.4917 -53.3344	46.3747 41.2286	-6.1470 -6.1958		1500.0	15.0969	14.0515	2% 14 84	7500.0	-85.4515	84.0481	-0.802
7500.0 8000.0	67.7542 67.4989	62.5670 59.6944	129.8257 123.6982	7500.0	-53.9359	47.9201	-6.0159		8000.0	11.6169	12.6155		8000.U 8500.0	-80.6787	19.8667 75.5853	-0.812
8500.0	60.9058	56.4575	317.8613	#000+0 #500+0	-54. J21 7 -54. 5300	48.4157 48.7434	-5,9060 -5,7826		8200+0 4000+0	12.3498	10.3342	21 = 5 55 5	9000.0	-17.5553	71.7316	-0.823
4000.0	51.9768	54.3435	112.3203	9000+0	-54.5834	48.9327	-5.4505		9500.0	10.3057	9.4281		4500.0 10000.0	-69.0/22 -65.9059	68.2458 65.0787	-0.826
4500.0	57.5497	51.4550 49.4933	107.0475	9500.0 10000.0	-54,5062	48.9919	-5.5142		10000.0	4.4131 5.1409	H.6352 7.4195		10500.0	-03.0009	62.1890	-0.826
10500.0	50.1144	47.7516	47.3711	10500.0		48.944 <u>1</u> 48.8024	-5.3755 -5.2?7}		11000.0	8.0414	1.1254	15.41 78	11000.0	-60.3668	54.5425	-0.824
11000.0	47.7888 45.590 A	45.12/2	42.9160 88.7056		E2 4014	48.5816	->.'000		11500.0	7.5141 6.9971	6.7819 6.2972		11500.0	-57.4307 -55.6829	57.1099 54.8667	-0.820 -0.816
12000.0	43.5169	41.7102			-53.2625	48.2970 47.9541	-4.955 -4.H342		12009+0		5.8634	12+3558	12500.0	-53,6023	52.7916	-0.810
12200-0	41.561 0	74.4073	1044011	12500.0	-57.2707	47.5641	-4.7065		13000-0	6.1132	5.4134	11.5866	13030-0	-51-6711	50.8668 49.0764	-0.804
13000+0 14500+0	39.7160 37.0757	37.7015 36.0973	1144117	1 2000 h	-61 7100	47.1368	-4.5831		14500.0		5.1215 4.8628		13500.0		41.4070	-0.769
14000.0	16.331 6	54.5595	1010717	14000.0	-51.1409	46.6771 46.1971	-4.463A -4.34H7		14500+0		4.51 32	9.5810	14520.0	-46.6282	45.8468	-0./81
14500.0	14.7797	77,1134		14500.0	-49.9233	45.6854	-4,?380		15000+0	4./860	4.2442		15000.0		44.9854 43.0138	-0.172
15000.0	33,3142 31,9286	31 • 7449 30 • 44 R4	0340341	15000.0	-49.2940	45.1626	-4.1374		15500.0		4.00/8 3./865		15500.0	-42.4788	41.7239	-0.754
16000.0	30.6188	29.2206	3-0344	14000-0	-48.6562 -48.0134	44.6272 44.0829	-4.0290 -3.9305		16500.0	4.7556	3.5830	1.6387	15500.0	-41.2544	40.5688	-0.745
15500.0	24, 374 A 28, 206 A	28,0569 26,9538	57.4465 55.1684	14500 0	-67 3686	43.5374	-3.8340		17000.0		3. 1956	1.2443	11000.0	-40.6981	39.3620	-(.736)

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tield	Vxx	σχχ	, UXX	field	бху	σxy	бху		field	OXX	б×х	QX X	field	σχλ	Фху	σху
0. 100.0	1/0.5856	165.24/4	345.8340	0.	- O .	0.	0.			63375.88714		816,7177	0.	-0.	0.	-0. -260.3969
200.0	170.0520 167.8065	164.1088 161.5155	334.16C8 329.3220	100.0 200.0	-10.8388 -21.8104	10.6810 20.3528	-0.1578		100.0	445.7674 341.4893	315.6714	761,4388 640,5451		-226.5403	57.2421	-198.3346
0.00	163.1215	158.0651	321. 1925	300.0	-32.0062	29,2211	-2.7851		400.0	755 9947	247.6915	518.6963	300.0	-253.2598	109.1204	-144.7394
400.+0 500.+0	158.3756	153.8304 148.905C	312.2060 301.2017	400.0 500.0	-40.9103 -48.4365	37.3685 44.7160	-3.5419		400.0 509.0	144.7844	222.2213	420,0112 344,4679	400.0	-237.1281 -219.0235	135.3950	-73.0236
600.0	145.9086	143.4475	289.3564	600.00	-54.6919	51.1906	-3,5012		6011.0	124.7065	156,8779	285,5843	600.0	-202.2504	148.1172	-54.1331 -41.4847
800.D	139.4476 133.0661	137.6367	211.0863	700+0 803+0	-59.4513 -64.0904	56.7703 61.4816	-3.C810 -2.6088		199.9	1112,4520	124.1945	241,5565		-187.3245 -374.1026	145.8405 141.3611	-32.7415
400.0	120.0424	125.6078	252+4503	403.0	-67.5595	65.3850	-2.1745		900.0	42.075H 19.0071	913.0254 08.1974	205,4522	900.0	-162.3494	135.8559	-26.4925
1100.0	120.8163	114.0326	240.4489 228.8054	1000.0	-70.3785 -72.6418	68,5586 71.0869	-1.8199	N to - d	(000.0	48.5219	95 . 7048	154.2767	1000.0	-151.8562 -142.4528	129.9713 124.05R7	-21.9849 -}8.3940
1200.0	109.4295	108.1541	217.5030	1200.0	-14.4243	73.0524	-1.3719	Derived	++nn.n +200.0	59.4677 57.9145	75,256) 66,5801			-133.9993	118.3117	-15.6876.
1300.0 1400.0	104.0864 98.984j	102.1371	206.8240	1300.0	-75.7881	74.5316	-1.2565		+ 400 • 0 + 400 • 0	47.0452	57. 41 91	196.3644		-126.3775	112.8310	-13.5464 -11.823ª
1500.0	94.1233	91.5657 52.6451	196.5500	1433.0 1503.0	-76.7861 -77.4648	75.5936 76.2995	-1.1925		+ 400+0	42.120) 48.9554	53.1927 47.9893			-119.4869	107.5629 102.8224	-10.418*
1400.0	d¥.5034	81.9413	117.4941	1600.0	-77.8657	76.7028	- 1.163C	Conductivity.	(600.0	14.4081	47.5755	17.9435	1500.0	-107.5631	98.3058	-9.2563
1700.0 L800.0	60.9/38	83.58/5 /9.4336	168.7097	1/00.0	-/8.0263 -77.9801	76.8499 76.7813	-1.1764 -1.1987	Conductivity	1700.0	41.9452	19.1044	71.9464	1700.0 1800.0	-102.3889	90,1938	-9.2958 -7.4668
L400+0	11.0532	15.5196	152.5/28	1400.0	-11.1512	76.5319	-1,2253	×10-14	+ 900 * 0	28.1408 26.4515	74.3775 74.4910		1900.0	-93.3284	85.5596	- f . 759R
2000.0 2100.0	13.3522 69.8621	11.8361 68.3726	145.1083 138.2341	2000.0	-77.3845	76.1318	-1.2527	×10 ···	2000.0	74 .4 702	30.9472	55.4124	2000.0	-89,3488 -85,6839	83.1768 80.0283	-6.1720 -5.6555
2200.0	66.5/34	65.1158	1 31.6852	2100.0	-76.8859 -16.2822	75.6069 74.9794	-1.2790		2108.0 2200.0	72 . 121 9 21 .1 /87	24.7055 24.7252	51, 47 74 47, 9040	2100.0	-82.3004	77.0935	-5.2068
2.100.0	63.4/61	62.0558	125.5319	2300.0	-15.5919	74.2685	-1.3233		/300.0	10,8100	74.9644	44 7734	2400.0	-79.1591	74.3551	-4.8141 -4.4697
2400.0 7500.0	60.5601 51.8153	59,1804 56,4703	119.7405	2400.0 2500.0	-74.8309 -74.0131	73.4905 72.6592	-1.3404		2400+0	18.5902	23.3402	41.9803 31.4767	7400.0	-76.2048	71.79AL 69.4014	-4.7636
2600.0	55.2315	53.9386	109.1701	2600.0	-73.1505	71.7866	-1.3635		*500 <u>*</u> 0 2500 <u>*</u> 0	17,4084	20.7070	41.2238	2400.0	-71.0498	67.1574	-3.8924
;800°0 >100°0	56.5C86	51.5566 49,3045	104.3497 99.8131	2733.3	-72.2532	70.8826	-1.3707		7 700.P	15.4410	10.5576	45.1 884	2700.0	-48.7019 -66.5059	45.0515 63.0723	-3.6504 -3.4336
1400+0	48.3510	47.1968	45.5418	2800 .D	-71.3301 -70.3886	69.9557 69.0132	-1.3744		5800°0	14+879A 14+099(18,5349 17,5657	33. 34 34 71. 6846	2900.0	-64.4480	61.2095	-3.2385
1000.0	46.31/8	45.2005	91.5183	1000 .J	-69.4351	- 68.0610	-1.3741		4000.0	12.4731	15.5999	40.1377	3000.0		59.4537	-3.0024
\$100.0 \$200.0	44.4004 42.5926	43.3204 41.5078	87.7263	3100.0	-68.4748	67.1043	-1.3765		4100.0	17.4720	15,9850	29.7740	3100.0	-58.9881	57.7965	-2.9028 -2.7577
0.0066	40.8858	34,6902	80.1100	3203.0 3303.0	-67.5123	66.1472 65.1932	-1.3651 -1.3581		3200.0	12.2545 11.7480	15.1755	21.4+94 24.7576	3300.0	-57.3736	54.7483	-2+6253
5400.0 5500.0	34.2738 31.1504	38.3161 36.827C	71.5899 14.5154	3403.0	-65.5950	64.2453	-1.3497	. W2	3400.0	11.2129	13.9841	25.1560	3400.0	-55.8481	53.3439 52.0116	-2.5042
\$600.0	36.3090	35.4232	11. 7330	3503.0 3603.0	-64.6459 -63.7363	63.3059 62.3769	-1.340C -1.3294	· ** Z	4500.0 4609.0	10,4420 10,4725	17.7045	24,1404 23,1976	3500.0	->3.0367	50.7459	-2.3929 -2.2908
3700.0	34.9465	34.0933	69.0358	3700.0	-62,7778	61.4598	-1.318C		4709.0	10.0414	12,7748	27.3207	3700.0	-51.7389	49.5474	-2.1964
9.0086 9.0096	33.6555 32.4322	12.8343 11.0414	66.4891 64.0736	3800+0	-61.8618	60.5560	-1.3058		1480.8	9.6851	11.8150	21.5017	3900.0	-50.5058	48.3966 47.3044	-2.1092 -7.0284
4000.0	31.2721	30.5105	61./826	3903.0 4003.0	-60.9595 -60.0717	59.6665 58.7919	-1.293C -1.2799	63°K	4000.0	0,1520 9,0411	4898.15 4876.01	20. 01 99 20. 01 99	4000.0	-48.2157	46.2625	-1.9532
4500.0 5000.0	26.2897 22.3928	25.6551 21.8586	51.9448 44.2513	4503.0	-55.8089	54.6588	-1.2100	UJN ,	4500.0	7.1449	0.7H4+	11.0744	4500.0	-43.3437	41.6973 37.9863	-1.6464 -1.4220
2200.0	19.2963	18.8415	38,1382	5000.0 5500.0	-52.0/32 -48.6695	50.9341 47.5986	-1.1351		5500.0	6.1472	# 0110 7.0091	14 . 1 487 12. 9565	5500.0	-36.1608	34.9092	-1.2516
1000.0 5500.0	16.000 14.761 C	16.4098	33.2698	6000.0	-45.6234	44.6161	-1.0073		5000-0	5.4(:4)	6.2021	11.5061	6000.0	-33.4322	32.3142	-1.)180
1000.0	13.0755	12.7/99	29.1837 25.8554	6506.0	-42.8955 -40.4472	41.9467 39.5518	-0.5489 -0.8954	498	6500.C	4,7642	5.5375	20.3057	6500.0 7000.0	-31.2045	30.0939	-0.9225
/500.0	11.6672	11.466	23.0/41	7000.0 7500.0	-40 .4472	37.3968	-0.8467		7900.0	4.3147 3.9761	4,9802 4,5083	9.2044 9.4304	7500.0	-27.3751	26.4862	-0.8489
3000.0 3500.0	10.4789 9.4670	10.2479 4.2605	2C.7268 18.7279	8000.0	-36.2534	35.4511	-0.8024		8000.0	4.5454	4.0995	7.5439	8500.0	-25.7842	24.4977	-D.7865 -D.7329
r000+0	8.5984	8.4134	1/.0118	8500.0 9000.0	-34.4500 -32.0102	33.6881 32.0852	-0.7619		4000.0	3,2885	4.7441 1.4317	7 <u>0</u> 9326 504603	9000.0	-23.1678	72.4816	-0.6863
0.0004	7.8471 7.1928	7.68C2 7.0414	15.5273	4202.0	-31.3139	30.6227	-0.6912		4500.0	2.7040	4.1600	3.9540	9500.0	-22.0527	21.4072	-0.6455
200.00	6.6192	6.4814	13.1667	10000.0	-29.9442 -28.6863	29.2839 28.0545	-0.6602	•	0000.0	2.5854	7.9172		0000.0	-21.04/3	20.4319	-0.6094 -0.5772
1000.0 1500.0	6.1116	5.58/6	12.1012	11000.0	-21.>215	26.9221	-0.6055			7.4004	2.7008	4.73.48	1,000.0	-19-2753	18.7259	-0.5484
1000.0	5.665 J 5.266 Q	5.15491	11.2150	11500.0	-20.4571	25.8759	-0.5812		11 500.0	2.0917	2.4377	4.4144	1500.0	-18.4993	17.9770	-0.5223 -0.4987
1500.0	4.4085	4.8162	9.7182	12000.0	-25.4655 -24.5446	24.9068 24.0067	-0.5587 -0.5379		2000.0	8440.1 F058.1	2.1754 2.0431	1,8514	2500+0	-17.1207	16.6435	-0.4772
1000.0 1500.0	4.5872	4,4461 4,2125	9.0832 8.5657	1300.0	-23.6872	23.1687	-0.5184		14090.0	1,7070	1.4018	1.6108	13000.0	-16.5054	16.0479	-0.4575
·JUU.0	4.0 14 4	1.9556	1.9500	13500.0	-22.8970 -22.1387	22.3867 21.65>3	-0.50C3 -0.4834		4500.4	1.5087	1 <u>.7851</u> 1.6788		1400.0		14.9751	-0.4394 -0.4226
· 200.0	· 3.1456 3.5111	3.1226 3.5089	7.5175 1.0866	14500.0	-21.4373	20.9697	-0.4675		4000.0	1.4218	1.5P/34	3-0021	4500.0	-14.8976	14.4903	-0.4073
.500.0	3.1/85	3.31.35	6.6523	15003.0	-20.1787 -20.1590	20.3260 19.7203	-0.4527		5000.0	1.4414	1.4901	4 6 0774	15900.0 15500.0		14.0355 13.0082	-0.3930 -0.3796
-000.0 500.0	3.1956	3.1350	6. 3 106	15500.0	~19.5/50	19.1494	-0.4255		15000.0	1.2694 1.2004	1.4071	2.537	6000.0	-13-5729	13.2058	-0.3672
500.0 1000.0	3.02/5 2.8724	2.9/04 2.8186	5.5979 5.6910	16503.0	-19.0236	18.6105	-0.4131		*******	1.1374	1.7407	2.107A	16500.0	-13.19)7	12.8752	-0.3556
				1/000.0	-18,5023	18.1009	-0.4014		· /000.0	1.0795	1.1950	2.7744			120-010	-0.3446

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freid	۳ «xx	۲ ۲×۲	Схх	field	σ×̈́y	б×у	бху		field	σxx	σŦx	_ Cx x	field	σxy	σxy	бху
0. 109.1	1 13 . P6 78 1 17 . 4423	213+1342	245.0020 744.9654	0.	-0.	0.	-0.		0.	1 49.9114	213.0226	402-9340	0.	-0.	, o.	0.
200.0	199.7441		244.8557	100.0 200.0	-1,5936 -3,1485	1,3392 2,6959	-0.2443 -0.4527		100+9	197.0687	207.6569	400.1756	100.0	-7.4192	18.5205	11.1013
466.0	134,2127	ւլը, գեղ գ	744.5704	300.0	-4.7102	4.057 B	-0.4574		200.D 307.0	193.4354	201.0564		200.0 300.0	-19.7372 -31.3959	30.7460 41.3075	11.0148
500.0	135.6347 141.6466	110,7922	744 . 41 114	400.0	-6.2886	5. 3881	-0.9005		400.0		158.1018		400.0	-41.5356	50.7774	9.2418
500.0		110.4572	244.0751 244.6577	500.0 500.0	-7.8860 -9.4939	A.6946 7.9933	-1.1895 -1.5106		500.0	179.8144	181.3778	361 1427	509.0	-50.2544	59,1326	8.8582
P111, 0	1.43 214.58	110,1005	241.1433	100.0	-11.1025	9.2539	-1.9486	•	A00.0	173.649)	1 /4.0/25	347-1616	A00.0 700.9	-57.7877 -64,7810	86.4080 77.575P	8.6203 8.3948
#110 "J	132,7721	100.4117	247.5848	800.0	-17,7041	10+5176	-2.1925		100.0 ND0.0	147,3740	159,190H	333.9840 370.0329	800.0	-69.8773	78.0135	8.1361
000.0	1 12 1141 1	1104.5071		0.000 1000.0	-14.2931)1.7570 12.9894	-7.5361 -7.4761	Destined	400.0	1 14 .32.50	151.1479	304.0739	900.0	-74.6752	P2.4945	7.8183
• * D(1, P	1 42 . 4054	104.7948			-17.41 92	14.2074	-3.7109	Derived	1000.0	147+8394	144.4024	242-7404	1000.0	-78.7567 -82.1859	86.1897 89.1697	7.4330 6.9828
\$00°0 \$00°0	1 41 . 1 / / 5	1 94 . 4074			-18.4486	15.4092	-3.5395		1100.0	141.4311 145.1476	190.2169	278.6460	1200.0	-85+0250	91.5008	6.4759
400.0	130,0509	107.5211			-20.4547 -21.4347	15.5030 17.7575	-3.8675		1100.0	1 20 07 16	171.5042	252 . 52 79	1300.0	-87.3311	97.2549	5.9238
· >00, 0	24.4540	107,0419	246.4999		-21,347	14,9013	-4.4860	0	1400.0	123.0876	111.4504	240.1380	1400.0	-89.1590 -90.5605	94.49PO 95.7942	5.3390 4.7337
1.500.0	129.4317	106,5382	235, 3649	1400.0	-74,8114	20.0244	-4.7920	Conductivity	1500+0	111.8586	105,0457	228.2549	1600.0	-91.5847	95.7036	4.1193
1900.0	174.1764 127.4882	105.5645	244.1843 232.4577	1900.0	-20.2063 -27.5714	7).1271 72.1998	-5.0977		+ 700+0	105.5900	00,5179	204-1028	1/00.0	-92.2758	95,7817	3,5058
1 400.0	176.7144		731.4778	1.00.0	-29.0063	27.2532	-5.4531	X10 ¹⁴	1800.0	111.5597	94.2919	145.9506	0.0081 1900.0	-92.6771 -92.8260	95.3401	2.9018 2.3141
2000.0	126.0375	104.3124	230. 4449	2000.0	-30,2109	74.2411	-5.9?76		1900.0	96.75#3 92.2134	89.3750 84.7557	184.1433	2000.0	-92.7570	94.5053	1.7484
2700.n 2200.n	125.2164	103.7106	274.9473	2100.0 2200.0	-31.4848 -32.7284	25.2896 76.2776	-6.1952 -6.4558		2.00.0	R F , qRQA		168.3131	2100.0	-92.5007	93.7095	1.2088
/100.0	1/1 . 6979		226.1547	2300.0	-33,9416	27.2323	-6.7093		2200.0	83.7910		3 60 .1494	2300.0	-92.0845	97.7830	0.6985
2400-0	172.8730		224.6901	2400.0	-35.1246	28.1688	-6.9558		2400.0	79,9089 16,2345		152.4413 145.2234	2400.0	-90.8660	90.6388	-0.2272
2509.9 2500.0	127.0361 127.1837		273.1965 221.6763	2500.0	-36.2775	29.0825 29.9735	-7.1951		2500+0	77.7589	65.6575	1 48 .47 1 4	2500.0	-90.1035	89.4676	-0.6409
2700.0	120 2120		270.1311	2500.0	-37,4007 -39,4944	20.8471	-7.4273 -7.6523	•	2600.0	59.4721	62.5289	1 37 .0010	2600.0	-84.7617	88.2395 86.9830	-1.0237 -1.3703
2800+0	114.4170		718.5633	2400.0	-39.5599	31.6885	-7.9703		2700.0	55.4251	54•ንበ3። 56•ጽ638	125.9684	2700.0 7800.0	-88,3537 -87,3921	85.7047	-1.6874
1000°0	118.9449		215.3669	7900.0 3000.0	-40.5943	32.5132 33.3162	-8.0811 -8.2848	14/ 2	290010	50.6493	54.2954	114,0451	2000.0	-86.3883	P4.4139	-1.9744
4100.0	116.7283		213.3004	3300.0	-42.5794	34.0980	-8.4814	W 3	4000.0	58+0233	51.5877	144.9110	3000.0	-85.3510	43,1184	-2.2325
3700.0	115,8058	96.2946		3200.0	-43.5297	34. 9587	-8.6710		4.00"0	55.5401		105.1481	3100.0	-84.2882 -83.2069	81.8249	-2.4533
4400.0	114.4749	95.5698	210.4447	3300.0	-44.4522	35.5986	-9.8576		3200.n	53.1913	47.5050	100.5474	3300.0	-83.2009	80.5385 79.2635	-7.6684 -2.8494
3400.0 3900.0	113.9365	94.8375 94.1(141	208.7761 207.0957	3400+0	-45.3474 -46.7154	36.3181 37.0173	-9.1993 -9.1991		3400.0	60.9692 48.8663	45.5114		3400.0	-41.0113	78.0034	-3.0079
1600.0	112.0409	44. 164.5	205.4051	3500.0 3600.0	-47.0566	31.6964	-9.3602	300°K	1200-0	45.4751	41.8711	48.7447	3500.0	-79,9965	76.7609	-1.1456
4700,0	111.0850	97.5205	203.7055	3700.0	-47.6714	78.3559	-9.5155	500 N	3600.0	44.9895 43.7030	40.2079 38.6397	H5 .1 0/4	1700.0	-78.8022 -77.7016	75.538J 74.3368	-3.2640 -3.3648
380A.0 440A.0	110,1248	91.8755	291.9981	3800.0	-48.6602	38.9959 34.6166	-9.6643		1700.1 1800.0	41.5096	31.1597	18.6694	3800.0	-76.6073	73.1581	-3.4493
4000.0	108.1942	91.1742 90.3796		3900.0 4000.0	-49,4232 -50,1608	40.2184	-9,9424		1910.0	14.0030	35, 76° P	15.4457	3900.0	-75.5218	72.0028	-3.5189
4500.0	103.4388	PA.5855		4500.0	-53.4R74	47.9575	-10.5299	7701/	4000.0	38.1807	34.4402	12.8208	4000.0 4500.0	-14.4468 -69.2775	70.8717 65.583P	-3+5751 -3,6937
5000.0	98.4994	82.8005		5000.0	-56.7296	45.2537	-10.9759	77°K	4590.9 5080.0	41 •8400 26 • 7441	28,81159 24,4450	50,6464 51,1901	5000.0	-64.5193	60. 9977	-3.6282
5500.0 5000.0	44.74/1 89.0471	19.0546	172.7957 164.4918	5500.0 6000.0	-58.4559 -60.2162	47.1583		•••••	5500.0	12.1756	71.0056	43.7*)0	5500.0	-60-2014	56, /385	-7.4630
6500.0	94.6142	11.8354		6500.0	-61.5549	49.9793	-11.6366		6000.0	19.51 80	18.2455	17,7635	6000.0 6500.0	-56.3098 -52.8115	53.0591 49.7987	-3.2507
1000-1	90.4119		148.7124	1000.0			-11.6857		6500.0 7000.0	14.8138	15.9485 14.1454	37,926h 28,9597	7000.0	-49.6674	46.8700	-2.7973
7500.0 8000.0	76.2050	45.1078 61.4508		7500.0		51.5586	-11.6114		1500.0	13.0447	12.5947	75.6644	7500.0 8000.0	-46+8374	44.2541	-2.5834
85KG.0	68.6026	54.9442	127.5508	8500.0	-03.P275	52.3175	-11.5100		R000.0	13.6168	11.2975	72,9143	8500.0	-44.2847 -41.9755	41.8493 39.7707	-2.3854 -7.2049
4000.0	65.1074	55.1456		9000.0	-63.8198		-11.3778		9000+0	10.3955 East.P	10.1905 9.2419	20,586) 19,6021	9000.0	-39.8807	37.8390	-2.0417
9509.0 10000.0	58.7056	57,7914 50,8719		9500.0	-63.6508 -63.3474	52.2988	-11.2220		9500.0	A .475R	P.4270	15,8047		-37.9741	34.0793	-1,8948
10500.0	55.7H3H	48.4123	104.1461	10500.0	-62,9324	52.0702	-10.8622		10000.0	1 - 11 46	7.7111	15.4258	10000.0	-36,7336 -34,6397	34.4705 32.9949	-1.7630 -1.6448
11000.0	54,0763	46.)270	99.1633	11000.0	-62.4256	51.7587			10500.0	7.0557	7±0848 6±5415	13,0217	11000.0	-33.1757	31.6371	-1.5386
+1509.0	50.4537 48.0265	47.9890 41.9346		11500.0		51.3781	-10.2618		11500.0	5.4760	6.0579	12.0338	11500.0	-31.8272	30,3840	-).4432
.2200.0	45.7454	40.0145		12500.0		50.4557	-10.0565		12000.0	5.5114	5+6282	11.1596	12000.0	-70.5816 -29.4281	29.2244 28.1485	-1.3572 -1.7796
14000.0	41.6111 3	34.2044	81.RU47	13000.0	-59.7836	49.9320	-9.8516		12500.0	4.785b	5.2440	LO, 3973 9,6880	13000.0	-28.3571	27.1477 -	-1.2094
14000+0	41 • 7474 19 • 6494	36.494H 34.98/8	78.0807 74.5777	13500.0	-59.0265 -58.2480	49,3781 48,8000	-9.6484 -9.4480		14500.0	4.4778	4.5925	9,0654		-27.3605	26.2147	-1.1457
14500+0	47.905 4	37, 3615		14500.0		49.2033	-9.2509	1	14000.0	4.1911	4.3136	8,5047		-26.4309 -25.5639	25.3431 24.5270	-1.0350
15000.0	36.1254	31,9254	68.1517	15000.0	-56.6505	47.5927	-9.0577	,	14500.0	3+93/1 3+/072	4.0610 3.8313	7,4480 1.5385	15000.0	-24.7481	23.7514	-0.9860
16000.0	14.6447 33.1534	30.5692 29.2840	A5.2177	15500.0		46.9724			15500.0	3.4985	3.4219	7.1204	15500.0	-23.9943	23.0470	-0.9473
16500.0	41,7474	29.2040	59.4748			45.7156	-8,5054	•	16000.0	3.3084	3.4304	6.7388		-23.2662	22.3646 21.7258	-0.9016
11000.0	30.421 A	26.9314			-53.4155	45.0846	-8.3300	1	15500.0	7,1347	3,254R 3,0934	6,3845 6,0688		-21.9519	21.1225	-0.A294
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	1126.00006			٥.	-0.	0.	0.		0.	1407.7364	896.6426	2 304. 3790	0. 100.0	-0.	0. 302.6244	-0. -378-4534
100.0	258.0658	235.1854	443,251/			2893.0378	22.5431		200.0	539.2325	>70.4444	1109.6769	200.0	-653.2232	466, 5583	
200.0	227.3699	207.9005	435.2704		1461.2544	499.1157	4.8972 -1.285C		300.0	328.8829	366.8780	695. 7609	300 .0	-552.8333	462.4817	
	204.3620	142. 3762	396, 7382	400.0	-114.9034	//1.4864	-3.4170		400.0	221.9602	247.5821	464.5423 338.2682		-467,2894 -401,1442		-56.4789
500.0	193.9362	184. 3/84	318.3140			638.6659	-3.6862		600.0	120.3472	135.8338	250.1010	60 3 • 0	-349.6612	317.0927	
600.0	189.6915	175.4968 166.0512	359.1285		-555.4745 -494.2242		-3.2168		100.0	94.1031	107.32/1		760.0	-309.0164	282.1416	-26.2688
100.0	103.5214	156.4014	320.0922			446.4756	-2.1057		800.0 900.0	15.4043	81.2611 12.5401	163.1 <i>1</i> 11 133.2297	900-0	-276.4022 -249.1995	254.7635	-21.6387
4CU.+	154.2098	146.8415	301.0511			411.2769	-1.8214		1000.0	52.8021	61.3874	114.1855	1000.0	-221.7605	212.2538	-15.5067
1000.0	145.1296	131.5/89	202.1086		-364.2451	382.8C07 359.0703	-1.7445 -1.8347		1100.0	45,2032	52.7185	97.9216	1100.0	-209.2388	195.7971	-13.4418
1160.0 1200.0		120.4117	248./103		-340.8638		-2.0427		1200.0	34.2263 34.4320	45.8365 40.2748	85.0628 14.1067	1 100 -0	-193,4755 -179,4059	181.6633	-11.8122
1300.0	120.5165	112.6103	255.1268		-323.5354		-2.3232	Derived	1400.L	30.5208	15.7111	66.2318	1400.0	-168,1078	158.6690	-9.4388
	113.3181 100.5148	105.3444	218.6625			305.6646 291.1676	-2.6398 -2.9656	DELIACO	1500.0	21.2831	31.9168	59.1999	1500.0	-157.7577	149.1979	-8.5597
1600.0	100.5140		192.5070	1600.0	-242.5035	279.2214	-3.2820		1600.0	24.5693 22.2692	28.7255	53.2948 43.2835		-148.6053	133.2530	-7.8242 -7.2015
1700.0	94.2111		190-1401	1/00.0	-271.3768	267.8014	-3.5774 -3.8450		1 401. 0	20.3009	23.6903	43.9412	1800.0	-133.1492		-6.6683
1900.0	80*0145 80*0145		164,9144 154,8298	1900-0	-251.1007	257.3357 241.6849	-4.0816	Conductivity	1900.0	18.6024	21.6820	40.2844		-126.5648	120.3565	-6,2083
2000.0	18./196	/1./455		2000.0	-243.0436	238.1571	-4.0816 -4.2866	CONTRACTA	2000.0 2100.0	17,1253	14.9344	37.0397 34.2360		-120.5994	114.7914	-5.8080 -5.4553
2100.0	14.2345	67.5311	141./856			230.45(6	-4.4607 -4.6057	Conductivity	2200.0	14.6934	11.0552		2200.0	-110.2049	105.0608	-5.1442
2200.0	10.1013	63,6334 60,0262	133.1141			222.6995 215.4444	-4.7240	X10 ···	2 300+0	13.6848	15.8610	29.5458		-105.6495	100.7827	-4.8668
2400.0	62.6443	50.6454	119.3297	. 2400.0	-213.4537	208.6355	-4.6182		2400.0	12./873	14.7982			-101.4542 -97.5778	96.8359 93.1836	-4.6183 -4.3942
2500.0	59.2941	23. 2844	112.8886		-207.1209		-4.8907		2600.0	11.2044	12.7956			-43.9853	89.7940	-4.1913
2600.0 2700.0	54.1851 54.7851	50,7162 48,0487	101.1317		-195.4696	190.4888	-4.9441 -4.9808	•	2700.0	16.0152	12.2215	22.8421			46.6398	-4.0671
2800.0	54.5813	45.5643	46.1506	2800.0	-190.0960	185.0931	-5.0029		2400.0 2400.0	10+0280 9+4953	10.9033	21.5612 20.3985		-81.5362 -84.6307	83.6975 80.9468	-3.8387 -3.6839
2400.0	48.0595	43.2624	41.3/14			179.9801	-5.0109	•	3000.0	9.0104	10. 1304				78.3695	-3.5414
1000.0 1100.0	43.7(55 43.5(66	41.1140 39.1111	86.8196 82.61 <i>[[</i>			175.1282 170.5177	-5.0001		3100.0	8.5619	9.8076	18.3/55	3100.0	-19.3598	75.9445	-3.4102
1200.0	41.4508	31.2414	18.6421	3200.0	-1/1.1129	166.1314	-4.9814		3200.0 3304.0	8+1629 7+7913	9.3294 8.8908	17.4923	0.005£ 3300.0		73.6732 71.5285	-3.2888 -7.1754
\$ 100.0	39.5212	35.4957	15.0229			161.4535	-4.4560		3400.0	1.4496	8.48/5	15.93/2	3400.0	-72.5142	69.5039	-3.0703
1400.0 1500.0	31.1251 36.9172	33.0020 32.3343	11.5886	3400.0	-162.8945	157.9696	-4.9249 -4.8890	11/0	3500.0	1.1341	8.1161	15.2508			67.5899	-2.9722
1600.0	34.4531	10.4020	65. 1751	3606.0	-155.3829	150,5338	-4.8491	W3	3600.0	6.8438 6.3743	1.1131	14.6169	3600.0 3700.0	-68.6577	65.7778 64.0548	-2.8799 -2.7933
\$700.C	32.4651	29.5545	62.5242			147.0592	-4.8060		1100.0	6.3248	/.4558 /.1617		3800.0		62.4283	-2.7124
4800.0 3900.0	31.5678 10.2529	28.2972	54.8650 51.3641			143.7335	-4.7503 -4.7124		3900.0	6.0929	6.8835	12.9814	3900.0	-63,5133	60.8176	- 2.6 357
4009.0	29.0150	25.9961	55.011/		-142.1556		-4.6628		4000.0 4500.0	5.8771 4.9939	6.6344	12.5115		-01.9650 -55.2304	59.4016 52.9746	-2.5635
4500.9	21.8017	51.3041	45.1114		-128.3420		-4.4012	63°K -	5000.0	4.1939	5.5456 4.8348	10.5895	5000.0		47.7987	-2.0158
5000.0 5500.0	19.8492	1/./652	31.6144 31.8242		-116.8684		-4.137C -3.8849	UJ N	5500.0	3.8611	4.2/31	8.1408	5500.0		43.5433	-1.8223
6000.0	14.3909	12.8811	21.2120				-3.6507		6000.0 6500.0	3.4961 3.2041	3.8375	7.3336	6000.0 6500.0	-41.0474 -38.4944	39.9840 36.9639	-1.6634 -1.5305
6500.0	12.4705	11.1653	23.6358		-91.8/63		-3.4360		1000.0	2.9704	3.4955 3.2220	6.6996 6.1924	7000.0	-35.7872	34.3698	-1.4174
7009.0 7590.0	10.914C 9.6363	4.1/50 8.0354	20.6846 18.2717	1000.0 1500.0			-3.24C3 -3.C624	L°K	1500.0	2.1804	2.9999	5.7803	/500.0	-33.4383	32.1181	-1.1202
8000.0	8.5755	1.6840	16.2644	0.0004			-2.9006	4 11	8000.0 8500.0	2.6238	2.8168	5.4406		-31,3810 -29,5647	30.1455	-1.2354
a500.0	1.0855	6.8453	14.5868	8500.0			-2.7534			2.44931 2.3828	2.6642	5.1572 4.9182	9000.0	-27.9496	26.6542	-1.1612
9000.0 9560.0	6,4320 6,2885	0.2233 5.0446	13,1553 11,9381	9000.0 9500.0			-2.6191 -2.4964		9560.0	2.2880	2.4258	4. 1144		-20.5042	25.4675	-1.0367
10000.0	5.1341	5.1559	10.8406	10000.0			-2.3834	-	10000.0	2.2077	Z. 3315	4.5152		-25.2032 -24.0261	24.2192 23.0899	-0.9839
10500.0	5+2541	4.1214	9.9827	13500-0			-2.2806		11000.0	2.1374	2.2498 2.1794	4.3112 4.2544	11000.0	-22.9563	22+0633	-C.9363 -O.8930
11500.0	4.8360	4.3546 4.0210	4,1406 8,4455	11500.0			-2.1854		11500.0	2.0219	2.1150	4.1475	11>00.0	-21.9799	21.1261	-0.8538
12000.0	4.1442	3,13/8	1.8820	12000.0	-51.0576		-2.0101		12000.0	1.9/39	2.0600	A 0110	12000.0	-21.0851 -20.2622	20.2673 19.4775	-0.8177
12500.0	3.8565	3.4812		12500.0	-49.6053	41.1248	-1.9405		13000.0	1.4310	2.0104	3 4646	13000.0	-19,5031	14.1488	-C.7847 -C./543
13060.0	3.6001 3.4706	3.2525		13000.0			-1.8762		13500.0	1.8578	1.9259	4. 144.1	13200 -0	-18,8005	18.0745	-0.7261
14000.0	3.1042	2. 86 96		14000.0			-1.7435		14000.0	1.8263	1.8896	4. 7164	14000.0 14500.0	-18.1486	17.4487	-0.6999
14500.0	2.9719	2.64/3		14500.0	-42.4397	40./535	-1.6862		15000.0	1./9/4	1.8565	3 60/7	12000-0	-16,9762	16.8064 16.3234	-0.6756 -0.6528
15000.0	2.8092 2.6558	2.5467 2.4097		15000.0	-41.0539		-1.6324		15500.0	1.7467	1.7983	4 6/60	12200.0	-16.44/4	15.8157	-C.6316
16000.0	2.5154	2.2847	4.8006	16000.0	-38.53/8	37.0034	-1.5344		16000.0	1./241	1.1726	3.4958	19000.6	-15.9520 -15.4869	15.3402	-0.6118
16500.0	2.3879	2.1/04	4.5583	16500.0	-37.3922	35.9027	-1.4896		1/000.0	1./032	1.7488	3.4102	17000.0	-15.6496	14.8938 14.4741	-0.5931 -0.5756
		7.0654	4.3359	11000.0	-36.3131	34.8659	-1.4473								• • • •	
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B	1/B	۷	B	1/B	<u> </u>	B	1/ B	<u> </u>	B	1/ B	V	В	1/B	٧	В	1/B	V
บ		¥	9966+9	100-332	0.728	15527.5	64.402	2+873	6258.5	1-59.784	0,	9860.8	101+412	-3.359	15415.2	64.87	-10-295
5379.8	185+880	0.	10066+8	99.337	0.923	15629+9	63.980	3.172	6494.2	153+983	0.	9960.6	100+396	-4.660	15517+5	64 . 444	-5+960
5595.3	178+723	ů.	10166.7	98+360 97+402	0.988 0.923	15732+3	63.563	3.250	6907.4	144+772	0.	10060.4	99.400	-4.443	15619+6	64.021	0.
5820.7	171+801	0.	10366.7	96+463	0.832	15834+8 15937+4	63+152 62+746	3.224	7301.6	136+955	0.	10160.2	98-423	-2+709	15722.2	63.604	6+394
6115+1	163+530	0.	10466.8	95+541	0.663	16039.9	62+344	2.951	7745.9 8349.6	129+100	o.	10260+1	97.465 96.524	0.542	15824.6	63+193 62+786	12+137
6498+3	153.885	0.	10566.9	94.635	0.481	16142.6	61.948	2.834	9074+1	110.204	0. 0.	10460-1	95.502	6.069	16027.6	62+385	21+565
6872.4	145+510	0.	10667.0	93.747	0.273	16245+3	61+556	2.652	9761+1	102.448	0.	10560.1	94.696	6,502	16132.1	61.988	22+065
7237.2	138.175	0.	10767.2	92.875	0.	16349+0	61.170	2.444	10867.5	92.077	0.	10660.2	93-507	7+261	16224 B	61+596	24.491
7711+3	129+680	0.	10867.4	92+018	-0.234	16450.B	60,787	2+353	11844.5	84.427	0.	10760.3	92.934	6.502	16337.4	01+209	25+003
8285.5 8881.0	120.693	0.	10967.7	91.177	-0.494	16553+6	60+410	2.210	13499.9	74+124	0.	10860.5	92 . 077	6.177	16440.1	60+827	25.900
9697.4	112+600	٥.	11065.0	90.350	-0.780	16656.5	60.037	2.067	15108+6	66.187	0.	10960.7	91+235	4.877	16542.9	60.449	25,683
10747.2	93+048	0.	11168.4	89+538	-1.053	16759+4	59,568	1.950	18214.3	54.902	í0 🖕	11061.0	90+408	4.118	16645.7	60.076	25.249
11721.3	85+315	0.	11268+8	88.740	-1.274	16862+4	59:304	1 • 781	7775.6	128.608	۵.	11161+3	89=595	2.167	16748.5	59.707	24.708
13195+4	75+784	0.	11369.3	87.956	-1.300	16965.4	58,944	1.599	7973.4	125.418	1.626	11201+6	88+797	1.409	16851.4	59.342	23+641
14995+8	66+685	0. 0.	11469+8	87+185	-1.196	17068+5	58.588	1.456	8270.3	120+914	-0.542	11362+0	88.012	-0.433	16954.4	58+982	23+191
17698+2	56.503	0.	11670.9	85+683	-0.390	17171+6	58.236	. 1.300	8567.7	116+717	-2.384	11462.5	87+241	-2.384	17057.4	58.626	21.998
5810.9	172.091	-0.143	11771+6	84+950	0.104	17274+7	57+888 57+544	L+040 0+845	8815+8	113.433	0.	11562.9	86+483	-3+901 -5+635	17160.4	58.274	21+565
6007+1	166.470	0.169	11872+3	84.230	.0.702	17481.2	57.204	0.650	9064.2	110+324	4.335	11663.5	85.738 85.905	-7.477	17263.5	57+926	20+481 19+506
6203.5	161+200	-0.026	11973.0	83.521	1.170	17584.5	56.968	0.403	9561+7 9960+6	104.584 100.396	0. -4.335	11864+7	84+284	-8+453	17365.7	57+582 57+241	18+422
6400.0	156.250	-0.169	12073.8	82.824	1+560	17687.0	56+536	0.195	8171+3	122+379	0.325	11965+7	83+575	-8.453	17469.9 17573.1	56.905	16.905
6596+7	151+590	0+130	12174+6	82 . 138	1.807	17791.3	56.207	-0.039	R367+4	119.483	-1.517	12066.0	82+877	-7.802	17676+4	56+573	15.930
6793+6	147.197	0.130	12275.5	81.463	2+041	17894+7	55,982	-0.260	8567.7	116.717	-2.492	12165.A	82+191	-5.527	17779.7	56+244	14.196
6892+1	145.094	۰.	12376.4	80.799	2.080				8765+2	114.075	-0.650	12267.6	81+516	-2.384	17893.1	55.919	13.004
6990+6	143.048	-0.221	12477+3	80.145	2+054	10:33-	A 3.		8964.8	111+547	3,251	12368.4	80.851	1+517	17985.6	55+547	11.487
7089.2	141.059	-0.351	12578+3	79.502	1+963	(Fitte	ed to		9163.6	109.127	3.251	12469.3	B0.197	4.660	18090+1	55+279	9+861
7187.9	139+123	-0.312	12679.4	78.868	1.781				9362.6	106.808	2.059	12570+3	79.553	8,453	18103+6	54+964	8+453
7286.5	137.239	0.	12780+5	78+244	1+547	- I a	ndav)		9561.7	104.584	0.	12671 .2	78.919	10.945	18207+2	54+653	· 6.719
7385+2	135+405	0+299	12881+6	77+630	1.222	ະແ	narol		9761+1	102.448	-2.709	12772.3	78 • 295	13.004	18400.8	54 . 345	5.418
7582.8	133+618 131+877	0.403	12982+8	77.025	0.923				-			12873+3	77+680	13+654 13+979	18501.5	54.041	3.901
7681+6	130.180	0.208	13084.0	76+429	0.572				8.8	1		12974.5	77.074 76.478	13.112	18603.2	53.740	2.276
7780.5	128+526	-0.065	13185.3	75+842 75+264	0.247			all	M-	R		13075+6 13176+8	75+991	12.787			
7879.5	126+912	-0.312	13285+6	74.594	-0.364		n		IV!	N N		13278+1	75+312	11.487			
7978.4	125+338	-0.481	13489.4	74+132	-0.598			1 2 1 4				13379.4	74.742	9,970			
8077+4	123+802	-0,416	13590.9	73+579	-0.780		-			-		13482.7	74.180	8.344			
8176.5	122.302	-0.377	13692.4	73.033	-0.975	•						13582.1	73.626	6+502			
8275+6	120,837	-0.065	13793.9	72.496	-1+157				-			13683.6	73.080	4.768			
8374.7	119.407	0+156	13895.5	71.966	-1+326							13785+1	72 +542	3.251			
8473+9	118+009	0.468	13997.2	71.443	-1+521							13886+6	72.012	1+951			
8573.2	116+643	0.520	14095+9	70+928	-1.716							13988+2	71+489	0.			
8672.4	115+308	0.416	14200+6	70.420	-1.924							14069+8	70+973	-1+300			
8771.7	114.003	0.260	14302.4	69.918	-2.093							14191.5	70+465	-2.601			
8671+1	112+726	0.078	14404 .2	69.424	-2.210			M3	1	·201		14293.2	69.963	-4+118			
8970.5	111+477	-0.078	14505.1	68,936	-2.249		N	419 5		• / • H		14395+0	69.469	-5+635			
9069+9 9169+4	110.254	-0.260 -0.390	14605.0 14710.0	68+455 67+981	-2+223 -1+937		ŀ	/ V 🗸 🗸		6 IN	1	14495.8	68+981 68+500	-7+261 -8+886			
9269+0	107+867	-0.520	14812+0	67+513	-1+560					•••		14598+6	68+025	-10+837			
9368+5	106.740	-0.650	14914+1	67+051	-0+793	,	•					14700.5	67.556	-12.679			
9468+2	105+617	-0.754	15015+2	66+595	-0.286							14904.5	67.094	-13,979			
9567.8	104+517	-0.663	15118+4	66+145	0+546							15006.5	66.638	-15-388			
9667+5	103,439	-0.351	15220.6	65.701	1.378							15109.6	66+187	-16.255			
9767.1	102.383	0+169	15322+8	65.262	2.080							15210+8	65.743	-15.280			
9867+1	101.347	0.520	15425+1	64+829	2.496							15312+9	65.304	-14.088			

DATA - OSCILLATIONS.

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80+836 80+182

79-538

12370.7 12471.6 12572.6 33.071 35.827

35.236

B	1/ B	<u>v</u>	B	1/8	V	<u>B</u>	1/B	V
7184.6	139.186	-3.543	7125+5	140.342	. 0.	12673.6	78+904	34.843
7283.2	137.302	-5.906	7974+8	125+395	0.	12774+6	78.280	31+496
7381.9	135+466	-7.263	8559.3	116.831	0.	12875.7	77.666	28+346
7480.6	133+679	-2.165	9145+4	109.345	0.	12976.8	77.060	22.244
7579.4	131+937	4.331	9962.4	100.378	0.	13078.0	76+464	17+126
7678.2	130+239	7.874	10962.7	91+218	0.	13179+3	75.877	10.630
7777.0	128+584	7.874	11997+7	83+349	0.	13280.5	75 29B	3 937
7875.9	126.970	3.937	13371.7	74.785	0.	13381+9	74.728	-5.315
7974+8	125.395	-0.984	15295.3	65.379	0.	13483+2	74+166	-10.433
8073.8	123+858	-6+299	5906.3	169.310	~1+969	13584+6	73.613	-16-142
8172+8	122 • 357	-8.268	6004.4	166+545	-3.346	13686.1	73.067	-19.685
8271.8	120.892	-9.843	6102.5	163+867	0.	13787+6	72 • 529	-23,228
8370.9	119.461	-9.646	6200.7	161+273	3+543	13889+1	71.999	-26.575
8470.1	118.063	-3+937	6298.0	158+758	1.181	13990+7	71+476	-29+134
8569+3	116.696	0.984	6397+1	156.320	-0+394	14072.4	70.960	-32,480
8668.5	115.360	10.236	6495.4	153.955	-2+362	14194+1	70.452	-35.433
8767.8	114.034	11+417	6593.7	151+659	-1+772	14295+B	69+951	-38,976
8867.1	112.777	8.465	6692.1	149.430	-0+984	14397+6	69+456	-42,323
8966.4 9065.6	111+527	5+118 1+575	6790.5	147.264	3.937	14499+4	68.968	-45,276
9165.3	110.304	-0.591	6889.0	145+159	5.512	14601+3	68.487	-47.047
9264.7	107+936	-3.543	6987.5	143+113	4+134	14703.2	68.012	-47.244 -45.276
9364.3	106.789	-5.906	7086+0	141+123	0.394	14805-2	67+544	-39.764
946348	105+665	-9.843				14907.2	67.082	-31.299
9563.5	104.565	-11+614				15009.3	66+625	-21.260
966341	103.486	-13,386				15111.4	66+175 65+731	-8.465
9762.8	102+429	-13.386				15213.6	65.292	3,937
9862.6	101.393	-7.480				15315+B	64+859	22.638
9962 .4	100.378	3+346				15418.0	64.432	35.630
10062.2	99.382	9.843				15520+3 15622+7	64.010	43.701
10162+1	98.405	16+142				15725+1	63.593	48.819
10262.0	97.447	17.717				15827+5	63.181	53.543
10362.0	96.507	17.717				15930.0	62.775	54.724
10462.0	95.584	16.142				16032.5	62,373	54.134
10562.0	94.679	14.173		-		1003113	0	•••••
10662+1	93.790	11+811	847	n				
10762.3	92.917	7+874	W	5				
10862-5	92.060	3.937	44	ป				
10962.7	91.218	-1.575	••	-				
11063.0	90+391	-6.299						
11163+3	89+579	-13.386		. 1 1	9.1	Zok		
11263.7	88+781	-19+291				I ♥ {A		
11364.1	87.996	-23+819	110	III				
11464+6	87+225	-26+346						
11565.1	86+467	-27+756						
11665+6	85.722	-25+197						
11766+2	84.989	-21+654						
11865+8	84+268	-12+795						
11967.5	83.559	-3.346						
12068+3	82.86Z	12.008						
12169.0	82+176	22.047						
12269.8	81.501	28,937						

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APPENDIX 4

COMPUTER PROGRAMMES.

Only the two most important programmes are listed here.

The Lorentzian fitting programme is in the form of a main programme followed by three subroutines.

The more complicated programme FRIER, for fitting data to the generalised Landau expression, is in the form of a fairly long main programme followed by four subroutines and, finally, M.D. Powell's long subroutine VAO4A. This last subroutine is also essential to the working of the above Lorentzian fitting programme, of course.

	0 DIMENSION DATAX(100),DATAY(1001,X(5),E(5),W(40), 1 TEXT(13) , CDEFFB(5)
	COMMON DATAX, DATAY, COEFFB, NDATA READ(5,10D) NSETS
	100 FORMAT(15)
	DU 99 NSET = 1, NSETS READ(5,110) [TEXT(1], 1=1,13]
• • •	110 FORMAT(13A6) READ(5,120) ICUN, NDATA, JXXY, H, ESCALE
Lorentzian	120 FURMAT(11,14,11,14,F10.4 1
	1 READ(5,125) X(I), E(I) 125 FURMAT(2F10.))
8:88im m	MRITE(6,1151 (TEXT([],[=1,13) 115 FORMAT(1H),1X,13A6 ///)
fitting	IF(JXXY) 11,11,12
	12 OU 2 I= 1, NDATA READI5,1301 DATAX(1), DATAY(1)
	130 FDRMAT(F10.4,10x,F10.4) 2 DATAY(1)= DATAY(1)/DATAX111
programme.	WRITE(6,140) 140 FORMAT(IHO,9(2HXY,10X) ///)
programme.	GO TO 4
	11 DO 3 [# 1, NDATA 3 READI3,150) DATAX(1), DATAY(1)
	1>0 FORMAT(2F10.4) WR)TE(6,145)
	145 FORMAT(1H0,912HXX,10X) ///) 4 CUNTINUE
	MAXIT + 200 N3K = 40
	JPRINT = 1
	EXTERNAL CALCFX CALL VAO4A(X,E,M,F,ESCALE,IPRINT,ICON,MAXIT,CALCFX,W,N3N)
	WRITE(6,160) (TEXTIL), [+1,13) 160 FDRMAT(1H1,1X, 13A6 ///)
	IF(JXXY) 13,13,14
	14 WRITE16,170) 170 FORMATIIHO, 9(2HXY,10X) ///}
	60 TO 15 13 WRITE(6,180)
	180 FORMAT(1HO, 912HXX,1DX) ///)
	WRITE(6.190)
	190 FORMAT(1H0,13HFINAL VALUES-1 DU 6 [=1, M
	6 WRITE(6,2D0) 1, COEFFB(1), 1, X(1)
	WRITE(6,220) NDATA, JXXY, M, ESCALE, MAXIT, ICON 2200FDRMAT(1HO,15HDATA INPUT NAS- /1HO,2X,5HNDATA,1X,4HJXXY,3X, 1 6HNTERNS,3X.6HESCALE,3X,5HMAXIT /1HO,2X,13,6X,11,5X,11, 2 E10-3,1X,15 / 1HD,5HICON=, IZ 1 99 CONTINUE STOP
	END CONTRACTOR C
SUBRDUTINE CALCEX(M,X,F)	
DIMENSION X(5), DATAX(100 COMMON DATAX, DATAY, CDEFF	0),DATAY(1DD),COEFFB(5)
CALL LSTSQRLOATAX, DATAY	NDATA, M. X. CUEFFB, F)
ENO	
7.12 ·	
SUBROUTINE <u>LSTSGR</u> (X,Y,N,M,H,H,B1,SU O DIMENSIUN A(10,1D),B1101,C(10,100 1 RESIDI100),H131,B1(5) OUUSLE PRECISION A,B+C C SET UP C(1,J), WHERE OBS. EQU IS Y DU 6 L= 1, N DU 7 J= 1, N	1) + Y (100) + X (100) ,
C(1,j) = 0.0	1111 +1.0 J
G SET UP A= C+(TRANSPOSEC) AND B-D.	n season in the the second line in the second line in the second line is the second line
100 8 J= 1,14	
Burning DO 8 I= 1,1 Aligned DO 9 J= 1, H Burning A(1,1) = 0,0 B(1) = 0,0	
DO 8 [= 1,4 DO 9 J= 1,4 String Atijj = 0.0 String Atijj = 0.0 DO 10 K= 1, N BO Atijj = Ctikt + Ctikt + Atijj	International and the second secon
D0 8 $I = 1, M$ D0 9 $J = 1, M$ A11, J] = 0,0 B(I] = 0.0 D0 L0 K= 1, N B0 A11, J] = C(1, K) + C(J, K) + A11, J 9 CONTINUE D0 L1 K= 1, N	
DO 8 I= 1,4 DO 9 J= 1,4 A(I)J3 = 0.0 B(I) = 0.0 DO 10 K= 1, N BO A(I,J) = C(I.K) + C(J.K) + A(I.J) 9 CONTINUE	International and the second secon
DO 8 [= 1,4 DO 9 J= 1,4 A(1,J) = 0,0 G(1) = 0,0 DO 10 K= 1, N BO A(1,J) = C(1,K) + C(J,K) + A(1,J) 9 CONTINUE DO 11 K= 1,N 11 B(1) = C((,K) + Y(K) + B(1) 6 CONTINUE NUM = 10	International and the second secon
D0 8 [= 1, M D0 9 J= 1, M A11, J] = 0,0 B(1] = 0,0 D0 L0 K= 1, N B0 A(1, J) = C(1, K) + C(J, K) + A(1, J) 9 CUNTINUE D0 L1 K= 1, N 11 B(1] = C(1, K) + Y(K) + B(1) 6 CUNTINUE NUM = 10 C CALL MATRIX(A, B, M, NUM, DETER)	International and the second secon
D0 8 [= 1, H D0 9 J= 1, H A11, J1 = 0.0 B111 = 0.0 D0 10 K= 1, N B0 A11, J1 = C11, K1 + C1J, K1 + A11, J1 D0 11 K= 1, N 11 B111 = C11, K1 + Y1K1 + B111 B C0NTINUE NUM = 10 C C CALL MATRIX(A, B, M, NUM, DETER) C SUKR2 = 0.0	International and the second secon
D0 8 [= 1,4 D0 9 J= 1,4 A(1,J) = 0.0 G(1) = 0.0 D0 10 K= 1, N B0 A(1,J) = C(1,K) + C(J,K) + A(1,J) 9 CONTINUE D0 11 K= 1,N 11 B(1) = C(1,K) + Y(K) + B(1) 6 CONTINUE NUM = 10 C C CALL MATRIX(A,B,M,NUM,DETER) C	International and the second secon
D0 8 [= 1, M D0 9 J= 1, M A11, J1 = 0.0 B(1) = 0.0 D0 10 K= 1, N B0 A(1, J) = C(1, K) + C(J, K) + A(1, J) 9 CUNTINUE D0 11 K= 1, N 11 B(1) = C(1, K) + Y(K) + B(1) 6 CONTINUE NUM = 10 C CALL MATRIX(A, B, M, NUM, DETER) C SUMR2 = 0,0 D0 12 [= 1, N RESID(1) = Y(1) D0 13 J= 1, M	International and the second secon
D0 8 [= 1, M D0 9 J= 1, M A11, J1 = 0.0 B(1) = 0.0 D0 10 K= 1, N B0 A(1, J) = C(1, K) + C(J, K) + A(1, J) 9 CONTINUE D0 11 K= 1, N 11 B(1) = C(1, K) + Y(K) + B(1) 6 CONTINUE NUM = 10 C C CALL MATRIX(A, B, M, NUM, DETER) C SUKR2 = 0.0 D0 12 [= 1, N RESID(1) = RESID(1) - C(J, 1) + B(J) 12 SUMR2 = SU(R2 + RESID(1) + RESID(1) 12 SUMR2 = SU(R2 + RESID(1) + RESID(1) 12 SUMR2 = SU(R2 + RESID(1) + RESID(1) + RESID(1) 12 SUMR2 = SU(R2 + RESID(1) + RESID(1) + RESID(1)	International and the second secon
D0 8 [= 1, M D0 9 J= 1, M A(1, J) = 0,0 B(1) = 0,0 D0 10 K= 1, N B0 A(1, J) = C(1, K) + C(J, K) + A(1, J) 9 CONTINUE D0 11 K= 1,N 11 B(1) = C(1, K) + Y(K) + B(1) 6 CONTINUE RUM = 10 C C ALL MATRIX(A, B, M, NUM, DETER) G SUMR2 = 0.0 D0 12 [= 1,N RESID(1) = Y(1) D0 13 J= 1, M 13 RESID(1) = RESID(1) - C(J, 1]+8(J)	International and the second secon
D0 8 [= 1, M D0 9 J= 1, M A11, J1 = 0,0 g(1) = 0,0 D0 10 K= 1, N B0 A(1, J) = C(1, K) + C(J, K) + A(1, J) 9 CONTINUE D0 11 K= 1, N 11 B(1) = C(1, K) + Y(K) + B(1) 6 CONTINUE NUM = 10 C C CALL MATRIX(A, B, M, NUM, DETER) G SUMR2 = 0,0 D0 12 [= 1, N RESID(1) = Y(1) D0 13 J= 1, M 13 RESID(1) = RESID(1) - C(J, 1) + B(J) 12 SUMR2 = SUMR2 + RESID(1) + RESID(1) D0 14 [= 1, 5 14 B1(11 = D(1) RETURN	International and the second secon
D0 8 [= 1, M D0 9 J= 1, M A(1, J) = 0,0 g([] = 0,0 D0 10 K= 1, N B0 A(1, J) = C(1, K) + C(J, K) + A(1, J) 9 CONTINUE D0 11 K= 1,N 11 B(1] = C(1, K) + Y(K) + B(J) C CALL MATRIX(A, B, M, HUM, DETER) C C C CALL MATRIX(A, B, M, HUM, DETER) C C C C C C C C C C C C C C C C C C C	

Lorentzian fitting.

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SUBROUTINE MATRIX (A,8.N.M.DETER)
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THIS DECK REPLACES MATRXL

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THIS SOLVES THE SET OF LINEAR EQUATIONS ' A(1, 11x(11+A(1,21x12) A(1,N1X(N) = 811) A(N,11X(1)+A(N,2)X(2) A(N.N)X[N] = B(N) TU

M IS THE DIMENSION OF BOTH A(H,H) AND BUHI AND HUST BE SET EQUAL TO THAT OF THE MATRICES IN THE MAIN PROGRAMME. M NUST BE GREATER THAN DR EQUAL TO N.

AFTER COMPUTATION A CUNTAINS THE INVERSE OF THE ORIGINAL MATRIX. B CUNTAINS THE VALUES OF X(1) TO X(N) IN ORDER. OFTER CUNTAINS THE VALUE OF THE OFTERMINANT OF A.

ENTRY LINEON GIVES THE SULUTIONS OF THE EQUATIONS AND THE **ENVERSE OF A ONLY.**

ENTRY DETERM GIVES THE VALUE OF THE DETERMINANT OF A AND ITS INVERSE ONLY.

الوالد يحدد المالية ممصم المعام

THE MAXIMUM NUMBER OF EQUATIONS IS 100.

DIMENSION IPIVOT(1001, INDEX(100,21 DIRENSION ALM, MI, B(M) EQUIVALENCE IAMAX.T.SWAP) DUUBLE PRECISION A, B, AMAX, SWAP, PIVOT, T

ENTRY LINEON (A,8,N,M) IND = 1 GU TO 10 ENTRY DETERM (A.N. H.DETER)

INO # 2

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INITIALIZATION
```

1F (N.LT.101) GO TO 10 WRITE 16,51 N 5 FURMAT (19H TOO MANY EQUATIONS, 16)

STOP --- 10 DETER = 1+0 - -راستاند بدينت والمارد 15 OU 20 J= 1,N

```
c
      SEARCH FOR PIVOT ELEMENT
c
C
   40 AMAX =0.0
   45 DO 105 J=1+N
  50 IF ( IPIVOT(J)-11 60+105+60
  60 00 100 K-1,N
   70 1+ (IPIVUT(K)-11 80,100,740
   80 IF (ABS(AMAX1-ABS(A(J+K))) 85-100-100
   85 [RDW+J
   90 1CULU4-K
   95 AMAX=A(J+K)
  100 CUNTINUE
  105 CONTINUE
  110 IPIVOT() COLUM) = IPIVOT(ICOLUM)+L
      INTERCHANGE ROWS TO PUT PIVOT ELEMENT ON DIAGONAL
С
  130 IF ( IROW-ICOLUM) 140,260,140
  140 DETER = -DETER
  150 00 200 L +1.N
  160 SWAP = AL IROW,L)
  170 ALIROW, L )=A(ICULUM, L)
  200 ALLCOLUM, LI-SWAP
      1F ( IND .EQ.2) GU TO 260
  220 SWAP=B(IRDW)
  230 BEIROWI= SCICOLUMI
  250 BEICOLUMI-SWAP
  260 (NDEX(1, 1) = INOW
  270 (NDEX(I. 2) = ICOLUM
  310 PLYUT=AL ICOLUM, ICOLUM)
  320 DETER = DETER *PIVOT
  330 ACICULUMIICULUMI=1.0
С
      DIVIDE PIVOT ROW BY PIVOT ELEMENT
С
  340 DU 350 L=1.N
  350 ALICOLUM+LI=ALICOLUM+LI/PIVOT
      IF [ IND .EQ.21 GU TO 380
  370 BEICULUMI=BEICULUMI/PIVOT
С
      REDUCE NUN PIVOT ROWS
C
C
  380 DO 550 L1-1,N
  390 IF (L1-1COLUM) 400,550,400
  400 T-ALLI, ECULUM)
  420 A(L1, (COLUMI=0.0
  430 00 450 L=1.N
  450 AILI,L) =AILI,L)-AIICOLUM,LITT
      1F (INO .EQ.2) GU TO 550
  500 B(L1)=B(L1)-B(ICOLUM)+T
  550 CUNTINUE
c
¢
      INTERCHANGE COLUMNS
¢
                              ----
  600 00 710 1-1,N
  610 L=N+1-1
  620 IF (INDEX(1.11-INDEX(1.21) 630-710.630
  630 JRUW=[NDEX[L,1]
  640 JLOLUN=INDEXIL,2)
  650 00 705 K=1.N
  660 SHAP -A (K. JRUH)
  670 ALK, JROWI-ALK, JCOLUNE
  700 ALK, JCUL UNI - SHAP
  705 CONTINUE
  TIO CUNTINUE
  740 RETURN
  750 END
```

30 00 550 I=1.N

SUBRUUTINE VA04A IX. E. N. F. ESCALE . IPRINT. ICUN. MAXIT. CALCEX. W. N3N1 REAL XINI, EINI - _____ REAL WINSNI ABS+(XY2 1231=ABS(XY2123) ----IF(N3N-N*(N+31) 80CU,8002,8002 8000 WRITEL6. 80011 8001 FURMATIZER DIMENSION OF W TOU SHALL 1 UA=U8 51 0P GU TQ 29 71 DL =1. • 8002 CUNTINUE DUM AG= 0. 1* ESCAL E SCER =0.05/ESCALE FA=FP 11=N +V +V ____DA=-1. N+ LL = LLL K=N+1 F8=FHULD -----• • <u>م</u>ر بط UB=0. NFCC+1 D=1. IN D=1 INN=1 _____IO_FC=F______UC=D _____UC=D ______3O_A=IUB-UCI=IFA-FCI and a second contract of the second secon DU 1 1=1:N DO 2 J=1:N and the ____WLK3=0.]+{1-334,3,4 3 NEKT AUSH EL 111 _____33. EA=FB UA*DB WELL *ESCALE 4 K=K+1 2 CONTINUE 1 CUNTINUE ITERC=1 ISGRAU=2 CALL CALCHX(N, XIF) FKEEP = AUSH(+) + AUSH (+) 5 11 UN L= 1 FP=F SUH=0. IX P=JJ 00 6 1=1,N IXP=IXP+1 W(1XP)=X(1) 6 CUNTINUE IDIRN=N+1 LL IN E= 1 P OMAX=W(ILLINE1 PGAX25CR DMAGEAMAX1 (DVAG, 0.1*DMAX) DVAGEAMAX1 (DVAGA, 0.1*DMAX) DVAGAAMAX1 (DVA IL IN La 1 7 DHAX =WIILINE -....... 27 .70 DL=0. D= D4 AG K(IUIRN)=00FW(IUIRN) IDIRN=IDIRN=I 9 CONTINUE 32 22 8 DD=D-DL UL=0 21... A9. CONTINUE MI LLINE = W(LLINE1/DD TU USE TU USE T

 DU 9 1=1.N
 ILINE: H(ILINE: DD

 DU 9 1=1.N
 ILINE: UL=0 58 K=IDIRN DU 9 1=1+N X(1)=X(I)+DD+N(K) 60 10 (10,11,12,13,14,96),15 14 IF(F-FA) 15, 16, 24 16 IF (ABSE(D)-DIAXI 1/,1/,18 17 D=D+D 10 IF (ABSF(D)-DMAKI L/.1/.18 GU TO 8 18 WRITE(6, 19) 19 JORNAI (5X.44HVA04A MAXIMUM CHANGE DUES.NOT.ALTER.FUNCTION) GJ TO 20 19 AUTO 8 15 FB*F ----08=0 2 ---60 10 21 24 FB=FA DB=DA . **** DA=D DA=D ---- 21 GO TO (83,23), ISGRAD 23 OF DB+OD+ DA ES=1 ____ 60 10 8 GU 10 8 B3 D=0.5+1 DA+D8-1 FA-FB3/1 DA-DB33 . VAO&A 15=4 15=4 1+((CA-D)*(D-D3))25+8+8 25 15=1 ÷.,, LETABSELD-DBJ-DDHAX38,8,26

 IF (ABS+1 D- UB)-OUH AX (B, 8, 26)

 26 D= DB (S) (C) (UDH AX, UB-UA)

 IS=1

 OUM AX= UDH AX, DDH AX

 OUM AX= UDH AX (DDH AX)

 OUM AX= UDH AX (B, 8, 27)

 27 ODM AX= OUM AX (B, 8, 27)

 28 IS IF(1-FA) (28, 23, 23)

 29 IF (L)

 28 FC=F8 00=08 , orr DB=0 Gu 10 30 29 60 10 30 12 [F(F-F6) 28, 28, 31 _____31 +A++ سیمینیسی بیشتند بر بیش، میراند. سوره آروز را می آند. 100 م DA=U GU TU 30 11 1+(+-+6132,10,10 37 14=19 . .

	IF (FPREV-F-SUM) 94.95.		·	3 CO TO / 109.88). IND
	50M=FPREV-F	77	;. 53	3 GU TU (109,88), IND 9 IF (AAA-0,1) 89,89,76
73	JIL=IL INE		. 105	9 [F (AAA-0.1) 89,89110
				9 GD FU (20, 116), ICUN
	IF ((DIRN-JJ) 7, 1, 84	دايما په ۲۰۰۰، مېمېرېپې ساره د د د د د د د د د د د د د د د د د د د	110	
	GO TO (92, 72), IND	and the second		GU TU (100, 101), INN
92	HOLD=F	a a sea e guarda e antica e a com		0 INN=2
	[5=6			Kejij
	1X P=JJ	المالية ومحمطة دورساريك الرباب		DO 102 [=1.4
	DO 59 I=1,N			K=K+1
	IXP=IXP+1			WEK)=X(1)
	#{ [XP}=X{ [}~#{ [XP}			X(1)=X(1)+10.+E(1)
	CONTINUE		103	2 CUNTINUE
	00=1.			FK EEP=F
	GU TO 58			CALL CALCEX (N:X+F)
96	GU TO (112.87), IND			NFCC=VFCC+I
	1+ (+P-+1 3/.91.91	· · ·		
	0=2.+(+P++-2.++HOLD)/(++	Unit tak 2		DUM AG=0.
	IF (D+(FP-+HUL D-SUM)++ 2-		_	GD TO 108
97	' J=JIL+N+I			16 1+ (+-+P1 35,78,18
	IF (J-JJ1 60.60.61	• •	74	8 WRITE(6, 80)
40	DU 62 I=J,JJ	······································		0 FURMAL (5X) 371WA04A ACCURACY LINETED BY ERRORS IN FF
		· · ·	۰.	
	K = I-N		8	18 IND=1
	HEK3-HEI3		3	15 DUMAG=0+4+SQRI (+P-F) .
. 62	CONTINUE		-	ISGRAU=1
	DO 97 I=JIL _# N		101	B IIERC=IIERC+1
*	W(I-1)=WII}			
	CONTINUE			HUNTTHE A. H23 MAXIT
61	IDIKN=1DIRN-N	. . .		2 FURMAT(15, JOH TERATIONS COMPLETED BY VAGAAT
	ITONE= 3		0	1+ (+++K EEP) 20, 20, 110
	K=(D1RN			LO F=FKtEP
	IX P=JJ		44	
	AAA=0.		-	$00 111 1 = 1_{0}N$
	00 65 I=1.N	ى بى يېسىسىرىيىسە مىسىدەم سىسى مىلەر مېرىنى ئېرىنى ئېرى ئېرىكى ئېرىمى		JJJ=JJJ+1
	IXP=1XP+1			X[]]=A[]JJ]
	W(K)=W(IXP)		11	L1 CUNTINUE
		1 AL AT AT	• •	GO TO 20
	**************************************	1 66,67,67	10	JLJIL#J
60	WWW-WAAL CALLER (1 / 1 / 1			FP=FKEEP .
	CUNTINUE	······································		14 (1-1KEEP1 105, 18, 104
. 47	DDMAG=1.		10)4 JIL=2
				FP=F
		and the second state of th		t=FK ttp
	IL INTEN	an an an an an ann an an an an an an an	10	15 IXP#JJ
	60 10 7			DO 113 [=1,N
	IX P=JJ	the second se		IX P=1X P+1
	AAA=0.		-	K=IXP+N
	F=FHOLD			GO TU (114,115), JIL
	00 99 I=1,N	 A state of the sta		6 W([XP]=W(K)
	1x P= 1x P+1	· ·	**	GUTU113
· ·	<u> </u>		· · · ·	60 10 115 · · · · · · · · · · · · · · · · · ·
	1 F [AAA#A85717(]) = ARSF1	(W(1XP))) 08.00.00		
. 98	AAA+ AD 3 C \ W \ 1 AP 17 E \ 1 1 1			X(1)=H(K)
	CUNT INUE	(a) a serie de la serie este este este de la sub-sub-sub- tion.	. 11	13 CUNTINUE
5. S. S.	GO TO 72			JIL * Z
4.8	AAA= AAA*(1.+011	en en el ser en la comparte de la c		GO IO 92
	60 TO 177. 1041. IND			16 IF (AAA-0.1) 20,20,107
	1F (IPRINT-21 .53, 50, 50	- Alexandra et ante la la la la la la		LO RETURN
			10	D7 INN=1
		n na shi karantinini Viluzza e n		
			-	GO TO 35
				END

VA04A

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FRIER. Landau fitting programme.

CRAME TO DATA - ALTON AND ALTON AND ALTON AND ALTONAL AND ALTONAL AND ALTONAL AND ALTONAL AND ALTONAL AND ALTONAL C NSELS. THEN FOR EACH SET -

 Image: Sector E FINALLY, FIELD-AND-SAMPLE-VULTS. UP TU 200 CARUS. CANAL TO I IN THE C APPRUERIALE PLACE TO REEP-PERIOD, POWERIA, DIBI- CONST. C RESPECTIVELY. 1 2 3 4 . Analog and the second state of C DDIMENSION TEXT(13), UATAX(200), DATAY(200), POWER(2), PERIUD(2), A(2), 1 DIBIL 21 . AL 3. 21 . P SIL 3. 21 . E (20) . X(20) . NIRMC SL21 . AVA14001 . NHULUL4. 21 È. COMMON PERIODEDINERIA.UIBI.N.PSI.NCARRS.NIRMCS.DATAX.DATA. READLO, 1001 NSEIS 100 FURMAI(16) C DO 99 NSEI=1, NSEIS DO 99 NSEI=1, NSEIS REA0(5,10) (TEXT(1), 1=1,13) 110 FORMAT(13A6) C REAUL 5. 1201 ICON. NDATA, NCANR S. ESCALE, AGGUR NWT FURMAT(11, 14, 15, E10, 2, F 10. 1(5) IFI NCATA, LE, 200) GU IU 98 120 FORMAT(11, 14, 15, 10, 2, 10, 1(5) HENCATALLE, 200) GU U 98 WOITELA 91 ومستريب الم WRITEL6.97) - 97 FORMATCHI, 17HNDATA 100 LARGE. ///I GU 10 99 WRITE(6, 97) 98 CUNTINUE IFLICON.EQ.01 (CUN = 1 _____IF(LUMAEQ.0) ICUN = 1 IF(ACCUR.EQ.0.0) ACCUR = 1.0 C.______DREAU(5):301 NHRYCS(1);(NHULU(K,1),K=1,4),PERIOU(1);POWER11);A(1); 1 DT GT(1) 130 FURMA(1 511, 5X, E LU, 2, 3F 10, 4] READ(5, 131) (H(K, 1), PS1(K, 1), K=1, 3) · 54 - 5 LI STRAUDAIDE ERANTATIONE 1 CONTINUE en nierys enseringe 2 READIS-1401 DATAX113. DATAY13 140 FURMAT(F10.4,10X+F10.4) C DU 2 1=1, NDATA CALL ADJINL (PERIUD, PUNER, A.DTBT, N. PSI, NCARRS, NHRMCS, NHOLD, M. ž 10 WRITELS, 1501 LTEXILL, 1=1,131 ş÷ 그는 그는 가도 문제품 150 FURMAT(1HL, 1X, 1346///) **...** WRITELG, 2001 ICUN.NUATA, ESCALE, NGARRS, ACCUR, INHRMCS(1), 1=1, NCARRS) 1a a -2000FORMAI(12HOLATA INPUT-//IHO.4HICON,2X, 1 SHNDATA,9X,6HESCALE,4X,6HNCAKRS,5X,5HACCOM,5X,6HNHARCS/IH,2X, 2 II.4X,13,9X,64,2,4X,11,7X,16,1,7X,11/(IH,53X,111) WRITEL6,1721 (NHOLU(K,11,K=1,4)) ##stitut ind/USA;1:K=1:41
//2 FORMAI(140,9HCAR1ER 1 /HO,6HNHOLD=,411)
NHRMC = NHRMCS(1) 3 QWR(1E(6,1/1) PUMER(1),PER1UD(1),A(1),D(1),G(1),G(K,1),PS1(K,1),K=1,... 1 NHRMC1 1/10FURN ATT 1H0, 1X, 1HN, 5X, 6HPER 100, 18X, 1HA, 18X, 4H0T/T, 17X, 9HAMPLITUDE. NHRNE = NHRHESIZI OWRITE16, 1911 POWERIZI, PERIODIZI, ALZI, DTBT(2), (WIK, 2), PSIIX, 2), K= 1, 1 NHRMC 1 ___ 19 LOFORMAILING, 1X, 1HN, 5X, 6HPER LUD, 18X, 1HA, 18X, 4HOT/1, 17X, 9HAMPL IT UDE, 1000RHAIII1709142877758777 119X9 HPHASE //1H +F3+1, 2 El0+1+5X+2E2C+5+5X+E20+3+5X+E20+3/ .96 CUNT INUE

FRIER

WRITE 6, 182) 182 FURNAT(1H0, 25X, 1015		n
		a da far internet de la seconda de la se
IFINHT NE.11 GU TU XMIN # 1.0E06	1022	
XMAX = 0.0 DJ 1020 K= 1. NDATA		
AX = DATAX(K)		
XMAX = AMAX1(XMAX+AX) XMIN = AMINI(X4IN+AX)		
DENON # XMIN - XMAX		
CUNSTI = XMIN -100.0*/ CUNSIZ = 99.0*XHAX*XHI		
_ CUNST = CUNSTI/DENUM _	·	
SLOPE = CONST2/DENUM GU TU 1021		
022 CONST = 1.0	· · · · / ··	
DZ1 CONTINUE	<u>)</u>	
H* 0H* 0		
JIND = 0 DU 15 I= 1, NCARRS M = M + NHRMCS(1)		
<pre>00 95 1 = 1,4 95 1+1NH0L011;K1.EQ.11 J</pre>	1.0 = 11	Nisat
94 CONSINUE		
A.≠ A.→ JIND Contraction = Tint The Arriver		
	e i Alereza	
DO 11 J= 1, M	7	
11 E(1) = ABSLXXX1+(ACCU	1/100.01	
ET IPRINT #11		
MAXIJ = 200. EXTERNAL CALCEX	میں در اور اور اور اور اور اور اور اور اور او	
en el contenta el seal		
CALL VADAALX, E, MIFIES	ALE . IPR	INT. LCUN, MAXIT, CALCFX, 4YA.N3N1
WRITE(& 1601 1EXT(1)	. 1=1.13	
600HURM #[(1HL, 1X, 13A6 ///.		VALUES- ///1H +9HCARRIER 1 //)
-NHRMC = NHRMESTI	L 31/2 21/09 E	ALGES ZITEN PRODUCTED E FEVEL
00000000000000000000000000000000000000	PERIOUI	1;,A(1),DTBT(1),(W(K,1),PSJ(K,1),K*1)
	SHPERIOD	,183,1HA,18X,4HDT/T,17X,9HAMPLITUDE, -
2 3.11H ,65X, ±20.5, 5X, E2(\$10+313	X, 222C. >, >X, 220. 5, >X, 220. 5/
IFENCARKS.EQ.11 GO TO	13	
IBO FURMATI 1HO, 9HCARR 1HR 2	2 //)	
	PER 1001	2],A(2),UIBI12),(W(K,2),PSt(K,2),K=1,
		181,1HA.181,4HDT/T.171,9HAMPLITUDE.
119X. SHPHASE //1H .+5.1		X+ZEZC. 5+5X+EZC.5+5X+EZC.5/
3 11H ,65X,E20.5,5X;E20		
195 FURMATETHO, ISHSUM SQ R	ESIUS.=	,E20.5L
99 CONTINUE		
END		
ENU .		
21.0181121.w/3.71.05113.21		5 m
AX(200) .UA14Y(200)	• :*********	
	-	57

WRITE(6. 182)

SUBROUTINE CALCEXIN, XIFI	
C ODIMENS IUN PERIODIZI.PUWER() I NHRMCS[2],NHILD[4.2],X[20]	21,4(21,0(8)(2),w(3,2),PST (3,2), 1,UATAX(200),UATAY(2001
COMMUN PERTUD.PJHER.A.UIBT	. N, PSI, NCARRS, NRRCS.DATAX, DATAY, NDATA
SUMR2 = 0.0	
	UNER . A . U TH I . H . PSI . NCARRS . NHRRCS . NHULD, M.
C DJ 1 NO* 1, NDATA Field = DATAX(ND)	
CALL CALC(PERJUD,PUH	IER , A . DTB I . W, PSI . F TELD . F . NGARRS . NHRMCS]
C RESID + F - DATAYIND)	
L SLUPETUATAK(40) +CUN SUAAZ = SUARZ + GRESTUARES F = SUARZ RETURN ENU	

FRIER

	SUBROUTINE ADJINL(PERIOD, PUWER, A:DTBT.W, PSI, NCARRS, NHRMCS, NHOLD, M.	
	وي ي ورجم ، بعد مسممينديدي ، ال عليه	2
	INITIAL FILLING OF -X-	-
		-
	IOLNENS ION PER (OUT 2), POHER (2) . A (2) . U IBT(2) . W(3.2) . PSI (3.2) .	:
- (IDIMENS ION PERIOD(2), POWER(2), A(2), DIBT(2), N(3,2), PSI(3,2),	
	L NHRHCSI 21+NHOLDI 4+21+XI 201	
	DU 5 K = 1, NGARRS	·
	IF(NHOLD(1,KJ.EQ.1) GO TU 1	
	X(1) = PERIOD(K)	
	1 = [+]	
1	IF(NHOLD(2,K).EO.L) GU TU 2	
-	X(I) = POWERIK)	
-		
2	IF (NHOLD (J, K). EQ. 1) GU TU J	
. •	KIII w A(K).	
	1 * 1 * 1	
	1+ (NHQL D (4. K). EQ. 1) GD 10 4	
	X(I) = D(B)(K)	
	t = 1 + 1	
۰.	FORT FAULT	
7		
	KILD = W(L+K) - Triance and a the second sec	
	1 = 1 + 1 x(1) = PS(1),x) 1 = 1 + 1	
	IF(NHRHCSIK).EQ.11 GU TO 5	. **
<u>.</u>	IFUNERACSIKI EVEL W IV 2 2	
	X(1) = W(2,K)	•
	1 = 1 + 1	
	XLI) = PSI(2rK)	
	1FI NHRMCSI K 1. EQ. 21 GU TU 5	
	X(1) = H(3,K)	
	L= L + L	
	X(1) • PS1(3,K) (1) · · · · · · · · · · · · · · · · · · ·	
	1 = 1 + 1	
. 2	CUNT INUE	
	and an and supported to the second and an and an and an and an and an and an and and	
	RETURN	

۰.

OSU BRUUTINE ADJUSTOPER LUD, PUHER , A JUTET, M. PSL .NCARRS , NHRMCS , NHOLU, M. 1 81 C Ċ DDIMENS 10N PER 100(2), POWER (2), AL2), 0181(2), W(3,2), PSI (3,2), . 1 NHRHCS(21, NHULD(4, 21, X120) ς. 1 = 1 DO 5 K = 1. NCARRS 1-(NHOLD(1,K).EQ.1) GO TO 1 PERIOD(K) = X(1) 1 * 1 + 1 1 1HINHULD(2.K). EQ. 1) GO 10 2 POWEREK) = XEEP 1 = 1 + 1. .. 2 IFENHOLDE 3. KI. EQ. 11 GO TO 3 _____ ALKJ = X[1] 1=1+1 3 IFENHULD(4,K).E0.1) 60 10 4 DTBI(K) = XELL 1 = 1 + 1 4 CUNTINUE _____ H(1+K) = X(1) 1 = 1 + 1 . . ______ PSIL1,K) = XLL1 1 = 1 + 1 IFENHRHCSEK1.EQ.11 GO 10 5 $W{2_{3}K} = X{1}$ 1 = 1 + 1 P\$112,X3 = X(1) 1 = 1 + 11F(NHRMCS(K).EQ.2) 60 10 5 #(3,K) = X(1) ----1 1 = 1 + 1 PS1(3,K) = X(1) . 1 = 1 + 1 5 CUNT INUE ς... RETURN - - END SUBRUITINE CALCIPERIUD, POWER, A, OTHT, W. PSI, FIELD, F, NCARRS, NHR MCS) C ... C C CALCULATES FUNCTION GIVEN PARAMETERS AND FIELD. ¢ _ C DIMENS (DN PER 1001 21, PUNER (2) .A (2) .0 (81 (2) .W(3, 2) .PSI (3, 2) .U(2) . - -NHRHCS(2) C ----- - - - - - -F= 0.0 C 00 1 1 = 1. NCARRS U(1) A(1)/FIELD ARGEX = UEIJ+UIBILIE ARGCO = 12.0+3.141591/1+16L0*PER (00 11)1 NHRMC = NHRMCSIII G = 0.0 C 11 DO 2 KH IN NHRME ARGEXP = -1.0*ARGEX+FLUATIKI ARGEOS = ARGEO+FLOATIR) - PSILK.I) UK = DEI 1+FLUATEK) 2 G = WER, II*(UK/SINHIUK)I*EXPLANGEXPI*COSLARGCOSI . + G ٦_ -----ENN = POWERCTI - G = G+(+ 1EL D++ ENN) 1 F = F + G C... RETURN END